AO 120 (Rev 08/10)

DECISION/JUDGEMENT

Mail Stop 8 TO: Director of the U.S. Patent and Trademark Office P.O. Box 1450 Alexandria, VA 22313-1450		REPORT ON THE FILING OR DETERMINATION OF AN ACTION REGARDING A PATENT OR TRADEMARK	
		rn Distr	1116 you are hereby advised that a court action has been ict of Texas, Waco Division on the following is 35 U.S.C. § 292.):
DOCKET NO. 6:22-cv-00105	DATE FILED 1/27/2022	U.S. DI	STRICT COURT Western District of Texas, Waco Division
PLAINTIFF GREENTHREAD, LLC		DEFENDANT INTEL CORPORATION, DELL INC., AND DELL TECHNOLOGIES INC.,	
PATENT OR TRADEMARK NO.	DATE OF PATENT OR TRADEMARK	HOLDER OF PATENT OR TRADEMARK	
1 8,421,195	4/16/2013	GREENTHREAD, LLC	
2 9,190,502	11/17/2015	GREENTHREAD, LLC	
3 10,510,842	12/17/2019	GREENTHREAD, LLC	
4 10,734,481	8/4/2020	GREENTHREAD, LLC	
5 11,121,222	9/14/2021	GREENTHREAD, LLC	

In the above-entitled case, the following patent(s)/ trademark(s) have been included:

DATE INCLUDED	INCLUDED BY	
	🗹 Amen	dment 🔲 Answer 🔛 Cross Bill 🔛 Other Pleading
PATENT OR TRADEMARK NO.	DATE OF PATENT OR TRADEMARK	HOLDER OF PATENT OR TRADEMARK
1 11,316,014	4/26/2022	GREENTHREAD, LLC
2		
3		
4		
5		

In the above---entitled case, the following decision has been rendered or judgement issued:

CLERK (BY) DEPUTY CLERK DATE

Copy 1—Upon initiation of action, mail this copy to Director Copy 3—Upon termination of action, mail this copy to Director Copy 2—Upon filing document adding patent(s), mail this copy to Director Copy 4—Case file copy

AO 120 (Rev. 08/10)

DECISION/JUDGEMENT

TO: Mail Stop 8 Director of the U.S. Patent and Trademark Office P.O. Box 1450 Alexandria, VA 22313-1450		REPORT ON THE FILING OR DETERMINATION OF AN ACTION REGARDING A PATENT OR TRADEMARK		
A. O			1116 you are hereby advised that a court action has been ict of Texas, Waco Division on the following s 35 U.S.C. § 292.):	
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In the above---entitled case, the following patent(s)/ trademark(s) have been included:

DATE INCLUDED	INCLUDED BY			
	Amen	dment 🗌 Answer	Cross Bill	Other Pleading
PATENT OR TRADEMARK NO.	DATE OF PATENT OR TRADEMARK	HOLDI	ER OF PATENT OR	FRADEMARK
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CLERK (BY) DEPUTY CLERK DATE

Copy 1—Upon initiation of action, mail this copy to Director Copy 3—Upon termination of action, mail this copy to Director Copy 2—Upon filing document adding patent(s), mail this copy to Director Copy 4—Case file copy

ates Patent and Tradema	UNITED STA' United States Address: COMMI PO. Box 1 Alexandri	i, Virginia 22313-1450
FILING OR 371(C) DATE	FIRST NAMED APPLICANT	ATTY. DOCKET NO./TITLE
01/12/2007	G.R. Mohan Rao	GRTD.01.01.DV1
11/622,496 01/12/2007 40672 LAW OFFICE OF BILL NAIFEH PO BOX 803423 DALLAS, TX 75380		CONFIRMATION NO. 3086 F ATTORNEY NOTICE
	FILING OR 371(C) DATE 01/12/2007	United States Address: COMMS PO.Box 1 Adexandria www.uspt FILING OR 371(C) DATE FIRST NAMED APPLICANT 01/12/2007 G.R. Mohan Rao POWER O MFEH

NOTICE REGARDING CHANGE OF POWER OF ATTORNEY

This is in response to the Power of Attorney filed 10/07/2021.

• The Power of Attorney to you in this application has been revoked by the assignee who has intervened as provided by 37 CFR 3.71. Future correspondence will be mailed to the new address of record(37 CFR 1.33).

Questions about the contents of this notice and the requirements it sets forth should be directed to the Office of Data Management, Application Assistance Unit, at (571) 272-4000 or (571) 272-4200 or 1-888-786-0101.

/mbeyene/

page 1 of 1

UNITED ST	ates Patent and Tradema	UNITED STA' United States Address: COMMIS	a, Virginia 22313-1450
APPLICATION NUMBER	FILING OR 371(C) DATE	FIRST NAMED APPLICANT	ATTY. DOCKET NO./TITLE
11/622,496	01/12/2007	G.R. Mohan Rao	GRTD60-32611
25883 MUNCK WILSON MANDALA L.L.P P.O. Drawer 800889 DALLAS, TX 75380			CONFIRMATION NO. 3086 EPTANCE LETTER

NOTICE OF ACCEPTANCE OF POWER OF ATTORNEY

This is in response to the Power of Attorney filed 10/07/2021.

The Power of Attorney in this application is accepted. Correspondence in this application will be mailed to the above address as provided by 37 CFR 1.33.

Questions about the contents of this notice and the requirements it sets forth should be directed to the Office of Data Management, Application Assistance Unit, at (571) 272-4000 or (571) 272-4200 or 1-888-786-0101.

/mbeyene/

page 1 of 1

	U.S. Patent ar	Approved for use through 03/31/2021. OMB 0651-003 In Trademark Office; U.S. DEPARTMENT OF COMMERCE
Under the Paperwork Reduction Act of 1995 no persons are required to		
PATENT - POWER OF ATTORNEY	Patent Number	8,421,195
OR	Issue Date	2013-04-16
7.5	First Named Inventor	G.R. Mohan RAO
REVOCATION OF POWER OF ATTORNEY	Title	SEMICONDUCTOR
WITH A NEW POWER OF ATTORNEY		DEVICES WITH GRADED
AND		DOPANT REGIONS
CHANGE OF CORRESPONDENCE ADDRESS	Attorney Docket No.	GRTD60-32611
I hereby revoke all previous powers of attorney given in the above-ider	ntified patent.	
 A Power of Attorney is submitted herewith. I hereby appoint Practitioner(s) associated with the Customer Num attorney(s) or agent(s) with respect to the patent identified above States Patent and Trademark Office connected therewith: I hereby appoint Practitioner(s) named below as my/our attorney(all business in the United States Patent and Trademark Office conr 	, and to transact all busin s) or agent(s) with respec	ess in the United 25883
Practitioner(s) Name		egistration Number
OR The address associated with the above-identified Customer Numb OR The address associated with the Customer Number identified in th OR Firm or Individual Name Address	1	3
City	State	Zip
Country		
Telephone	Email	
I am the: Applicant. OR Patent owner. Statement under 37 CFR 3.73(c) (Form PTO/AIA/96) submitted her //	ewith or filed on licant or Patent Owner Greenbread, LLC	Date 7/2x-22x-21 Telephone 224 7/28 8/244
NOTE: Signatures of all the applicants or patent owners of the entire is required, submit multiple forms, check the box below, and identify t A total of forms are submitted.	nterest or their represen	
		a an eastain - than a star

PTO/AIA/81A (02-15)

This collection of information is required by 37 GFR 1.31, 1.32, and 1.33. The information is required to obtain or retain a benefit by the public, which is to update (and by the USPTO to process) the file of a patent or reexamination proceeding. Confidentiality is governed by 35 U.S.C. 122 and 37 GFR 1.14. This collection is estimated to take 3 minutes to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. 80x 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR

If you need assistance in completing the form, coll 1-800-PTO-9199 and select option 2.

Electronic Ac	Electronic Acknowledgement Receipt		
EFS ID:	43954488		
Application Number:	11622496		
International Application Number:			
Confirmation Number:	3086		
Title of Invention:	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS		
First Named Inventor/Applicant Name:	G.R. Mohan Rao		
Customer Number:	40672		
Filer:	Gregory Michael Howison		
Filer Authorized By:			
Attorney Docket Number:	GRTD.01.01.DV1		
Receipt Date:	07-OCT-2021		
Filing Date:	12-JAN-2007		
Time Stamp:	11:42:37		
Application Type:	Utility under 35 USC 111(a)		

Payment information:

Submitted with Payment		no				
File Listing	g:					
Document Number	Document Description		File Name	File Size(Bytes)/ Message Digest	Multi Part /.zip	Pages (if appl.)
				120620		
1	Assignee showing of ownership per 37 CFR 3.73		GRT32611373STMT.pdf	b2a7259e26c87f8e7a642c4b7fa9da3b56e8 aa23	no	3
Warnings:						

Information:					
		GRT32611POACHANGEADD.	1027082		
2	Power of Attorney	pdf	8f46fd57bac53173c2e2064aa1566b991ab2 0f01	no	1
Warnings:					
Information:					
		Total Files Size (in bytes)	11	47702	
This Acknowledgement Receipt evidences receipt on the noted date by the USPTO of the indicated documents, characterized by the applicant, and including page counts, where applicable. It serves as evidence of receipt similar to a Post Card, as described in MPEP 503. <u>New Applications Under 35 U.S.C. 111</u> If a new application is being filed and the application includes the necessary components for a filing date (see 37 CFR 1.53(b)-(d) and MPEP 506), a Filing Receipt (37 CFR 1.54) will be issued in due course and the date shown on this Acknowledgement Receipt will establish the filing date of the application. <u>National Stage of an International Application under 35 U.S.C. 371</u> If a timely submission to enter the national stage of an international application is compliant with the conditions of 35 U.S.C. 371 and other applicable requirements a Form PCT/DO/EO/903 indicating acceptance of the application as a national stage submission under 35 U.S.C. 371 will be issued in addition to the Filing Receipt, in due course. <u>New International Application Filed with the USPTO as a Receiving Office</u> If a new international application is being filed and the international application includes the necessary components for an international filing date (see PCT Article 11 and MPEP 1810), a Notification of the International Application Number and of the International Filing Date (Form PCT/RO/105) will be issued in due course, subject to prescriptions concerning national security, and the date shown on this Acknowledgement Receipt will establish the international filing date of			imilar to a 37 CFR nis ons of 35 n as a oonents for Number oncerning		

PTO/AIA/96 (08-12) Approved for use through 01/31/2013. OMB 0651-0031 U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMENCE Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number.

	STATEMENT UNDER 37 CFR 3.73(c)		
Applicant/Patent Owner	r: Greenthread, LLC		
Application No./Patent	No.: 8,421,195 Filed/Issue Date: 2013-04-16		
Titled: SEMICON	DUCTOR DEVICES WITH GRADED DOPANT REGIONS		
Greenthread, LL	C, a Limited Liability Company		
(Name of Assignee)	(Type of Assignee, e.g., corporation, partnership, university, government agency, etc.)		
states that, for the pate	nt application/patent identified above, it is (choose one of options 1, 2, 3 or 4 below):		
1. 🗴 The assignee o	f the entire right, title, and interest.		
2. 🗌 An assignee of	less than the entire right, title, and interest (check applicable box):		
	by percentage) of its ownership interest is%. Additional Statement(s) by the owners ance of the interest <u>must be submitted</u> to account for 100% of the ownership interest.		
There are un right, title and ir	nspecified percentages of ownership. The other parties, including inventors, who together own the entire nterest are:		
Additional St right, title, and i	atement(s) by the owner(s) holding the balance of the interest <u>must be submitted</u> to account for the entire nterest.		
	3. The assignee of an undivided interest in the entirety (a complete assignment from one of the joint inventors was made). The other parties, including inventors, who together own the entire right, title, and interest are:		
	Additional Statement(s) by the owner(s) holding the balance of the interest <u>must be submitted</u> to account for the entire right, title, and interest.		
	ia a court proceeding or the like (<i>e.g.</i> , bankruptcy, probate), of an undivided interest in the entirety (a mership interest was made). The certified document(s) showing the transfer is attached.		
The interest identified ir	n option 1, 2 or 3 above (not option 4) is evidenced by either (choose one of options A or B below):		
A. An assignment from the inventor(s) of the patent application/patent identified above. The assignment was recorded in the United States Patent and Trademark Office at Reel 035630, Frame 0391, or for which a copy thereof is attached.			
B. 🗌 A chain of title f	from the inventor(s), of the patent application/patent identified above, to the current assignee as follows:		
1. From:	То:		
The c	document was recorded in the United States Patent and Trademark Office at		
Reel	, Frame, or for which a copy thereof is attached.		
2. From:	То:		
The c	document was recorded in the United States Patent and Trademark Office at		
Reel	, Frame, or for which a copy thereof is attached.		
	[Page 1 of 2]		

This collection of information is required by 37 CFR 3.73(b). The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.11 and 1.14. This collection is estimated to take 12 minutes to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. **SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450**.

If you need assistance in completing the form, call 1-800-PTO-9199 and select option 2.

STATEMENT UNDER 37 CFR 3.73(c)		
3. From:	To:	
The document was recorded in the U	nited States Patent and Trademark Office at	
Reel, Frame	, or for which a copy thereof is attached.	
4. From:	To:	
The document was recorded in the U	nited States Patent and Trademark Office at	
Reel, Frame	, or for which a copy thereof is attached.	
5. From:	To:	
The document was recorded in the U	nited States Patent and Trademark Office at	
Reel, Frame	, or for which a copy thereof is attached.	
6. From:	To:	
The document was recorded in the U	nited States Patent and Trademark Office at	
Reel, Frame	, or for which a copy thereof is attached.	
Additional documents in the chain of title are listed on a supplemental sheet(s).		
As required by 37 CFR 3.73(c)(1)(i), the documentary evidence of the chain of title from the original owner to the assignee was, or concurrently is being, submitted for recordation pursuant to 37 CFR 3.11.		
[NOTE: A separate copy (i.e., a true copy of the original assignment document(s)) must be submitted to Assignment Division in accordance with 37 CFR Part 3, to record the assignment in the records of the USPTO. See MPEP 302.08]		
The undersigned (whose title is supplied below) is authorized to act on behalf of the assignee.		
/Gregory M. Howison, Reg. #30646/ October 5, 2021		
Signature	Date	
Gregory M. Howison	30,646	
Printed or Typed Name Title or Registration Number		

[Page 2 of 2]

Privacy Act Statement

The **Privacy Act of 1974 (P.L. 93-579)** requires that you be given certain information in connection with your submission of the attached form related to a patent application or patent. Accordingly, pursuant to the requirements of the Act, please be advised that: (1) the general authority for the collection of this information is 35 U.S.C. 2(b)(2); (2) furnishing of the information solicited is voluntary; and (3) the principal purpose for which the information is used by the U.S. Patent and Trademark Office is to process and/or examine your submission related to a patent application or patent. If you do not furnish the requested information, the U.S. Patent and Trademark Office may not be able to process and/or examine your submission, which may result in termination of proceedings or abandonment of the application or expiration of the patent.

The information provided by you in this form will be subject to the following routine uses:

- 1. The information on this form will be treated confidentially to the extent allowed under the Freedom of Information Act (5 U.S.C. 552) and the Privacy Act (5 U.S.C 552a). Records from this system of records may be disclosed to the Department of Justice to determine whether disclosure of these records is required by the Freedom of Information Act.
- 2. A record from this system of records may be disclosed, as a routine use, in the course of presenting evidence to a court, magistrate, or administrative tribunal, including disclosures to opposing counsel in the course of settlement negotiations.
- 3. A record in this system of records may be disclosed, as a routine use, to a Member of Congress submitting a request involving an individual, to whom the record pertains, when the individual has requested assistance from the Member with respect to the subject matter of the record.
- 4. A record in this system of records may be disclosed, as a routine use, to a contractor of the Agency having need for the information in order to perform a contract. Recipients of information shall be required to comply with the requirements of the Privacy Act of 1974, as amended, pursuant to 5 U.S.C. 552a(m).
- 5. A record related to an International Application filed under the Patent Cooperation Treaty in this system of records may be disclosed, as a routine use, to the International Bureau of the World Intellectual Property Organization, pursuant to the Patent Cooperation Treaty.
- 6. A record in this system of records may be disclosed, as a routine use, to another federal agency for purposes of National Security review (35 U.S.C. 181) and for review pursuant to the Atomic Energy Act (42 U.S.C. 218(c)).
- 7. A record from this system of records may be disclosed, as a routine use, to the Administrator, General Services, or his/her designee, during an inspection of records conducted by GSA as part of that agency's responsibility to recommend improvements in records management practices and programs, under authority of 44 U.S.C. 2904 and 2906. Such disclosure shall be made in accordance with the GSA regulations governing inspection of records for this purpose, and any other relevant (*i.e.*, GSA or Commerce) directive. Such disclosure shall not be used to make determinations about individuals.
- 8. A record from this system of records may be disclosed, as a routine use, to the public after either publication of the application pursuant to 35 U.S.C. 122(b) or issuance of a patent pursuant to 35 U.S.C. 151. Further, a record may be disclosed, subject to the limitations of 37 CFR 1.14, as a routine use, to the public if the record was filed in an application which became abandoned or in which the proceedings were terminated and which application is referenced by either a published application, an application open to public inspection or an issued patent.
- 9. A record from this system of records may be disclosed, as a routine use, to a Federal, State, or local law enforcement agency, if the USPTO becomes aware of a violation or potential violation of law or regulation.

Case 2:19-cv-00147-JRG Document 3 Filed 05/01/19 Page 1 of 1 PageID #: 135

AO 120 (Rev. 08/10)

DECISION/JUDGEMENT

TO: Director of the U.S. Patent and Trademark Office P.O. Box 1450 Alexandria, VA 22313-1450		REPORT ON THE Office FILING OR DETERMINATION OF AN ACTION REGARDING A PATENT OR TRADEMARK		
In Compliance with 35 U.S.C. § 290 and/or 15 U.S.C. § 1116 you are hereby advised that a court action has been filed in the U.S. District Court Eastern District of Texas, Marshall Division on the following Trademarks or Patents. (the patent action involves 35 U.S.C. § 292.):				
DOCKET NO. 2:19-cv-147	DATE FILED 4/30/2019	U.S. DISTRICT COURT Eastern District of Texas, Marshall Division		
PLAINTIFF Greenthread, LLC	•	DEFENDANT Samsung Electronics Co., Ltd, Samsung Semiconductor, Inc. Samsung Electronics America, Inc. Samsung Austin Semiconductor, LLC		
PATENT OR TRADEMARK NO.	DATE OF PATENT OR TRADEMARK	HOLDER OF PATENT OR TRADEMARK		
1 8,421,195 B2	4/16/2013	Greenthread, LLC		
2 9,190,502 B2	11/17/2015	Greenthread, LLC		
3 8,106,481 B2	1/31/2012	Greenthread, LLC		
4 9,647,070 B2	5/9/2017	Greenthread, LLC		
5				

In the above-entitled case, the following patent(s)/ trademark(s) have been included:

DATE INCLUDED	INCLUDED BY				
	Amen	dment	Answer	Cross Bill	Other Pleading
PATENT OR TRADEMARK NO.	DATE OF PATENT OR TRADEMARK		HOLDER	R OF PATENT OR 1	RADEMARK
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In the above-entitled case, the following decision has been rendered or judgement issued:

CLERK (BY) DEPUTY CLERK DATE

Copy 1---Upon initiation of action, mail this copy to Director Copy 3---Upon termination of action, mail this copy to Director Copy 2----Upon filing document adding patent(s), mail this copy to Director Copy 4---Case file copy



APPLICATION NUMBER	FILING OR 371(C) DATE	FIRST NAMED APPLICANT	ATTY.DOCKET NO./TITLE	REQUEST ID
11/622,496	01/12/2007	G.R. Mohan Rao	GRTD.01.01.DV1	121958

Acknowledgement of Loss of Entitlement to Entity Status Discount

The entity status change request below filed through Private PAIR on 09/28/2020 has been accepted.

CERTIFICATIONS:

Change of Entity	y Status:
× Applicant changir	ng to regular undiscounted fee status.
NOTE: Checking thi applicable.	s box will be taken to be notification of loss of entitlement to small or micro entity status, as

This portion must be completed by the signatory or signatories making the entity status change in accordance with 37 CFR 1.4(d)(4).

Signature: /Bill R. Naifeh, Reg. No. 44962/	
Name:	Bill R. Naifeh
Registration Number:	44962

Case 2:19-cv-00147-JRG Document 3 Filed 05/01/19 Page 1 of 1 PageID #: 135

AO	120 (Rev.	08/10)

TO: Mail Stop 8 Director of the U.S. Patent and Trademark Office P.O. Box 1450 Alexandria, VA 22313-1450		REPORT ON THE Diffice FILING OR DETERMINATION OF AN ACTION REGARDING A PATENT OR TRADEMARK			
filed in the U.S. Dist	In Compliance with 35 U.S.C. § 290 and/or 15 U.S.C. § 1116 you are hereby advised that a court action has been filed in the U.S. District Court Eastern District of Texas, Marshall Division on the following Trademarks or Patents. (the patent action involves 35 U.S.C. § 292.):				
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PLAINTIFF Greenthread, LLC		DEFENDANT Samsung Electronics Co., Ltd, Samsung Semiconductor, Inc. Samsung Electronics America, Inc. Samsung Austin Semiconductor, LLC			
PATENT OR TRADEMARK NO.	DATE OF PATENT OR TRADEMARK	HOLDER OF PATENT OR TRADEMARK			
i 8,421,195 B2	4/16/2013	Greenthread, LLC			
2 9,190,502 B2	11/17/2015	Greenthread, LLC			
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(BY) DEPUTY CLERK

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UNITED STATES PATENT AND TRADEMARK OFFICE United States Patent and Trademark Office Address: COMMISSIONER FOR PATENTS PO. Box 1450 Alexandria, Virginia 22313-1450 www.uspto.gov					
APPLICATION NUMBER	FILING OR 371(C) DATE	FIRST NAMED APPLICANT	ATTY. DOCKET NO./TITLE		
11/622,496	01/12/2007	G.R. Mohan Rao	GRTD-32611		
25883 MUNCK WILSON MAND/ P.O. Drawer 800889 DALLAS, TX 75380	11/622,496 01/12/2007 G.R. Mohan Rao GRTD-32611 CONFIRMATION NO. 3 5883 POWER OF ATTORNEY NOTICE 1UNCK WILSON MANDALA L.L.P .O. Drawer 800889				

NOTICE REGARDING CHANGE OF POWER OF ATTORNEY

This is in response to the Power of Attorney filed 03/24/2020.

• The Power of Attorney to you in this application has been revoked by the assignee who has intervened as provided by 37 CFR 3.71. Future correspondence will be mailed to the new address of record(37 CFR 1.33).

Questions about the contents of this notice and the requirements it sets forth should be directed to the Office of Data Management, Application Assistance Unit, at (571) 272-4000 or (571) 272-4200 or 1-888-786-0101.

/mmasfaw/

page 1 of 1

UNITED ST	ates Patent and Trademai	UNITED STA' United States Address: COMMI PO Box I	a, Virginia 22313-1450
APPLICATION NUMBER	FILING OR 371(C) DATE	FIRST NAMED APPLICANT	ATTY. DOCKET NO./TITLE
11/622,496	01/12/2007	G.R. Mohan Rao	GRTD.01.01.DV1
40672 BILL R. NAIFEH PO BOX 803423 DALLAS, TX 75380			CONFIRMATION NO. 3086 EPTANCE LETTER

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/mmasfaw/

page 1 of 1

PTO/AIA/81A (02-15) Approved for use through 03/31/2021. OMB 0651-0035 U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE Under the Paperwork Reduction Act of 1995 no persons are required to respond to a collection of information unless it displays a valid OMB control number Patent Number 8,421,195 **PATENT - POWER OF ATTORNEY** Issue Date 04-16-2013 np First Named Inventor G.R. Mohan Rao **REVOCATION OF POWER OF ATTORNEY** Title SEMICONDUCTOR DEVICES WITH A NEW POWER OF ATTORNEY WITH GRADED DOPANT AND REGIONS CHANGE OF CORRESPONDENCE ADDRESS Attorney Docket No. GRTD.01.01.DV1 I hereby revoke all previous powers of attorney given in the above-identified patent. A Power of Attorney is submitted herewith. OR I hereby appoint Practitioner(s) associated with the Customer Number identified in the box at right as my/our X attorney(s) or agent(s) with respect to the patent identified above, and to transact all business in the United 40672 States Patent and Trademark Office connected therewith: OR I hereby appoint Practitioner(s) named below as my/our attorney(s) or agent(s) with respect to the patent identified above, and to transact $m{J}$ all business in the United States Patent and Trademark Office connected therewith: Practitioner(s) Name **Registration Number** Please recognize or change the correspondence address for the above-identified patent to: \mathbf{X} The address associated with the above-identified Customer Number. The address associated with the Customer Number identified in the box at right: OR. Firm or Indivídual Name Address City State Zip Country Telephone Email 1 am the: Applicant. OR Patent owner Patent Owner. Statement under 37 CFR 3.73(c) (Form PTO/AIA/96) submitted herewith or filed on _06-01-2016 SIGNATURE of Applicant or Patent Owner Signature Date Sam Name Philip W. John, Telephone Title and Company PRESIDEN of GREENTHREAD, LLC NOTE: Signatures of all the applicants or patent owners of the entire interest or their representative(s) are required. If more than one signature is required, submit multiple forms, check the box below, and identify the total number of forms submitted in the blank below. 🖌 A total of 🕺 forms are submitted.

This collection of information is regulted by 37 CFR 1.31, 1.32, and 1.33. The information is required to obtain or retain a benefit by the public, which is to update (and by the USPTO to process) the file of a patent or reexamination proceeding. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 3 minutes to complete, including gathering, preparing, and submitting the completed application form to the USPTD. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450, DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

If you need assistance in completing the form, coll 1-800-PTO-9199 and select option 2.

Electronic Ac	Electronic Acknowledgement Receipt				
EFS ID:	38951953				
Application Number:	11622496				
International Application Number:					
Confirmation Number:	3086				
Title of Invention:	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS				
First Named Inventor/Applicant Name:	G.R. Mohan Rao				
Customer Number:	25883				
Filer:	Bill Naifeh/April Reasoner				
Filer Authorized By:	Bill Naifeh				
Attorney Docket Number:	GRTD-32611				
Receipt Date:	24-MAR-2020				
Filing Date:	12-JAN-2007				
Time Stamp:	13:35:00				
Application Type:	Utility under 35 USC 111(a)				

Payment information:

Submitted with Payment		no				
File Listing:						
Document Number	Document Description		File Name	File Size(Bytes)/ Message Digest	Multi Part /.zip	Pages (if appl.)
				2184135		
1	1 Power of Attorney	PC	DA_8421195_GRTD0101DV1. pdf	12cacaad717a3a8effb040956d502574c149 7c1d	no	1
Warnings:		-		<u> </u>	1	

Information:

Total Files Size (in bytes):

This Acknowledgement Receipt evidences receipt on the noted date by the USPTO of the indicated documents, characterized by the applicant, and including page counts, where applicable. It serves as evidence of receipt similar to a Post Card, as described in MPEP 503.

New Applications Under 35 U.S.C. 111

If a new application is being filed and the application includes the necessary components for a filing date (see 37 CFR 1.53(b)-(d) and MPEP 506), a Filing Receipt (37 CFR 1.54) will be issued in due course and the date shown on this Acknowledgement Receipt will establish the filing date of the application.

National Stage of an International Application under 35 U.S.C. 371

If a timely submission to enter the national stage of an international application is compliant with the conditions of 35 U.S.C. 371 and other applicable requirements a Form PCT/DO/EO/903 indicating acceptance of the application as a national stage submission under 35 U.S.C. 371 will be issued in addition to the Filing Receipt, in due course. New International Application Filed with the USPTO as a Receiving Office

If a new international application is being filed and the international application includes the necessary components for an international filing date (see PCT Article 11 and MPEP 1810), a Notification of the International Application Number and of the International Filing Date (Form PCT/RO/105) will be issued in due course, subject to prescriptions concerning national security, and the date shown on this Acknowledgement Receipt will establish the international filing date of the application.

UNITED ST	ates Patent and Tradem	UNITED STA United States Address COMMI PO. Box I	, Virginia 22313-1450
APPLICATION NUMBER	FILING OR 371(C) DATE	FIRST NAMED APPLICANT	ATTY. DOCKET NO./TITLE
11/622,496	01/12/2007	G.R. Mohan Rao	0299-0001.01
70653 EUGENE M. CUMMINGS 55 W. MONROE SUITE 3500 CHICAGO, IL 60603	, P.C.		CONFIRMATION NO. 3086 F ATTORNEY NOTICE

Date Mailed: 06/08/2015

NOTICE REGARDING CHANGE OF POWER OF ATTORNEY

This is in response to the Power of Attorney filed 06/01/2015.

• The Power of Attorney to you in this application has been revoked by the assignee who has intervened as provided by 37 CFR 3.71. Future correspondence will be mailed to the new address of record(37 CFR 1.33).

Questions about the contents of this notice and the requirements it sets forth should be directed to the Office of Data Management, Application Assistance Unit, at (571) 272-4000 or (571) 272-4200 or 1-888-786-0101.

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page 1 of 1

UNITED ST.	ates Patent and Trademai	UNITED STA' United States Address: COMMI PO. Box I	, Virginia 22313-1450
APPLICATION NUMBER	FILING OR 371(C) DATE	FIRST NAMED APPLICANT	ATTY. DOCKET NO./TITLE
11/622,496	01/12/2007	G.R. Mohan Rao	GRTD-32611
25883 HOWISON & ARNOTT, L P.O. BOX 741715 DALLAS, TX 75374-1715	.L.P		CONFIRMATION NO. 3086 EPTANCE LETTER

NOTICE OF ACCEPTANCE OF POWER OF ATTORNEY

This is in response to the Power of Attorney filed 06/01/2015.

The Power of Attorney in this application is accepted. Correspondence in this application will be mailed to the above address as provided by 37 CFR 1.33.

Questions about the contents of this notice and the requirements it sets forth should be directed to the Office of Data Management, Application Assistance Unit, at (571) 272-4000 or (571) 272-4200 or 1-888-786-0101.

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page 1 of 1

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PTC/98/81A (12-08)
Approved for use Investigh 11/30/2011. (2008)-0035
U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE
Under the Papenetek Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number.

PATENT - POWER OF ATTORNEY	Patent Number	8,421,195	
OR	Issue Date	04/16/2013	
REVOCATION OF POWER OF ATTORNEY	First Named Inventor	RAO, G.R. MOHAN	
WITH A NEW POWER OF ATTORNEY AND	Title	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS	
CHANGE OF CORRESPONDENCE ADDRESS	Attorney Docket Number	GRTD-32611	
r			0000
I hereby revoke all previous powers of attorney given i	n the above-identified p	21601.	0000
A Power of Attorney is submitted herewith.			
I hereby appoint Practitioner(s) associated with the fo attorney(s) or agent(s) with respect to the patent ident the United States Patent and Trademark Office conne OR	ified above, and to transau		
I hereby appoint Practitioner(s) named below as my/o above, and to transact all business in the United State			
Practitioner(s) Name	Re	gistration Number	
			0000
Please recognize or change the correspondence address for the abc			,
OR			
The address associated with Customer Number:	*****		
r Firm or			
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lam the:			vicia
Inventor, having exmanship of the patient.			
OR			
Statement under 37 CFR 3.73(b) (Form PTO/SIM98) submitte	d herewith or filed on		
SIGNATURE of Invent			-
Signature This I have been	Date	5/20/2015	1
Name PHILIP W JOHN JR	Teler	none 214-728-8244	
Title and Company PLASIDENT	GREENTHRE	AO, LLC	
NOTE: Signatures of all the inventors or patient owners of the entire interest signature la required, see below".	or their representative(s) are no	pined. Submit multiple forms i racon than ano	
Total of 1forms are submitted.			

If you need assistance in completing the form, call 1-800-PTO-9199 and select option 2.

This collection of information is required by 37 CFR 1.31, 1.32 and 1.23. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.3.C. 122 and 37 CFR 1.11 and 1.14. This collection is retinated to take 3 minutes to complete, including gathering, propering, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comparison the anticipant of time you require to complete the form and/or suggestions for reducing the build to the Crief Information Officer, U.S. Peters and the second to the USPTO. The will vary depending upon the individual case. Any comparison the anticipant of time you require to complete time form and/or suggestions for reducing this buntler, should be sent to the Crief Information Officer, U.S. Peters and Tradement Office, U.S. Department of Committee, P.O. Box 1480, Alexandria, VA 22313-1480. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissionation for Patents, P.O. Box 1450, Alexandria, VA 22313-1480.

PTO/S8/96 (07-06) Approved for use through 07/31/2012, CMB 0851-4031 indemark Office: U.S. DEPARTMENT OF COMMERCE

U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE	
Under the Papenwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid CMIB control number.	,

STATEMENT UNDER 37 CFR 3.73(b)									
Applicant/Patent Owner: Greenthread, LLC									
Application No./Patent No.: 8,421,195	Application No./Patent No.: 8,421,195 Filed/Issue Date: April 16, 2013								
Titled: SEMICONDUCTOR DEVICES WITH	H GRADED DOPANT REG	IONS							
Greenthread, LLC	a Corporation								
(Nerret of Assigned)	(Type of Assigner, e.c	., copuration, partnership, university, government agency, etc.							
states that it is:									
1. 🔀 the assignce of the entire right, tills, an	x) interest in;								
2 an assignee of less than the entire right (The extent (by percentage) of its owne		5); cr							
3. The assignee of an undivided interest in	the entirety of (a complete six	ignment from one of the joint inventors was made)							
the patent application/patent identified above, by vi		• • • • • • • • • • • • • • • • • • •							
A. X An assignment from the inventor(s) of t	the patent application/patent id-	antified above. The assignment was recorded in, Frame 0391, or for which a							
OR COR									
B. A chain of title from the inventor(s), of the inventor o	he patent application/patent ide	intified above, to the current assignee as follows:							
1. From:	To								
	in the United States Patent an								
Reel	, Frame	, or for which a copy thereof is attached.							
2. From:	To								
The document was recorded	in the United States Patent and								
Reel	, Frame	_, or for which a copy thereof is attached.							
3. From:	To:								
	in the United States Patent and								
Reel	, Frame	or for which a copy thereof is attached.							
Additional documents in the chain of tit	ie are listed on a supplemental	sheet(s).							
As required by 37 CFR 3.73(b)(1)(), the doo or concurrently is being, submitted for record		in of title from the original owner to the assignee was,							
accordance with 37 CFR Part 3, to record the	e assignment in the records of								
The undersigned (whose title is supplied below) is a	suthorized to act on behalf of it	e aesignae.							
Philippine Yaka Jr.		<u>5/20/20/5</u> Obte							
PHILIP W. Latin In		MESIDEN							
Printed or Typed Name		Tible							
This collection of information is required by 37 CFR 3.73(b). The is proceed on antibation. Confidentially is presented by 35 (1.5.0)									

processly an expansion. Lonnancesy is governed by do U.S.A. 122 and 37 CPH 1.11 and 1.14. The controllor is approach to the 12 minutes to complete, including galaxing, and submitting the complete application form to the USPN 0. Three will very depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing the busiest, should be said to the COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patenta, P.O. Box 1480, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patenta, P.O. Box 1480, Alexandria, VA 22313-1450.

If you must assistance in completing the form, call 1-800-PTO-9199 and select option 2.

Electronic A	cknowledgement Receipt
EFS ID:	22481607
Application Number:	11622496
International Application Number:	
Confirmation Number:	3086
Title of Invention:	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS
First Named Inventor/Applicant Name:	G.R. Mohan Rao
Customer Number:	70653
Filer:	Gregory Michael Howison/Heather Hamilton
Filer Authorized By:	Gregory Michael Howison
Attorney Docket Number:	0299-0001.01
Receipt Date:	01-JUN-2015
Filing Date:	12-JAN-2007
Time Stamp:	17:54:54
Application Type:	Utility under 35 USC 111(a)

Payment information:

Submitted with Payment			no				
File Listing:							
Document Number	Document Description		File Name	File Size(Bytes)/ Message Digest	Multi Part /.zip	Pages (if appl.)	
1	Power of Attorney		GRT32611POAEXE.pdf	642022	no	1	
				12e9c8c605e84c992a66f6dbf27d21bbf40e 0f93			
Warnings:							
Information:							

Warnings:						1
2	Assignee showing of ownership per 37 CFR 3.73	GRT32611STMT373bEXE.pdf	602530 7949fff2285221279cfa919f38bd9ff17abdb 5ae	no	1	

Information:

Total Files Size (in bytes):	1244552
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This Acknowledgement Receipt evidences receipt on the noted date by the USPTO of the indicated documents, characterized by the applicant, and including page counts, where applicable. It serves as evidence of receipt similar to a Post Card, as described in MPEP 503.

New Applications Under 35 U.S.C. 111

If a new application is being filed and the application includes the necessary components for a filing date (see 37 CFR 1.53(b)-(d) and MPEP 506), a Filing Receipt (37 CFR 1.54) will be issued in due course and the date shown on this Acknowledgement Receipt will establish the filing date of the application.

National Stage of an International Application under 35 U.S.C. 371

If a timely submission to enter the national stage of an international application is compliant with the conditions of 35 U.S.C. 371 and other applicable requirements a Form PCT/DO/EO/903 indicating acceptance of the application as a national stage submission under 35 U.S.C. 371 will be issued in addition to the Filing Receipt, in due course.

New International Application Filed with the USPTO as a Receiving Office

If a new international application is being filed and the international application includes the necessary components for an international filing date (see PCT Article 11 and MPEP 1810), a Notification of the International Application Number and of the International Filing Date (Form PCT/RO/105) will be issued in due course, subject to prescriptions concerning national security, and the date shown on this Acknowledgement Receipt will establish the international filing date of the application. UNITED STATES PATENT AND TRADEMARK OFFICE



APPLICATION NO.		ISSUE DATE	PATENT NO.	ATTORNEY DOCKET NO.	CONFIRMATION NO.
11/622,496		04/16/2013	8421195	0299-0001.01	3086
70653	7590	03/27/2013			

LAW OFFICES OF EUGENE M. CUMMINGS, P.C. ONE NORTH WACKER DRIVE SUITE 4130 CHICAGO, IL 60606

ISSUE NOTIFICATION

The projected patent number and issue date are specified above.

Determination of Patent Term Adjustment under 35 U.S.C. 154 (b)

(application filed on or after May 29, 2000)

The Patent Term Adjustment is 0 day(s). Any patent to issue from the above-identified application will include an indication of the adjustment on the front page.

If a Continued Prosecution Application (CPA) was filed in the above-identified application, the filing date that determines Patent Term Adjustment is the filing date of the most recent CPA.

Applicant will be able to obtain more detailed information by accessing the Patent Application Information Retrieval (PAIR) WEB site (http://pair.uspto.gov).

Any questions regarding the Patent Term Extension or Adjustment determination should be directed to the Office of Patent Legal Administration at (571)-272-7702. Questions relating to issue and publication fee payments should be directed to the Application Assistance Unit (AAU) of the Office of Data Management (ODM) at (571)-272-4200.

APPLICANT(s) (Please see PAIR WEB site http://pair.uspto.gov for additional applicants):

G.R. Mohan Rao, McKinney, TX;

The United States represents the largest, most dynamic marketplace in the world and is an unparalleled location for business investment, innovation, and commercialization of new technologies. The USA offers tremendous resources and advantages for those who invest and manufacture goods here. Through SelectUSA, our nation works to encourage and facilitate business investment. To learn more about why the USA is the best country in the world to develop technology, manufacture products, and grow your business, visit <u>SelectUSA.gov</u>.

PART B - FEE(S) TRANSMITTAL

Complete and send this form, together with applicable fee(s), to: <u>Mail</u> Mail Stop ISSUE FEE Commissioner for Patents

Com	miss	ion	er f	or	P	ai
P.O.	Box	145	50			

Alexandria, Virginia	22313-1450
(571)-273-2885	

	2 Michandra,
or <u>Fax</u>	(571)-273-28

INSTRUCTIONS: This appropriate. All further indicated unless correcte maintenance fee notifica	form should be used correspondence include ed below or directed of tions.	for transmitting the IS ing the Patent, advance therwise in Block 1, by	SUE FEE and PUBLICAT orders and notification of 1 (a) specifying a new corre	ION FEE (if required in the second se	ired). Blocks vill be maile ; and/or (b) i	s 1 through 5 sl d to the current indicating a sepa	hould be completed where correspondence address as arate "FEE ADDRESS" for
70653 LAW OFFICE	7590 12/1 S OF EUGENE N VACKER DRIVE	3lock 1 for any change of address 2/2012 M. CUMMINGS,	Fee pap hav F.C. I he Stat add tran	(s) Transmittal. Thi ers. Each additiona e its own certificate FUTRONIとト Cer reby certify that th	is certificate l paper, such of mailing c - λ λ G tificate of M is Fee(s) Tra vith sufficient I Stop ISSU TO (571) 273	cannot be used f as an assignme or transmission. failing or Transmission. Insmittal is being t postage for firs E FEE address 3-2885, on the data	g deposited with the United st class mail in an envelope above, or being facsimile ate indicated below.
			M	arch 12,	2013		(Date)
APPLICATION NO.	FILING DATE	3	FIRST NAMED INVENTOR		ATTORNEY	DOCKET NO.	CONFIRMATION NO.
11/622,496	01/12/2007	and the second secon	G.R. Mohan Rao		0299-	0001.01	3086
TITLE OF INVENTION	SEMICONDUCTOR	DEVICES WITH GRAI	DED DOPANT REGIONS				
APPLN. TYPE	SMALL ENTIFY	ISSUE FEE DUE	PUBLICATION FEE DUE	PREV. PAID ISSUE	E FEE TO	TAL FEE(S) DUE	DATE DUE
nonprovisional	YES	\$885	\$300	\$0		\$1185	03/12/2013
EXAM	INER	ART UNIT	CLASS-SUBCLASS				
ARORA	, AJAY	2892	257-371000	•			
"Fee Address" indication (or "Fee Address" Indication form registered attorney or agent) and the names of up to					• M. Cummings, *		
PLEASE NOTE: Unle recordation as set forth (A) NAME OF ASSIC	ess an assignee is ident 1 in 37 CFR 3.11. Comj 3NEE	ified below, no assigned pletion of this form is NO	THE PATENT (print or type e data will appear on the p OT a substitute for filing an (B) RESIDENCE: (CITY	ttent. If an assigned assignment. and STATE OR C	OUNTRY)		ocument has been filed for
Please check the appropri		·····	· · · · · · · · · · · · · · · · · · ·	total and the second			- <u></u>
4a. The following fee(s) a Issue Fee Publication Fee (N Advance Order - #	re submitted: o small entity discount j of Copies	permitted)	 4b. Payment of Fee(s): (Plea A check is enclosed. Payment by credit can The Director is hereby overpayment, to Depo 	d. Form PTO-2038	is attached.	-	·
5. Change in Entity Stat	us (from status indicate SMALL ENTITY state	,	b. Applicant is no long	er claiming SMAI	L ENTITY s	status. See 37 CF	R 1.27(g)(2)
			ed from anyone other than the Voltage of the second				
Authorized Signature	Uil W.	funt		Mar Date	ch 12	, 2013	
Typed or printed name				Registration No			
Alexandria, virginia 223 i	.3-1450.		ion is required to obtain or r t 1.14. This collection is esti- y depending upon the indiv- he Chief Information Office COMPLETED FORMS TO espond to a collection of info				

Electronic Patent Application Fee Transmittal						
Application Number:	116	522496				
Filing Date:	12-	Jan-2007				
Title of Invention:	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS					
First Named Inventor/Applicant Name:	G.R. Mohan Rao					
Filer:	David Michael Mundt/Francisca Hubbard					
Attorney Docket Number:	029	99-0001.01				
Filed as Small Entity						
Utility under 35 USC 111(a) Filing Fees						
Description		Fee Code	Quantity	Amount	Sub-Total in USD(\$)	
Basic Filing:						
Pages:						
Claims:						
Miscellaneous-Filing:						
Petition:						
Patent-Appeals-and-Interference:						
Post-Allowance-and-Post-Issuance:						
Utility Appl Issue Fee		2501	1	885	885	
Publ. Fee- Early, Voluntary, or Normal		1504	1	300	300	

Fee Code	Quantity	Amount	Sub-Total in USD(\$)				
Extension-of-Time:							
Miscellaneous:							
Total in USD (\$) 1185							

Electronic A	Electronic Acknowledgement Receipt						
EFS ID:	15191627						
Application Number:	11622496						
International Application Number:							
Confirmation Number:	3086						
Title of Invention:	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS						
First Named Inventor/Applicant Name:	G.R. Mohan Rao						
Customer Number:	70653						
Filer:	David Michael Mundt/Francisca Hubbard						
Filer Authorized By:	David Michael Mundt						
Attorney Docket Number:	0299-0001.01						
Receipt Date:	12-MAR-2013						
Filing Date:	12-JAN-2007						
Time Stamp:	15:32:54						
Application Type:	Utility under 35 USC 111(a)						

Payment information:

Submitted with Payment	yes				
ayment Type Deposit Account					
Payment was successfully received in RAM \$1185					
RAM confirmation Number 3028					
Deposit Account 504199					
Authorized User					
The Director of the USPTO is hereby authorized to charge indicated fees and credit any overpayment as follows:					
Charge any Additional Fees required under 37 C.F.R. Section 1.21 (Miscellaneous fees and charges)					

File Listin	g:				
Document Number	Document Description	File Name	File Size(Bytes)/ Message Digest	Multi Part /.zip	Pages (if appl.)
1	Issue Fee Payment (PTO-85B)	lssueFee.pdf	169875 03bcbf9d7d2927752ec0c60b4ff01d078e7f	no	1
Warnings:			afc1		
Information:					
2	Fee Worksheet (SB06)	31843	no	2	
_		fee-info.pdf	3959a4d0703527cbda6bd4c321ef249fa66 5b73d	110	L
Warnings:		1		1	
Information:					
		Total Files Size (in bytes):	20	01718	
Post Card, as <u>New Applica</u> If a new appl 1.53(b)-(d) an Acknowledge <u>National Stag</u> If a timely su U.S.C. 371 an national stag <u>New Internat</u> If a new inter an internatio and of the In	d by the applicant, and including page described in MPEP 503. <u>tions Under 35 U.S.C. 111</u> lication is being filed and the applica nd MPEP 506), a Filing Receipt (37 CF ement Receipt will establish the filin <u>ge of an International Application ur</u> bmission to enter the national stage ad other applicable requirements a F ge submission under 35 U.S.C. 371 wi <u>tional Application Filed with the USP</u> rnational application is being filed an onal filing date (see PCT Article 11 an ternational Filing Date (Form PCT/RC urity, and the date shown on this Ack on.	tion includes the necessary of R 1.54) will be issued in due g date of the application. <u>Inder 35 U.S.C. 371</u> of an international applicati orm PCT/DO/EO/903 indicati ill be issued in addition to the <u>PTO as a Receiving Office</u> and the international applicati d MPEP 1810), a Notification D/105) will be issued in due co	omponents for a filin course and the date s on is compliant with f ng acceptance of the Filing Receipt, in du ion includes the nece of the International J ourse, subject to pres	g date (see hown on th the condition application e course. ssary comp Application criptions co	37 CFR is ons of 35 as a onents for Number oncerning

UNITED STATES PATENT AND TRADEMARK OFFICE



UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Address: COMMISSIONER FOR PATENTS P.O. Box 1450 Alexandria, Virginia 22313-1450 www.uspto.gov

NOTICE OF ALLOWANCE AND FEE(S) DUE

⁷⁰⁶⁵³ 7590 12/12/2012 LAW OFFICES OF EUGENE M. CUMMINGS, P.C. ONE NORTH WACKER DRIVE SUITE 4130 CHICAGO, IL 60606 EXAMINER

ARORA, AJAY

ART UNIT PAPER NUMBER

DATE MAILED: 12/12/2012

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
11/622,496	01/12/2007	G.R. Mohan Rao	0299-0001.01	3086

TITLE OF INVENTION: SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS

APPLN. TYPE	SMALL ENTITY	ISSUE FEE DUE	PUBLICATION FEE DUE	PREV. PAID ISSUE FEE	TOTAL FEE(S) DUE	DATE DUE
nonprovisional	YES	\$885	\$300	\$0	\$1185	03/12/2013

THE APPLICATION IDENTIFIED ABOVE HAS BEEN EXAMINED AND IS ALLOWED FOR ISSUANCE AS A PATENT. <u>PROSECUTION ON THE MERITS IS CLOSED</u>. THIS NOTICE OF ALLOWANCE IS NOT A GRANT OF PATENT RIGHTS. THIS APPLICATION IS SUBJECT TO WITHDRAWAL FROM ISSUE AT THE INITIATIVE OF THE OFFICE OR UPON PETITION BY THE APPLICANT. SEE 37 CFR 1.313 AND MPEP 1308.

THE ISSUE FEE AND PUBLICATION FEE (IF REQUIRED) MUST BE PAID WITHIN <u>THREE MONTHS</u> FROM THE MAILING DATE OF THIS NOTICE OR THIS APPLICATION SHALL BE REGARDED AS ABANDONED. <u>THIS STATUTORY PERIOD CANNOT BE EXTENDED</u>. SEE 35 U.S.C. 151. THE ISSUE FEE DUE INDICATED ABOVE DOES NOT REFLECT A CREDIT FOR ANY PREVIOUSLY PAID ISSUE FEE IN THIS APPLICATION. IF AN ISSUE FEE HAS PREVIOUSLY BEEN PAID IN THIS APPLICATION (AS SHOWN ABOVE), THE RETURN OF PART B OF THIS FORM WILL BE CONSIDERED A REQUEST TO REAPPLY THE PREVIOUSLY PAID ISSUE FEE TOWARD THE ISSUE FEE NOW DUE.

HOW TO REPLY TO THIS NOTICE:

I. Review the SMALL ENTITY status shown above.

If the SMALL ENTITY is shown as YES, verify your current SMALL ENTITY status:	If the SMALL ENTITY is shown as NO:
A. If the status is the same, pay the TOTAL FEE(S) DUE shown above.	A. Pay TOTAL FEE(S) DUE shown above, or
B. If the status above is to be removed, check box 5b on Part B - Fee(s) Transmittal and pay the PUBLICATION FEE (if required) and twice the amount of the ISSUE FEE shown above, or	B. If applicant claimed SMALL ENTITY status before, or is now claiming SMALL ENTITY status, check box 5a on Part B - Fee(s) Transmittal and pay the PUBLICATION FEE (if required) and 1/2 the ISSUE FEE shown above.

II. PART B - FEE(S) TRANSMITTAL, or its equivalent, must be completed and returned to the United States Patent and Trademark Office (USPTO) with your ISSUE FEE and PUBLICATION FEE (if required). If you are charging the fee(s) to your deposit account, section "4b" of Part B - Fee(s) Transmittal should be completed and an extra copy of the form should be submitted. If an equivalent of Part B is filed, a request to reapply a previously paid issue fee must be clearly made, and delays in processing may occur due to the difficulty in recognizing the paper as an equivalent of Part B.

III. All communications regarding this application must give the application number. Please direct all communications prior to issuance to Mail Stop ISSUE FEE unless advised to the contrary.

IMPORTANT REMINDER: Utility patents issuing on applications filed on or after Dec. 12, 1980 may require payment of maintenance fees. It is patentee's responsibility to ensure timely payment of maintenance fees when due.

031

PART B - FEE(S) TRANSMITTAL

Complete and send this form, together with applicable fee(s), to: <u>Mail</u> Mail Stop ISSUE FEE Commissioner for Patents P.O. Box 1450 Alexandria, Virginia 22313-1450

or <u>Fax</u> (571)-273-2885

INSTRUCTIONS: This form should be used for transmitting the ISSUE FEE and PUBLICATION FEE (if required). Blocks 1 through 5 should be completed where appropriate. All further correspondence including the Patent, advance orders and notification of maintenance fees will be mailed to the current correspondence address as indicated unless corrected below or directed otherwise in Block 1, by (a) specifying a new correspondence address; and/or (b) indicating a separate "FEE ADDRESS" for maintenance fees will be mailed to the current correspondence. maintenance fee notifications.

CURRENT CORRESPONDENCE ADDRESS (Note: Use Block 1 for any change of address)				Note: A certificate of mailing can only be used for domestic mailings of the Fee(s) Transmittal. This certificate cannot be used for any other accompanying papers. Each additional paper, such as an assignment or formal drawing, must have its own certificate of mailing or transmission.				
LAW OFFICES OF EUGENE M. CUMMINGS, P.C. ONE NORTH WACKER DRIVE SUITE 4130 CHICAGO, IL 60606			?.С.	Certificate of Mailing or Transmission I hereby certify that this Fee(s) Transmittal is being deposited with the United States Postal Service with sufficient postage for first class mail in an envelop addressed to the Mail Stop ISSUE FEE address above, or being facsimil- transmitted to the USPTO (571) 273-2885, on the date indicated below.				
, _								(Depositor's name)
								(Signature)
								(Date)
APPLICATION NO.	FILING DATE		FIRST NAMED INVEN	TOR		ATTOR	NEY DOCKET NO.	CONFIRMATION NO.
11/622,496	01/12/2007	•	G.R. Mohan Rac	,		0	299-0001.01	3086
	: SEMICONDUCTOR I	DEVICES WITH GRADE	ED DOPANT REGIO	NS				
APPLN. TYPE	SMALL ENTITY	ISSUE FEE DUE	PUBLICATION FEE I	DUE	PREV. PAID ISSUE	E FEE	TOTAL FEE(S) DUE	DATE DUE
nonprovisional	YES	\$885	\$300		\$0		\$1185	03/12/2013
EXAM	INER	ART UNIT	CLASS-SUBCLASS	8				
ARORA	, AJAY	2892	257-371000					
 1. Change of correspondence address or indication of "Fee Address" (37 CFR 1.363). Change of correspondence address (or Change of Correspondence Address form PTO/SB/122) attached. The Address " indication (or "Fee Address" Indication form PTO/SB/47; Rev 03-02 or more recent) attached. Use of a Customer Number is required. 2. For printing on the patent front page, list (1) the names of up to 3 registered patent attorneys (2) the name of a single firm (having as a member a registered patent attorneys or agents. If no name is listed, no name will be printed. 3. ASSIGNEE NAME AND RESIDENCE DATA TO BE PRINTED ON THE PATENT (print or type) 								
(A) NAME OF ASSIC	GNEE	r categories (will not be pr	(B) RESIDENCE: (C	CITY	and STATE OR C	OUNTR	XY)	ocument has been filed for
4a. The following fee(s) are submitted: 4b. Payment of Fee(s): (Please first reapply any previously paid issue fee shown above) Issue Fee A check is enclosed. Publication Fee (No small entity discount permitted) Payment by credit card. Form PTO-2038 is attached. Advance Order - # of Copies The Director is hereby authorized to charge the required fee(s), any deficiency, or credit any overpayment, to Deposit Account Number (enclose an extra copy of this form							ficiency, or credit any	
5. Change in Entity Stat	· · · · · · · · · · · · · · · · · · ·	/	—					
	s SMALL ENTITY stat		b. Applicant is no	-	-			
NOTE: The Issue Fee and interest as shown by the r	d Publication Fee (if req records of the United Sta	uired) will not be accepted ates Patent and Trademark	d from anyone other the office.	nan th	ne applicant; a regi	stered at	torney or agent; or th	e assignee or other party in
Authorized Signature					Date			
Typed or printed name	e				Registration N	lo		
This collection of inform an application. Confident submitting the completec this form and/or suggesti Box 1450, Alexandria, V Alexandria, Virginia 223	tiality is governed by 35 1 application form to the ons for reducing this bu firginia 22313-1450. DC	CFR 1.311. The informatic 5 U.S.C. 122 and 37 CFR 2 USPTO. Time will vary rden, should be sent to th 0 NOT SEND FEES OR (on is required to obtain 1.14. This collection to depending upon the e Chief Information C COMPLETED FORM	n or re is esti indivi Office S TO	etain a benefit by tl imated to take 12 r idual case. Any co r, U.S. Patent and ' 'THIS ADDRESS	he public ninutes (mments Tradema . SEND	e which is to file (and to complete, includin on the amount of tir urk Office, U.S. Depa TO: Commissioner f	by the USPTO to process) g gathering, preparing, and ne you require to complete urtment of Commerce, P.O. or Patents, P.O. Box 1450,

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number.

	ted States Pate	ENT AND TRADEMARK OFFICE	UNITED STATES DEPAR United States Patent and Address: COMMISSIONER F P.O. Box 1450 Alexandria, Virginia 22: www.usplo.gov	OR PATENTS
APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
11/622,496	01/12/2007	G.R. Mohan Rao	0299-0001.01	3086
70653 75	90 12/12/2012	EXAMINER		
LAW OFFICES	OF EUGENE M. CU CKER DRIVE	ARORA, AJAY		
SUITE 4130			ART UNIT	PAPER NUMBER
CHICAGO, IL 606	506	2892		
			DATE MAILED: 12/12/2012	

Determination of Patent Term Adjustment under 35 U.S.C. 154 (b)

(application filed on or after May 29, 2000)

The Patent Term Adjustment to date is 0 day(s). If the issue fee is paid on the date that is three months after the mailing date of this notice and the patent issues on the Tuesday before the date that is 28 weeks (six and a half months) after the mailing date of this notice, the Patent Term Adjustment will be 0 day(s).

If a Continued Prosecution Application (CPA) was filed in the above-identified application, the filing date that determines Patent Term Adjustment is the filing date of the most recent CPA.

Applicant will be able to obtain more detailed information by accessing the Patent Application Information Retrieval (PAIR) WEB site (http://pair.uspto.gov).

Any questions regarding the Patent Term Extension or Adjustment determination should be directed to the Office of Patent Legal Administration at (571)-272-7702. Questions relating to issue and publication fee payments should be directed to the Customer Service Center of the Office of Patent Publication at 1-(888)-786-0101 or (571)-272-4200.

Privacy Act Statement

The Privacy Act of 1974 (P.L. 93-579) requires that you be given certain information in connection with your submission of the attached form related to a patent application or patent. Accordingly, pursuant to the requirements of the Act, please be advised that: (1) the general authority for the collection of this information is 35 U.S.C. 2(b)(2); (2) furnishing of the information solicited is voluntary; and (3) the principal purpose for which the information is used by the U.S. Patent and Trademark Office is to process and/or examine your submission related to a patent application or patent. If you do not furnish the requested information, the U.S. Patent and Trademark Office may not be able to process and/or examine your submission, which may result in termination of proceedings or abandonment of the application or expiration of the patent.

The information provided by you in this form will be subject to the following routine uses:

- 1. The information on this form will be treated confidentially to the extent allowed under the Freedom of Information Act (5 U.S.C. 552) and the Privacy Act (5 U.S.C 552a). Records from this system of records may be disclosed to the Department of Justice to determine whether disclosure of these records is required by the Freedom of Information Act.
- 2. A record from this system of records may be disclosed, as a routine use, in the course of presenting evidence to a court, magistrate, or administrative tribunal, including disclosures to opposing counsel in the course of settlement negotiations.
- 3. A record in this system of records may be disclosed, as a routine use, to a Member of Congress submitting a request involving an individual, to whom the record pertains, when the individual has requested assistance from the Member with respect to the subject matter of the record.
- 4. A record in this system of records may be disclosed, as a routine use, to a contractor of the Agency having need for the information in order to perform a contract. Recipients of information shall be required to comply with the requirements of the Privacy Act of 1974, as amended, pursuant to 5 U.S.C. 552a(m).
- 5. A record related to an International Application filed under the Patent Cooperation Treaty in this system of records may be disclosed, as a routine use, to the International Bureau of the World Intellectual Property Organization, pursuant to the Patent Cooperation Treaty.
- 6. A record in this system of records may be disclosed, as a routine use, to another federal agency for purposes of National Security review (35 U.S.C. 181) and for review pursuant to the Atomic Energy Act (42 U.S.C. 218(c)).
- 7. A record from this system of records may be disclosed, as a routine use, to the Administrator, General Services, or his/her designee, during an inspection of records conducted by GSA as part of that agency's responsibility to recommend improvements in records management practices and programs, under authority of 44 U.S.C. 2904 and 2906. Such disclosure shall be made in accordance with the GSA regulations governing inspection of records for this purpose, and any other relevant (i.e., GSA or Commerce) directive. Such disclosure shall not be used to make determinations about individuals.
- 8. A record from this system of records may be disclosed, as a routine use, to the public after either publication of the application pursuant to 35 U.S.C. 122(b) or issuance of a patent pursuant to 35 U.S.C. 151. Further, a record may be disclosed, subject to the limitations of 37 CFR 1.14, as a routine use, to the public if the record was filed in an application which became abandoned or in which the proceedings were terminated and which application is referenced by either a published application, an application open to public inspection or an issued patent.
- 9. A record from this system of records may be disclosed, as a routine use, to a Federal, State, or local law enforcement agency, if the USPTO becomes aware of a violation or potential violation of law or regulation.

	Application No.	Applicant(s)	Applicant(s)		
	11/622,496	2,496 RAO, G.R. MOHAN			
Notice of Allowability	Examiner	Art Unit			
	AJAY K. ARORA	2892			
The MAILING DATE of this communication a All claims being allowable, PROSECUTION ON THE MERITS herewith (or previously mailed), a Notice of Allowance (PTOL- NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT of the Office or upon petition by the applicant. See 37 CFR 1.	IS (OR REMAINS) CLOSED in 85) or other appropriate commu RIGHTS. This application is s	this application. If not included nication will be mailed in due co	urse. THIS		
1. 🛛 This communication is responsive to <u>11/13/12</u> .					
 An election was made by the applicant in response to a requirement and election have been incorporated into thi 		during the interview on; t	he restriction		
 The allowed claim(s) is/are <u>10-16 & 18-24</u>. As a result of Prosecution Highway program at a participating intellec please see <u>http://www.uspto.gov/patents/init_events/pph</u> 	ctual property office for the corre	sponding application. For more			
 4. ☐ Acknowledgment is made of a claim for foreign priority u a) ☐ All b) ☐ Some* c) ☐ None of the: 	nder 35 U.S.C. § 119(a)-(d) or (f).			
1. 🔲 Certified copies of the priority documents have been received.					
2. 🔲 Certified copies of the priority documents h	ave been received in Applicatio	n No			
Copies of the certified copies of the priority	documents have been received	l in this national stage applicatio	n from the		
International Bureau (PCT Rule 17.2(a)).					
* Certified copies not received:					
Applicant has THREE MONTHS FROM THE "MAILING DAT noted below. Failure to timely comply will result in ABANDC THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.		a reply complying with the requi	rements		
5. CORRECTED DRAWINGS (as "replacement sheets") must be submitted.					
including changes required by the attached Examir Paper No./Mail Date	ner's Amendment / Comment or	in the Office action of			
Identifying indicia such as the application number (see 37 CF each sheet. Replacement sheet(s) should be labeled as such			ack) of		
6. DEPOSIT OF and/or INFORMATION about the deposit of attached Examiner's comment regarding REQUIREMENT					
Attachment(s) 1. ☐ Notice of References Cited (PTO-892)	5. 🔲 Examiner's	Amendment/Comment			
2. Information Disclosure Statements (PTO/SB/08),	6. 🛛 Examiner's	Statement of Reasons for Allowa	ance		
 Paper No./Mail Date 3. Examiner's Comment Regarding Requirement for Depos of Biological Material 4. Interview Summary (PTO-413) 	it 7. ☐ Other	<u>.</u>			

4. 🔲 mierv	new Summary (r	-10-413),
Pape	er No./Mail Date	·
	10001/	

/AJAY K. ARORA/ Primary Examiner, Art Unit 2892

U.S. Patent and Trademark Office PTOL-37 (Rev. 09-12)

Notice of Allowability

DETAILED ACTION

Continued Examination Under 37 CFR 1.114

1. A request for continued examination under 37 CFR 1.114, including the fee set forth in 37 CFR 1.17(e), was filed in this application after final rejection. Since this application is eligible for continued examination under 37 CFR 1.114, and the fee set forth in 37 CFR 1.17(e) has been timely paid, the finality of the previous Office action has been withdrawn pursuant to 37 CFR 1.114. Applicant's submission filed on 11/13/2012 has been entered.

Reasons for Allowance

1. Claims 10-16 and 18-24 are allowed. The following is an examiner's statement of reasons for allowance:

2. Claims 10-16 and 18-24 are allowed because the prior art of record does not teach or suggest, singularly or in combination, at least the limitations of base claim 10 which requires "at least one well region disposed in said single drift layer, said well region having a graded concentration of dopants and a second static unidirectional electric drift field to aid the movement of minority carriers from said surface layer to said

036
Application/Control Number: 11/622,496Page 3Art Unit: 2892substrate" (see last 3 lines of claim 10). Base claim 18 recites similar limitations (seelast 3 lines of claim 18).

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Conclusion

3. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to AJAY K. ARORA whose telephone number is (571)272-8347. The examiner can normally be reached on Mon through Fri, 8:30am to 5:00pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Thao X. Le can be reached on (571) 272-1708. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Application/Control Number: 11/622,496 Art Unit: 2892

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

/AJAY K. ARORA/ Primary Examiner, Art Unit 2892

	Application/Control No.	Applicant(s)/Patent Under Reexamination
Search Notes	11622496	RAO, G.R. MOHAN
	Examiner	Art Unit
	AJAY K ARORA	2892

	SEARCHED		
Class	Subclass	Date	Examiner
257	655	12/16/2011	AKA

SEARCH NOTES		
Search Notes	Date	Examiner
Revised EAST search history report	12/16/2011	AKA
Revised EAST search history report	8/10/2012	AKA
Revised EAST search history	11/19/2012	AKA
Inventor search	11/19/2012	AKA
.clm. interference search	11/19/2012	AKA

	INTERFERENCE SEARCH	l	
Class	Subclass	Date	Examiner
257	655	12/16/2011	AKA

	/A. K. A./ Primary Examiner.Art Unit 2892

	Application/Control No.	Applicant(s)/Patent Under Reexamination
Issue Classification	11622496	RAO, G.R. MOHAN
	Examiner	Art Unit
	AJAY K ARORA	2892

ORIGINAL					INTERNATIONAL CLASSIFICATION										
	CLASS			SUBCLASS					С	LAIMED			N	ON-	CLAIMED
257			655			н	0	1	L	21 / 02 (2006.01.01)					
	CR	OSS REFI	ERENCE(S)											
CLASS	SUB	CLASS (ONE	SUBCLAS	S PER BLO	CK)										
257	611	E33.048													
438	510														

\boxtimes	Claims renumbered in the same order as presented by applicant CPA T.D. R.1.47														
Final	Original	Final	Original	Final	Original	Final	Original	Final	Original	Final	Original	Final	Original	Final	Original
-	1	-	17												
-	2	8	18												
-	з	9	19												
-	4	10	20												
-	5	11	21												
	6	12	22												
-	7	13	23												
-	8	14	24												
-	9	-	25												
1	10														
2	11														
3	12														
4	13														
5	14														
6	15														
7	16														

NONE		Total Clain	ns Allowed:
(Assistant Examiner)	(Date)	1	4
/AJAY K ARORA/ Primary Examiner.Art Unit 2892	12/04/2012	O.G. Print Claim(s)	O.G. Print Figure
(Primary Examiner)	(Date)	1	5b

U.S. Patent and Trademark Office

Part of Paper No. 20121119

EAST Search History

EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	(unidirectional WITH field WITH drift) AND ((gradient OR grading OR graded) WITH dop\$3).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2012/11/19 14:46
L2	0	(unidirectional WITH field WITH drift) AND ((gradient OR grading OR graded) WITH dop\$3).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2012/11/19 14:46
L3	0	((GR) near2 (RAO)).INV.	US-PGPUB; USPAT	OR	ON	2012/11/19 14:48
L4	0	((GR) near2 (RAO)).INV.	EPO; JPO; DERWENT	OR	ON	2012/11/19 14:48
L5	0	(("G.R.") near2 (RAO)).INV.	EPO; JPO; DERWENT	OR	ON	2012/11/19 14:49
L6	89	(mohan near2 RAO).INV.	EPO; JPO; DERWENT	OR	ON	2012/11/19 14:49
L7	245	(mohan near2 RAO).INV.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2012/11/19 14:49
L8	2	I7 and (grad\$3 WITH dop\$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2012/11/19 14:50
S1	2	("20070158790").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/08 11:10
S2	58	("20020074585" "20040063288" "4001864" "4347654" "4866000" "5130262" "5213988" "5329144" "5480816" "5496746" "5569612" "5575862" "5797999" "6211028" "6452086" "6472715" "6670544" "6683343" "6696314" "6706550" "6713813" "6737722" "6744117" "6747883" "6753202" "6754093" "6756616" "RE37441").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/08 11:19
S3	1096	(graded OR gradation) WITH (dopant OR	US-PGPUB;	OR	ON	2008/04/08

		doping) WITH concentration	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB			11:47
S4	805	S3 AND ("257" OR "438").clas.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/08 11:47
S5	253	(graded OR gradation) WITH (dopant OR doping) WITH concentration WITH (semiconductor OR silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/08 11:49
S6	7	S5 SAME (carrier WITH (movement OR mobility))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/08 11:51
S7	48	S5 AND (((carrier OR electron OR hole) WITH (movement OR mobility)) SAME ((emitter WITH collector) OR (source WITH drain)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/08 11:55
S8	58	("20020074585" "20040063288" "4001864" "4347654" "4866000" "5130262" "5213988" "5329144" "5480816" "5496746" "5569612" "5575862" "5797999" "6211028" "6452086" "6472715" "6670544" "6683343" "6696314" "6706550" "6713813" "6737722" "6744117" "6747883" "6753202" "6754093" "6756616" "RE37441").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/18 12:16
S10	13	S8 AND ("dopant concentration" OR "concentration of dopant")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/18 12:17
S11	0	S8 AND (dop\$3 WITH (concentrat\$3 OR amount OR quantity) WITH (variable OR varying OR grad\$3)) AND ((doping OR dopant) WITH well) AND ((carrier OR charge) WITH (moving OR movement OR mobile OR mobility))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/18 12:22
S12	1136	(graded OR gradation) WITH (dopant OR doping) WITH concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/18 12:22
S13	86	S12 AND (dop\$3 WITH (concentrat\$3 OR amount OR quantity) WITH (variable OR varying OR grad\$3)) AND ((doping OR dopant) WITH well) AND ((carrier OR	US-PGPUB; USPAT; USOCR; EPO; JPO;		ON	2008/07/18 12:22

		charge) WITH (moving OR movement OR mobile OR mobility))	DERWENT; IBM_TDB			
S14	29	("20020068409" "6303450" "6437406" "6458665" "6483158" "6489223" "6509241").PN. OR ("6743684").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/07/18 13:13
S15	34	uniform\$2 WITH dop\$3 WITH drift WITH epitaxial	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/23 15:19
S16	2	("5637898"). PN .	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/23 15:26
S17	0	(non-uniform\$2 OR nonuniform\$2 OR grad43 OR grading OR gradient) WITH (dopant OR doping) WITH well WITH carrier WITH (movement OR mobility) WITH ((away WITH active WITH surface) OR (towards WITH substrate))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/23 15:40
S18	4	(non-uniform\$2 OR nonuniform\$2 OR grad\$3 OR grading OR gradient) WITH (dopant OR doping) WITH well WITH carrier WITH (movement OR mobility) WITH ((away WITH active WITH surface) OR (towards WITH substrate))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/23 15:40
S19	4	("4001864"). PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/23 15:43
S20	58	("20020074585" "20040063288" "4001864" "4347654" "4866000" "5130262" "5213988" "5329144" "5480816" "5496746" "5569612" "5575862" "5797999" "6211028" "6452086" "6472715" "6670544" "6683343" "6696314" "6706550" "6713813" "6737722" "6744117" "6747883" "6753202" "6754093" "6756616" "RE37441").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/23 15:57
S21	92	S15 S19 S20	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/23 15:58
S22	39	S21 AND ((non-uniform\$2 OR nonuniform\$2 OR grad\$3 OR grading OR gradient) WITH (dopant OR doping))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/23 15:58
S23	60	S21 AND well	US-PGPUB; USPAT; USOCR;	OR	ON	2008/07/23 15:59

			EPO; JPO; DERWENT; IBM_TDB			
S24	39	S22 AND well	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/23 15:59
S25	2	S22 AND (well WITH carrier WITH (movement OR mobility) WITH ((away WITH active WITH surface) OR (towards WITH substrate)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/23 16:00
S26	3	S22 AND (well WITH (carrier OR movement OR mobility) WITH ((away WITH active WITH surface) OR (towards WITH substrate)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/23 16:00
S27	2	("20030042511").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/23 16:05
S28	2	S21 AND (substrate WITH carrier WITH away WITH ((active WITH surface) OR (towards NEAR2 substrate) OR (direction NEAR4 substrate)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/23 17:17
S29	3	S21 AND (substrate WITH (carrier OR holes OR electron OR majority OR charge) WITH away WITH ((active WITH surface) OR (towards NEAR2 substrate) OR (direction NEAR4 substrate)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB		ON	2008/07/23 17:18
S30	30	S21 AND ((non-uniform\$2 OR nonuniform\$2 OR grad\$3 OR grading OR gradient) WITH (dopant OR doping) WITH substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/23 17:26
S31	253	(grad\$3 OR grading OR gradient) NEAR2 (dopant OR doping) NEAR4 substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/23 17:33
S32	5	dopant WITH concentration WITH donor WITH acceptor WITH optimiz\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/23 18:02
S33	2	10/182,784	US-PGPUB; USPAT; USOCR;	OR	ON	2008/07/23 18:06

			EPO; JPO; DERWENT; IBM_TDB			
S34	0	S20 AND (dopant WITH concentration WITH donor WITH acceptor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/23 18:22
S35	0	S20 AND (dopant WITH donor WITH acceptor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/23 18:22
S36	5	(dopant WITH donor WITH acceptor WITH optimiz\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/23 18:26
S37	5	(dopant WITH donor WITH acceptor WITH (optimiz\$ OR optimization OR optimal))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/23 18:27
S38	487	(donor WITH acceptor WITH (optimiz\$ OR optimization OR optimal))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/23 18:27
S39	14	S38 AND semiconductor.ab.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/23 18:28
S40	0	(layer WITH dopant WITH wafer WITH transfer\$4 WITH ((another OR second OR alternate) NEAR1 wafer)) AND (wafer NEAR1 bond\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/23 18:49
S41	0	(dopant WITH wafer WITH transfer\$4 WITH ((another OR second OR alternate) NEAR1 wafer)) AND (wafer NEAR1 bond\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/23 18:49
S42	0	(dopant WITH transfer\$4 WITH ((another OR second OR alternate) NEAR1 wafer)) AND (wafer NEAR1 bond\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/23 18:50
S43	0	(dopant WITH transfer\$4 WITH ((another OR second OR alternate) NEAR1 wafer))	US-PGPUB; USPAT; USOCR;	OR	ON	2008/07/23 18:50

			EPO; JPO; DERWENT; IBM_TDB			
S44	14807	wafer NEAR1 bond\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/23 18:51
S45	33	S44 AND (dopant WITH transfer\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/23 18:51
S46	579	(257/655,269).COLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/24 09:14
S47	539	(257/655).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/01/02 21:01
S48	695	VLSI AND ((graded OR gradation OR gradient) WITH (dopant OR doping OR impurit\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/24 11:04
S49	62	S48 AND (((carrier OR electron OR hole) WITH (movement OR mobility)) SAME ((emitter WITH collector) OR (source WITH drain)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/24 11:05
S50	4	S48 AND (well WITH carrier WITH (movement OR mobility) WITH ((away WITH active WITH surface) OR (towards WITH substrate)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/24 11:06
S51	4	("4001864").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/24 11:10
S52	2	("6831292").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/24 11:36
S53	2	("5029277").PN.	US-PGPUB; USPAT; USOCR;	OR	OFF	2009/05/24 12:17

			EPO; JPO; DERWENT; IBM_TDB			
S54	551	(257/655).OCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/24 12:52
S55	564	(257/655).OCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/12/22 10:12
S56	2	("6831292"). P N.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/12/22 10:14
S57	10	(US-20040072395-\$ or US-20010046753- \$ or US-20010050382-\$ or US- 20020093281-\$ or US-20030042511- \$).did. or (US-6743684-\$ or US-5359221- \$ or US-5637898-\$ or US-5627092-\$ or US-5029277-\$).did. or (US-20020093281- A-\$).did.	US-PGPUB; USPAT; DERWENT	OR	ON	2009/12/22 10:26
S58	0	S57 AND drift WITH aid\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/22 10:27
S59	7	(drift WITH aid\$3) WITH dopant WITH concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/22 10:27
S60	173	((graded OR gradient OR gradation) NEAR2 (dop\$3 OR impurity)) WITH between WITH substrate AND (active OR source OR drain OR source/drain)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/08/01 12:45
S61	74	S60 AND CMOS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/08/01 13:43
S62	5	(complementary WITH error WITH function WITH gradient)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/08/01 19:12
S64	55	CMOS AND (exponential WITH gradient)	US-PGPUB; USPAT;	OR	ON	2010/08/01 19:13

S72	371	(semiconductor OR CMOS OR FET OR "field effect" OR NMOS OR PMOS).ab. S71 AND (drift WITH field)	EPO; JPO; DERWENT; IBM_TDB US-PGPUB; USPAT;	OR	ON	2010/08/02 04:29
S71	3377	((graded OR gradation OR gradient) NEAR3 (dopant OR doping OR impurity OR donor OR acceptor)) AND	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; USPAT; USOCR;	OR	ON	20:02 20:02 2010/08/02 04:28
S69 S70	4	(grad\$3 WITH (dop\$3 OR donor)) SAME ((dopant OR donor) WITH driv\$3 WITH (toward OR into OR deep\$2) WITH substrate) (layer WITH (dopant OR donor) WITH	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB US-PGPUB;	OR	ON	2010/08/01 20:00 2010/08/01
S68	7	(grad\$3 WITH (dop\$3 OR donor)) SAME ((dopant OR donor) WITH (sweep\$3 OR mov\$3 OR attract\$3) WITH substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/08/01 19:58
S67	0	S66 AND S62	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/08/01 19:15
S66	12	S64 AND S65	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/08/01 19:14
	712	OMOS AND (linear WITH gradient)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/08/01 19:14
			USOCR; EPO; JPO; DERWENT; IBM_TDB			

504	۷	("20020084430"). PN .	US-PGPUB; USPAT;	UK		2010/08/02 05:26
S83 S84		S72 AND S78	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB		ON	2010/08/02 05:20
S82	98	S71 AND S78	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB		ON	2010/08/02 05:20
S81	7	S71 AND S77	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/08/02 05:14
S80	0	S78 AND S77	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/08/02 05:14
S79	0	S78 AND S76	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/08/02 05:14
	8028	photodiode WITH CMOS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/08/02 05:13
S77	7	S76 AND (drift WITH layer WITH between WITH substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/08/02 04:48
S76		OR gradation OR gradient) WITH (dopant OR doping OR impurity OR donor OR acceptor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB		ON	2010/08/02 04:47
S75		S72 AND S74	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB		ON	2010/08/02 04:30
			USOCR; EPO; JPO; DERWENT; IBM_TDB			

			USOCR; EPO; JPO; DERWENT; IBM_TDB			
S85	172	(drift WITH layer WITH epitaxial) AND S71	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/08/02 07:16
S86	47	S71 AND (linear AND exponential)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/08/02 08:04
S87	3	S86 AND "complimentary error function"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/08/02 08:04
S88	8	S86 AND donor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/08/02 08:38
S89	583	(257/655).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/08/02 10:21
S90	593	(257/655).OCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2011/01/11 11:40
S91	598	(257/655).OCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2011/04/10 20:57
S92	1	("4481522").PN.	USPAT; USOCR	OR	OFF	2011/12/16 08:02
S93	456	(257/655).CCLS.	USPAT; USOCR	OR	OFF	2011/12/16 09:45
S94	0	(single WITh static WITH drift) AND ((gradient OR grading OR graded) WITH dop\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2012/08/10 00:21
S95	22	(static WITH drift) AND ((gradient OR grading OR graded) WITH dop\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2012/08/10 00:21

S96 1	(unidirectional WITH field WITH drift)	US-PGPUB; OR USPAT:	ON	2012/08/10 00:24
	AND ((gradient OR grading OR graded) WITH dop\$3)	EPO; JPO;		00.24
		DERWENT; IBM TDB		

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	Claims r	enumbered	in the s	ame	order as pi	esented by a	applican	t			СРА] T.[D. 🗆	R.1.47
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PTO/SB/30 (07-09) Approved for use through 07/31/2012. OMB 0651-0031 U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

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Request	Application Number	11/622496	11/622496							
for Continued Examination (RCE)	Filing Date	01/12/2007								
Transmittal	First Named Inventor	G.R. Mohan F	lao							
Address to:	Art Unit	2892								
Mail Stop RCE Commissioner for Patents	Examiner Name	Ajay Arora								
P.O. Box 1450 Alexandria, VA 22313-1450	Attorney Docket Number	0299-0001.01								
This is a Request for Continued Examination (RCE) under 37 CFR 1.114 of the above-identified application. Request for Continued Examination (RCE) practice under 37 CFR 1.114 does not apply to any utility or plant application filed prior to June 8, 1995, or to any design application. See Instruction Sheet for RCEs (not to be submitted to the USPTO) on page 2.										
 Submission required under 37 CFR 1.114 Not amendments enclosed with the RCE will be entered in th applicant does not wish to have any previously filed unen amendment(s). a. Previously submitted. If a final Office action is considered as a submission even if this box is 	e order in which they were filed u tered amendment(s) entered, ap outstanding, any amendments fil	nless applicant inst plicant must reques	ructs otherwise. If t non-entry of such							
i. Consider the arguments in the Appeal B	i. Consider the arguments in the Appeal Brief or Reply Brief previously filed on									
b. Enclosed										
i. Amendment/Reply	iii. 🗌 Informatio	n Disclosure Stater	nent (IDS)							
ii. Affidavit(s)/ Declaration(s)	iv. Other									
2. Miscellaneous										
Suspension of action on the above-identified application is a period of months. (Period of suspension b Other	shall not exceed 3 months; Fee und	-	red)							
3. Fees The RCE fee under 37 CFR 1.17(e) is require The Director is hereby authorized to charge th a. Deposit Account No. <u>50-4199</u> .			any overpayments to							
i. RCE fee required under 37 CFR 1.17(e)			· · · · · · · · · · · · · · · · · · ·							
ii Extension of time fee (37 CFR 1.136 and	1.17)									
iii Other										
b. Check in the amount of \$	enclosed									
c. Payment by credit card (Form PTO-2038 enclose WARNING: Information on this form may become public. Cr	,	ot be included on t	his form. Provide credit							
card information and authorization on PTO-2038.	NT, ATTORNEY, OR AGENT R									
Signature //David M. Mundt/	Date		ember 13, 2012							
Name (Print/Type) David M. Mundt			207							
CERTIFICATE OF	MAILING OR TRANSMISSION									
I hereby certify that this correspondence is being deposited with the United State addressed to: Mail Stop RCB, Commissioner for Patents, P. O. Box 1450, Alexa Office on the date shown delow.										
Name (Print/Type) Francisca M. A. Hubbard										
Name (Print/Type) Francisca IM. A. Hubbard Date November 13, 2012 This collection of information is required by 37 CFR 1.114. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.11 and 1.14. This collection is estimated to take 12 minutes to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Mail Stop RCE, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450. If you need assistance in completing the form, call 1-800-PTO-9199 and select option 2. American LegalNet, Inc. Waw, FormsWorkFlow, can										

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application No.	:	11/622,496
Confirmation No.	:	3086
Inventor	:	G. R. Mohan Rao
Filed	:	January 12, 2007
TC/A.U.	:	2892
Examiner	:	Ajay Arora
Title	:	SEMICONDUCTOR DEVICES WITH GRADED
		DOPANT REGIONS
Docket No.	:	0299-0001.01

REQUEST FOR CONTINUED EXAMINATION

AMENDMENT F

Sir:

In response to the Advisory Action of October 24, 2012, Applicant submits the following

amendment:

Claims. Amendments to the claims begin on page 2 of this amendment.

Remarks. Remarks begin on page 6 of this amendment.

LISTING OF CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

Claims:

1. (Canceled)

2. (Canceled)

3. (Canceled)

4. (Canceled)

5. (Canceled)

6. (Canceled)

7. (Canceled)

8. (Canceled)

9. (Canceled)

Page 2 of 8

10. (Currently Amended) A CMOS Semiconductor device comprising:

a surface layer;

a substrate;

an active region including a source and a drain, disposed on one surface of said surface layer; and

a single drift layer disposed between the other surface of said surface layer and said substrate, said drift layer having a graded concentration of dopants extending between said surface layer and said substrate, said drift layer further having a first to create and maintain a single static unidirectional electric drift field to aid the movement of minority carriers from said surface layer to said substrate; and

at least one well region disposed in said single drift layer, said well region having a graded concentration of dopants and a second static unidirectional electric drift field to aid the movement of minority carriers from said surface layer to said substrate.

11. (Original) The CMOS Semiconductor device of claim 10 wherein said drift layer is a deeplyimplanted layer.

12. (Original) The CMOS Semiconductor device of claim 10 wherein said drift layer is an epitaxial layer.

13. (Original) The CMOS Semiconductor device of claim 10 wherein said graded concentration follows a linear gradient.

14. (Original) The CMOS Semiconductor device of claim 10 wherein said graded concentration follows a quasi-linear gradient.

15. (Original) The CMOS Semiconductor device of claim 10 wherein said graded concentration follows an exponential gradient.

16. (Original) The CMOS Semiconductor device of claim 10 wherein said graded concentration follows a complimentary error function gradient.

17. (Canceled)

18. (Currently amended) A CMOS Semiconductor device comprising:

a surface layer;

a substrate;

an active region including a source and a drain, disposed on one surface of said surface layer; and

a single drift layer disposed between the other surface of said surface layer and said substrate, said drift layer having a graded concentration of dopants extending between said surface layer and said substrate, said drift layer further having a first to create and maintain a single static unidirectional electric drift field to aid the movement of minority carriers from said substrate to said surface layer; and

at least one well region disposed in said single drift layer, said well region having a graded concentration of dopants and a second static unidirectional electric drift field to aid the

movement of minority carriers from said substrate to said surface layer.

19. (Original) The CMOS Semiconductor device of claim 18 wherein said drift layer is a deeplyimplanted layer.

20. (Original) The CMOS Semiconductor device of claim 18 wherein said drift layer is an epitaxial layer.

21. (Original) The CMOS Semiconductor device of claim 18 wherein said graded concentration follows a linear gradient.

22. (Original) The CMOS Semiconductor device of claim 18 wherein said graded concentration follows a quasi-linear gradient.

23. (Original) The CMOS Semiconductor device of claim 18 wherein said graded concentration follows an exponential gradient.

24. (Original) The CMOS Semiconductor device of claim 18 wherein said graded concentration follows a complimentary error function gradient.

25. (Canceled)

<u>REMARKS</u>

Applicant has carefully reviewed the Advisory Action of October 24, 2012. In addition, Applicant incorporates herein by reference the October 15, 2012 Response to the Final Office Action and states as follows:

Claims 10-16 and 18-24 stand rejected pursuant to 35 U.S.C. 112, first paragraph because Applicant's specification does not enable "to create and <u>maintain</u> a <u>single static</u> unidirectional electric drift field." Office Action at ¶2. Without conceding the merits of this rejection, Applicant has further amended base claims 10 and 18 to overcome the rejection pursuant to 35 U.S.C. 112, first paragraph. In particular, Applicant has removed any reference to the terms "create," "maintain" and "single." With regard to the remaining term "static," Applicant respectfully notes that prior art reference Kamins (US 4,160,985), just like Applicant, discloses the presence of a "static" drift field, "because the drift field is created by graded concentration of dopants which does not change over time." See Office Action ¶4 p.4 lines 1-3, further citing to Kamins, Col. 2, lines 15-16; Col. 2, line 64 - Col. 3, line 2; Col. 1, lines 38-46; and Col. 3, lines 8-11.

Claims 10-11 and 18-19 stand rejected as obvious in view of the combined teachings of Kamins (of prior record) in view of Jastrzebski (US 4,481,522) (of prior record) and Bamji (US 2002/0084430) (of prior record). Applicant has previously summarized the disclosure of these references. Without conceding any of Applicant's positions, Applicant has further amended independent claims 10 and 18 to better distinguish over the cited prior art by claiming "at least one well region disposed in said single drift layer, said well region having a graded concentration of dopants and a second static unidirectional electric drift field to aid the movement of minority carriers." Applicant respectfully submits that neither Kamins nor Jastrzebski, disclose the above limitation.

Finally, Applicant has further amended claims 10 and 18 to address the Examiner's position that claims 10 and 18 as previously submitted are product by process claims. See Office Action at p.5. In particular, Applicant has amended claim 10 as follows:

"a single drift layer disposed between the other surface of said surface layer and said substrate, said drift layer having a graded concentration of dopants extending between said surface layer and said substrate, said drift layer further having a first to create and maintain a single static unidirectional electric drift field to aid the movement of minority carriers from said substrate to said surface layer ..."

Claims 11-16 depend on claim 10 and for at least the same reason that claim 10 is patentable over the cited prior art, claims 11-16 are patentable as well. Claims 19-24 depend on claim 18 and for at least the reasons that claim 18 is patentable over the cited prior art, claims 19-24 are patentable as well.

CONCLUSION

Applicant respectfully submits that in view of the amendments made to the claims and the discussion set forth herein, this application is now in condition for allowance. However, should Examiner be of the opinion that further amendment or response is required; Applicant encourages Examiner to contact the undersigned attorney at the telephone number set forth below. The Commissioner is authorized to charge any additional fees or deficiencies or credit any overpayments to Eugene M. Cummings, P.C., Deposit Account No. **50-4199**, with reference to attorney docket number (0299-0001.01).

Respectfully submitted,

Date: November 13, 2012

By: /David M. Mundt/ David M. Mundt, Reg. No. 41,207

Law Offices of Eugene M. Cummings, P.C. 1 North Wacker Drive Suite 4130 Chicago, Illinois 60606

Telephone: (312) 984-0144 Facsimile: (312) 984-0146

Electronic Patent Application Fee Transmittal								
Application Number:	11	622496						
Filing Date:	12	-Jan-2007						
Title of Invention:	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS							
First Named Inventor/Applicant Name:	G.R. Mohan Rao							
Filer:	David Michael Mundt/Francisca Hubbard							
Attorney Docket Number:	02	99-0001.01						
Filed as Small Entity								
Utility under 35 USC 111(a) Filing Fees								
Description		Fee Code	Quantity	Amount	Sub-Total in USD(\$)			
Basic Filing:								
Pages:								
Claims:								
Miscellaneous-Filing:								
Petition:								
Patent-Appeals-and-Interference:								
Post-Allowance-and-Post-Issuance:								
Extension-of-Time:								

Description	Fee Code	Quantity	Amount	Sub-Total in USD(\$)	
Miscellaneous:					
Request for continued examination	2801	1	465	465	
	Tot	al in USD) (\$)	465	

Electronic A	cknowledgement Receipt
EFS ID:	14209126
Application Number:	11622496
International Application Number:	
Confirmation Number:	3086
Title of Invention:	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS
First Named Inventor/Applicant Name:	G.R. Mohan Rao
Customer Number:	70653
Filer:	David Michael Mundt/Francisca Hubbard
Filer Authorized By:	David Michael Mundt
Attorney Docket Number:	0299-0001.01
Receipt Date:	13-NOV-2012
Filing Date:	12-JAN-2007
Time Stamp:	09:12:35
Application Type:	Utility under 35 USC 111(a)

Payment information:

Submitted with Payment	yes			
Payment Type	Deposit Account			
Payment was successfully received in RAM	\$465			
RAM confirmation Number	17230			
Deposit Account	504199			
Authorized User				
The Director of the USPTO is hereby authorized to charge indicated fees and credit any overpayment as follows:				
Charge any Additional Fees required under 37 C.F.R. Section 1.21 (Miscellaneous fees and charges)				

	Document Description	File Name	File Size(Bytes)/ Message Digest	Multi Part /.zip	Pages (if appl.)
1	Request for Continued Examination (RCE)	RCE.pdf	151110	no	1
	()		669bd13352097826785b6b507e921bb2d2 1f3ba0		
Warnings:					
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Information:					
2	Amendment After Final	American dimension for a df	726410	no	0
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Information:					
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3	Fee Worksheet (SB06)	fee-info.pdf	1669af2e315b53327c32b94c85ccbe287af2 f2ce	no	
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Information:					
		Total Files Size (in bytes)	90)7953	
	edgement Receipt evidences receip l by the applicant, and including pag described in MPEP 503.	•			

PTO/SB/06 (07-06)

Approved for use through 1/31/2007. OMB 0651-0032 I.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond PATENT APPLICATION FEE DETERMINATION RECORD Substitute for Form PTO-875						nd to	d to a collection of information unle Application or Docket Number 11/622,496				OMB control number.
APPLICATION AS FILED – PART I (Column 1) (Column 2)						SMALL	entity 🛛	OR		HER THAN	
	FOR	N	NUMBER FILED		NUMBER EXTRA		RATE (\$)	FEE (\$)		RATE (\$)	FEE (\$)
	BASIC FEE (37 CFR 1.16(a), (b), (or (c))	N/A		N/A		N/A			N/A	
	SEARCH FEE (37 CFR 1.16(k), (i), c	or (m))	N/A		N/A		N/A			N/A	
	EXAMINATION FE (37 CFR 1.16(o), (p), (N/A		N/A		N/A			N/A	
(37	"AL CLAIMS CFR 1.16(i))		min	us 20 = *			X \$ =		OR	X\$ =	
	EPENDENT CLAIM CFR 1.16(h))	S	mi	inus 3 = *			X \$ =			X \$ =	
	APPLICATION SIZE FEE (37 CFR 1.16(s)) If the specification and sheets of paper, the ap is \$250 (\$125 for small additional 50 sheets of 35 U.S.C. 41(a)(1)(G)			er, the applicatio for small entity) sheets or fraction a)(1)(G) and 37	n size fee due for each n thereof. See						
	MULTIPLE DEPEN		,	477					1		
* If t	he difference in colu	umn 1 is less than	zero, ente	r "0" in column 2.			TOTAL		J	TOTAL	
(Column 1) (Column 2) (Column 3)						SMAL	L ENTITY	OR		ER THAN	
T	11/13/2012	CLAIMS REMAINING AFTER		HIGHEST NUMBER PREVIOUSLY	PRESENT EXTRA		RATE (\$)	ADDITIONAL FEE (\$)		RATE (\$)	ADDITIONAL FEE (\$)
AMENDMENT	Total (37 CFR	AMENDMENT	Minus	PAID FOR	= 0		X \$31 =	0	OR	X \$ =	
NDN	1.16(i)) Independent	* 2	Minus	***8	= 0		X \$125 =	0	OR	X \$ = X \$ =	
(37 OFR 1.16(h)) 2 Millius 300 = 0				= 0		X 9123 -	0	on	χφ =		
A				DENT CLAIM (37 CFI	R 1.16(j))				OR		
FIRST PRESENTATION OF MULTIPLE DEPENDENT CLAIM (37 CFR 1.16(j))						TOTAL ADD'L FEE	0	OR	TOTAL ADD'L FEE		
		(Column 1)		(Column 2)	(Column 3)				-		
		CLAIMS REMAINING AFTER AMENDMENT		HIGHEST NUMBER PREVIOUSLY PAID FOR	PRESENT EXTRA		RATE (\$)	ADDITIONAL FEE (\$)		RATE (\$)	ADDITIONAL FEE (\$)
EN	Total (37 CFR 1.16(i))	*	Minus	**	=		X \$ =		OR	X\$ =	
ENDMENT	Independent (37 CFR 1.16(h))	*	Minus	***	=		X \$ =		OR	X\$ =	
ΠN	Application Si	ze Fee (37 CFR 1	.16(s))								
AMI		TATION OF MULTIP		DENT CLAIM (37 CFI	R 1.16(j))				OR		
** If	he entry in column ' the "Highest Numbe	er Previously Paid	For" IN TH	IIS SPACE is less	than 20, enter "20"			nstrument Ex N HICKSON/	OR amin	TOTAL ADD'L FEE er:	
	f the "Highest Numb "Highest Number P					oun			mn 1		
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This collection of information is required by 37 CFR 1.16. The information is required to obtain or retain a benefit by the public which is to file (and by the USP10 to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 12 minutes to complete, including gathering, preparing, and submitting the completed application form to the USP10. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

If you need assistance in completing the form, call 1-800-PTO-9199 and select option 2.

	ed States Paten	T AND TRADEMARK OFFICE	UNITED STATES DEPAR United States Patent and Address: COMMISSIONER F P.O. Box 1450 Alexandria, Virginia 22. www.uspto.gov	FOR PATENTS
APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
11/622,496	01/12/2007	G.R. Mohan Rao	0299-0001.01	3086
LAW OFFICES	70653 7590 10/24/2012 LAW OFFICES OF EUGENE M. CUMMINGS, P.C. ONE NORTH WACKER DRIVE			IINER A, AJAY
SUITE 4130 CHICAGO, IL	60606		ART UNIT	PAPER NUMBER
0111011000,112	00000		2892	
			MAIL DATE	DELIVERY MODE
			10/24/2012	PAPER

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

	A 1' 1' N						
Advisory Action	Application No. 11/622,496	Applicant(s) RAO, G.R. MOHAN					
Before the Filing of an Appeal Brief	Before the Filing of an Appeal Brief Examiner Art Unit AJAY K. ARORA 2892						
The MAILING DATE of this communication appears on the cover sheet with the correspondence address							
THE REPLY FILED <u>15 October 2012</u> FAILS TO PLACE THIS APPLICATION IN CONDITION FOR ALLOWANCE. NO NOTICE OF APPEAL FILED							
1. X The reply was filed after a final rejection. No Notice of Appeal has been filed. To avoid abandonment of this application, applicant must timely file one of the following replies: (1) an amendment, affidavit, or other evidence, which places the application in condition for allowance;							
(2) a Notice of Appeal (with appeal fee) in compliance with 37 CFR 41.31; or (3) a Request for Continued Examination (RCE) in compliance with 37 CFR 1.114 if this is a utility or plant application. Note that RCEs are not permitted in design applications. The reply must be filed within one of the following time periods:							
 a) The period for reply expiresmonths from the mailing date of the final rejection. b) The period for reply expires on: (1) the mailing date of this Advisory Action; or (2) the date set forth in the final rejection, whichever is later. 							
In no event, however, will the statutory period for reply expir	e later than SIX MONTH	IS from the mailing date of the final rejection.					
c) A prior Advisory Action was mailed more than 3 months after the mailing date of the final rejection in response to a first after-final reply filed within 2 months of the mailing date of the final rejection. The current period for reply expires months from the mailing date of the prior Advisory Action or SIX MONTHS from the mailing date of the final rejection, whichever is earlier. <i>Examiner Note</i> : If box 1 is checked, check either box (a), (b) or (c). ONLY CHECK BOX (b) WHEN THIS ADVISORY ACTION IS THE FIRST RESPONSE TO APPLICANT'S FIRST AFTER-FINAL REPLY WHICH WAS FILED WITHIN TWO MONTHS OF THE FINAL REJECTION. ONLY CHECK BOX (c) IN THE LIMITED SITUATION SET FORTH UNDER BOX (c). See MPEP 706.07(f).							
Extensions of time may be obtained under 37 CFR 1.136(a). The c							
extension fee have been filed is the date for purposes of determining appropriate extension fee under 37 CFR 1.17(a) is calculated from: set in the final Office action; or (2) as set forth in (b) or (c) above, if mailing date of the final rejection, even if timely filed, may reduce an NOTICE OF APPEAL	(1) the expiration date checked. Any reply re	e of the shortened statutory period for reply originally acceived by the Office later than three months after the					
2. The Notice of Appeal was filed on A brief in compliance with 37 CFR 41.37 must be filed within two months of the date of filing the Notice of Appeal (37 CFR 41.37(a)), or any extension thereof (37 CFR 41.37(e)), to avoid dismissal of the appeal. Since a Notice of Appeal has been filed, any reply must be filed within the time period set forth in 37 CFR 41.37(a). <u>AMENDMENTS</u>							
3. The proposed amendments filed after a final rejection, but proposed amendments filed after a final rejection, but provide the second	rior to the date of filing	a brief, will <u>not</u> be entered because					
a) X They raise new issues that would require further consideration and/or search (see NOTE below);							
 b) They raise the issue of new matter (see NOTE below); c) They are not deemed to place the application in better form for appeal by materially reducing or simplifying the issues for 							
appeal; and/or d) They present additional claims without canceling a co	responding number of	finally rejected claims.					
NOTE: <u>The new limitations of base claims 10 requiring "at least one well region disposed in said single drift layer, said well region having a graded concentration of dopants and a second static unidirectional electric drift field to aid the movement of minority carriers from said surface layer to said substrate" (see last 3 lines of claim 10). Amended base claim 18 also recites similar new limitations (see last 3 lines of claim 18). (See 37 CFR 1.116 and 41.33(a)).</u>							
4. The amendments are not in compliance with 37 CFR 1.121.		of Non-Compliant Amendment (PTOL-324).					
5. Applicant's reply has overcome the following rejection(s):							
 Newly proposed or amended claim(s) would be allow allowable claim(s). 	able if submitted in a s	eparate, timely filed amendment canceling the non-					
 7. For purposes of appeal, the proposed amendment(s): (a) new or amended claims would be rejected is provided below 		r (b) \square will be entered, and an explanation of how the					
AFFIDAVIT OR OTHER EVIDENCE	and the state of City						
8. The affidavit or other evidence filed after final action, but before or on the date of filing a Notice of Appeal will <u>not</u> be entered because applicant failed to provide a showing of good and sufficient reasons why the affidavit or other evidence is necessary and was not earlier presented. See 37 CFR 1.116(e).							
9. The affidavit or other evidence filed after the date of filing the because the affidavit or other evidence failed to overcome <u>all</u> and sufficient reasons why it is necessary and was not earlie	rejections under appe	al and/or appellant fails to provide a showing of good					
10. The affidavit or other evidence is entered. An explanation of	the status of the claim	s after entry is below or attached.					
REQUEST FOR RECONSIDERATION/OTHER 11. The request for reconsideration has been considered but do	es NOT place the app	lication in condition for allowance because:					
12. Note the attached Information <i>Disclosure Statement</i> (s). (PTC 13. Other:	O/SB/08) Paper No(s).						
STATUS OF CLAIMS							
 The status of the claim(s) is (or will be) as follows: Claim(s) allowed: 							
Claim(s) objected to: /AJAY K. ARORA/							
		aminer, Art Unit 2892					

Receipt date: 10/15/2012

DO NOT ENTER: /A.A./

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application No.	:	11/622,496
Confirmation No.	:	3086
Inventor	:	G. R. Mohan Rao
Filed	:	January 12, 2007
TC/A.U.	:	2892
Examiner	:	Ajay Arora
Title	:	SEMICONDUCTOR DEVICES WITH GRADED
		DOPANT REGIONS
Docket No.	:	0299-0001.01

RESPONSE PURSUANT TO 37 CFR 1.114

AMENDMENT F

Sir:

In response to the final Office Action of August 13, 2012, Applicant submits the following amendment:

Claims. Amendments to the claims begin on page 2 of this amendment.

Remarks. Remarks begin on page 6 of this amendment.

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application No.	:	11/622,496
Confirmation No.	:	3086
Inventor	:	G. R. Mohan Rao
Filed	:	January 12, 2007
TC/A.U.	:	2892
Examiner	:	Ajay Arora
Title	:	SEMICONDUCTOR DEVICES WITH GRADED
		DOPANT REGIONS
Docket No.	:	0299-0001.01

RESPONSE PURSUANT TO 37 CFR 1.114

AMENDMENT F

Sir:

In response to the final Office Action of August 13, 2012, Applicant submits the following amendment:

Claims. Amendments to the claims begin on page 2 of this amendment.

Remarks. Remarks begin on page 6 of this amendment.

Appl. No. 11/622,496 Response to Final Office Action of August 13, 2012

LISTING OF CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

<u>Claims:</u>

1. (Canceled)

2. (Canceled)

3. (Canceled)

4. (Canceled)

5. (Canceled)

6. (Canceled)

7. (Canceled)

8. (Canceled)

9. (Canceled)

Page 2 of 8

10. (Currently Amended) A CMOS Semiconductor device comprising:

a surface layer;

a substrate;

an active region including a source and a drain, disposed on one surface of said surface layer; and

a single drift layer disposed between the other surface of said surface layer and said substrate, said drift layer having a graded concentration of dopants extending between said surface layer and said substrate, said drift layer further having a first to create and maintain a single static unidirectional electric drift field to aid the movement of minority carriers from said surface layer to said substrate; and

at least one well region disposed in said single drift layer, said well region having a graded concentration of dopants and a second static unidirectional electric drift field to aid the movement of minority carriers from said surface layer to said substrate.

11. (Original) The CMOS Semiconductor device of claim 10 wherein said drift layer is a deeplyimplanted layer.

12. (Original) The CMOS Semiconductor device of claim 10 wherein said drift layer is an epitaxial layer.

13. (Original) The CMOS Semiconductor device of claim 10 wherein said graded concentration follows a linear gradient.

Page 3 of 8

072
Appl. No. 11/622,496 Response to Final Office Action of August 13, 2012

14. (Original) The CMOS Semiconductor device of claim 10 wherein said graded concentration follows a quasi-linear gradient.

15. (Original) The CMOS Semiconductor device of claim 10 wherein said graded concentration follows an exponential gradient.

16. (Original) The CMOS Semiconductor device of claim 10 wherein said graded concentration follows a complimentary error function gradient.

17. (Canceled)

18. (Currently amended) A CMOS Semiconductor device comprising:

a surface layer;

a substrate;

an active region including a source and a drain, disposed on one surface of said surface layer; and

a single drift layer disposed between the other surface of said surface layer and said substrate, said drift layer having a graded concentration of dopants extending between said surface layer and said substrate, said drift layer further having a first to create and maintain a single static unidirectional electric drift field to aid the movement of minority carriers from said substrate to said surface layer; and

at least one well region disposed in said single drift layer, said well region having a graded concentration of dopants and a second static unidirectional electric drift field to aid the

movement of minority carriers from said substrate to said surface layer.

19. (Original) The CMOS Semiconductor device of claim 18 wherein said drift layer is a deeplyimplanted layer.

20. (Original) The CMOS Semiconductor device of claim 18 wherein said drift layer is an epitaxial layer.

21. (Original) The CMOS Semiconductor device of claim 18 wherein said graded concentration follows a linear gradient.

22. (Original) The CMOS Semiconductor device of claim 18 wherein said graded concentration follows a quasi-linear gradient.

23. (Original) The CMOS Semiconductor device of claim 18 wherein said graded concentration follows an exponential gradient.

24. (Original) The CMOS Semiconductor device of claim 18 wherein said graded concentration follows a complimentary error function gradient.

25. (Canceled)

Page 5 of 8

REMARKS

Applicant has carefully reviewed the final Office Action of August 13, 2012 ("Office Action") and in response thereto states as follows:

Claims 10-16 and 18-24 stand rejected pursuant to 35 U.S.C. 112, first paragraph because Applicant's specification does not enable "to create and <u>maintain</u> a <u>single static</u> unidirectional electric drift field." Office Action at ¶2. Without conceding the merits of this rejection, Applicant has further amended base claims 10 and 18 to overcome the rejection pursuant to 35 U.S.C. 112, first paragraph. In particular, Applicant has removed any reference to the terms "create," "maintain" and "single." With regard to the remaining term "static," Applicant respectfully notes that prior art reference Kamins (US 4,160,985), just like Applicant, discloses the presence of a "static" drift field, "because the drift field is created by graded concentration of dopants which does not change over time." See Office Action ¶4 p.4 lines 1-3, further citing to Kamins, Col. 2, lines 15-16; Col. 2, line 64 – Col. 3, line 2; Col. 1, lines 38-46; and Col. 3, lines 8-11.

Claims 10-11 and 18-19 stand rejected as obvious in view of the combined teachings of Kamins (of prior record) in view of Jastrzebski (US 4,481,522) (of prior record) and Bamji (US 2002/0084430) (of prior record). Applicant has previously summarized the disclosure of these references. Without conceding any of Applicant's positions, Applicant has further amended independent claims 10 and 18 to better distinguish over the cited prior art by claiming "at least one well region disposed in said single drift layer, said well region having a graded concentration of dopants and a second static unidirectional electric drift field to aid the movement of minority carriers." Applicant respectfully submits that neither Kamins nor Jastrzebski, disclose the above limitation.

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position that claims 10 and 18 as previously submitted are product by process claims. See Office

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Claims 11-16 depend on claim 10 and for at least the same reason that claim 10 is patentable over the cited prior art, claims 11-16 are patentable as well. Claims 19-24 depend on claim 18 and for at least the reasons that claim 18 is patentable over the cited prior art, claims 19-24 are patentable as well.

Page 7 of 8

Appl. No. 11/622,496 Response to Final Office Action of August 13, 2012

CONCLUSION

Applicant respectfully submits that in view of the amendments made to the claims and the discussion set forth herein, this application is now in condition for allowance. However, should Examiner be of the opinion that further amendment or response is required; Applicant encourages Examiner to contact the undersigned attorney at the telephone number set forth below. The Commissioner is authorized to charge any additional fees or deficiencies or credit any overpayments to Eugene M. Cummings, P.C., Deposit Account No. **50-4199**, with reference to attorney docket number (0299-0001.01).

Respectfully submitted,

By:

David M. Mundt, Reg. No. 41,207

Law Offices of Eugene M. Cummings, P.C. 1 N. Wacker Suite 4130 Chicago, Illinois 60606

Telephone: (312) 984-0144 Facsimile: (312) 984-0146

Electronic A	cknowledgement Receipt
EFS ID:	13981170
Application Number:	11622496
International Application Number:	
Confirmation Number:	3086
Title of Invention:	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS
First Named Inventor/Applicant Name:	G.R. Mohan Rao
Customer Number:	70653
Filer:	David Michael Mundt/Francisca Hubbard
Filer Authorized By:	David Michael Mundt
Attorney Docket Number:	0299-0001.01
Receipt Date:	15-OCT-2012
Filing Date:	12-JAN-2007
Time Stamp:	11:20:04
Application Type:	Utility under 35 USC 111(a)

Payment information:

Submitted with F	Payment	no	no								
File Listing:											
Document Number	Document Description	File Name	File Size(Bytes)/ Message Digest	Multi Part /.zip	Pages (if appl.)						
1	Amendment After Final	AmendmentF.pdf	473206	no	8						
	Amendment Arter Final	Amenumenti .pur	200b0f61139362e54ef9b9229051b8cc71a 7b5e7	110							
Warnings:											
Information:											

This Acknowledgement Receipt evidences receipt on the noted date by the USPTO of the indicated documents, characterized by the applicant, and including page counts, where applicable. It serves as evidence of receipt similar to a Post Card, as described in MPEP 503.

New Applications Under 35 U.S.C. 111

If a new application is being filed and the application includes the necessary components for a filing date (see 37 CFR 1.53(b)-(d) and MPEP 506), a Filing Receipt (37 CFR 1.54) will be issued in due course and the date shown on this Acknowledgement Receipt will establish the filing date of the application.

National Stage of an International Application under 35 U.S.C. 371

If a timely submission to enter the national stage of an international application is compliant with the conditions of 35 U.S.C. 371 and other applicable requirements a Form PCT/DO/EO/903 indicating acceptance of the application as a national stage submission under 35 U.S.C. 371 will be issued in addition to the Filing Receipt, in due course.

New International Application Filed with the USPTO as a Receiving Office

If a new international application is being filed and the international application includes the necessary components for an international filing date (see PCT Article 11 and MPEP 1810), a Notification of the International Application Number and of the International Filing Date (Form PCT/RO/105) will be issued in due course, subject to prescriptions concerning national security, and the date shown on this Acknowledgement Receipt will establish the international filing date of the application.

PTO/SB/06 (07-06)

Approved for use through 1/31/2007. OMB 0651-0032 LLC Detent and T

PATENT APPLICATION FEE DETERMINATION RECORD Substitute for Form PTO-875								Docket Number 2,496		ing Date 12/2007	To be Maile
	AF	PLICATION	AS FILE	D – PART I			_			IER THAN	
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	SEARCH FEE (37 CFR 1.16(k), (i), c	or (m))	N/A		N/A		N/A			N/A	
	EXAMINATION FE (37 CFR 1.16(o), (p), o		N/A		N/A	1 [N/A			N/A	
	TAL CLAIMS CFR 1.16(i))		mir	us 20 = *		1 T	X \$ =		OR	X\$ =	
D	EPENDENT CLAIM CFR 1.16(h))	s	m	inus 3 = *		1 T	X\$ =		1	X\$ =	
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							TOTAL ADD'L FEE	0	OR	TOTAL ADD'L FEE	
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	Independent (37 CFR 1.16(h))	*	Minus	***	=] [X \$ =		OR	X\$ =	
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This collection of information is required by 37 CFR 1.16. The information is required to obtain of retain a benefit by the public which is to file (and by the USP 10 to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 12 minutes to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR 0000 COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

If you need assistance in completing the form, call 1-800-PTO-9199 and select option 2.

	ed States Paten	UNITED STATES DEPARTMENT OF COMMEI United States Patent and Trademark Office Address: COMMISSIONER FOR PATENTS P.O. Box 1450 Alexandria, Virginia 22313-1450 www.uspto.gov				
APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.		
11/622,496	01/12/2007	G.R. Mohan Rao	0299-0001.01	3086		
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SUITE 4130 CHICAGO, IL	60606		ART UNIT	PAPER NUMBER		
Cilicii00, III	00000		2892			
			MAIL DATE	DELIVERY MODE		
			08/13/2012	PAPER		

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

	Application No.	Applicant(s)							
	11/622,496	RAO, G.R. MOHAN							
Office Action Summary	Examiner	Art Unit							
	AJAY K. ARORA	2892							
The MAILING DATE of this communication app Period for Reply	ears on the cover sheet with the o	correspondence address							
 A SHORTENED STATUTORY PERIOD FOR REPLY WHICHEVER IS LONGER, FROM THE MAILING DA Extensions of time may be available under the provisions of 37 CFR 1.13 after SIX (6) MONTHS from the mailing date of this communication. If NO period for reply is specified above, the maximum statutory period w Failure to reply within the set or extended period for reply will, by statute, Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b). 	ATE OF THIS COMMUNICATION 36(a). In no event, however, may a reply be tir vill apply and will expire SIX (6) MONTHS from cause the application to become ABANDONE	N. nely filed the mailing date of this communication. ED (35 U.S.C. § 133).							
Status									
 1) Responsive to communication(s) filed on <u>17 April 2012</u>. 2a) This action is FINAL. 2b) This action is non-final. 3) An election was made by the applicant in response to a restriction requirement set forth during the interview on; the restriction requirement and election have been incorporated into this action. 4) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i>, 1935 C.D. 11, 453 O.G. 213. 									
Disposition of Claims									
 5) ∑ Claim(s) <u>10-16 and 18-24</u> is/are pending in the 5a) Of the above claim(s) is/are withdraw 6) ☐ Claim(s) is/are allowed. 7) ∑ Claim(s) <u>10-16 & 18-24</u> is/are rejected. 8) ☐ Claim(s) is/are objected to. 9) ☐ Claim(s) are subject to restriction and/or 	vn from consideration.								
Application Papers									
 10) The specification is objected to by the Examine 11) The drawing(s) filed on is/are: a) access Applicant may not request that any objection to the object that any objection to the object of the drawing sheet(s) including the correct 12) The oath or declaration is objected to by the Examine 	epted or b) objected to by the drawing(s) be held in abeyance. Se ion is required if the drawing(s) is ob	e 37 CFR 1.85(a). jected to. See 37 CFR 1.121(d).							
Priority under 35 U.S.C. § 119									
 13) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f). a) All b) Some * c) None of: Certified copies of the priority documents have been received. Certified copies of the priority documents have been received in Application No 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)). * See the attached detailed Office action for a list of the certified copies not received. 									
Attachment(s) 1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO/SB/08) Paper No(s)/Mail Date U.S. Patent and Trademark Office	4) Interview Summary Paper No(s)/Mail D 5) Notice of Informal F 6) Other:	ate							

DETAILED ACTION

Claim Rejections - 35 USC § 112

1. The following is a quotation of the first paragraph of 35 U.S.C. 112:

The specification shall contain a written description of the invention, and of the manner and process of making and using it, in such full, clear, concise, and exact terms as to enable any person skilled in the art to which it pertains, or with which it is most nearly connected, to make and use the same and shall set forth the best mode contemplated by the inventor of carrying out his invention.

2. Claim 10-16 and 18-24 rejected under 35 U.S.C. 112, first paragraph, because the specification, while being enabling for "to create a unidirectional electric drift field" (see lines 8-9 of base claims 10 and 18), does not reasonably provide enablement for "to create and <u>maintain</u> a <u>single static</u> unidirectional electric drift field" (emphasis added, as recited in lines 8-9 of the currently amended claims 10 and 18). The specification does not enable any person skilled in the art to which it pertains, or with which it is most nearly connected, to make and use the invention commensurate in scope with these claims. Applicant has not pointed out to the part of the specification that supports the above amendment. Also, in view of arguments that applicant has presented on pages 8-9 of applicant's response of 04/17/2012 to argue that Jastrzebski reference does not read on "to create and <u>maintain</u> a <u>single static</u> unidirectional electric drift field", it is not clear how any of applicant's Figures conveys the above limitation any more than Figure 1 of Jastrzebski.

Claim Rejections - 35 USC § 103

3. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all

obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

4. Claims 10-11, and 18-19 are rejected under 35 U.S.C. 103(a) as being

unpatentable over Kamins (US 4,160,985) of prior record, hereinafter Kamins, in view

Jastrzebski (US 4,481,522) of prior record, hereinafter Jastrzebski, and further in view

of Bamji (US 2002/0084430) of prior record, hereinafter Bamji.

Regarding claim 10, Kamins (refer to Figures 2-3) teaches a semiconductor device comprising:

a surface layer (23);

s substrate (19);

an active region (comprising photodiodes 11, 13, 15 and 17 are formed),

disposed on one surface (i.e. upper surface in Figure 2) of said surface layer (23); and

a single drift layer (21) disposed between the other surface (i.e. lower surface in Figure 2) of said surface layer (23) and said substrate (19), said drift layer having a graded concentration of dopants (see Figure 3) extending between said surface layer and said substrate, which is capable of creating and maintaining a single static electric

drift field (because the drift field is created by graded concentration of dopants which does not change over time; i.e. it is "single static"). Also see Col. 2, lines 15-16; Col. 2, line 64 - Col. 3, line 2; Col. 1, lines 38-46; and Col. 3, lines 8-11).

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Kamins does not teach that the drift field is a "unidirectional drift field" that is capable of aiding the movement of minority carriers in a given direction. Jastrzebski (refer to Figures 1a-b) teaches a semiconductor device in which a drift field utilized is a "unidirectional drift field" so as aid movement of minority carriers in a specific direction; i.e. direction of the unidirectional drift field (Col. 5, lines 17-20 and 25-30). It would have been obvious to one of ordinary skills in the art at the time of the invention to modify Kamins so that the drift field is a unidirectional drift field that is capable of aiding the movement of minority carriers in a given direction. The ordinary artisan would have been motivated to modify Kamins for at least the purpose of optimizing the performance of any device that may be used in conjunction with transistors (as part of an integrated circuit) that may require drawing of minority carriers in a specific direction to improve performance (see Jastrzebski, Col. 2, lines 22-42).

Further, whereas Kamins teaches photosensing elements like photodiodes and associated integrated circuit structures (Col. 2, lines 56-59), Kaminis does not teach that the semiconductor device is a "CMOS" semiconductor device and with the active region including "a source and a drain". Bamji teaches that integrated circuit structures with photo detectors such as photodiodes may be arrays of CMOS devices (page 1, para 0004) wherein active regions may include a source and a drain (page 9, para 0098, 1st sentence). It would have been obvious to one of ordinary skills in the art at the time of

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the invention to modify Kamins so that the semiconductor device is a CMOS semiconductor device and with the active region includes a source and a drain. The ordinary artisan would have been motivated to modify Kamins for at least the purpose of using CMOS technology that is suitable for field effect devices with source and drain regions, as CMOS technology enables integration of images sensors on a single integrated circuit and reduction in power consumption (see Bamji, page 1, para 0002).

It is noted that claim 10 is a product claim but recites a method therein (i.e. "create and maintain a single static unidirectional electric drift field"; emphasis added). Therefore, claim 10 (same applies to claim 18) amounts to a product by process claim. "Even though product-by-process claims are limited by and defined by the process, determination of patentability is based on the product itself. The patentability of a product does not depend on its method of production. If the product in the product-byprocess claim is the same as or obvious from a product of the prior art, the claim is unpatentable even though the prior product was made by a different process." In re Thorpe, 777 F.2d 695, 698, 227 USPQ 964, 966 (Fed. Cir. 1985). See MPEP 2113. To the extent the limitation of "create and maintain a single static unidirectional electric drift field" applies to the electric drift field inherently created by the claimed "graded concentration of dopants", it conveys a structural limitation. However, if the above implies absence of other electric fields (see applicant's arguments on page 8 of applicant's response of 4/17/2012), that does not constitute a structural limitation but rather method steps.

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Claim 18 is similar to claim 10 (and hence the same rejection applies) except for the direction of drawing minority carriers. However, Kamins also teaches the direction of drawing minority carriers as in claim 18; i.e. drawing minority carriers (Col. 2, lines 15-16) may also be from said substrate to said surface layer (Col. 1, lines 38-46 and Col. 3, lines 6-18).

Regarding claims 11 and 19, Kamins teaches that said drift layer (21) is a deeply implanted layer (see Figures 2-3; also see Col. 2, lines 36-42).

5. Claims 12 and 20 are rejected under 35 U.S.C. 103(a) as being unpatentable over Kamins, Jastrzebski and Bamji as applied to claims 10 and 18 above above, and further in view of Baliga (US 2002/0056883) of prior record, hereinafter Baliga.

Regarding claims 12 and 20, Kamins (refer to Figures 2-3) teaches substantially the claimed structure but does not teach that the drift layer is an "epitaxial" layer. Baliga (US 2002/0056883) teaches that it is known in the art that a drift layer with graded dopant concentration may be an epitaxial layer (page 2, para 0008, 2^{nd} and 3rd sentences and page 9, para 0063, especially $7^{th} - 9^{th}$ sentences). It would have been obvious to one of ordinary skills in the art at the time of the invention to modify Kamins so that the drift layer is an epitaxial layer. The ordinary artisan would have been motivated to modify Kamins for at least the purpose of using a layer that has a uniform crystal structure

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which makes electrical properties more predictable and can also act as a base for further epitaxial layers in which devices may be formed.

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6. Claims 13-16 and 21-24 are rejected under 35 U.S.C. 103(a) as being unpatentable over Kamins, Jastrzebski and Bamji as applied to claims 10 and 18 above above, and further in view of Fujimoto (2002/0102783) of prior record, hereinafter Fujimoto; and Ishaque (US 5,517,052) of prior record, hereinafter Ishaque.

Regarding claims 13-16 and 21-24, Kamins (refer to Figure 3) teaches substantially the claimed structure but does not specifically state if the gradient is "linear", "quasi-linear", "exponential"; or "complimentary error function". Fujimoto teaches that an impurity region having a concentration gradient may have a profile that is linear, exponential, "or a combination thereof (page 3, para 0038). Further, Ishaque teaches that doping gradient is typically complementary error function or Gaussian if a deep diffusion process is used (Col. 3, line 49 to Col. 4, line 14). Given that Kamins teaches that a desired electric field is formed as a result of the gradient in doping (thus suggesting the gradient affects profile of the field) and various profiles of concentration gradient are known (as explained above in view of Fujimoto and Ishaque), it would have been obvious to one of ordinary skills in the art at the time of the invention to modify Kamins so that the gradient is linear, exponential; or alternatively other profiles such as "quasi-linear" or "complimentary error function", which are essentially combinations of linear and exponential profiles. The ordinary artisan would have been motivated to modify

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Response to Arguments

7. Applicant's arguments with respect to 35 USC 112, 1st paragraph rejection of claims 10 and 18 related to "drawing <u>all</u> minority carriers from said substrate to said surface layer" have been considered but are moot because the arguments do not apply in view of the amendment to the claims. However, the amendments result in new 35 USC 112, 1st paragraph rejections, which have been outlined above.

Applicant's arguments with respect to 35 USC 103(a) rejections of claims 10 and
 18 (see 2nd last paragraph of page 7 to page 9) have been considered but they are not persuasive.

9. On page 7, last paragraph to page 9, 1st paragraph of applicant's response, applicant argues that because Jastrzebski reference teaches "clocking signals" in addition to the drift field created by graded dopant concentration, it does not read on "create and maintain a single static unidirectional electric drift field". This argument is not persuasive. This argument is addressed in the revised rejection of claims 10 and 18, which now points out product-by-process limitations.

Conclusion

 Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to AJAY K. ARORA whose telephone number is (571)272-8347. The examiner can normally be reached on Mon through Fri, 8:30am to 5:00pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Thao X. Le can be reached on (571) 272-1708. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information

system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

/AJAY K. ARORA/ Primary Examiner, Art Unit 2892

	Application/Control No.	Applicant(s)/Patent Under Reexamination			
Search Notes	11622496	RAO, G.R. MOHAN			
	Examiner	Art Unit			
	AJAY K ARORA	2892			

SEARCHED									
Class	Subclass	Date	Examiner						
257	655	12/16/2011	AKA						

SEARCH NOTES									
Search Notes	Date	Examiner							
Revised EAST search history report	12/16/2011	AKA							
Revised EAST search history report	8/10/2012	AKA							

INTERFERENCE SEARCH								
Class	Subclass	Date	Examiner					

	/A. K. A./ Primary Examiner.Art Unit 2892
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EAST Search History

EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S94		(single WITh static WITH drift) AND ((gradient OR grading OR graded) WITH dop\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2012/08/10 00:21
S96			US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2012/08/10 00:24

8/10/2012 1:40:03 AM

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application No.	:	11/622,496
Confirmation No.	:	3086
Inventor	:	G. R. Mohan Rao
Filed	:	January 12, 2007
TC/A.U.	:	2892
Examiner	:	Ajay Arora
Title	:	SEMICONDUCTOR DEVICES WITH GRADED
		DOPANT REGIONS
Docket No.	:	0299-0001.01

RESPONSE PURSUANT TO 37 CFR 1.114

AMENDMENT E

Sir:

In response to the non-final Office Action of December 20, 2011, Applicant submits the following amendment:

Claims. Amendments to the claims begin on page 2 of this amendment.

Remarks. Remarks begin on page 6 of this amendment.

Appl. No. 11/622,496 Response to Non-Final Office Action of December 20, 2011

LISTING OF CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

Claims:

1. (Canceled)

- 2. (Canceled)
- 3. (Canceled)
- 4. (Canceled)
- 5. (Canceled)
- 6. (Canceled)
- 7. (Canceled)
- 8. (Canceled)
- 9. (Canceled)

10. (Currently Amended) A CMOS Semiconductor device comprising:

a surface layer;

a substrate;

an active region including a source and a drain, disposed on one surface of said surface

layer; and

a single drift layer disposed between the other surface of said surface layer and said substrate, said drift layer having a graded concentration of dopants extending between said surface layer and said substrate to create <u>and maintain</u> a <u>single static</u> unidirectional <u>electric</u> drift field <u>to aid the movement of drawing all</u> minority carriers from said surface layer to said substrate.

11. (Original) The CMOS Semiconductor device of claim 10 wherein said drift layer is a deeplyimplanted layer.

12. (Original) The CMOS Semiconductor device of claim 10 wherein said drift layer is an epitaxial layer.

13. (Original) The CMOS Semiconductor device of claim 10 wherein said graded concentration follows a linear gradient.

14. (Original) The CMOS Semiconductor device of claim 10 wherein said graded concentration follows a quasi-linear gradient.

15. (Original) The CMOS Semiconductor device of claim 10 wherein said graded concentration follows an exponential gradient.

16. (Original) The CMOS Semiconductor device of claim 10 wherein said graded concentration follows a complimentary error function gradient.

17. (Canceled)

18. (Currently amended) A CMOS Semiconductor device comprising:

a surface layer;

a substrate;

an active region including a source and a drain, disposed on one surface of said surface layer; and

a single drift layer disposed between the other surface of said surface layer and said substrate, said drift layer having a graded concentration of dopants extending between said surface layer and said substrate to create <u>and maintain</u> a <u>single static</u> unidirectional <u>electric</u> drift field <u>to aid the movement of drawing all</u> minority carriers from said substrate to said surface layer.

19. (Original) The CMOS Semiconductor device of claim 18 wherein said drift layer is a deeplyimplanted layer. 20. (Original) The CMOS Semiconductor device of claim 18 wherein said drift layer is an epitaxial layer.

21. (Original) The CMOS Semiconductor device of claim 18 wherein said graded concentration follows a linear gradient.

22. (Original) The CMOS Semiconductor device of claim 18 wherein said graded concentration follows a quasi-linear gradient.

23. (Original) The CMOS Semiconductor device of claim 18 wherein said graded concentration follows an exponential gradient.

24. (Original) The CMOS Semiconductor device of claim 18 wherein said graded concentration follows a complimentary error function gradient.

25. (Canceled)

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REMARKS

Applicant has carefully reviewed the non-final Office Action of December 20, 2012 ("Office Action") and in response thereto states as follows:

The Office Action maintains a rejection pursuant to 35 U.S.C. §112, first paragraph, and in particular states that, because "movement of minority carriers is affected by multiple forces and fields ... it does not appear that simply the presence of 'a unidirectional drift field' in itself can achieve 'drawing all minority carriers from said surface layer to said substrate.'" Office Action at ¶3.

Applicant respectfully disagrees with this position because (as previously argued by Applicant) a unidirectional drift (electric) field <u>necessarily</u> affects <u>all</u> the present minority carriers in the same way – moving all minority carriers in the same direction because of the unidirectional drift due to the existence of the electric field. *See* "Physics and Technology of Semiconductor Devices," A.S. Grove, pp. 224-225, John Wiley and Sons, Inc., New York, 1st Edition 1967 ("This same electric field will then be of such direction as to aid the motion of injected holes. Thus the injected minority carriers will now move not only by diffusion but also by drift due to the existence of this electric field."). Depending on the particular slope of the graded concentration of dopant, all minority carriers are either swept "down" (from the surface layer to the substrate) or "up" (from the substrate to the surface layer). *See* Applicant's Figs. 5(b) and 5(c).

The Office Action also states that "such a unidirectional drift field may attempt to apply a force on all minority carriers in a specific direction, it does not appear to ensure (without knowing other parameters of the device) that it will draw 'all' minority carriers..." Yet, this argument appears to not consider that the graded dopant concentration <u>itself</u> creates a "built-in"

electrical field that forces the movement of carriers into a particular direction, whereby the "direction" of the electrical field and the resulting direction of the carrier movement depends solely on the slope of the graded concentration of dopant. With regard to the existence of a "built-in" electric field created by a graded dopant density, *see*, e.g., Jastrzebski (US 4,481,522) col. 5, lines 11-13 (cited in Office Action). Applicant respectfully submits that this inherent "built-in" unidirectional electric field is the additional parameter for ensuring that all minority carriers are being moved in one direction and which parameter the Office Action deemed to be missing from the disclosure.

However, without conceding Applicant's position on this issue, Applicant has further amended claims 10 and 18 to overcome the rejection pursuant to 35 U.S.C. 112, first paragraph. In particular, Applicant has removed the word "all" from the rejected claim language which now reads: "unidirectional electric drift field to aid the movement of minority carriers ..." This claim language is supported at least by Applicant's disclosure in paragraph 11 and original claim 6.

Independent claims 10 and 18 stand rejected as obvious in view of the combined teachings of Kamins (US 4,160,985) of prior record in view of Jastrzebski (US 4,481,522) and Bamji (US 2002/0084430) of prior record. Kamins discloses a photosensing device in which selective doping of a semiconductor substrate of the device produces electric fields in the substrate which accelerate photogenerated charge carriers toward or away from the surface of the device. Abstract, Fig. 3. As the Office Action acknowledges, Kamins does not teach that the electric drift field is a "unidirectional electric drift field."

Jastrzebski discloses three-phase charge-coupled device (CCD) imagers having unidirectional electric drift fields in their semiconductive substrates to improve the operation of the CCD (*see* e.g., col. 1, lines 5-8, col 2, lines 62-64, col. 3, lines 20-52 and Fig. 1a). Jastrzebski

Page 7 of 10

describes the three-phase clocking signals as follows:

Electrodes 13 and 16 are shown connected to receive a first phase ϕ_1 of the three-phase clocking signals; electrodes 14 and 17, to receive a second phase ϕ_2 of those signals; and electrodes 15 and 18, to receive a third phase ϕ_3 of those signals. The successive application of the clocking signals ϕ_1 , ϕ_2 , and ϕ_3 in order of their ordinal number subscripts will, as known, cause shift of charge packets in potential wells induced under the electrodes in a rightward direction on each clocking signal transition. These potential wells are associated with the charge depletion regions induced below the electrodes receiving relatively positive clocking signal phases. In FIG. 1 the depletion regions are shown in dashed outline being induced under electrode pairs 13, 14 and 16, 17 presumed to be receiving ϕ_1 , ϕ_2 clock voltages relatively positive to the ϕ_3 clock voltage applied to electrodes 15 and 18.

(Jastrzebski, Col. 3, lines 20-36, underlines added).

As the underlined text above indicates, the application of clocking signals causes a shift of charge packets in the regions directly underneath the electrodes which causes a change of value of the unidirectional electric drift field located directly underneath the electrodes. Unlike the capacitor electrodes/gates in a CMOS image sensor, which have a fixed potential, the electrodes/gates in a CCD shift register do not have a fixed potential. As made clear in Jastrzebski, successive application of clocked signals effectively creates multiple electrical fields underneath the gates with varying electric values (potentials), or at least, arguably, one <u>dynamic</u> (varying with time) unidirectional electric field with varying electric (values) potentials. That is so because the electric field described in Jastrzebski is influenced by at least two factors. First, $\varphi 1$, $\varphi 2$ and $\varphi 3$ "swing" back and forth (shift) their charge and therefore modulate the electric field created by the graded dopant concentration in the substrate. Second, this modulation disturbs the electric field and affects the effectiveness of the electric field to aid the movement of carriers in a single desired direction. Because a CMOS image sensor only has electrodes/gates with a fixed potential, there is no modulation of the electric unidirectional drift field. Consequently, Applicant's claimed CMOS semiconductor device includes a single <u>static</u> (timeinvariant) unidirectional electric drift field.

Applicant has amended claims 10 and 18 to better distinguish over the cited prior art by claiming "a graded concentration of dopants extending between said surface layer and said substrate to create and maintain a single static unidirectional electric drift field to aid the movement of minority carriers."

Bamji discloses a method to measure distance or brightness using a CMOS sensor. The most recent office action cites Bamji against claim 10 for the proposition that integrated circuit structures with photo detectors may be arrays of CMOS devices. However, Applicant respectfully submits that this disclosure is moot in view of the above recited shortcomings in the disclosure of Kamins and Jastrzebski and in view of Applicant's additional amendments to claims 10 and 18.

Claims 11-16 depend on claim 10 and for at least the same reason that claim 10 is patentable over the cited prior art, claims 11-16 are patentable as well. Claims 19-24 depend on claim 18 and for at least the reasons that claim 18 is patentable over the cited prior art, claims 19-24 are patentable as well.

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Appl. No. 11/622,496 Response to Non-Final Office Action of December 20, 2011

CONCLUSION

Applicant respectfully submits that in view of the amendments made to the claims and the discussion set forth herein, this application is now in condition for allowance. However, should Examiner be of the opinion that further amendment or response is required; Applicant encourages Examiner to contact the undersigned attorney at the telephone number set forth below. The Commissioner is authorized to charge any additional fees or deficiencies or credit any overpayments to Eugene M. Cummings, P.C., Deposit Account No. **50-4199**, with reference to attorney docket number (0299-0001.01).

Respectfully submitted,

By:

David M. Mundt, Reg. No. 41,207

Law Offices of Eugene M. Cummings, P.C. 1 N. Wacker Suite 4130 Chicago, Illinois 60606

Telephone: (312) 984-0144 Facsimile: (312) 984-0146

PTO/SB/22 (09-11)

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U.S. Patent and	Trademark Off	Ce; U.S. DE	PARMENT OF COMMERCE
Under the paperwork Reduction Act of 1995, no persons are required to respond to a collection of info	ormation unles	s it displays	a valid OMB control number.

PETITION FOR EXTENSION OF TIME UNDER 37 CFR 1.136(a)			Docket Number (Option 0299-0001.01	Docket Number (Optional) 0299-0001.01		
Application Number 11/622496		Filed 01/12/2007				
For SEM	ICONDUCTOR DEVICES WITH GRA	DED DOPANT R	EGIONS			
Art Unit 28	92		Examiner Ajay Aror	a		
This is a rec application.	quest under the provisions of 37 CFR 1.130	6(a) to extend the pe	eriod for filing a reply in th	e above identified		
The request	ted extension and fee are as follows (chec	k time period desire	d and enter the appropriat	te fee below):		
		Fee	Small Entity Fee	75.00		
\checkmark	One month (37 CFR 1.17(a)(1))	\$150	\$75	\$_75.00		
	Two months (37 CFR 1.17(a)(2))	\$560	\$280	\$		
	Three months (37 CFR 1.17(a)(3))	\$1270	\$635	\$		
	Four months (37 CFR 1.17(a)(4))	\$1980	\$990	\$		
	Five months (37 CFR 1.17(a)(5))	\$2690	\$1345	\$		
Applica	nt claims small entity status. See 37 CFR	1.27.				
A chec	k in the amount of the fee is enclosed					
Payme	Payment by credit card. Form PTO-2038 is attached.					
The Director has already been authorized to charge fees in this application to a Deposit Account.						
The Di Depos	rector is hereby authorized to charge a it Account Number <u>50-4199</u>	any fees which ma	ay be required, or credit	t any overpayment, to		
WARNI	NG: Information on this form may become pu credit card information and authorization or	ıblic. Credit card info ı PTO-2038.	rmation should not be incl	uded on this form.		
I am the	applicant/inventor.					
	assignee of record of the entire Statement under 37 CFR 3.					
	attorney or agent of record. Re	gistration Number	41,207			
attorney or agent under 37 CFR 1.34. Registration number if acting under 37 CFR 1.34						
/David	M. Mundt/		April 17, 2012			
Signature			Date			
David M. Mundt		312-984-0144	312-984-0144			
	Typed or printed name		Telepho	one Number		
	res of all the inventors or assignees of record of the en uired, see below.	tire interest or their repres	entative(s) are required. Submit	multiple forms if more than one		
Total		e submitted.				
	information is required by 37 CFR 1.136(a). The inform ss) an application. Confidentiality is governed by 35 U.					

USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.11 and 1.14. This collection is estimated to take 6 minutes to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. **SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.**

If you need assistance in completing the form, call 1-800-PTO-9199 and select option 2.

Electronic Patent Application Fee Transmittal					
Application Number:	11622496				
Filing Date:	12-	Jan-2007			
Title of Invention:	SEP	MICONDUCTOR DEV	/ICES WITH GR	ADED DOPANT REG	iIONS
First Named Inventor/Applicant Name:	G.R. Mohan Rao				
Filer:	David Michael Mundt/Francisca Hubbard				
Attorney Docket Number:	0299-0001.01				
Filed as Small Entity					
Utility under 35 USC 111(a) Filing Fees					
Description		Fee Code	Quantity	Amount	Sub-Total in USD(\$)
Basic Filing:					
Pages:					
Claims:					
Miscellaneous-Filing:					
Petition:					
Patent-Appeals-and-Interference:					
Post-Allowance-and-Post-Issuance:					
Extension-of-Time:					
Extension - 1 month with \$0 paid		2251	1	75	75

Description	Fee Code	Quantity	Amount	Sub-Total in USD(\$)
Miscellaneous:				
	Total in USD (\$)			75

Electronic A	Electronic Acknowledgement Receipt				
EFS ID:	12560817				
Application Number:	11622496				
International Application Number:					
Confirmation Number:	3086				
Title of Invention:	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS				
First Named Inventor/Applicant Name:	G.R. Mohan Rao				
Customer Number:	70653				
Filer:	David Michael Mundt/Francisca Hubbard				
Filer Authorized By:	David Michael Mundt				
Attorney Docket Number:	0299-0001.01				
Receipt Date:	17-APR-2012				
Filing Date:	12-JAN-2007				
Time Stamp:	15:20:02				
Application Type:	Utility under 35 USC 111(a)				

Payment information:

Submitted with Payment	yes					
Payment Type	Deposit Account					
Payment was successfully received in RAM	\$75					
RAM confirmation Number	1922					
Deposit Account	504199					
Authorized User						
The Director of the USPTO is hereby authorized to charge indicated fees and credit any overpayment as follows:						
Charge any Additional Fees required under 37 C.F.R. Section 1.21 (Miscellaneous fees and charges)						
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1	Amendment/Req. Reconsideration-After		694682			
1	Non-Final Reject	AmendmentE.pdf	df7ff0ed5b70459b2c714986b91a259d9e2 6330c	no	10	
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Information						
2	Extension of Time	ExtOfTime.pdf	132721	20	1	
2	Extension of time	Extornine.pu	dee7fa1a4348d38dd841d010681af572790 a8c55	no	I	
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Information						
Total Files Size (in bytes): 857716						
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	ed States Paten	T AND TRADEMARK OFFICE	UNITED STATES DEPAR United States Patent and Address: COMMISSIONER F P.O. Box 1450 Alexandria, Virginia 22: www.uspto.gov	FOR PATENTS
APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
11/622,496	01/12/2007	G.R. Mohan Rao	0299-0001.01	3086
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SUITE 4130 CHICAGO, IL	60606		ART UNIT	PAPER NUMBER
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			MAIL DATE	DELIVERY MODE
			12/20/2011	PAPER

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

	Application No.	Applicant(s)
	11/622,496	RAO, G.R. MOHAN
Office Action Summary	Examiner	Art Unit
	AJAY K. ARORA	2892
The MAILING DATE of this communication	n appears on the cover sheet with	h the correspondence address
Period for Reply		
 A SHORTENED STATUTORY PERIOD FOR RI WHICHEVER IS LONGER, FROM THE MAILIN Extensions of time may be available under the provisions of 37 Cf after SIX (6) MONTHS from the mailing date of this communicatio If NO period for reply is specified above, the maximum statutory p Failure to reply within the set or extended period for reply will, by s Any reply received by the Office later than three months after the earned patent term adjustment. See 37 CFR 1.704(b). 	G DATE OF THIS COMMUNIC. FR 1.136(a). In no event, however, may a rep n. eriod will apply and will expire SIX (6) MONTI statute, cause the application to become ABA	ATION. Jy be timely filed HS from the mailing date of this communication. NDONED (35 U.S.C. § 133).
Status		
1) \boxtimes Responsive to communication(s) filed on _	12 October 2011.	
	This action is non-final.	
3) An election was made by the applicant in 1		ment set forth during the interview on
; the restriction requirement and ele	ction have been incorporated in	to this action.
4) Since this application is in condition for all	owance except for formal matte	rs, prosecution as to the merits is
closed in accordance with the practice und	der <i>Ex parte Quayle</i> , 1935 C.D.	11, 453 O.G. 213.
Disposition of Claims		
5)X Claim(s) <u>10-16 and 18-24</u> is/are pending i	n the application.	
5a) Of the above claim(s) is/are with	ndrawn from consideration.	
6) Claim(s) is/are allowed.		
7) Claim(s) <u>10-16 and 18-24</u> is/are rejected.		
8) Claim(s) is/are objected to.		
9) Claim(s) are subject to restriction a	nd/or election requirement.	
Application Papers		
10) The specification is objected to by the Exam	miner.	
11) The drawing(s) filed on is/are: a)	accepted or b) objected to by	y the Examiner.
Applicant may not request that any objection to	the drawing(s) be held in abeyanc	e. See 37 CFR 1.85(a).
Replacement drawing sheet(s) including the co	prrection is required if the drawing(s) is objected to. See 37 CFR 1.121(d).
12) The oath or declaration is objected to by the table \square	e Examiner. Note the attached	Office Action or form PTO-152.
Priority under 35 U.S.C. § 119		
13) Acknowledgment is made of a claim for for	eign priority under 35 U.S.C. §	119(a)-(d) or (f).
a) All b) Some * c) None of:		
1. Certified copies of the priority docur	nents have been received.	
2. Certified copies of the priority docur	nents have been received in Ap	plication No
3. Copies of the certified copies of the	priority documents have been r	eceived in this National Stage
application from the International Bu		
* See the attached detailed Office action for a	a list of the certified copies not re	eceived.
Attachment(s)		(PTO 412)
 Notice of References Cited (PTO-892) Notice of Draftsperson's Patent Drawing Review (PTO-948 		ımmary (PTO-413) /Mail Date
3) 🛛 Information Disclosure Statement(s) (PTO/SB/08)	5) 📃 Notice of Inf	ormal Patent Application
Paper No(s)/Mail Date <u>10/12/2011</u> . J.S. Patent and Trademark Office	6) 🚺 Other:	
	ce Action Summary	Part of Paper No./Mail Date 20111216

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DETAILED ACTION

Continued Examination Under 37 CFR 1.114

1. A request for continued examination under 37 CFR 1.114, including the fee set forth in 37 CFR 1.17(e), was filed in this application after final rejection. Since this application is eligible for continued examination under 37 CFR 1.114, and the fee set forth in 37 CFR 1.17(e) has been timely paid, the finality of the previous Office action has been withdrawn pursuant to 37 CFR 1.114. Applicant's submission filed on 10/12/2011 has been entered.

Claim Rejections - 35 USC § 112

2. The following is a quotation of the first paragraph of 35 U.S.C. 112:

The specification shall contain a written description of the invention, and of the manner and process of making and using it, in such full, clear, concise, and exact terms as to enable any person skilled in the art to which it pertains, or with which it is most nearly connected, to make and use the same and shall set forth the best mode contemplated by the inventor of carrying out his invention.

3. Claim 10-16 and 18-24 rejected under 35 U.S.C. 112, first paragraph, because the specification, while being enabling for "a unidirectional drift field" (see line 8 of base claims 10 and 18, each, which is shown in Figure 2 of the specification), does not reasonably provide enablement for "drawing <u>all</u> minority carriers from said substrate to said surface layer" (emphasis added, see last two lines each of base claims 10 and 18). The specification does not enable any person skilled in the art to which it pertains, or

Page 3

with which it is most nearly connected, to make and use the invention commensurate in scope with these claims. It is not clear if simply the application of "a unidirectional drift field" is sufficient to achieve the effect of "drawing <u>all</u> minority carriers from said substrate to said surface layer". In a complex electronic device, movement of minority carriers is affected by multiple forces and fields, and it does not appear that simply the presence of "a unidirectional drift field" in itself can achieve "drawing <u>all</u> minority carriers from said surface layer to said substrate". Whereas it is true that such a unidirectional drift field may attempt to apply a force on all minority carriers in a specific direction, it does not appear to ensure (without knowing other parameters of the device) that it will draw "all" minority carriers from said surface layer to said surface layer to said surface layer to said surface layer.

Claim Rejections - 35 USC § 103

4. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

5. Claims 10-11, and 18-19 are rejected under 35 U.S.C. 103(a) as being unpatentable over Kamins (US 4,160,985) of prior record, hereinafter Kamins, in view Jastrzebski (US 4,481,522), hereinafter Jastrzebski, and further in view of Bamji (US 2002/0084430) of prior record, hereinafter Bamji.

Regarding claim 10, Kamins (refer to Figures 2-3) teaches a semiconductor device comprising:

a surface layer (23);

s substrate (19);

an active region (comprising photodiodes 11, 13, 15 and 17 are formed), disposed on one surface (i.e. upper surface in Figure 2) of said surface layer (23); and

a single drift layer (21) disposed between the other surface (i.e. lower surface in Figure 2) of said surface layer (23) and said substrate (19), said drift layer having a graded concentration of dopants (see Figure 3) extending between said surface layer and said substrate to create a drift field (Col. 2, line 64 - Col. 3, line 2) drawing minority carriers (Col. 2, lines 15-16) from said surface layer to said substrate (Col. 1, lines 38-46 and Col. 3, lines 8-11).

Kamins does not teach that the drift field is a "unidirectional drift field" so that it draws "all" minority carriers in a given direction. Jastrzebski (refer to Figures 1a-b) teaches a semiconductor device in which a drift field utilized is a "unidirectional drift field" so as to tend to draw "all" minority carriers in a specific direction' i.e. direction of the unidirectional drift field (Col. 5, lines 17-20 and 25-30). It would have been obvious to one of ordinary skills in the art at the time of the invention to modify Kamins so that the the drift field is a unidirectional drift field that it draws all minority carriers in a given direction. The ordinary artisan would have been motivated to modify Kamins for at least the purpose of optimizing the performance of any device that may be used in

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conjunction with transistors (as part of an integrated circuit) that may require drawing of minority carriers in a specific direction to improve performance (see Jastrzebski, Col. 2, lines 22-42).

Further, whereas Kamins teaches photosensing elements like photodiodes and associated integrated circuit structures (Col. 2, lines 56-59), Kaminis does not teach that the semiconductor device is a "CMOS" semiconductor device and with the active region including "a source and a drain". Bamji teaches that integrated circuit structures with photo detectors such as photodiodes may be arrays of CMOS devices (page 1, para 0004) wherein active regions may include a source and a drain (page 9, para 0098, 1st sentence). It would have been obvious to one of ordinary skills in the art at the time of the invention to modify Kamins so that the semiconductor device is a CMOS semiconductor device and with the active region includes a source and a drain. The ordinary artisan would have been motivated to modify Kamins for at least the purpose of using CMOS technology that is suitable for field effect devices with source and drain regions, as CMOS technology enables integration of images sensors on a single integrated circuit and reduction in power consumption (see Bamji, page 1, para 0002).

Claim 18 is similar to claim 10 (and hence the same rejection applies) except for the direction of drawing minority carriers. However, Kamins also teaches the direction of drawing minority carriers as in claim 18; i.e. drawing minority carriers (Col. 2, lines 15-16) may also be from said substrate to said surface layer (Col. 1, lines 38-46 and Col. 3, lines 6-18).

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Regarding claims 11 and 19, Kamins teaches that said drift layer (21) is a deeply implanted layer (see Figures 2-3; also see Col. 2, lines 36-42).

6. Claims 12 and 20 are rejected under 35 U.S.C. 103(a) as being unpatentable over Kamins, Jastrzebski and Bamji as applied to claims 10 and 18 above above, and further in view of Baliga (US 2002/0056883) of prior record, hereinafter Baliga.

Regarding claims 12 and 20, Kamins (refer to Figures 2-3) teaches substantially the claimed structure but does not teach that the drift layer is an "epitaxial" layer. Baliga (US 2002/0056883) teaches that it is known in the art that a drift layer with graded dopant concentration may be an epitaxial layer (page 2, para 0008, 2^{nd} and 3rd sentences and page 9, para 0063, especially $7^{th} - 9^{th}$ sentences). It would have been obvious to one of ordinary skills in the art at the time of the invention to modify Kamins so that the drift layer is an epitaxial layer. The ordinary artisan would have been motivated to modify Kamins for at least the purpose of using a layer that has a uniform crystal structure which makes electrical properties more predictable and can also act as a base for further epitaxial layers in which devices may be formed.

7. Claims 13-16 and 21-24 are rejected under 35 U.S.C. 103(a) as being unpatentable over Kamins, Jastrzebski and Bamji as applied to claims 10 and 18 above

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above, and further in view of Fujimoto (2002/0102783) of prior record, hereinafter Fujimoto; and Ishaque (US 5,517,052) of prior record, hereinafter Ishaque.

Regarding claims 13-16 and 21-24, Kamins (refer to Figure 3) teaches substantially the claimed structure but does not specifically state if the gradient is "linear", "guasi-linear", "exponential"; or "complimentary error function". Fujimoto teaches that an impurity region having a concentration gradient may have a profile that is linear, exponential, "or a combination thereof (page 3, para 0038). Further, Ishaque teaches that doping gradient is typically complementary error function or Gaussian if a deep diffusion process is used (Col. 3, line 49 to Col. 4, line 14). Given that Kamins teaches that a desired electric field is formed as a result of the gradient in doping (thus suggesting the gradient affects profile of the field) and various profiles of concentration gradient are known (as explained above in view of Fujimoto and Ishague), it would have been obvious to one of ordinary skills in the art at the time of the invention to modify Kamins so that the gradient is linear, exponential; or alternatively other profiles such as "quasilinear" or "complimentary error function", which are essentially combinations of linear and exponential profiles. The ordinary artisan would have been motivated to modify Kamins for at least the purpose of creating a specific profile of the electric field that is suitable for directing the minority carriers in a specific direction.

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Response to Arguments

8. Applicant's arguments with respect to claims 10 and 18 (see pages 6-8 of applicant's response of 10/12/2011) have been considered but are moot in view of the new ground(s) of rejection. However, applicant's response related to advisory action (on page 7 of applicant's response) is still relevant. This has been addressed in the 35 USC 112, 1st paragraph rejection above.

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to AJAY K. ARORA whose telephone number is (571)272-8347. The examiner can normally be reached on Mon through Fri, 8:30am to 5:00pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Thao X. Le can be reached on (571) 272-1708. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information

system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

/AJAY K. ARORA/ Primary Examiner, Art Unit 2892

Examiner Art Unit Page 1 of 1	Notice of References Cited	Application/Control No.Applicant(s)/Patent Under Reexamination11/622,496RAO, G.R. MOHAN		
	Notice of herefences oned	Examiner AJAY K. ARORA	Art Unit 2892	Page 1 of 1

U.S. PATENT DOCUMENTS

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	А	US-4,481,522	11-1984	Jastrzebski et al.	257/229
	В	US-			
	С	US-			
	D	US-			
	ш	US-			
	F	US-			
	G	US-			
	Т	US-			
	-	US-			
	J	US-			
	К	US-			
	L	US-			
	М	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	Ν					
	0					
	Р					
	Q					
	R					
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NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).) Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.

	Application/Control No.	Applicant(s)/Patent Under Reexamination
Search Notes	11622496	RAO, G.R. MOHAN
	Examiner	Art Unit
	AJAY K ARORA	2892

	SEARCHED		
Class	Subclass	Date	Examiner
257	655	12/16/2011	AKA

SEARCH NOTES		
Search Notes	Date	Examiner
Revised EAST search history report	12/16/2011	AKA
	12/10/2011	7404

	INTERFERENCE SEARCH	1	
Class	Subclass	Date	Examiner

/A. K. A./ Primary Examiner.Art Unit 2892

11622496 - GAU: 2892

Doc code: IDS

Doc description: Information Disclosure Statement (IDS) Filed

PTO/SB/08a (01-10) Approved for use through 07/31/2012. OMB 0651-0031 U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Not for submission under 37 CFR 1.99)	Application Number		11622496	
	Filing Date		2007-01-12	
	First Named Inventor G.R.		, Mohan Rao	
	Art Unit		2892	
	Examiner Name	Examiner Name Ajay Arora		
	Attorney Docket Num	ber	0299-0001.01	

	U.S.PATENTS							
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11622496 - GAU: 2892

INFORMATION DISCLOSURE	Application Number		11622496	
	Filing Date		2007-01-12	
	First Named Inventor G.R. M		. Mohan Rao	
STATEMENT BY APPLICANT (Not for submission under 37 CFR 1.99)	Art Unit		2892	
	Examiner Name Ajay		y Arora	
	Attorney Docket Number		0299-0001.01	

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	Application Number		11622496	
INFORMATION DISCLOSURE	Filing Date		2007-01-12	
	First Named Inventor G.R. N		Mohan Rao	
STATEMENT BY APPLICANT (Not for submission under 37 CFR 1.99)	Art Unit		2892	
	Examiner Name Ajay A		Arora	
	Attorney Docket Number		0299-0001.01	

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	That no item of information contained in the information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application, and, to the knowledge of the person signing the certification after making reasonable inquiry, no item of information contained in the information disclosure statement was known to any individual designated in 37 CFR 1.56(c) more than three months prior to the filing of the information disclosure statement. See 37 CFR 1.97(e)(2).							
	See attached ce	rtification statement.						
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SIGNATURE A signature of the applicant or representative is required in accordance with CFR 1.33, 10.18. Please see CFR 1.4(d) for the form of the signature.								
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EAST Search History

EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	456	(257/655).CCLS.	USPAT; USOCR	OR	OFF	2011/12/16 09:45
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Under the Paperwork Reduction Act of 1995, no persons are requ	U.S. Patent a ired to respond to a collection of	nd Trader	mark Office; U.S. DEPARTMENT OF COMMERCE tion unless it contains a valid OMB control number.				
Request	Application Number		11/622496				
for Continued Examination (DOE)	Filing Date		01/12/2007				
Continued Examination (RCE) Transmittal	First Named Invento	or	G.R. Mohan Rao				
Address to:	Art Unit		2892				
Mail Stop RCE Commissioner for Patents	Examiner Name		Ajay Arora				
P.O. Box 1450 Alexandria, VA 22313-1450	Attorney Docket Nur	mber	0299-0001.01				
This is a Request for Continued Examination (RCE) under 37 CFR 1 .114 of the above-identified application. Request for Continued Examination (RCE) practice under 37 CFR 1.114 does not apply to any utility or plant application filed prior to June 8, 1995, or to any design application. See Instruction Sheet for RCEs (not to be submitted to the USPTO) on page 2.							
 Submission required under 37 CFR 1.114 Not amendments enclosed with the RCE will be entered in the applicant does not wish to have any previously filed uner amendment(s). a. Previously submitted. If a final Office action is 	ne order in which they were ntered amendment(s) enter outstanding, any amendme	filed unl ed, appli	ess applicant instructs otherwise. If cant must request non-entry of such				
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I hereby certify that this correspondence is being deposited with the United Stat addressed to: Mail Stop RCE/Commissioner for Patents, P. O Box1450, Alex Office on the date shown below.							
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Name (Print/Type) Francisca M. A. Hubbard		Date	October 12, 2011				

This collection of information is required by 37 CFR 1.114. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.11 and 1.14. This collection is estimated to take 12 minutes to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Mail Stop RCE, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

If you need assistance in completing the form, call 1-800-PTO-9199 and select option 2.



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application No.	:	11/622,496
Confirmation No.	:	3086
Inventor	:	G. R. Mohan Rao
Filed	:	January 12, 2007
TC/A.U.	:	2892
Examiner	:	Ajay Arora
Title	:	SEMICONDUCTOR DEVICES WITH GRADED
		DOPANT REGIONS
Docket No.	:	0299-0001.01

REQUEST FOR CONTINUED EXAMINATION

AMENDMENT D

Sir:

In response to the Advisory Action of June 27, 2011, Applicant submits the following amendment:

Claims. Amendments to the claims begin on page 2 of this amendment.

Remarks. Remarks begin on page 6 of this amendment.

Appl. No. 11/622,496 Response to Advisory Action of June 27, 2011

LISTING OF CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

<u>Claims:</u>

1. (Canceled)

2. (Canceled)

- 3. (Canceled)
- 4. (Canceled)
- 5. (Canceled)
- 6. (Canceled)
- 7. (Canceled)
- 8. (Canceled)
- 9. (Canceled)

10. (currently amended) A CMOS Semiconductor device comprising:

a surface layer;

a substrate;

an active region including a source and a drain, disposed on one surface of said surface

layer; and

a <u>single</u> drift layer disposed between the other surface of said surface layer and said substrate, said drift layer having a graded concentration of dopants extending between said surface layer and said substrate to create a <u>unidirectional</u> drift field drawing <u>all</u> minority carriers from said surface layer to said substrate.

11. (Previously presented) The CMOS Semiconductor device of claim 10 wherein said drift layer is a deeply-implanted layer.

12. (Previously presented) The CMOS Semiconductor device of claim 10 wherein said drift layer is an epitaxial layer.

13. (Previously presented) The CMOS Semiconductor device of claim 10 wherein said graded concentration follows a linear gradient.

14. (Previously presented) The CMOS Semiconductor device of claim 10 wherein said graded concentration follows a quasi-linear gradient.

15. (Previously presented) The CMOS Semiconductor device of claim 10 wherein said graded concentration follows an exponential gradient.

16. (Previously presented) The CMOS Semiconductor device of claim 10 wherein said graded concentration follows a complimentary error function gradient.

17. (Canceled)

18. (Currently amended) A CMOS Semiconductor device comprising:

a surface layer;

a substrate;

an active region including a source and a drain, disposed on one surface of said surface layer; and

a <u>single</u> drift layer disposed between the other surface of said surface layer and said substrate, said drift layer having a graded concentration of dopants extending between said surface layer and said substrate to create a <u>unidirectional</u> drift field drawing <u>all</u> minority carriers from said substrate to said <u>surface</u> layer.

19. (Previously presented) The CMOS Semiconductor device of claim 18 wherein said drift layer is a deeply-implanted layer.

20. (Previously presented) The CMOS Semiconductor device of claim 18 wherein said drift layer is an epitaxial layer.

Page 4 of 9

21. (Previously presented) The CMOS Semiconductor device of claim 18 wherein said graded concentration follows a linear gradient.

22. (Previously presented) The CMOS Semiconductor device of claim 18 wherein said graded concentration follows a quasi-linear gradient.

23. (Previously presented) The CMOS Semiconductor device of claim 18 wherein said graded concentration follows an exponential gradient.

24. (Previously presented) The CMOS Semiconductor device of claim 18 wherein said graded concentration follows a complimentary error function gradient.

25. (Canceled)

Page 5 of 9

REMARKS

Applicant has carefully reviewed the Advisory Action of June 27, 2011. In addition, Applicant incorporates herein by reference his June 13, 2011 Response to the Final Office Action. In further response to the Advisory Action and the particular issues raised therein, Applicant states as follows:

Applicant has previously amended claims 10 and 18 to better define the invention. Claim 10 stands rejected as obvious in view of the combined teachings of Kamins–Pat. No. 4,160,985 and Bamji–Pub. No. 2002/0084430. Kamins discloses a photosensing device in which selective doping of a semiconductor substrate of the device produces electric fields in the substrate which accelerate photogenerated charge carriers toward or away from the surface of the device . Abstract, Fig. 3. In particular, Kamins' disclosure further states that "[t]he carriers therefore tend to be accelerated either toward the nearest photosensor or away from the surface. More specifically, carriers created below the maximum dopant concentration are accelerated into the substrate [...], while carriers created above the maximum dopant concentration are accelerated into the substrate <u>and</u> the surface layer, depending on the location of the carriers relative to the maximum dopant concentration within the "buried layer" 21) and Fig. 3 (showing two electrical fields with opposing directions, away from the area of maximum dopant concentration towards both the surface layer and the substrate, respectively).

The amendments to claim 10 further clarify that Applicant's claimed "drift layer" is a <u>single unidirectional</u> layer with a graded dopant concentration which draws <u>all</u> minority carriers away from the surface layer to the substrate – none of the carriers is drawn from the substrate to the surface layer. The amendments to claim 18 further clarify that Applicant's claimed "drift

Page 6 of 9

layer" is a <u>single unidirectional</u> layer with a graded dopant concentration that, which draws <u>all</u> minority carriers away from the substrate to the surface layer – none of the carriers is drawn from the surface layer to the substrate.

The Advisory Action contends that Applicant "has not recited the specific structure that enables the drift field to have the properties of being 'unidirectional' or possessing the ability of drawing 'all minority carriers'." In response, Applicant respectfully states that a unidirectional drift field and its structure is well known in the prior art. The corresponding structure is illustrated in Applicant's Fig. 1 (Prior Art), which shows two types of popular bipolar junction transistors – a uniform (dopant) base "A" and a graded (dopant) base "B," commonly referred to as a "drift transistor." The drift transistor comprising an aiding drift field was invented by Herbert Kroemer in 1954. *See* "Herb's Bipolar Transistors," Berinder Brar *et al.*, *IEEE Transactions on Electron Devices*, Vol. 48, No. 11, Nov. 2001; *see also*, "Influence of Mobility and Lifetime Variations on Drift-Field Effects in Silicon-Junction Devices," W. Murray Bullis *et al.*, *IEEE Transactions on Electron Devices*, Vol. Ed. 14, No. 2, Feb. 1967.

As described in paragraph [0011] of Applicant's specification, the aiding drift field is graded whereby "the gradient can be linear, quasi liner, exponential or complimentary error function." The specification further states that "the relative slope of the donor concentration throughout the base creates a suitable aiding drift electric field, to help the holes (p-n-p transistor) transverse from emitter to collector." In other words, the drift field for the holes (minority carriers) is unidirectional, i.e., from the emitter (surface layer) to the collector (substrate) because of the particular slope of the donor concentration. This unidirectional drift (electric) field <u>necessarily</u> affects all the present minority carriers in the same way – moving all minority carriers in the same direction because of the unidirectional drift due to the existence of

the electric field. *See* "Physics and Technology of Semiconductor Devices," A.S. Grove, pp. 224-225, John Wiley and Sons, Inc., New York, 1st Edition 1967. Depending on the particular slope of the graded concentration of dopant, all minority carriers are either swept "down" (from the surface layer to the substrate) or "up" (from the substrate to the surface layer). *See* Applicant's Figs. 5(b) and 5(c).

Bamji discloses a method to measure distance or brightness using a CMOS sensor. The most recent office action cites Bamji against claim 10 for the proposition that integrated circuit structures with photo detectors may be arrays of CMOS devices. However, Applicant respectfully submits that this disclosure is moot in view of the above recited shortcomings in the disclosure of Kamins and in view of Applicant's amendments to claims 10 and 18.

Claims 11-16 depend on claim 10 and for at least the reason that claim 10 is patentable over the cited prior art, claims 11-16 are patentable as well. Claims 19-24 depend on claim 18 and for at least the reason that claim 18 is patentable over the cited prior art, claims 19-24 are patentable as well.

Appl. No. 11/622,496 Response to Advisory Action of June 27, 2011

CONCLUSION

Applicant respectfully submits that in view of the amendments made to the claims and the discussion set forth herein, this application is now in condition for allowance. However, should Examiner be of the opinion that further amendment or response is required; Applicant encourages Examiner to contact the undersigned attorney at the telephone number set forth below. The Commissioner is authorized to charge any additional fees or deficiencies or credit any overpayments to Eugene M. Cummings, P.C., Deposit Account No. **50-4199**, with reference to attorney docket number (0299-0001.01).

Respectfully submitted,

Date: October 12, 2011

Bv:

David M. Mundt, Reg. No. 41,207

Law Offices of Eugene M. Cummings, P.C. 1 N. Wacker Suite 4130 Chicago, Illinois 60606

Telephone: (312) 984-0144 Facsimile: (312) 984-0146

Page 9 of 9

Doc code: IDS

Doc description: Information Disclosure Statement (IDS) Filed

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STATEMENT BY APPLICANT (Not for submission under 37 CFR 1.99)	Art Unit		2892	
	Examiner Name Ajay		jay Arora	
	Attorney Docket Numb	ber	0299-0001.01	

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	Application Number		11622496	
	Filing Date		2007-01-12	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Not for submission under 37 CFR 1.99)	First Named Inventor G.R		B.R. Mohan Rao	
	Art Unit		2892	
	Examiner Name Aja		Arora	
	Attorney Docket Numb	er	0299-0001.01	

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	A. S. GROVE, Physics and Technology of Semiconductor Devices, John Wiley Sons, Inc., New York, November 1967								
	W. MURRAY BULLIS and W. R. RUNYAN, Influence of Mobility and Lifetime Variations on Drift-Field Effects in Silicon- Junction Devices, IEEE Transactions on Electron Devices, Vol. Ed-14, No. 2, February 1967								
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	Filing Date		2007-01-12	
	First Named Inventor G.R. I		. Mohan Rao	
	Art Unit		2892	
	Examiner Name Ajay		y Arora	
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PTO/SB/22 (09-11) Approved for use through 07/31/2012. OMB 0651-0031 U.S. Patent and Trademark Office; U.S. DEPARMENT OF COMMERCE Under the paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number.

PETITION FOR EXTENSION OF TIME UND	Docket Number (Optional) 0299-0001.01							
Application Number 11/622496	Filed 01/12/2007							
For SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS								
Art Unit 2892 Examiner Ajay Arora								
This is a request under the provisions of 37 CFR 1. application.	136(a) to extend the perio	od for filing a reply in th	e above identified					
The requested extension and fee are as follows (ch	eck time period desired a	nd enter the appropria	te fee below):					
	Fee	<u>Small Entity Fee</u>						
One month (37 CFR 1.17(a)(1))	\$150	\$75	\$					
Two months (37 CFR 1.17(a)(2))	\$560	\$280	\$					
Three months (37 CFR 1.17(a)(3))	\$1270	\$635	\$ <u>635.00</u>					
Four months (37 CFR 1.17(a)(4))	\$1980	\$990	\$					
Five months (37 CFR 1.17(a)(5))	\$2690	\$1345	\$					
Applicant claims small entity status. See 37 CF	R 1.27.							
A check in the amount of the fee is enclose	ed.							
Payment by credit card. Form PTO-2038 is	s attached.							
The Director has already been authorized	to charge fees in this a	pplication to a Depo	sit Account.					
The Director is hereby authorized to charg Deposit Account Number 50-4199	e any fees which may	be required, or credi	t any overpayment, to					
WARNING: Information on this form may become Provide credit card information and authorization	public. Credit card inform on PTO-2038.	ation should not be inc	luded on this form.					
I am the applicant/inventor.								
assignee of record of the en Statement under 37 CFR								
✓ attorney or agent of record.	Registration Number 4	1,207	- 					
attorney or agent under 37 (Registration number if acting un			·					
/David M. Mundt/		October 12, 2	011					
Signature			Date					
David M. Mundt		312-984-0144	L					
Typed or printed name		,	ione Number					
NOTE: Signatures of all the inventors or assignees of record of the signature is required, see below.		ative(s) are required. Submit	multiple forms if more than one					
Total of forms	are submitted.	rotoin a bonofit butter subli-						

This collection of information is required by 37 CFR 1.136(a). The mormation is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.11 and 1.14. This collection is estimated to take 6 minutes to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

If you need assistance in completing the form, call 1-800-PTO-9199 and select option 2.

Electronic Patent Application Fee Transmittal						
Application Number:	116	11622496				
Filing Date:	12-	12-Jan-2007				
Title of Invention:	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS				iions	
First Named Inventor/Applicant Name:	G.F	G.R. Mohan Rao				
Filer:	David Michael Mundt/Francisca Hubbard					
Attorney Docket Number:	0299-0001.01					
Filed as Small Entity						
Utility under 35 USC 111(a) Filing Fees						
Description		Fee Code	Quantity	Amount	Sub-Total in USD(\$)	
Basic Filing:						
Pages:						
Claims:						
Miscellaneous-Filing:						
Petition:						
Patent-Appeals-and-Interference:						
Post-Allowance-and-Post-Issuance:						
Extension-of-Time:						
Extension - 3 months with \$0 paid		2253 141	1	635	635	

Description	Fee Code	Quantity	Amount	Sub-Total in USD(\$)
Miscellaneous:				
Request for continued examination	2801	1	465	465
Submission- Information Disclosure Stmt	1806	1	180	180
	Tot	1280		

Electronic A	Electronic Acknowledgement Receipt						
EFS ID:	11169330						
Application Number:	11622496						
International Application Number:							
Confirmation Number:	3086						
Title of Invention:	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS						
First Named Inventor/Applicant Name:	G.R. Mohan Rao						
Customer Number:	70653						
Filer:	David Michael Mundt/Francisca Hubbard						
Filer Authorized By:	David Michael Mundt						
Attorney Docket Number:	0299-0001.01						
Receipt Date:	12-OCT-2011						
Filing Date:	12-JAN-2007						
Time Stamp:	13:34:33						
Application Type:	Utility under 35 USC 111(a)						

Payment information:

Submitted with Payment	yes					
Payment Type	Deposit Account					
Payment was successfully received in RAM	\$1280					
RAM confirmation Number	10379					
Deposit Account	504199					
Authorized User						
The Director of the USPTO is hereby authorized to ch	The Director of the USPTO is hereby authorized to charge indicated fees and credit any overpayment as follows:					
Charge any Additional Fees required under 37 C.F.R. Section 1.21 (Miscellaneous fees and charges)						

Document Number	Document Description	File Name	File Size(Bytes)/ Message Digest	Multi Part /.zip	Pages (if appl.)
	Request for Continued Examination		161862		
1	(RCE)	RCE.pdf	ef00f0e2a65ffc745ea1f300b71bef8424b83 79c	no	1
Warnings:			1		
This is not a USI	PTO supplied RCE SB30 form.				
Information:					
2	Amendment After Final	Amondmont.pdf	558486	20	0
2	Amendment After Final	Amendment.pdf	9fd2d566e0f3b9a4ed0efc0565dbc3457936 332b	no	9
Warnings:			- 1		
Information:					
2	Information Disclosure Statement (IDS)		327332		2
3	Form (SB08)	IDS.pdf	6230733906e2d79abc352cdb16e8cab3b42 02c81	no	3
Warnings:					
Information:					
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		NDI 1 m df	636718	20	2
4 Non Patent Literature	NPL1.pdf	700dcded84d49b37e100633d61b66eda32 597b75	no	3	
Warnings:					
Information:					
5	Non Patent Literature	NPL2.pdf	1692888	no	7
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Information:					
6	Non Patent Literature	NPL3.pdf	1539230	no	1
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Warnings:			·		
Information:	•				
7	Extension of Time	ExtOfTime.pdf	193401	no	1
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Warnings:					
Information:					
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8	Fee Worksheet (SB06)	fee-info.pdf	0810aec2afa88c6b23b93f1acdf5f74aa9980 8c5	no	
Warnings:			0.00		
Information:

Total Files Size (in bytes):

This Acknowledgement Receipt evidences receipt on the noted date by the USPTO of the indicated documents, characterized by the applicant, and including page counts, where applicable. It serves as evidence of receipt similar to a Post Card, as described in MPEP 503.

New Applications Under 35 U.S.C. 111

If a new application is being filed and the application includes the necessary components for a filing date (see 37 CFR 1.53(b)-(d) and MPEP 506), a Filing Receipt (37 CFR 1.54) will be issued in due course and the date shown on this Acknowledgement Receipt will establish the filing date of the application.

National Stage of an International Application under 35 U.S.C. 371

If a timely submission to enter the national stage of an international application is compliant with the conditions of 35 U.S.C. 371 and other applicable requirements a Form PCT/DO/EO/903 indicating acceptance of the application as a national stage submission under 35 U.S.C. 371 will be issued in addition to the Filing Receipt, in due course.

New International Application Filed with the USPTO as a Receiving Office

If a new international application is being filed and the international application includes the necessary components for an international filing date (see PCT Article 11 and MPEP 1810), a Notification of the International Application Number and of the International Filing Date (Form PCT/RO/105) will be issued in due course, subject to prescriptions concerning national security, and the date shown on this Acknowledgement Receipt will establish the international filing date of the application.

PTO/SB/06 (07-06)

Approved for use through 1/31/2007. OMB 0651-0032

P	Under the Par		E DETI	RMINATION		nd to	a collection of Application or I	of information unle Docket Number 2,496	Filing Date 01/12/2007		To be Mailed	
	AF	PLICATION A	AS FILE (Column 1		Column 2)		SMALL	entity 🛛	OR		HER THAN	
	FOR	N	JMBER FIL	.ED NUN	MBER EXTRA		RATE (\$)	FEE (\$)		RATE (\$)	FEE (\$)	
	BASIC FEE (37 CFR 1.16(a), (b), (or (c))	N/A		N/A		N/A			N/A		
	SEARCH FEE (37 CFR 1.16(k), (i), c	or (m))	N/A		N/A		N/A			N/A		
	EXAMINATION FE (37 CFR 1.16(o), (p), (N/A		N/A		N/A			N/A		
(37	AL CLAIMS CFR 1.16(i))		min	us 20 = *			X \$ =		OR	X \$ =		
	EPENDENT CLAIM CFR 1.16(h))	S	m	nus 3 = *			X \$ =			X\$ =		
	APPLICATION SIZE 37 CFR 1.16(s))	FEE shee is \$2 addit 35 U	ts of pape 50 (\$125 ional 50 s .S.C. 41(a	tion and drawing er, the applicatio for small entity) sheets or fractior a)(1)(G) and 37 (n size fee due for each n thereof. See							
× 16 t	MULTIPLE DEPEN		,	477			TOTAL			TOTAL		
							TOTAL		1	TOTAL		
	APPI	(Column 1)	AMENL	ED – PART II (Column 2)	(Column 3)		SMAL	L ENTITY			ER THAN ALL ENTITY	
AMENDMENT	10/12/2011	CLAIMS REMAINING AFTER AMENDMENT		HIGHEST NUMBER PREVIOUSLY PAID FOR	PRESENT EXTRA		RATE (\$)	ADDITIONAL FEE (\$)		RATE (\$)	ADDITIONAL FEE (\$)	
OME	Total (37 CFR 1.16(i))	∗ 1 4	Minus	** 20	= 0		X \$30 =	0	OR	X \$ =		
IN I	Independent (37 CFR 1.16(h))	* 2	Minus	***8	= 0		X \$125 =	0	OR	X \$ =		
AMI	Application Si	ze Fee (37 CFR 1	.16(s))									
	FIRST PRESEN	ITATION OF MULTIP	LE DEPEN	DENT CLAIM (37 CFF	R 1.16(j))				OR			
						-	TOTAL ADD'L FEE	0	OR	TOTAL ADD'L FEE		
		(Column 1)		(Column 2)	(Column 3)	_						
		CLAIMS REMAINING AFTER AMENDMENT		HIGHEST NUMBER PREVIOUSLY PAID FOR	PRESENT EXTRA		RATE (\$)	ADDITIONAL FEE (\$)		RATE (\$)	ADDITIONAL FEE (\$)	
EN	Total (37 CFR 1.16(i))	*	Minus	**	=		X \$ =		OR	X\$ =		
MO	Independent (37 CFR 1.16(h))	*	Minus	***	=		X \$ =		OR	X\$ =		
IEN	Total (37 CFR * Minus *** = Independent (37 CFR 1.16(h)) * Minus *** = Application Size Fee (37 CFR 1.16(s)) = = = FIRST PRESENTATION OF MULTIPLE DEPENDENT CLAIM (37 CFR 1.16(ii)) = =											
AN		ITATION OF MULTIP	LE DEPEN	DENT CLAIM (37 CFF	R 1.16(j))				OR			
** lf *** l	he entry in column the "Highest Numbe f the "Highest Numb	er Previously Paid er Previously Paid	For" IN TH	IIS SPACE is less HIS SPACE is less	than 20, enter "20" than 3, enter "3".		/LINDA	nstrument Ex 18 WISE/		TOTAL ADD'L FEE er:		
	"Highest Number P	reviously Paid For			÷							

This collection of information is required by 37 CFR 1.16. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 12 minutes to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450. *Human et al.* 1900 PTO 0109 and calculatentia pain 2.

If you need assistance in completing the form, call 1-800-PTO-9199 and select option 2.

	ed States Paten	T AND TRADEMARK OFFICE	UNITED STATES DEPAR United States Patent and Address: COMMISSIONER F P.O. Box 1450 Alexandria, Virginia 22: www.uspto.gov	FOR PATENTS		
APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.		
11/622,496	01/12/2007	G.R. Mohan Rao	0299-0001.01	3086		
LAW OFFICE	7590 06/27/201. S OF EUGENE M. CUI WACKER DRIVE		EXAMINER ARORA, AJAY			
SUITE 4130 CHICAGO, IL	60606		ART UNIT	PAPER NUMBER		
cilicitoo, ili	00000		2892			
			MAIL DATE	DELIVERY MODE		
			06/27/2011	PAPER		

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

Γ		
	Application No.	Applicant(s)
Advisory Action	11/622,496	RAO, G.R. MOHAN
Before the Filing of an Appeal Brief	Examiner	Art Unit
	AJAY K. ARORA	2892
The MAILING DATE of this communication appe	ears on the cover sheet with the e	correspondence address
THE REPLY FILED <u>13 June 2011</u> FAILS TO PLACE THIS APP		
 The reply was filed after a final rejection, but prior to or on application, applicant must timely file one of the following application in condition for allowance; (2) a Notice of App for Continued Examination (RCE) in compliance with 37 (periods: The period for reply expiresmonths from the mailing 	replies: (1) an amendment, affidavi eal (with appeal fee) in compliance CFR 1.114. The reply must be filed	t, or other evidence, which places the with 37 CFR 41.31; or (3) a Request
 b) X The period for reply expires on: (1) the mailing date of this A 		in the final rejection, whichever is later. In
no event, however, will the statutory period for reply expire I	ater than SIX MONTHS from the mailin	g date of the final rejection.
Examiner Note: If box 1 is checked, check either box (a) or MONTHS OF THE FINAL REJECTION. See MPEP 706.07(FIRST REPLY WAS FILED WITHIN TWO
Extensions of time may be obtained under 37 CFR 1.136(a). The date have been filed is the date for purposes of determining the period of ex under 37 CFR 1.17(a) is calculated from: (1) the expiration date of the set forth in (b) above, if checked. Any reply received by the Office later may reduce any earned patent term adjustment. See 37 CFR 1.704(b) NOTICE OF APPEAL	on which the petition under 37 CFR 1.1 tension and the corresponding amount shortened statutory period for reply origi than three months after the mailing dat	of the fee. The appropriate extension fee nally set in the final Office action; or (2) as e of the final rejection, even if timely filed,
2. The Notice of Appeal was filed on A brief in comp filing the Notice of Appeal (37 CFR 41.37(a)), or any exte Notice of Appeal has been filed, any reply must be filed w	nsion thereof (37 CFR 41.37(e)), to	avoid dismissal of the appeal. Since a
AMENDMENTS		
 3. The proposed amendment(s) filed after a final rejection, (a) They raise new issues that would require further co (b) They raise the issue of new matter (see NOTE belo (c) They are not deemed to place the application in belo appeal; and/or (d) They present additional claims without canceling a second s	nsideration and/or search (see NO w); ter form for appeal by materially re	ΓE below); ducing or simplifying the issues for
NOTE: <u>See Continuation Sheet</u> . (See 37 CFR 1.1		
4. The amendments are not in compliance with 37 CFR 1.1	21. See attached Notice of Non-Co	mpliant Amendment (PTOL-324).
5. Applicant's reply has overcome the following rejection(s)		
6. Newly proposed or amended claim(s) would be al non-allowable claim(s).		
 7. For purposes of appeal, the proposed amendment(s): a) how the new or amended claims would be rejected is provided to the claim(s) is (or will be) as follows: Claim(s) allowed: Claim(s) objected to: Claim(s) rejected: <u>10-16 and 18-24</u>. Claim(s) withdrawn from consideration: 		i be entered and an explanation of
AFFIDAVIT OR OTHER EVIDENCE		
 The affidavit or other evidence filed after a final action, but because applicant failed to provide a showing of good and was not earlier presented. See 37 CFR 1.116(e). 		
9. The affidavit or other evidence filed after the date of filing entered because the affidavit or other evidence failed to o showing a good and sufficient reasons why it is necessary	vercome <u>all</u> rejections under appear and was not earlier presented. So	al and/or appellant fails to provide a se 37 CFR 41.33(d)(1).
10. The affidavit or other evidence is entered. An explanatio	n of the status of the claims after e	ntry is below or attached.
11. The request for reconsideration has been considered bu	t does NOT place the application ir	condition for allowance because:
12. INote the attached Information <i>Disclosure Statement</i> (s).	(PTO/SB/08) Paper No(s)	
	/AJAY K. ARORA/	
	Primary Examiner, Art L	nit 2892

Continuation of 3. NOTE: The amendments to base claim 10 to include the limitations of a "single" dirft layer (see line 6 of claim 10) and a "unidirectional" drift field drawing "all" minority carriers (see 2nd last line of claim 10) raise new issues that would require further consideration and/or search. It is noted that applicant has not recited the specific structure that enables the drift field to have the properties of being "unidirectional" or possessing the ability of drawing "all minority carriers".

Receipt date: 06/13/2011

DO NOT ENTER: /AA/

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application No.	: 11/622,496
Confirmation No.	: 3086
Inventor	: G. R. Mohan Rao
Filed	: January 12, 2007
TC/A.U.	: 2892
Examiner	: Ajay Arora
Title	: SEMICONDUCTOR DEVICES WITH GRADED
	DOPANT REGIONS
Docket No.	: 0299-0001.01

RESPONSE TO FINAL OFFICE ACTION

AMENDMENT C

Sir:

In response to the Final Office Action of April 13, 2011, Applicant submits the following amendment:

Claims. Amendments to the claims begin on page 2 of this amendment.

Remarks. Remarks begin on page 6 of this amendment.

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application No.	:	11/622,496
Confirmation No.	:	3086
Inventor	:	G. R. Mohan Rao
Filed	:	January 12, 2007
TC/A.U.	:	2892
Examiner	:	Ajay Arora
Title	:	SEMICONDUCTOR DEVICES WITH GRADED
		DOPANT REGIONS
Docket No.	:	0299-0001.01

RESPONSE TO FINAL OFFICE ACTION

AMENDMENT C

Sir:

In response to the Final Office Action of April 13, 2011, Applicant submits the following amendment:

Claims. Amendments to the claims begin on page 2 of this amendment.

Remarks. Remarks begin on page 6 of this amendment.

Appl. No. 11/622,496 Response to Final Office Action of April 13, 2011

LISTING OF CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

Claims:

1. (Canceled)

2. (Canceled)

3. (Canceled)

4. (Canceled)

5. (Canceled)

6. (Canceled)

7. (Canceled)

8. (Canceled)

9. (Canceled)

10. (currently amended) A CMOS Semiconductor device comprising:

a surface layer;

a substrate;

an active region including a source and a drain, disposed on one surface of said surface layer; and

a <u>single</u> drift layer disposed between the other surface of said surface layer and said substrate, said drift layer having a graded concentration of dopants extending between said surface layer and said substrate to create a <u>unidirectional</u> drift field drawing <u>all</u> minority carriers from said surface layer to said substrate.

11. (Previously presented) The CMOS Semiconductor device of claim 10 wherein said drift layer is a deeply-implanted layer.

12. (Previously presented) The CMOS Semiconductor device of claim 10 wherein said drift layer is an epitaxial layer.

13. (Previously presented) The CMOS Semiconductor device of claim 10 wherein said graded concentration follows a linear gradient.

14. (Previously presented) The CMOS Semiconductor device of claim 10 wherein said graded concentration follows a quasi-linear gradient.

15. (Previously presented) The CMOS Semiconductor device of claim 10 wherein said graded

Page 3 of 8

concentration follows an exponential gradient.

16. (Previously presented) The CMOS Semiconductor device of claim 10 wherein said graded concentration follows a complimentary error function gradient.

17. (Canceled)

18. (Currently amended) A CMOS Semiconductor device comprising:

a surface layer;

a substrate;

an active region including a source and a drain, disposed on one surface of said surface layer; and

a <u>single</u> drift layer disposed between the other surface of said surface layer and said substrate, said drift layer having a graded concentration of dopants extending between said surface layer and said substrate to create a <u>unidirectional</u> drift field drawing <u>all</u> minority carriers from said substrate to said <u>surface</u> layer.

19. (Previously presented) The CMOS Semiconductor device of claim 18 wherein said drift layer is a deeply-implanted layer.

20. (Previously presented) The CMOS Semiconductor device of claim 18 wherein said drift layer is an epitaxial layer.

Page 4 of 8

21. (Previously presented) The CMOS Semiconductor device of claim 18 wherein said graded concentration follows a linear gradient.

22. (Previously presented) The CMOS Semiconductor device of claim 18 wherein said graded concentration follows a quasi-linear gradient.

23. (Previously presented) The CMOS Semiconductor device of claim 18 wherein said graded concentration follows an exponential gradient.

24. (Previously presented) The CMOS Semiconductor device of claim 18 wherein said graded concentration follows a complimentary error function gradient.

25. (Canceled)

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REMARKS

Applicant has carefully reviewed the most recent communication from the Patent Office, as well as the cited art. In response, Applicant has amended claims 10 and 18 to better define the invention.

Claim 10 stands rejected as obvious in view of the combined teachings of Kamins–Pat. No. 4,160,985 and Bamji–Pub. No. 2002/0084430. Kamins discloses a photosensing device in which selective doping of a semiconductor substrate of the device produces electric fields in the substrate which accelerate photogenerated charge carriers toward or away from the surface of the device . Abstract, Fig. 3. In particular, Kamins' disclosure further states that "[t]he carriers therefore tend to be accelerated either toward the nearest photosensor or away from the surface. More specifically, carriers created below the maximum dopant concentration are accelerated into the substrate [...], while carriers created above the maximum dopant concentration are accelerated into the substrate [...]," Col. 3, Lines 6-13, Fig. 2 (showing minority carries relative to the maximum dopant concentration within the "buried layer" 21) and Fig. 3 (showing two electrical fields with opposing directions, away from the area of maximum dopant concentration towards both the surface layer and the substrate, respectively).

The amendments to claim 10 further clarify that Applicant's claimed "drift layer" is a single unidirectional layer with a graded dopant concentration which draws all minority carriers away from the surface layer to the substrate – none of the carriers is drawn from the substrate to the surface layer. The amendments to claim 18 further clarify that Applicant's claimed "drift layer" is a single unidirectional layer with a graded dopant concentration that, which draws all minority carriers away from the substrate to the surface layer – none of the carriers is drawn from the draws all

Page 6 of 8

from the surface layer to the substrate.

Bamji discloses a method to measure distance or brightness using a CMOS sensor. The most recent office action cites Bamji against claim 10 for the proposition that integrated circuit structures with photo detectors may be arrays of CMOS devices. However, Applicant respectfully submits that this disclosure is moot in view of the above recited shortcomings in the disclosure of Kamins and in view of Applicant's amendments to claims 10 and 18.

Claims 11-16 depend on claim 10 and for at least the reason that claim 10 is patentable over the cited prior art, claims 11-16 are patentable as well. Claims 19-24 depend on claim 18 and for at least the reason that claim 18 is patentable over the cited prior art, claims 19-24 are patentable as well.

Page 7 of 8

Appl. No. 11/622,496 Response to Final Office Action of April 13, 2011

CONCLUSION

Applicant respectfully submits that in view of the amendments made to the claims and the discussion set forth herein, this application is now in condition for allowance. However, should Examiner be of the opinion that further amendment or response is required, Applicant encourages Examiner to contact the undersigned attorney at the telephone number set forth below. Although no additional fees are believed to be due at this time, the Commissioner is authorized to charge any additional fees or deficiencies or credit any overpayments to Eugene M. Cummings, P.C., Deposit Account No. **50-4199**, with reference to attorney docket number (0299-0001.01).

Respectfully submitted,

Date: June 13, 2011

By:

David M. Mundt, Reg. No. 41,207

Law Offices of Eugene M. Cummings, P.C. 1 N. Wacker Suite 4130 Chicago, Illinois 60606

Telephone: (312) 984-0144 Facsimile: (312) 984-0146

Page 8 of 8

Electronic A	cknowledgement Receipt
EFS ID:	10285731
Application Number:	11622496
International Application Number:	
Confirmation Number:	3086
Title of Invention:	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS
First Named Inventor/Applicant Name:	G.R. Mohan Rao
Customer Number:	70653
Filer:	David Michael Mundt/Francisca Hubbard
Filer Authorized By:	David Michael Mundt
Attorney Docket Number:	0299-0001.01
Receipt Date:	13-JUN-2011
Filing Date:	12-JAN-2007
Time Stamp:	10:55:27
Application Type:	Utility under 35 USC 111(a)

Payment information:

Submitted with F	Payment	no								
File Listing:										
Document Number	Document Description	File Name	File Size(Bytes)/ Message Digest	Multi Part /.zip	Pages (if appl.)					
1	Amendment After Final	Response.pdf	437841 f8ef0cde04222718a5cb9a08af0722802f080 1c0	no	8					
Warnings:										
Information:										

This Acknowledgement Receipt evidences receipt on the noted date by the USPTO of the indicated documents, characterized by the applicant, and including page counts, where applicable. It serves as evidence of receipt similar to a Post Card, as described in MPEP 503.

New Applications Under 35 U.S.C. 111

If a new application is being filed and the application includes the necessary components for a filing date (see 37 CFR 1.53(b)-(d) and MPEP 506), a Filing Receipt (37 CFR 1.54) will be issued in due course and the date shown on this Acknowledgement Receipt will establish the filing date of the application.

National Stage of an International Application under 35 U.S.C. 371

If a timely submission to enter the national stage of an international application is compliant with the conditions of 35 U.S.C. 371 and other applicable requirements a Form PCT/DO/EO/903 indicating acceptance of the application as a national stage submission under 35 U.S.C. 371 will be issued in addition to the Filing Receipt, in due course.

New International Application Filed with the USPTO as a Receiving Office

If a new international application is being filed and the international application includes the necessary components for an international filing date (see PCT Article 11 and MPEP 1810), a Notification of the International Application Number and of the International Filing Date (Form PCT/RO/105) will be issued in due course, subject to prescriptions concerning national security, and the date shown on this Acknowledgement Receipt will establish the international filing date of the application.

PTO/SB/06 (07-06)

Approved for use through 1/31/2007. OMB 0651-0032 U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

P	ATENT APPL	Substitute f				or Docket Number 522,496		ling Date 12/2007	To be Maile	
	AF	PLICATION	AS FILE	D – PART I						IER THAN
			(Column 1) (Column 2)	SMAL		OR	SMA	LL ENTITY
_	FOR	1	NUMBER FIL	.ED NUM	MBER EXTRA	RATE (\$)	FEE (\$)	1	RATE (\$)	FEE (\$)
	BASIC FEE (37 CFR 1.16(a), (b), (or (c))	N/A		N/A	N/A			N/A	
	SEARCH FEE (37 CFR 1.16(k), (i), d	or (m))	N/A		N/A	N/A			N/A	
	EXAMINATION FE (37 CFR 1.16(o), (p), (N/A		N/A	N/A]	N/A	
	FAL CLAIMS CFR 1.16(i))		mir	us 20 = *		X \$ =	:	OR	X \$ =	
	EPENDENT CLAIM CFR 1.16(h))	S	m	nus 3 = *		X \$ =		1	X \$ =	
	APPLICATION SIZE (37 CFR 1.16(s)) MULTIPLE DEPEN	FEE is \$ add 35 l	ets of pap 250 (\$125 itional 50 J.S.C. 41(ation and drawing er, the applicatio for small entity) sheets or fraction a)(1)(G) and 37	n size fee due for each n thereof. See					
ft	he difference in colu		`			TOTAL		1	TOTAL	
)ED – PART II						
	7411	(Column 1)		(Column 2)	(Column 3)	SM	ALL ENTITY	OR		R THAN LL ENTITY
	06/13/2011	CLAIMS REMAINING AFTER AMENDMENT		HIGHEST NUMBER PREVIOUSLY PAID FOR	PRESENT EXTRA	RATE (\$)	ADDITIONAL FEE (\$)		RATE (\$)	ADDITIONAL FEE (\$)
	Total (37 CFR 1.16(i))	* 14	Minus	** 20	= 0	X \$26 =	0	OR	X \$ =	
	Independent (37 CFR 1.16(h))	* 2	Minus	***8	= 0	X \$110=	0	OR	X \$ =	
	Application Si	ze Fee (37 CFR	1.16(s))							
	FIRST PRESEN	ITATION OF MULT	IPLE DEPEN	DENT CLAIM (37 CFF	R 1.16(j))			OR		
						TOTAL ADD'L FEE	0	OR	TOTAL ADD'L FEE	
		(Column 1)		(Column 2)	(Column 3)				_	
		CLAIMS REMAINING AFTER AMENDMENT		HIGHEST NUMBER PREVIOUSLY PAID FOR	PRESENT EXTRA	RATE (\$)	ADDITIONAL FEE (\$)		RATE (\$)	ADDITIONAI FEE (\$)
	Total (37 CFR 1.16(i))	*	Minus	**	=	X \$ =		OR	X \$ =	
	Independent (37 CFR 1.16(h))	*	Minus	***	=	X \$ =		OR	X \$ =	
	Application Si	Application Size Fee (37 CFR 1.16(s))								
		ITATION OF MULT	IPLE DEPEN	DENT CLAIM (37 CFF	R 1.16(j))			OR		
						TOTAL ADD'L FEE	1	OR	TOTAL ADD'L FEE	
lf T	the entry in column ' the "Highest Numbe f the "Highest Numb "Highest Number P	er Previously Pai er Previously Pa	d For" IN TH id For" IN T	HS SPACE is less HIS SPACE is less	than 20, enter "20" s than 3, enter "3".	Legal /RENI	Instrument E EE HAWKINS/			

This collection of information is required by 37 CFR 1.16. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 12 minutes to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

If you need assistance in completing the form, call 1-800-PTO-9199 and select option 2.

	ed States Paten	T AND TRADEMARK OFFICE	UNITED STATES DEPAR United States Patent and Address: COMMISSIONER F P.O. Box 1450 Alexandria, Virginia 22: www.uspto.gov	FOR PATENTS		
APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.		
11/622,496	01/12/2007	G.R. Mohan Rao	0299-0001.01	3086		
LAW OFFICES	7590 04/13/201. S OF EUGENE M. CU WACKER DRIVE	-	EXAMINER ARORA, AJAY			
SUITE 4130 CHICAGO, IL	60606		ART UNIT	PAPER NUMBER		
Cilici100, IL	00000		2892			
			MAIL DATE	DELIVERY MODE		
			04/13/2011	PAPER		

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

		Application No.	Applicant(s)
		11/622,496	RAO, G.R. MOHAN
	Office Action Summary	Examiner	Art Unit
		AJAY K. ARORA	2892
Period fo	The MAILING DATE of this communication ap or Reply	pears on the cover sheet with the o	correspondence address
WHIC - Exte after - If NC - Failu Any	ORTENED STATUTORY PERIOD FOR REPL CHEVER IS LONGER, FROM THE MAILING D nsions of time may be available under the provisions of 37 CFR 1.1 SIX (6) MONTHS from the mailing date of this communication.) period for reply is specified above, the maximum statutory period ' re to reply within the set or extended period for reply will, by statute reply received by the Office later than three months after the mailin ed patent term adjustment. See 37 CFR 1.704(b).	ATE OF THIS COMMUNICATION 36(a). In no event, however, may a reply be tir will apply and will expire SIX (6) MONTHS from a, cause the application to become ABANDONE	N. mely filed n the mailing date of this communication. ED (35 U.S.C. § 133).
Status			
1)	Responsive to communication(s) filed on 27 J	anuary 2011.	
· ·		action is non-final.	
· · ·	Since this application is in condition for allowa		osecution as to the merits is
	closed in accordance with the practice under I	Ex parte Quayle, 1935 C.D. 11, 4	53 O.G. 213.
Disposit	ion of Claims		
-	Claim(s) 10-16 and 18-24 is/are pending in the	application	
	4a) Of the above claim(s) is/are withdra		
	Claim(s) is/are allowed.		
· · _	Claim(s) <u>10-16 & 18-24</u> is/are rejected.		
7)			
· · _	Claim(s) are subject to restriction and/c	or election requirement.	
		·	
	ion Papers		
·	The specification is objected to by the Examine		
10)	The drawing(s) filed on is/are: a) acc		
	Applicant may not request that any objection to the		
	Replacement drawing sheet(s) including the correc		•
¹¹)∐	The oath or declaration is objected to by the Ex	kaminer. Note the attached Office	e Action or form PTO-152.
Priority u	under 35 U.S.C. § 119		
·	Acknowledgment is made of a claim for foreign	ı priority under 35 U.S.C. § 119(a	u)-(d) or (f).
(a)	All b) Some * c) None of:	a have been received	
	 Certified copies of the priority document Certified copies of the priority document 		ion No
	3. Copies of the certified copies of the priority document		
	application from the International Burea	-	ed in this National Stage
* (See the attached detailed Office action for a list		ed
Attach	*(~)		
Attachmen	τ(s) e of References Cited (PTO-892)	4) 🔲 Interview Summary	(PTO-413)
	e of Draftsperson's Patent Drawing Review (PTO-948)	Paper No(s)/Mail D	pate
3) Infor	mation Disclosure Statement(s) (PTO/SB/08)	5) D Notice of Informal F	Patent Application
U.S. Patent and T	r No(s)/Mail Date	6) 🗌 Other:	
PTOL-326 (F		ction Summary Pa	art of Paper No./Mail Date 20110410

DETAILED ACTION

Claim Rejections - 35 USC § 103

1. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all

obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

2. Claims 10-11, and 19 are rejected under 35 U.S.C. 103(a) as being unpatentable over Kamins (US 4,160,985), hereinafter Kamins, in view of Bamji (US 2002/0084430), hereinafter Bamji.

Regarding claim 10, Kamins (refer to Figures 2-3) teaches a semiconductor device comprising:

a surface layer (23);

s substrate (19);

an active region (comprising photodiodes 11, 13, 15 and 17 are formed),

disposed on one surface (i.e. upper surface in Figure 2) of said surface layer (23); and

a drift layer (21) disposed between the other surface (i.e. lower surface in Figure

2) of said surface layer (23) and said substrate (19), said drift layer having a graded

concentration of dopants (see Figure 3) extending between said surface layer and said

substrate to create a drift field (Col. 2, line 64 - Col. 3, line 2) drawing minority carriers (Col. 2, lines 15-16) from said surface layer to said substrate (Col. 1, lines 38-46 and Col. 3, lines 8-11).

Whereas Kamins teaches photosensing elements like photodiodes and associated integrated circuit structures (Col. 2, lines 56-59), Kaminis does not teach that the semiconductor device is a "CMOS" semiconductor device and with the active region including "a source and a drain". Bamji teaches that integrated circuit structures with photo detectors such as photodiodes may be arrays of CMOS devices (page 1, para 0004) wherein active regions may include a source and a drain (page 9, para 0098, 1st sentence). It would have been obvious to one of ordinary skills in the art at the time of the invention to modify Kamins so that the semiconductor device is a CMOS semiconductor device and with the active region includes a source and a drain. The ordinary artisan would have been motivated to modify Kamins for at least the purpose of using CMOS technology that is suitable for field effect devices with source and drain regions, as CMOS technology enables integration of images sensors on a single integrated circuit and reduction in power consumption (see Bamji, page 1, para 0002).

Claim 18 is similar to claim 10 (and hence the same rejection applies) except for the direction of drawing minority carriers. However, Kamins also teaches the direction of drawing minority carriers as in claim 18; i.e. drawing minority carriers (Col. 2, lines 15-16) may also be from said substrate to said surface layer (Col. 1, lines 38-46 and Col. 3, lines 6-18).

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Regarding claims 11 and 19, Kamins teaches that said drift layer (21) is a deeply implanted layer (see Figures 2-3; also see Col. 2, lines 36-42).

3. Claims 12 and 20 are rejected under 35 U.S.C. 103(a) as being unpatentable over Kamins and Bamji as applied to claims 10 and 18 above above, and further in view of Baliga (US 2002/0056883), hereinafter Baliga.

Regarding claims 12 and 20, Kamins (refer to Figures 2-3) teaches substantially the claimed structure but does not teach that the drift layer is an "epitaxial" layer. Baliga (US 2002/0056883) teaches that it is known in the art that a drift layer with graded dopant concentration may be an epitaxial layer (page 2, para 0008, 2^{nd} and 3rd sentences and page 9, para 0063, especially $7^{th} - 9^{th}$ sentences). It would have been obvious to one of ordinary skills in the art at the time of the invention to modify Kamins so that the drift layer is an epitaxial layer. The ordinary artisan would have been motivated to modify Kamins for at least the purpose of using a layer that has a uniform crystal structure which makes electrical properties more predictable and can also act as a base for further epitaxial layers in which devices may be formed.

4. Claims 13-16 and 21-24 are rejected under 35 U.S.C. 103(a) as being unpatentable over Kamins and Bamji as applied to claims 10 and 18 above above, and

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further in view of Fujimoto (2002/0102783), hereinafter Fujimoto; and Ishaque (US 5,517,052), hereinafter Ishaque.

Regarding claims 13-16 and 21-24, Kamins (refer to Figure 3) teaches substantially the claimed structure but does not specifically state if the gradient is "linear", "quasi-linear", "exponential"; or "complimentary error function". Fujimoto teaches that an impurity region having a concentration gradient may have a profile that is linear, exponential, "or a combination thereof (page 3, para 0038). Further, Ishaque teaches that doping gradient is typically complementary error function or Gaussian if a deep diffusion process is used (Col. 3, line 49 to Col. 4, line 14). Given that Kamins teaches that a desired electric field is formed as a result of the gradient in doping (thus suggesting the gradient affects profile of the field) and various profiles of concentration gradient are known (as explained above in view of Fujimoto and Ishague), it would have been obvious to one of ordinary skills in the art at the time of the invention to modify Kamins so that the gradient is linear, exponential; or alternatively other profiles such as "quasilinear" or "complimentary error function", which are essentially combinations of linear and exponential profiles. The ordinary artisan would have been motivated to modify Kamins for at least the purpose of creating a specific profile of the electric field that is suitable for directing the minority carriers in a specific direction.

Page 5

Response to Arguments

5. Applicant's arguments filed 01/27/2011 have been fully considered but they are not persuasive. On page 6 of applicant's response, applicant argues that Kamins reference does not teach the limitation "a drift layer disposed between the other surface of said surface layer and said substrate, said drift layer having a graded concentration of dopants extending between said surface layer and said substrate..." (see last sentence of para 2 on page 6 of applicant's response). To explain the above argument, applicant points out that "Kamins uses a heavily doped 'buried layer' and a lightly doped epitaxial film over a lightly doped substrate", and based on the above, concludes that Kamins reference to "dopant gradients" is to use of "two separate layers of different dopant concentrations"; and not to "a single layer with a gradient established in donor concentration as required by claim" (see page 6, 2nd para of applicant's response). In response to applicant's argument that the references fail to show certain features of applicant's invention, it is noted that the features upon which applicant relies (i.e., drift layer is required to be a "single layer"; i.e. the drift layer cannot have a multilayer structure) are not recited in the rejected claim(s). Although the claims are interpreted in light of the specification, limitations from the specification are not read into the claims. See In re Van Geuns, 988 F.2d 1181, 26 USPQ2d 1057 (Fed. Cir. 1993).

Further, Figure 3 shows that the N+ buried layer of Figure 2 (i.e. layer 21, which is the drift layer as explained in rejection of claim 10) does have a variable doping profile represented by the central hump of the dopant profile 24 of Figure 3 (y-axis of

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Figure 3 represents doping concentration). As can be seen, this dopant profile has a gradient. Kamins also explains that one of the steps "redistributes" the dopant (i.e. phosphorous) – see Col. 2, lines 51-59), which also explains the doping gradient shown by central part of 24 in Figure 3 as it relates to the the drift layer (i.e. the N+ layer 21 or drift layer of Figure 2). Thus, the Kamins reference does read on the limitation "a drift layer disposed between the other surface of said surface layer and said substrate, said drift layer having a graded concentration of dopants extending between said surface layer and said substrate..." of claim 10 (and claim 18 is similar).

Conclusion

6. **THIS ACTION IS MADE FINAL.** Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the mailing date of this final action.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to AJAY K. ARORA whose telephone number is (571)272-8347. The examiner can normally be reached on Mon through Fri, 8:30am to 5:00pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Thao X. Le can be reached on (571) 272-1708. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

> /Ajay K. Arora/ Primary Examiner, Art Unit 2892

EAST Search History

EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	598	(257/655). CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2011/04/10 20:57

EAST Search History (Interference)

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							Application/Control No.				Applicant(s)/Patent Under Reexamination					
	Ind	lex of (Claim	IS		11622496				RAO, G.R. MOHAN						
						Exa	aminer					Art Ui	nit			
						AJ	AY K ARC	RA				2892				
1	R	ejected		-	С	an	celled		N	Non	-Ele	ected		A	A Appeal	
=	A	llowed		÷	R	est	ricted		I	Interference			0	Objected		
	Claims r	enumbered	in the s	ame	order as	s pre	sented by a	applica	ant			CPA] T.C	D. 🗆	R.1.47
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	Application/Control No.	Applicant(s)/Patent Under Reexamination
Search Notes	11622496	RAO, G.R. MOHAN
	Examiner	Art Unit
	AJAY K ARORA	2892

	SEARCHED		
Class	Subclass	Date	Examiner
257	655	4/10/2011	AKA

Date	Examiner
4/10/2011	AKA
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	INTERFERENCE SEARCH		
Class	Subclass	Date	Examiner

	/A. K. A./ Primary Examiner.Art Unit 2892
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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application No.	:	11/622,496
Confirmation No.	:	3086
Inventor	:	G. R. Mohan Rao
Filed	:	January 12, 2007
TC/A.U.	:	2892
Examiner	:	Ajay Arora
Title	:	SEMICONDUCTOR DEVICES WITH GRADED
		DOPANT REGIONS
Docket No.	:	0299-0001.01

RESPONSE TO NOTICE OF NON-COMPLIANT AMENDMENT

Sir:

In response to the Notice of Non-Compliant Amendment of January 19, 2011 and the

Office Action of August 4, 2010, Applicant submits the following amendment:

Claims. Amendments to the claims begin on page 2 of this amendment.

Remarks. Remarks begin on page 6 of this amendment.

Appl. No. 11/622,496 Reply to Office Action of August 4, 2010

LISTING OF CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

Claims:

- 1. (Canceled)
- 2. (Canceled)
- 3. (Canceled)
- 4. (Canceled)
- 5. (Canceled)
- 6. (Canceled)
- 7. (Canceled)
- 8. (Canceled)
- 9. (Canceled)

10. (Previously presented) A CMOS Semiconductor device comprising:

a surface layer;

a substrate;

an active region including a source and a drain, disposed on one surface of said surface layer; and

a drift layer disposed between the other surface of said surface layer and said substrate, said drift layer having a graded concentration of dopants extending between said surface layer and said substrate to create a drift field drawing minority carriers from said surface layer to said substrate.

11. (Previously presented) The CMOS Semiconductor device of claim 10 wherein said drift layer is a deeply-implanted layer.

12. (Previously presented) The CMOS Semiconductor device of claim 10 wherein said drift layer is an epitaxial layer.

13. (Previously presented) The CMOS Semiconductor device of claim 10 wherein said graded concentration follows a linear gradient.

14. (Previously presented) The CMOS Semiconductor device of claim 10 wherein said graded concentration follows a quasi-linear gradient.

15. (Previously presented) The CMOS Semiconductor device of claim 10 wherein said graded

Page 3 of 8

concentration follows an exponential gradient.

16. (Previously presented) The CMOS Semiconductor device of claim 10 wherein said graded concentration follows a complimentary error function gradient.

17. (Canceled)

18. (Currently amended) A CMOS Semiconductor device comprising:

a surface layer;

a substrate;

an active region including a source and a drain, disposed on one surface of said surface layer; and

a drift layer disposed between the other surface of said surface layer and said substrate, said drift layer having a graded concentration of dopants extending between said surface layer and said substrate to create a drift field drawing minority carriers from said substrate to said <u>surface</u> layer.

19. (Previously presented) The CMOS Semiconductor device of claim 18 wherein said drift layer is a deeply-implanted layer.

20. (Previously presented) The CMOS Semiconductor device of claim 18 wherein said drift layer is an epitaxial layer.

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21. (Previously presented) The CMOS Semiconductor device of claim 18 wherein said graded concentration follows a linear gradient.

22. (Previously presented) The CMOS Semiconductor device of claim 18 wherein said graded concentration follows a quasi-linear gradient.

23. (Previously presented) The CMOS Semiconductor device of claim 18 wherein said graded concentration follows an exponential gradient.

24. (Previously presented) The CMOS Semiconductor device of claim 18 wherein said graded concentration follows a complimentary error function gradient.

25. (Canceled)

Page 5 of 8

REMARKS

Applicant has carefully reviewed the most recent communication from the Patent Office, as well as the cited art. In response, Applicant has canceled claims 17 and 25, as well as amended claim 18. Applicant respectfully traverses the rejections made under 35 U.S.C. § 103(a) as explained below.

Claim 10 stands rejected as obvious in view of the combined teachings of Kamins–Pat. No. 4,160,985 and Bamji–Pub. No. 2002/0084430. Kamins discloses a photosensing device in which different layers of the semiconductor are doped with different concentrations of carriers. Abstract, Fig. 3. In particular, Kamins disclosure states that "[t]he subsurface fields are obtained by incorporating suitable dopant gradients into the structure[...] [T]he subsurface field is formed using a heavily doped 'buried layer' and a lightly doped epitaxial film over a lightly doped substrate [...]" Col. 1, Lines 44-50. Accordingly, Kamins use of the phrase "dopant gradients" refers to layers of different dopant concentrations, and not a single layer with a gradient established in donor concentration as required by the claim element "a drift layer disposed between the other surface of said surface layer and said substrate, said drift layer having a graded concentration of dopants extending between said surface layer and said substrate [...]"

Bamji discloses a method to measure distance or brightness using a CMOS sensor. The most recent office action cites Bamji against claim 10 for the proposition that "integrated circuit structures with photo detectors may be arrays of CMOS devices [...]", which is certainly correct. Office Action of August 4, pp. 4-5. However, Applicant respectfully submits that this disclosure is moot in view of the above recited shortcomings in the disclosure of Kamins.

Claims 11-16 claim varying preferred embodiments that add additional distinction over the prior art. For at least the reason that claim 10 is patentable over the cited prior art, claims 11-

Page 6 of 8

16 are patentable as well.

As pointed out in the most recent Office Action, claim 18 is similar to claim 10, and is patentable for at least the same reasons as claim 10, as recited above. In addition, claims 19-24 further supplement claim 18 by claiming varying preferred embodiments that further distinguish over the prior art. Accordingly, for at least the same reason that claim 18 (and claim 10) is patentable, claims 19-24 are patentable as well.

Page 7 of 8
Appl. No. 11/622,496 Reply to Office Action of August 4, 2010

CONCLUSION

Applicant respectfully submits that in view of the amendments made to the claims and the discussion set forth herein, this application is now in condition for allowance. However, should Examiner be of the opinion that further amendment or response is required, Applicant encourages Examiner to contact the undersigned attorney at the telephone number set forth below. Although no additional fees are believed to be due at this time, the Commissioner is authorized to charge any additional fees or deficiencies or credit any overpayments to Eugene M. Cummings, P.C., Deposit Account No. **50-4199**, with reference to attorney docket number (0299-0001.01).

Respectfully submitted,

Date: January 26, 2011_____

By:

David M. Mundt, Reg. No. 41,207

Law Offices of Eugene M. Cummings, P.C. 1 N. Wacker Suite 4130 Chicago, Illinois 60606

Telephone: (312) 984-0144 Facsimile: (312) 984-0146

Electronic A	Electronic Acknowledgement Receipt						
EFS ID:	9316990						
Application Number:	11622496						
International Application Number:							
Confirmation Number:	3086						
Title of Invention:	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS						
First Named Inventor/Applicant Name:	G.R. Mohan Rao						
Customer Number:	70653						
Filer:	David Michael Mundt/Francisca Hubbard						
Filer Authorized By:	David Michael Mundt						
Attorney Docket Number:	0299-0001.01						
Receipt Date:	27-JAN-2011						
Filing Date:	12-JAN-2007						
Time Stamp:	10:09:52						
Application Type:	Utility under 35 USC 111(a)						

Payment information:

Submitted with Payment			no						
File Listing:									
Document Number	Document Description		File Name	File Size(Bytes)/ Message Digest	Multi Part /.zip	Pages (if appl.)			
1	Amendment/Req. Reconsideration-After Non-Final Reject	F	Response.pdf	244409 df477f2ab6cf8b248f6cb55e63d4bf663a380 efd	no	8			
Warnings: Information:				eiu					

This Acknowledgement Receipt evidences receipt on the noted date by the USPTO of the indicated documents, characterized by the applicant, and including page counts, where applicable. It serves as evidence of receipt similar to a Post Card, as described in MPEP 503.

New Applications Under 35 U.S.C. 111

If a new application is being filed and the application includes the necessary components for a filing date (see 37 CFR 1.53(b)-(d) and MPEP 506), a Filing Receipt (37 CFR 1.54) will be issued in due course and the date shown on this Acknowledgement Receipt will establish the filing date of the application.

National Stage of an International Application under 35 U.S.C. 371

If a timely submission to enter the national stage of an international application is compliant with the conditions of 35 U.S.C. 371 and other applicable requirements a Form PCT/DO/EO/903 indicating acceptance of the application as a national stage submission under 35 U.S.C. 371 will be issued in addition to the Filing Receipt, in due course.

New International Application Filed with the USPTO as a Receiving Office

If a new international application is being filed and the international application includes the necessary components for an international filing date (see PCT Article 11 and MPEP 1810), a Notification of the International Application Number and of the International Filing Date (Form PCT/RO/105) will be issued in due course, subject to prescriptions concerning national security, and the date shown on this Acknowledgement Receipt will establish the international filing date of the application.

PTO/SB/06 (07-06)

Approved for use through 1/31/2007. OMB 0651-0032 LLC Detent and Tr

Under the Paperwork Reduction Act of 1995, no persons are required to respond PATENT APPLICATION FEE DETERMINATION RECORD Substitute for Form PTO-875							Application of information unle Application or Docket Number 11/622,496		Filing Date 01/12/2007		OMB control number.
	AF	D – PART I) (SMALL	entity 🛛	OR		HER THAN			
	FOR	N	UMBER FIL	.ED NU	ED NUMBER EXTRA		RATE (\$)	FEE (\$)		RATE (\$)	FEE (\$)
	BASIC FEE (37 CFR 1.16(a), (b), (or (c))	N/A		N/A		N/A			N/A	
	SEARCH FEE (37 CFR 1.16(k), (i), d	or (m))	N/A		N/A		N/A			N/A	
	EXAMINATION FE (37 CFR 1.16(o), (p), o		N/A		N/A		N/A			N/A	
	CFR 1.16(i))		min	us 20 = *			X \$ =		OR	X\$ =	
	EPENDENT CLAIM CFR 1.16(h))	s	m	nus 3 = *			X \$ =			X\$ =	
	APPLICATION SIZE 37 CFR 1.16(s))	FEE shee is \$2 addit 35 U	ts of pape 50 (\$125 ional 50 s .S.C. 41(ation and drawin er, the application for small entity) sheets or fraction a)(1)(G) and 37	n size fee due for each n thereof. See						
× 16 1	MULTIPLE DEPEN		,	477			TOTAL		1	TOTAL	
							TOTAL		1	TOTAL	
	APPI	(Column 1)	AMENL	ED — PART II	(Column 3)		OTHER T SMALL ENTITY OR SMALL			ER THAN ALL ENTITY	
AMENDMENT	01/27/2011	CLAIMS REMAINING AFTER AMENDMENT		HIGHEST NUMBER PREVIOUSLY PAID FOR	PRESENT EXTRA		RATE (\$)	ADDITIONAL FEE (\$)		RATE (\$)	ADDITIONAL FEE (\$)
OME	Total (37 CFR 1.16(i))	* 14	Minus	** 20	= 0		X \$26 =	0	OR	X \$ =	
IN I	Independent (37 CFR 1.16(h))	* 2	Minus	***3	= 0		X \$110=	0	OR	X \$ =	
AMI	Application Si	ze Fee (37 CFR 1	.16(s))								
	FIRST PRESEN	TATION OF MULTIF	LE DEPEN	DENT CLAIM (37 CF	R 1.16(j))				OR		
						•	TOTAL ADD'L FEE	0	OR	TOTAL ADD'L FEE	
		(Column 1)		(Column 2)	(Column 3)	_					
		CLAIMS REMAINING AFTER AMENDMENT		HIGHEST NUMBER PREVIOUSLY PAID FOR	PRESENT EXTRA		RATE (\$)	ADDITIONAL FEE (\$)		RATE (\$)	ADDITIONAL FEE (\$)
L N	Total (37 CFR 1.16(I))	*	Minus	**	=		X \$ =		OR	X \$ =	
DMENT	Independent (37 CFR 1.16(h))	*	Minus	***	=		X \$ =		OR	X\$ =	
Z U	Application Si	ze Fee (37 CFR 1	.16(s))								
AMI		TATION OF MULTIF	LE DEPEN	DENT CLAIM (37 CF	R 1.16(j))				OR		
** lf *** l	FIRST PRESENTATION OF MULTIPLE DEPENDENT CLAIM (37 CFR 1.16(j)) TOTAL ADD'L FEE * If the entry in column 1 is less than the entry in column 2, write "0" in column 3. ** If the "Highest Number Previously Paid For" IN THIS SPACE is less than 20, enter "20". *** If the "Highest Number Previously Paid For" IN THIS SPACE is less than 3, enter "3". The "Highest Number Previously Paid For" (Total or Independent) is the highest number found in the appropriate box in column 1.										

This collection of information is required by 37 CFR 1.16. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 12 minutes to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. **SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.**

If you need assistance in completing the form, call 1-800-PTO-9199 and select option 2.

	ed States Paten	T AND TRADEMARK OFFICE	UNITED STATES DEPAR United States Patent and Address: COMMISSIONER F P.O. Box 1450 Alexandria, Virginia 22: www.uspto.gov	FOR PATENTS
APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
11/622,496	01/12/2007	G.R. Mohan Rao	0299-0001.01	3086
LAW OFFICES	7590 01/19/201. S OF EUGENE M. CU WACKER DRIVE	-	EXAM	
SUITE 4130 CHICAGO, IL	60606		ART UNIT	PAPER NUMBER
0000, 12	00000		2892	
			MAIL DATE	DELIVERY MODE
			01/19/2011	PAPER

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

	Application No.	Applicant(s)						
Nation of Non Compliant								
Notice of Non-Compliant Amendment (37 CFR 1.121)	11/622,496 Examiner	RAO, G.R. MOHAN						
Amenament (37 Cr H 1.121)	AJAY K. ARORA	2892						
The MAILING DATE of this communication app								
The amendment document filed on <u>01 November 2010</u> is requirements of 37 CFR 1.121 or 1.4. In order for the an item(s) is required.								
 1. Amendments to the specification: A. Amended paragraph(s) do not include 	 A. Amended paragraph(s) do not include markings. B. New paragraph(s) should not be underlined. 							
 2. Abstract: A. Not presented on a separate sheet. 37 B. Other 	7 CFR 1.72.							
"Annotated Sheet" as required by 37 (B. The practice of submitting proposed d	 A. The drawings are not properly identified in the top margin as "Replacement Sheet," "New Sheet," or "Annotated Sheet" as required by 37 CFR 1.121(d). B. The practice of submitting proposed drawing correction has been eliminated. Replacement drawings showing amended figures, without markings, in compliance with 37 CFR 1.84 are required. 							
 B. The listing of claims does not include t C. Each claim has not been provided with of each claim cannot be identified. Not number by using one of the following (Previously presented), (New), (Not end) D. The claims of this amendment paper to E. Other: 	 A. A complete listing of all of the claims is not present. B. The listing of claims does not include the text of all pending claims (including withdrawn claims) C. Each claim has not been provided with the proper status identifier, and as such, the individual status of each claim cannot be identified. Note: the status of every claim must be indicated after its claim number by using one of the following status identifiers: (Original), (Currently amended), (Canceled), (Previously presented), (New), (Not entered), (Withdrawn) and (Withdrawn-currently amended). D. The claims of this amendment paper have not been presented in ascending numerical order. 							
For further explanation of the amendment format require	ed by 37 CFR 1.121, see MPEP §	714.						
TIME PERIODS FOR FILING A REPLY TO THIS NOTION	CE:							
 Applicant is given no new time period if the non-co filed after allowance. If applicant wishes to resubmit entire corrected amendment must be resubmitted 	t the non-compliant after-final am							
2. Applicant is given one month , or thirty (30) days, whichever is longer, from the mail date of this notice to supply the correction, if the non-compliant amendment is one of the following: a preliminary amendment, a non-final amendment (including a submission for a request for continued examination (RCE) under 37 CFR 1.114), a supplemental amendment filed within a suspension period under 37 CFR 1.103(a) or (c), and an amendment filed in response to a <i>Quayle</i> action. If any of above boxes 1. to 4. are checked, the correction required is only the corrected section of the non-compliant amendment in compliance with 37 CFR 1.121.								
Extensions of time are available under 37 CFR 1.136(a) only if the non-compliant amendment is a non-final amendment or an amendment filed in response to a <i>Quayle</i> action.								
Failure to timely respond to this notice will result in: Abandonment of the application if the non-compliant amendment is a non-final amendment or an amendment filed in response to a <i>Quayle</i> action; or Non-entry of the amendment if the non-compliant amendment is a preliminary amendment or supplemental amendment.								
/Ajay K. Arora/ Examiner, Art Unit 2892								

Continuation Sheet (PTOL-324)

Application No.

Continuation of Item 4C above: For example, status identifier of claim 10 is not proper as the status identifier is "new" although claim 10 was also presented in applicant's submission of 05/14/2010 to which were addressed in the office action of 8/4/2010. Similar issues exists with claims 11-16 and 19-24

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application No.	;	11/622,496
Confirmation No.	;	3086
Inventor	:	G. R. Mohan Rao
Filed	:	January 12, 2007
TC/A.U.	:	2892
Examiner	:	Ajay Arora
Title	:	SEMICONDUCTOR DEVICES WITH GRADED
		DOPANT REGIONS
Docket No.	;	0299-0001.01

AMENDMENT B

Sir:

In response to the Office Action of August 4, 2010, Applicant submits the following

amendment:

Claims. Amendments to the claims begin on page 2 of this amendment.

Remarks. Remarks begin on page 6 of this amendment.

Appl. No. 11/622,496 Reply to Office Action of August 4, 2010

LISTING OF CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

<u>Claims:</u>

- 1. (canceled)
- 2. (canceled)
- 3. (canceled)
- 4. (canceled)
- 5. (canceled)
- 6. (canceled)
- 7. (canceled)
- 8. (canceled)
- 9. (canceled)

10. (new) A CMOS Semiconductor device comprising:

a surface layer;

a substrate;

an active region including a source and a drain, disposed on one surface of said surface layer; and

a drift layer disposed between the other surface of said surface layer and said substrate, said drift layer having a graded concentration of dopants extending between said surface layer and said substrate to create a drift field drawing minority carriers from said surface layer to said substrate.

11. (new) The CMOS Semiconductor device of claim 10 wherein said drift layer is a deeplyimplanted layer.

12. (new) The CMOS Semiconductor device of claim 10 wherein said drift layer is an epitaxial layer.

13. (new) The CMOS Semiconductor device of claim 10 wherein said graded concentration follows a linear gradient.

14. (new) The CMOS Semiconductor device of claim 10 wherein said graded concentration follows a quasi-linear gradient.

15. (new) The CMOS Semiconductor device of claim 10 wherein said graded concentration

Page 3 of 8

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follows an exponential gradient.

16. (new) The CMOS Semiconductor device of claim 10 wherein said graded concentration follows a complimentary error function gradient.

17. (canceled)

18. (currently amended) A CMOS Semiconductor device comprising:

a surface layer;

a substrate;

an active region including a source and a drain, disposed on one surface of said surface layer; and

a drift layer disposed between the other surface of said surface layer and said substrate, said drift layer having a graded concentration of dopants extending between said surface layer and said substrate to create a drift field drawing minority carriers from said substrate to said <u>surface</u> layer.

19. (new) The CMOS Semiconductor device of claim 18 wherein said drift layer is a deeplyimplanted layer.

20. (new) The CMOS Semiconductor device of claim 18 wherein said drift layer is an epitaxial layer.

21. (new) The CMOS Semiconductor device of claim 18 wherein said graded concentration follows a linear gradient.

22. (new) The CMOS Semiconductor device of claim 18 wherein said graded concentration follows a quasi-linear gradient.

23. (new) The CMOS Semiconductor device of claim 18 wherein said graded concentration follows an exponential gradient.

24. (new) The CMOS Semiconductor device of claim 18 wherein said graded concentration follows a complimentary error function gradient.

25. (canceled)

Page 5 of 8

<u>REMARKS</u>

Applicant has carefully reviewed the most recent communication from the Patent Office, as well as the cited art. In response, Applicant has canceled claims 17 and 25, as well as amended claim 18. Applicant respectfully traverses the rejections made under 35 U.S.C. § 103(a) as explained below.

Claim 10 stands rejected as obvious in view of the combined teachings of Kamins–Pat. No. 4,160,985 and Bamji–Pub. No. 2002/0084430. Kamins discloses a photosensing device in which different layers of the semiconductor are doped with different concentrations of carriers. Abstract, Fig. 3. In particular, Kamins disclosure states that "[t]he subsurface fields are obtained by incorporating suitable dopant gradients into the structure[...] [T]he subsurface field is formed using a heavily doped 'buried layer' and a lightly doped epitaxial film over a lightly doped substrate [...]" Col. 1, Lines 44-50. Accordingly, Kamins use of the phrase "dopant gradients" refers to layers of different dopant concentrations, and not a single layer with a gradient established in donor concentration as required by the claim element "a drift layer disposed between the other surface of said surface layer and said substrate, said drift layer having a graded concentration of dopants extending between said surface layer and said substrate [...]"

Bamji discloses a method to measure distance or brightness using a CMOS sensor. The most recent office action cites Bamji against claim 10 for the proposition that "integrated circuit structures with photo detectors may be arrays of CMOS devices [...]", which is certainly correct. Office Action of August 4, pp. 4-5. However, Applicant respectfully submits that this disclosure is moot in view of the above recited shortcomings in the disclosure of Kamins.

Claims 11-16 claim varying preferred embodiments that add additional distinction over the prior art. For at least the reason that claim 10 is patentable over the cited prior art, claims 1116 are patentable as well.

As pointed out in the most recent Office Action, claim 18 is similar to claim 10, and is patentable for at least the same reasons as claim 10, as recited above. In addition, claims 19-24 further supplement claim 18 by claiming varying preferred embodiments that further distinguish over the prior art. Accordingly, for at least the same reason that claim 18 (and claim 10) is patentable, claims 19-24 are patentable as well.

Appl. No. 11/622,496 Reply to Office Action of August 4, 2010

CONCLUSION

Applicant respectfully submits that in view of the amendments made to the claims and the discussion set forth herein, this application is now in condition for allowance. However, should Examiner be of the opinion that further amendment or response is required, Applicant encourages Examiner to contact the undersigned attorney at the telephone number set forth below. Although no additional fees are believed to be due at this time, the Commissioner is authorized to charge any additional fees or deficiencies or credit any overpayments to Eugene M. Cummings, P.C., Deposit Account No. **50-4199**, with reference to attorney docket number (0299-0001.01).

Respectfully submitted,

Date: November 1, 2010

By:

David M. Mundt, Reg. No. 41,207

Law Offices of Eugene M. Cummings, P.C. 1 N. Wacker Suite 4130 Chicago, Illinois 60606

Telephone: (312) 984-0144 Facsimile: (312) 984-0146

Electronic Ac	Electronic Acknowledgement Receipt						
EFS ID:	8742028						
Application Number:	11622496						
International Application Number:							
Confirmation Number:	3086						
Title of Invention:	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS						
First Named Inventor/Applicant Name:	G.R. Mohan Rao						
Customer Number:	70653						
Filer:	David Michael Mundt/Francisca Hubbard						
Filer Authorized By:	David Michael Mundt						
Attorney Docket Number:	0299-0001.01						
Receipt Date:	01-NOV-2010						
Filing Date:	12-JAN-2007						
Time Stamp:	14:36:28						
Application Type:	Utility under 35 USC 111(a)						

Payment information:

Submitted with Payment			no					
File Listing:								
Document Number	Document Description		File Name	File Size(Bytes)/ Message Digest	Multi Part /.zip	Pages (if appl.)		
1	Amendment/Req. Reconsideration-After		Amendment.pdf	231626	no	8		
	Non-Final Reject			2e0c3163549e985d12298a79818ad54d919 b163b	110			
Warnings:								
Information:								

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New Applications Under 35 U.S.C. 111

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PTO/SB/06 (07-06)

Approved for use through 1/31/2007. OMB 0651-0032 ademark Office; U.S. DEPARTMENT OF COMMERCE LLS Datent and Trad

PATENT APPLICATION FEE DETERMINATION RECORD Substitute for Form PTO-875							Docket Number 22,496		ing Date 12/2007	To be Maile
	AF	PLICATION /					57			IER THAN
			(Column '	· · ·	Column 2)			OR		
	FOR	N	JMBER FII	.ED NUM	MBER EXTRA	RATE (\$)	FEE (\$)	4	RATE (\$)	FEE (\$)
	BASIC FEE (37 CFR 1.16(a), (b), c	or (c))	N/A		N/A	N/A			N/A	
	SEARCH FEE (37 CFR 1.16(k), (i), c	or (m))	N/A		N/A	N/A			N/A	
	EXAMINATION FE (37 CFR 1.16(o), (p), c		N/A		N/A	N/A			N/A	
	AL CLAIMS CFR 1.16(i))		mir	us 20 = *		X\$ =		OR	X\$ =	
١D	EPENDENT CLAIM	s	m	inus 3 = *		X\$ =		1	X\$ =	
	APPLICATION SIZE 37 CFR 1.16(s)) MULTIPLE DEPEN	FEE shee is \$2 addit 35 U	ts of pap 50 (\$125 ional 50 S.C. 41(ation and drawing er, the applicatio for small entity) sheets or fractior a)(1)(G) and 37 7 CFR 1.16(l))	n size fee due for each n thereof. See					
lf t	he difference in colu		,			TOTAL		1	TOTAL	
		(Column 1) CLAIMS		(Column 2) HIGHEST	(Column 3)	SMA		OR		R THAN LL ENTITY
	11/01/2010	Remaining After Amendment		NUMBER PREVIOUSLY PAID FOR	PRESENT EXTRA	RATE (\$)	ADDITIONAL FEE (\$)		RATE (\$)	ADDITIONAL FEE (\$)
	Total (37 CFR 1.16(i))	* 14	Minus	** 20	= 0	X \$26 =	0	OR	X \$ =	
	Independent (37 CFR 1.16(h))	* 2	Minus	***3	= 0	X \$110 =	0	OR	X \$ =	
	Application Si	ze Fee (37 CFR 1	.16(s))							
	FIRST PRESEN	ITATION OF MULTIF	LE DEPEN	DENT CLAIM (37 CFF	R 1.16(j))			OR		
						TOTAL ADD'L FEE	0	OR	TOTAL ADD'L FEE	
		(Column 1)		(Column 2)	(Column 3)					
-		CLAIMS REMAINING AFTER AMENDMENT		HIGHEST NUMBER PREVIOUSLY PAID FOR	PRESENT EXTRA	RATE (\$)	ADDITIONAL FEE (\$)		RATE (\$)	ADDITIONAL FEE (\$)
	Total (37 CFR 1.16(i))	*	Minus	**	=	X \$ =		OR	X \$ =	
	Independent (37 CFR 1.16(h))	*	Minus	***	=	X\$ =		OR	X \$ =	
	Application Si	ze Fee (37 CFR 1	.16(s))							
	FIRST PRESEN	ITATION OF MULTIF	LE DEPEN	DENT CLAIM (37 CFF	R 1.16(j))			OR		
_						TOTAL ADD'L FEE		OR	TOTAL ADD'L FEE	
lf * I	he entry in column 1 the "Highest Numbe f the "Highest Numb "Highest Number P	er Previously Paid er Previously Paid	For" IN TH	IIS SPACE is less HIS SPACE is less	than 20, enter "20" s than 3, enter "3".	Legal I /VENE	nstrument Ex SSA JONES/		•	

process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.16. The information is required to obtain or retain a benefit by the public which is to ime (and by including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450, DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

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	ed States Patent	UNITED STATES DEPAR United States Patent and Address: COMMISSIONER F P. O. Box 1450 Alexandria, Virginia 22: www.uspto.gov	FOR PATENTS	
APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
11/622,496	01/12/2007	G.R. Mohan Rao	0299-0001.01	3086
LAW OFFICE	7590 08/04/2010 S OF EUGENE M. CUM WACKER DRIVE	IMINGS, P.C.	EXAM	
SUITE 4130 CHICAGO, IL	60606		ART UNIT	PAPER NUMBER
cincildo, il	00000		2892	
			MAIL DATE	DELIVERY MODE
			08/04/2010	PAPER

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

	Application No.	Applicant(s)				
	11/622,496	RAO, G.R. MOHAN				
Office Action Summary	Examiner	Art Unit				
	AJAY K. ARORA	2892				
The MAILING DATE of this communication a Period for Reply	appears on the cover sheet with the o	correspondence address				
 A SHORTENED STATUTORY PERIOD FOR REF WHICHEVER IS LONGER, FROM THE MAILING Extensions of time may be available under the provisions of 37 CFR after SIX (6) MONTHS from the mailing date of this communication. If NO period for reply is specified above, the maximum statutory peri Failure to reply within the set or extended period for reply will, by sta Any reply received by the Office later than three months after the max earned patent term adjustment. See 37 CFR 1.704(b). 	DATE OF THIS COMMUNICATIO 1.136(a). In no event, however, may a reply be the od will apply and will expire SIX (6) MONTHS from tute, cause the application to become ABANDONE	N. mely filed n the mailing date of this communication. ED (35 U.S.C. § 133).				
Status						
1) Responsive to communication(s) filed on $\underline{14}$	Mav 2010.					
	his action is non-final.					
3) Since this application is in condition for allow	vance except for formal matters, pr	osecution as to the merits is				
closed in accordance with the practice under	• •					
Disposition of Claims						
4)⊠ Claim(s) <u>10-25</u> is/are pending in the applica	tion					
4a) Of the above claim(s) is/are withd						
5) Claim(s) is/are allowed.						
6)⊠ Claim(s) <u>10-25</u> is/are rejected.						
$7) Claim(s) _ is/are objected to.$						
8) Claim(s) are subject to restriction and	d/or election requirement					
Application Papers						
9) The specification is objected to by the Exam	iner.					
10) The drawing(s) filed on is/are: a) a	ccepted or b) objected to by the	Examiner.				
Applicant may not request that any objection to t	he drawing(s) be held in abeyance. Se	e 37 CFR 1.85(a).				
Replacement drawing sheet(s) including the corr	ection is required if the drawing(s) is ob	pjected to. See 37 CFR 1.121(d).				
11) The oath or declaration is objected to by the	Examiner. Note the attached Office	e Action or form PTO-152.				
Priority under 35 U.S.C. § 119						
12) Acknowledgment is made of a claim for forei	an priority under 35 U.S.C. § 119(a)-(d) or (f)				
a) All b) Some * c) None of:		, (2) 01 (1).				
1. Certified copies of the priority docume	ents have been received.					
2. Certified copies of the priority docume		ion No.				
3. Copies of the certified copies of the p						
application from the International Burg		g-				
* See the attached detailed Office action for a l		ed.				
Attachment(s)						
 1) X Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 	4) 🛄 Interview Summary Paper No(s)/Mail D					
3) Information Disclosure Statement(s) (PTO/SB/08)	5) D Notice of Informal F					
Paper No(s)/Mail Date	6) 🗌 Other:					
U.S. Patent and Trademark Office PTOL-326 (Rev. 08-06) Office	Action Summary Pa	art of Paper No./Mail Date 20100802				

200

DETAILED ACTION

Continued Examination Under 37 CFR 1.114

1. A request for continued examination under 37 CFR 1.114, including the fee set forth in 37 CFR 1.17(e), was filed in this application after final rejection. Since this application is eligible for continued examination under 37 CFR 1.114, and the fee set forth in 37 CFR 1.17(e) has been timely paid, the finality of the previous Office action has been withdrawn pursuant to 37 CFR 1.114. Applicant's submission filed on 05/14/2010 has been entered.

Claim Rejections - 35 USC § 112

2. The following is a quotation of the first paragraph of 35 U.S.C. 112:

The specification shall contain a written description of the invention, and of the manner and process of making and using it, in such full, clear, concise, and exact terms as to enable any person skilled in the art to which it pertains, or with which it is most nearly connected, to make and use the same and shall set forth the best mode contemplated by the inventor of carrying out his invention.

3. Claims 17 and 25 are rejected under 35 U.S.C. 112, first paragraph, as failing to comply with the written description requirement. The claim(s) contains subject matter which was not described in the specification in such a way as to reasonably convey to one skilled in the relevant art that the inventor(s), at the time the application was filed, had possession of the claimed invention. Claims 17 and recites "said graded concentration of dopants comprises "solely donor dopants" (as recited in claim 17) and

"solely acceptor dopants" (as recited in claim 25). Whereas donors in general are described, they have not been described in conjunction with the configuration of claim 10, which appears to read on Figure 5b, and more specifically, not described as "solely donor dopants" or "solely acceptor dopants".

4. The following is a quotation of the second paragraph of 35 U.S.C. 112:

The specification shall conclude with one or more claims particularly pointing out and distinctly claiming the subject matter which the applicant regards as his invention.

5. Claims 18-25 are rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention.

Claim 18 recites "said layer" (see last two words of claim 18). However, it is not clear if "said layer" refers to "surface layer" (see line 2 of claim 18) or "drift layer" (see line 6 of claim 18). For the purpose of this office action, it will be assumed that "said layer" may refer to either the surface layer or the drift layer.

Claim Rejections - 35 USC § 103

6. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the

7. Claims 10-11, 17, 19 and 25 are rejected under 35 U.S.C. 103(a) as being unpatentable over Kamins (US 4,160,985), hereinafter Kamins, in view of Bamji (US 2002/0084430), hereinafter Bamji.

Regarding claim 10, Kamins (refer to Figures 2-3) teaches a semiconductor device comprising:

a surface layer (23);

s substrate (19);

an active region (comprising photodiodes 11, 13, 15 and 17 are formed),

disposed on one surface (i.e. upper surface in Figure 2) of said surface layer (23); and

a drift layer (21) disposed between the other surface (i.e. lower surface in Figure 2) of said surface layer (23) and said substrate (19), said drift layer having a graded concentration of dopants (see Figure 3) extending between said surface layer and said substrate to create a drift field (Col. 2, line 64 - Col. 3, line 2) drawing minority carriers (Col. 2, lines 15-16) from said surface layer to said substrate (Col. 1, lines 38-46 and Col. 3, lines 8-11).

Whereas Kamins teaches photosensing elements like photodiodes and associated integrated circuit structures (Col. 2, lines 56-59), Kaminis does not teach that the semiconductor device is a "CMOS" semiconductor device and with the active region including "a source and a drain". Bamji teaches that integrated circuit structures with photo detectors such as photodiodes may be arrays of CMOS devices (page 1, para

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0004) wherein active regions may include a source and a drain (page 9, para 0098, 1st sentence). It would have been obvious to one of ordinary skills in the art at the time of the invention to modify Kamins so that the semiconductor device is a CMOS semiconductor device and with the active region includes a source and a drain. The ordinary artisan would have been motivated to modify Kamins for at least the purpose of using CMOS technology that is suitable for field effect devices with source and drain regions, as CMOS technology enables integration of images sensors on a single integrated circuit and reduction in power consumption (see Bamji, page 1, para 0002).

Claim 18 is similar to claim 10 (and hence the same rejection applies) except for the direction of drawing minority carriers. However, Kamins also teaches the direction of drawing minority carriers as in claim 18; i.e. drawing minority carriers (Col. 2, lines 15-16) may also be from said substrate to said layer (Col. 1, lines 38-46 and Col. 3, lines 6-18).

Regarding claims 11 and 19, Kamins teaches that said drift layer (21) is a deeply implanted layer (see Figures 2-3; also see Col. 2, lines 36-42).

Regarding claims 17, Kamins (refer to Figure 3) teaches that said graded concentration of dopants comprises solely of donor dopants (donors such as phosphorous atoms; see Col. 2, lines 45-56).

Regarding claim 25, the embodiment of Figures 2-3 of Kamnis teaches substantially the claimed structure but does not teach that said graded concentration of dopants comprises "solely acceptor dopants". See rejection of claim 17 and also note that figures 2-3 of Kamins teach that the direction of electric field (ϵ) depends on type of doping (i.e. n-type or p-type) of various layers (19, 21, 23 of Figure 20 - electric field direction is shown by arrows in Figures 2 and 3 for n-type doping. Thus, it would have been obvious to one of ordinary skills in the art at the time of the invention to modify Kamins so that said graded concentration of dopants comprises solely acceptor dopants (i.e. when layers 19, 21 and 23 are p-type). The ordinary artisan would have been motivated to modify Kamins for at least the purpose of creating a specific profile of the electric field that is suitable for a device that is formed in a p-type substrate.

8. Claims 12 and 20 are rejected under 35 U.S.C. 103(a) as being unpatentable over Kamins and Bamji as applied to claims 10 and 18 above above, and further in view of Baliga (US 2002/0056883), hereinafter Baliga.

Regarding claims 12 and 20, Kamins (refer to Figures 2-3) teaches substantially the claimed structure but does not teach that the drift layer is an "epitaxial" layer. Baliga (US 2002/0056883) teaches that it is known in the art that a drift layer with graded dopant concentration may be an epitaxial layer (page 2, para 0008, 2^{nd} and 3rd sentences and page 9, para 0063, especially $7^{th} - 9^{th}$ sentences). It would have been obvious to one of ordinary skills in the art at the time of the invention to modify Kamins so that the drift

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layer is an epitaxial layer. The ordinary artisan would have been motivated to modify Kamins for at least the purpose of using a layer that has a uniform crystal structure which makes electrical properties more predictable and can also act as a base for further epitaxial layers in which devices may be formed.

9. Claims 13-16 and 21-24 are rejected under 35 U.S.C. 103(a) as being unpatentable over Kamins and Bamji as applied to claims 10 and 18 above above, and further in view of Fujimoto (2002/0102783), hereinafter Fujimoto; and Ishaque (US 5,517,052), hereinafter Ishaque.

Regarding claims 13-16 and 21-24, Kamins (refer to Figure 3) teaches substantially the claimed structure but does not specifically state if the gradient is "linear", "quasi-linear", "exponential"; or "complimentary error function". Fujimoto teaches that an impurity region having a concentration gradient may have a profile that is linear, exponential, "or a combination thereof (page 3, para 0038). Further, Ishaque teaches that doping gradient is typically complementary error function or Gaussian if a deep diffusion process is used (Col. 3, line 49 to Col. 4, line 14). Given that Kamins teaches that a desired electric field is formed as a result of the gradient in doping (thus suggesting the gradient affects profile of the field) and various profiles of concentration gradient are known (as explained above in view of Fujimoto and Ishaque), it would have been obvious to one of ordinary skills in the art at the time of the invention to modify Kamins so that the gradient is linear, exponential; or alternatively other profiles such as "quasi-

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linear" or "complimentary error function", which are essentially combinations of linear and exponential profiles. The ordinary artisan would have been motivated to modify Kamins for at least the purpose of creating a specific profile of the electric field that is suitable for directing the minority carriers in a specific direction.

Response to Arguments

10. Applicant's arguments with respect to claims 10 and 11 (as explained in applicant's interview summary of 05/24/2010) and remarks of 05/14/2010 have been considered but are moot in view of the new ground(s) of rejection.

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to AJAY K. ARORA whose telephone number is (571)272-8347. The examiner can normally be reached on Mon through Fri, 8:30am to 5:00pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Thao X. Le can be reached on (571) 272-1708. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information

system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

/Ajay K. Arora/ Examiner, Art Unit 2892

Notice of References Cited	Application/Control No. 11/622,496	Applicant(s)/Pat Reexamination RAO, G.R. MO			
Notice of References Cited	Examiner	Art Unit			
	AJAY K. ARORA	2892	Page 1 of 1		

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	А	US-4,160,985	07-1979	Kamins et al.	257/443
*	В	US-2002/0056883	05-2002	Baliga, Bantval Jayant	257/390
*	С	US-2002/0084430	07-2002	Bamji et al.	250/559.05
*	D	US-2002/0102783	08-2002	Fujimoto et al.	438/200
*	ш	US-5,517,052	05-1996	Ishaque, Ahmad N.	257/462
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FOREIGN PATENT DOCUMENTS

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NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).) Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.

EAST Search History

EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L28	583	(257/655).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/08/02 10:21
L19	8	L16 AND donor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/08/02 08:38
L17	3	L16 AND "complimentary error function"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/08/02 08:04
L16	47	L1 AND (linear AND exponential)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/08/02 08:04
L15	172	(drift WITH layer WITH epitaxial) AND L1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/08/02 07:16
L14	2	("20020084430").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/08/02 05:26
L13	9	L2 AND L8	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/08/02 05:20

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L12	98	L1 AND L8	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/08/02 05:20
L11	7	L1 AND L7	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/08/02 05:14
L10	0	L8 AND L7	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/08/02 05:14
L9	0	L8 AND L6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/08/02 05:14
L8	8028	photodiode WITH CMOS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/08/02 05:13
L7	7	L6 AND (drift WITH layer WITH between WITH substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/08/02 04:48
L6	88	L1 AND (drift WITH layer WITH (graded OR gradation OR gradient) WITH (dopant OR doping OR impurity OR donor OR acceptor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/08/02 04:47
L5	33	L2 AND L4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/08/02 04:30

L4	114	L1 AND (minority WITH carrier WITH substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/08/02 04:30
L3	0	L1 AND (minority WITH carrier WITH into WITH substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/08/02 04:29
L2	371	L1 AND (drift WITH field)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/08/02 04:29
L1	3377	((graded OR gradation OR gradient) NEAR3 (dopant OR doping OR impurity OR donor OR acceptor)) AND (semiconductor OR CMOS OR FET OR "field effect" OR NMOS OR PMOS).ab.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/08/02 04:28
S70	16	(layer WITH (dopant OR donor) WITH concentration WITH minority WITH substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/08/01 20:02
S69	4	(grad\$3 WITH (dop\$3 OR donor)) SAME ((dopant OR donor) WITH driv\$3 WITH (toward OR into OR deep \$2) WITH substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/08/01 20:00
S68	7	(grad\$3 WITH (dop\$3 OR donor)) SAME ((dopant OR donor) WITH (sweep\$3 OR mov \$3 OR attract\$3) WITH substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/08/01 19:58
S67	0	S66 AND S62	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM TDB	OR	ON	2010/08/01 19:15

S66	12	S64 AND S65	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/08/01 19:14
S 65	712	CMOS AND (linear WITH gradient)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/08/01 19:14
S64	55	CMOS AND (exponential WITH gradient)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/08/01 19:13
S62	5	(complementary WITH error WITH function WITH gradient)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/08/01 19:12
S61	74	S60 AND CMOS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/08/01 13:43
S60	173	((graded OR gradient OR gradation) NEAR2 (dop \$3 OR impurity)) WITH between WITH substrate AND (active OR source OR drain OR source/ drain)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/08/01 12:45

EAST Search History (Interference)

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	Inc	lex of (Claim	ıs		Application/Control No.			Reexa	Applicant(s)/Patent Under Reexamination RAO, G.R. MOHAN				
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						Examiner				Art U	nit			
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	Application/Control No.	Applicant(s)/Patent Under Reexamination
Search Notes	11622496	RAO, G.R. MOHAN
	Examiner	Art Unit
	AJAY K ARORA	2892

	SEARCHED		
Class	Subclass	Date	Examiner
257	655	8/2/2010	AKA

SEARCH NOT	ES	
Search Notes	Date	Examiner
Refer to EAST search history report	8/2/2010	AKA

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Class	Subclass	Date	Examiner

/A. K. A./ Examiner.Art Unit 2892	

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

7

Application No.	:	11/622,496
Confirmation No.	:	3086
Inventor	:	G. R. Mohan Rao
Filed	:	January 12, 2007
TC/A.U.	:	2892
Examiner	:	Ajay Arora
Title	:	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS
Docket No.	;	0299-0001.01

STATEMENT OF THE SUBSTANCE OF THE INTERVIEW

Sir:

Pursuant to MPEP § 713.04, Applicant submits this Statement of the Substance of the Interview. Foremost, Applicant wishes to thank Examiner Arora for the courtesy extended to Applicant's representatives Eugene Cummings and Konrad Sherinian during the office interview of April 29, 2010. During the interview, Applicant presented new claims 10 and 11 and explained that a critical feature of the invention is that the dopant region of Figure 5b disposed just above the P-substrate forms a distinct drift layer disposed between an active region and a substrate layer. Examiner agreed that the prior art of record did not teach such a feature and that further consideration and/or search would be necessary.

Applicant then filed an RCE under CFR 1.114 on May 14, 2010 to submit this new claim set as well as to withdraw the Notice of Appeal of March 10, 2010.
Although no additional fees are believed to be due at this time, the Commissioner is authorized to charge any additional fees or deficiencies or credit any overpayments to Eugene M. Cummings, P.C., Deposit Account No. 50-4199, with reference to attorney docket number (0299-0001.01).

Respectfully submitted,

EUGENE M. CUMMINGS, P.C.

By:

David M. Mundt, Reg. No. 41,207 1 North Wacker Drive Suite 4130 Chicago, Illinois 60606 Telephone: (312) 984-0144 Facsimile: (312) 984-0146

Page 2 of 2

Electronic A	Electronic Acknowledgement Receipt						
EFS ID:	7669247						
Application Number:	11622496						
International Application Number:							
Confirmation Number:	3086						
Title of Invention:	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS						
First Named Inventor/Applicant Name:	G.R. Mohan Rao						
Customer Number:	70653						
Filer:	David Michael Mundt/Francisca Hubbard						
Filer Authorized By:	David Michael Mundt						
Attorney Docket Number:	0299-0001.01						
Receipt Date:	24-MAY-2010						
Filing Date:	12-JAN-2007						
Time Stamp:	12:01:19						
Application Type:	Utility under 35 USC 111(a)						

Payment information:

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Document Number	Document Description		File Name	File Size(Bytes)/ Message Digest	Multi Part /.zip	Pages (if appl.)
1	Applicant summary of interview with examiner		Statement.pdf	63076 20dcb5f07770eea0bbc9b8294794eaff27de 0580	no	2
Warnings:						
Information:						

This Acknowledgement Receipt evidences receipt on the noted date by the USPTO of the indicated documents, characterized by the applicant, and including page counts, where applicable. It serves as evidence of receipt similar to a Post Card, as described in MPEP 503.

New Applications Under 35 U.S.C. 111

If a new application is being filed and the application includes the necessary components for a filing date (see 37 CFR 1.53(b)-(d) and MPEP 506), a Filing Receipt (37 CFR 1.54) will be issued in due course and the date shown on this Acknowledgement Receipt will establish the filing date of the application.

National Stage of an International Application under 35 U.S.C. 371

If a timely submission to enter the national stage of an international application is compliant with the conditions of 35 U.S.C. 371 and other applicable requirements a Form PCT/DO/EO/903 indicating acceptance of the application as a national stage submission under 35 U.S.C. 371 will be issued in addition to the Filing Receipt, in due course.

New International Application Filed with the USPTO as a Receiving Office

If a new international application is being filed and the international application includes the necessary components for an international filing date (see PCT Article 11 and MPEP 1810), a Notification of the International Application Number and of the International Filing Date (Form PCT/RO/105) will be issued in due course, subject to prescriptions concerning national security, and the date shown on this Acknowledgement Receipt will establish the international filing date of the application.

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Under the Paperwork Reduction Act of 1995, no persons are requ	ineu to respond to a conection of infor	nation uniess it contains a valid ontil control nation
Request	Application Number	11/622,496
for Continued Examination (PCE)	Filing Date	01-12-2007
Continued Examination (RCE) Transmittal	First Named Inventor	G. R. Mohan Rao
Address to:	Art Unit	2892
Mail Stop RCE Commissioner for Patents	Examiner Name	Ajay Arora
P.O. Box 1450 Alexandria, VA 22313-1450	Attorney Docket Number	0299-0001.01
This Is a Request for Continued Examination (RCE) Request for Continued Examination (RCE) practice under 37 C 1995, or to any design application. See Instruction Sheet for RC	FR 1.114 does not apply to any u	tility or plant application filed prior to June 8,
 Submission required under 37 CFR 1.114 No amendments enclosed with the RCE will be entered in the applicant does not wish to have any previously filed une amendment(s). 	ne order in which they were filed u	inless applicant instructs otherwise. If
a. Previously submitted. If a final Office action is considered as a submission even if this box is		ed after the final Office action may be
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il. Affidavit(s)/ Declaration(s)	iv. \square Other \underline{Ex}	tension of Time (2 months)
2. Miscellaneous		
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c. Payment by credit card (Form PTO-2038 enclos WARNING: Information on this form may become public. C card information and authorization on PTO-2038.	ed)	ot be included on this form. Provide credit
SIGNATURE OF APPLICA	ANT, ATTORNEY, OR AGENT R	
Signature	Date	
Name (Print/Type) David M. Mundt	Regi	stration No. 41,207
CERTIFICATE O I hereby certify that this correspondence is being deposited with the United Sta addressed to: Mail Stop RCE, Commissioner for Palents, P. O. Box 1450, Ale: Office on the date shown below. Electroomic Filling		as first class mail in an envelope
Signature Anamana MANCull		
Name (Print/Type) Francisca M.A. Hubbard	Date	
This collection of information is required by 37 CFR 1.114. The informati to process) an application. Confidentiality is governed by 35 U.S.C. 122 including gathering, preparing, and submitting the completed application the amount of time you require to complete this form and/or suggestions.	2 and 37 CFR 1.11 and 1.14. This col form to the USPTO. Time will vary de	lection is estimated to take 12 minutes to complete pending upon the individual case. Any comments of

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PTO/SB/22 (07-09) Approved for use through 07/31/2012. OMB 0651-0031 U.S. Patent and Trademark Office; U.S. DEPARMENT OF COMMERCE Under the paperwork Reduction Act of 1995, no persons are required to respond to a collection of Information unless if displays a valid OMB control number.

PETITION FOR EXTENSION OF TIME UNDER 37 CFR 1.136(a) FY 2009 (Fees pursuant to the Consolidated Appropriations Act, 2005 (H.R. 4818).)	Docket Number (Optional) 0299-0001.01
Application Number 11/622,496	Filed 01-12-2007
For SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGION	18
Art Unit 2892	Examiner Ajay Arora

This is a request under the provisions of 37 CFR 1.136(a) to extend the period for filing a reply in the above identified application.

The requested extension and fee are as follows (check time period desired and enter the appropriate fee below):

	<u>Fee</u>	Small Entity Fee	
One month (37 CFR 1.17(a)(1))	\$130	\$65	\$,
X Two months (37 CFR 1.17(a)(2))	\$490	\$245	\$ 245.00
Three months (37 CFR 1.17(a)(3))	\$1110	\$555	\$
Four months (37 CFR 1.17(a)(4))	\$1730	\$865	\$
Five months (37 CFR 1.17(a)(5))	\$2350	\$1175	\$
Applicant claims small entity status. See 37 CFI	R 1.27.		

A check in the amount of the fee is enclosed.

Payment by credit card. Form PTO-2038 is attached.

The Director has already been authorized to charge fees in this application to a Deposit Account.

 \bowtie The Director is hereby authorized to charge any fees which may be required, or credit any overpayment, to Deposit Account Number 50-4199.

WARNING: Information on this form may become public. Credit card information should not be included on this form. Provide credit card information and authorization on PTO-2038.

I am the applicant/inventor.

 \boxtimes

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assignee of record of the entire interest. See 37 CFR 3.71. Statement under 37 CFR 3.73(b) is enclosed (Form PTO/SB/96).

attorney or agent of record. Registration Number 41,207

attorney or agent under 37 CFR 1.34.

Registration number if acting under 37 CFR 1.34

David M. Mundt

Signature

Typed or printed name

NOTE: Signatures of all the inventors or assignees of record of the entire interest or their representative(s) are required. Submit multiple forms if more than one signature is required, see below.

Total of _____ forms are submitted.

This collection of information is required by 37 CFR 1.136(a). The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.11 and 1.14. This collection is estimated to take 6 minutes to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

If you need assistance in completing the form, call 1-800-PTO-9199 and select option 2.

May 14, 2010

Date

312-984-0144

Telephone Number

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application No.	: 11/622,496
Confirmation No.	: 3086
Inventor	: G. R. Mohan Rao
Filed	: January 12, 2007
TC/A.U.	: 2892
Examiner	: Ajay Arora
Title	: SEMICONDUCTOR DEVICES WITH GRADED
	DOPANT REGIONS
Docket No.	: 0299-0001.01

REQUEST FOR CONTINUED EXAMINATION

AMENDMENT A

Sir:

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In response to the Office Action of December 30, 2009, Applicant submits the following amendment:

Claims. Amendments to the claims begin on page 2 of this amendment.

Remarks. Remarks begin on page 6 of this amendment.

LISTING OF CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

<u>Claims:</u>

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- 1. (canceled)
- 2. (canceled)
- 3. (canceled)
- 4. (canceled)
- 5. (canceled)
- 6. (canceled)
- 7. (canceled)
- 8. (canceled)
- 9. (canceled)

10. (new) A CMOS Semiconductor device comprising:

a surface layer;

a substrate;

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an active region including a source and a drain, disposed on one surface of said surface layer; and

a drift layer disposed between the other surface of said surface layer and said substrate, said drift layer having a graded concentration of dopants extending between said surface layer and said substrate to create a drift field drawing minority carriers from said surface layer to said substrate.

11. (new) The CMOS Semiconductor device of claim 10 wherein said drift layer is a deeplyimplanted layer.

12. (new) The CMOS Semiconductor device of claim 10 wherein said drift layer is an epitaxial layer.

13. (new) The CMOS Semiconductor device of claim 10 wherein said graded concentration follows a linear gradient.

14. (new) The CMOS Semiconductor device of claim 10 wherein said graded concentration follows a quasi-linear gradient.

15. (new) The CMOS Semiconductor device of claim 10 wherein said graded concentration

Page 3 of 7

follows an exponential gradient.

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16. (new) The CMOS Semiconductor device of claim 10 wherein said graded concentration follows a complimentary error function gradient.

17. (new) The CMOS Semiconductor device of claim 10 wherein said graded concentration of dopants comprises solely donor dopants.

18. (new) A CMOS Semiconductor device comprising:

a surface layer;

a substrate;

an active region including a source and a drain, disposed on one surface of said surface layer; and

a drift layer disposed between the other surface of said surface layer and said substrate, said drift layer having a graded concentration of dopants extending between said surface layer and said substrate to create a drift field drawing minority carriers from said substrate to said layer.

19. (new) The CMOS Semiconductor device of claim 18 wherein said drift layer is a deeplyimplanted layer.

20. (new) The CMOS Semiconductor device of claim 18 wherein said drift layer is an epitaxial layer.

Page 4 of 7

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21. (new) The CMOS Semiconductor device of claim 18 wherein said graded concentration follows a linear gradient.

22. (new) The CMOS Semiconductor device of claim 18 wherein said graded concentration follows a quasi-linear gradient.

23. (new) The CMOS Semiconductor device of claim 18 wherein said graded concentration follows an exponential gradient.

24. (new) The CMOS Semiconductor device of claim 18 wherein said graded concentration follows a complimentary error function gradient.

25. (new) The CMOS Semiconductor device of claim 18 wherein said graded concentration of dopants comprises solely acceptor dopants.

REMARKS

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a.

Applicant wishes to thank Examiner Arora for the courtesy extended to Applicant's representatives Eugene Cummings and Konrad Sherinian during the office interview of April 29, 2010. During this interview a new claim set was presented that incorporated a distinct drift layer, which Applicant's contend is not present in the art of record. It was further agreed that Applicant would withdraw the pending notice of appeal, and file a request for continued examination, along with a new set of claims contained herein.

Applicant awaits a first action on these new claims, which Applicant believes are patentable over the known art.

Page 6 of 7

CONCLUSION

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Applicant respectfully submits that in view of the amendments made to the claims and the discussion set forth herein, this application is now in condition for allowance. However, should Examiner be of the opinion that further amendment or response is required, Applicant encourages Examiner to contact the undersigned attorney at the telephone number set forth below. Although no additional fees are believed to be due at this time, the Commissioner is authorized to charge any additional fees or deficiencies or credit any overpayments to Eugene M. Cummings, P.C., Deposit Account No. **50-4199**, with reference to attorney docket number (0299-0001.01).

Respectfully submitted,

Date: May 14, 2010

By:

David M. Mundt, Reg. No. 41,207

Law Offices of Eugene M. Cummings, P.C. 1 N. Wacker Suite 4130 Chicago, Illinois 60606

Telephone: (312) 984-0144 Facsimile: (312) 984-0146

Electronic Patent Application Fee Transmittal							
Application Number:	110	522496					
Filing Date:	12-	12-Jan-2007					
Title of Invention:	SEI	MICONDUCTOR DEV	/ICES WITH GR	ADED DOPANT REC	SIONS		
First Named Inventor/Applicant Name:	G.F	8. Mohan Rao					
Filer:	Da	vid Michael Mundt/	'Francisca Hub	bard			
Attorney Docket Number:	Attorney Docket Number: 0299-0001						
Filed as Small Entity							
Utility under 35 USC 111(a) Filing Fees							
Description		Fee Code	Quantity	Amount	Sub-Total in USD(\$)		
Basic Filing:							
Pages:							
Claims:							
Miscellaneous-Filing:							
Petition:							
Patent-Appeals-and-Interference:							
Post-Allowance-and-Post-Issuance:							
Extension-of-Time:							
Extension - 2 months with \$0 paid		2252	1	245	245		

Description	Fee Code Quantity		Amount	Sub-Total in USD(\$)	
Miscellaneous:					
Request for continued examination	2801	1	405	405	
	Tot	al in USD) (\$)	650	

Electronic Ac	knowledgement Receipt					
EFS ID:	7613062					
Application Number:	11622496					
International Application Number:						
Confirmation Number:	3086					
Title of Invention:	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS					
First Named Inventor/Applicant Name:	G.R. Mohan Rao					
Customer Number:	70653					
Filer:	David Michael Mundt/Francisca Hubbard					
Filer Authorized By:	David Michael Mundt					
Attorney Docket Number:	0299-0001					
Receipt Date:	14-MAY-2010					
Filing Date:	12-JAN-2007					
Time Stamp:	12:19:46					
Application Type:	Utility under 35 USC 111(a)					

Payment information:

Submitted with Payment	yes				
Payment Type	Deposit Account				
Payment was successfully received in RAM	\$650				
RAM confirmation Number	8031				
Deposit Account 504199					
Authorized User					
The Director of the USPTO is hereby authorized to c	harge indicated fees and credit any overpayment as follows:				
Charge any Additional Fees required under 37 C.F	.R. Section 1.21 (Miscellaneous fees and charges)				

File Listing	j :				
Document Number	Document Description	File Name	File Size(Bytes)/ Message Digest	Multi Part /.zip	Pages (if appl.)
1	Request for Continued Examination (RCE)	RCE.pdf	95537	no	1
	(NCL)		83a7001b6664b26e8cc6b15887e56cca84 83a7001b6664b26e8cc6b15887e56cca84 79508 no b068ebf90ba2770a3d21d7adca284f27cbb no 187796 no 5a0f1decaae50b1ba1e4c00313e8df35cf16 70 32354 no		
Warnings:					
This is not a USF	PTO supplied RCE SB30 form.				
Information:					
2	Extension of Time	ExtOfTime.pdf	79508	no	1
Warnings:					
Information:					
3	Amendment After Final	AmendmentA.pdf	187796	no	7
Warnings:					
Information:					
4	Fee Worksheet (PTO-875)	fee-info.pdf	32354	no 2	
			0311a75122a1875e6f4002d6add25f0c709 0d4e5		
Warnings:					
Information:					
		Total Files Size (in bytes)	: 39	95195	
characterized Post Card, as <u>New Applicat</u> If a new appli 1.53(b)-(d) an	edgement Receipt evidences receip I by the applicant, and including pag described in MPEP 503. <u>ions Under 35 U.S.C. 111</u> cation is being filed and the applica od MPEP 506), a Filing Receipt (37 CF ement Receipt will establish the filin	ge counts, where applicable. tion includes the necessary c R 1.54) will be issued in due	It serves as evidence components for a filin	of receipt s g date (see	imilar to a 37 CFR
If a timely sub U.S.C. 371 and national stag <u>New Internat</u> If a new intern an internation and of the Int	e of an International Application un omission to enter the national stage d other applicable requirements a F e submission under 35 U.S.C. 371 wi ional Application Filed with the USP national application is being filed ar nal filing date (see PCT Article 11 an cernational Filing Date (Form PCT/RC rity, and the date shown on this Ack on.	of an international applicati orm PCT/DO/EO/903 indicati ill be issued in addition to the <u>TO as a Receiving Office</u> nd the international applicat d MPEP 1810), a Notification D/105) will be issued in due c	ng acceptance of the e Filing Receipt, in du ion includes the nece of the International <i>i</i> ourse, subject to pres	application e course. ssary comp Application scriptions co	onents for Number Docerning

PTO/SB/06 (07-06)

Approved for use through 1/31/2007. OMB 0651-0032 ademark Office; U.S. DEPARTMENT OF COMMERCE LLS Datent and Trad

P	ATENT APPLI	CATION FE Substitute for			N RECORD		Docket Number 22,496		ing Date 12/2007	To be Maile
	AF	PLICATION /			0-1 0)			0.0		
	505		(Column 1	· · ·	Column 2)			OR		
FOR NUMBER FILED BASIC FEE N/A		.ED NUM	MBER EXTRA	RATE (\$)	FEE (\$)		RATE (\$) N/A	FEE (\$)		
-	(37 CFR 1.16(a), (b), o SEARCH FEE	or (c))						•		
-	(37 CFR 1.16(k), (i), o		N/A		N/A	N/A			N/A	
	(37 CFR 1.16(o), (p), o AL CLAIMS		N/A		N/A	N/A			N/A	
7 (CFR 1.16(i)) EPENDENT CLAIM	<u></u>	min	us 20 = *		×\$ =		OR	X\$ =	
	CFR 1.16(h))	5	m	inus 3 = *		X\$ =			X\$ =	
	APPLICATION SIZE 37 CFR 1.16(s)) MULTIPLE DEPEN	FEE shee is \$2 addit 35 U	ts of pape 50 (\$125 ional 50 s S.C. 41(ation and drawing er, the applicatio for small entity) sheets or fraction a)(1)(G) and 37 (7 CER 1.16(0))	n size fee due for each n thereof. See					
ft	he difference in colu		,			TOTAL		1	TOTAL	
		(Column 1) CLAIMS		(Column 2) HIGHEST	(Column 3)	SMA	LL ENTITY	OR		R THAN LL ENTITY
AMENUMEN I	05/14/2010	REMAINING AFTER AMENDMENT		NUMBER PREVIOUSLY PAID FOR	PRESENT EXTRA	RATE (\$)	ADDITIONAL FEE (\$)		RATE (\$)	ADDITIONAL FEE (\$)
	Total (37 CFR 1.16(i))	* 16	Minus	** 20	= 0	X \$26 =	0	OR	X\$ =	
	Independent (37 CFR 1.16(h))	* 3	Minus	***3	= 0	X \$110 =	0	OR	X \$ =	
	Application Si	ze Fee (37 CFR 1	.16(s))							
	FIRST PRESEN	ITATION OF MULTIF	LE DEPEN	DENT CLAIM (37 CFF	R 1.16(j))			OR		
						TOTAL ADD'L FEE	0	OR	TOTAL ADD'L FEE	
		(Column 1)		(Column 2)	(Column 3)					
		CLAIMS REMAINING AFTER AMENDMENT		HIGHEST NUMBER PREVIOUSLY PAID FOR	PRESENT EXTRA	RATE (\$)	ADDITIONAL FEE (\$)		RATE (\$)	Additional Fee (\$)
	Total (37 CFR 1.16(i))	*	Minus	**	=	X \$ =		OR	X \$ =	
	Independent (37 CFR 1.16(h))	*	Minus	***	=	X\$ =		OR	X\$ =	
	Application Si	ze Fee (37 CFR 1	.16(s))					1		
	FIRST PRESEN	ITATION OF MULTIF	LE DEPEN	DENT CLAIM (37 CFF	R 1.16(j))			OR		
						TOTAL ADD'L FEE		OR	TOTAL ADD'L FEE	
lf ' l	he entry in column 1 the "Highest Numbe f the "Highest Numb "Highest Number P collection of informat	er Previously Paid er Previously Paid reviously Paid For	For" IN TH For" IN T	IIS SPACE is less HIS SPACE is less	than 20, enter "20" s than 3, enter "3".	/DONN	nstrument Ex IA L. PRICE/ opriate box in colu		•	

process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.16. The information is required to obtain or retain a benefit by the public which is to ime (and by including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450, DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

If you need assistance in completing the form, call 1-800-PTO-9199 and select option 2.

	ed States Paten	T AND TRADEMARK OFFICE	UNITED STATES DEPAR United States Patent and Address: COMMISSIONER F P.O. Box 1450 Alexandria, Virginia 22: www.uspto.gov	FOR PATENTS
APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
11/622,496	01/12/2007	G.R. Mohan Rao	0299-0001	3086
LAW OFFICES	70653 7590 05/11/2010 LAW OFFICES OF EUGENE M. CUMMINGS, P.C. ONE NORTH WACKER DRIVE			IINER A, AJAY
SUITE 4130 CHICAGO, IL	60606		ART UNIT	PAPER NUMBER
			2892	
			MAIL DATE	DELIVERY MODE
			05/11/2010	PAPER

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

	Application No.	Applicant(s)				
Interview Summary	11/622,496	RAO, G.R. MOH	IAN			
Interview Summary	Examiner	Art Unit				
	AJAY K. ARORA	2892				
All participants (applicant, applicant's representative, PTO personnel):						
(1) <u>Eugene M. Cummings</u> . (3) <u>Ajay K. Arora</u> .						
(2) <u>Konrad Sherinian</u> .	(4)					
Date of Interview: <u>29 April 2010</u> .						
Type: a) Telephonic b) Video Conference c)⊠ Personal [copy given to: 1) applicant 2	2)X applicant's representative	9]				
Exhibit shown or demonstration conducted: d) Yes If Yes, brief description:	e)⊠ No.					
Claim(s) discussed: <u>1</u> .						
Identification of prior art discussed: Currie and Pendharkar	:					
Agreement with respect to the claims f) was reached.	ı)⊠ was not reached. h)∏ N	J/A.				
Substance of Interview including description of the general reached, or any other comments: <u>See Continuation Sheet</u> .	nature of what was agreed to	if an agreement	was			
(A fuller description, if necessary, and a copy of the amend allowable, if available, must be attached. Also, where no c allowable is available, a summary thereof must be attached	opy of the amendments that v					
THE FORMAL WRITTEN REPLY TO THE LAST OFFICE ACTION MUST INCLUDE THE SUBSTANCE OF THE INTERVIEW. (See MPEP Section 713.04). If a reply to the last Office action has already been filed, APPLICANT IS GIVEN A NON-EXTENDABLE PERIOD OF THE LONGER OF ONE MONTH OR THIRTY DAYS FROM THIS INTERVIEW DATE, OR THE MAILING DATE OF THIS INTERVIEW SUMMARY FORM, WHICHEVER IS LATER, TO FILE A STATEMENT OF THE SUBSTANCE OF THE INTERVIEW. See Summary of Record of Interview requirements on reverse side or on attached sheet.						
/Ajay K. Arora/						
Examiner, Art Unit 2892 U.S. Patent and Trademark Office						
PTOL-413 (Rev. 04-03) Interview	Summary	Paper	No. 20100429			

Summary of Record of Interview Requirements

Manual of Patent Examining Procedure (MPEP), Section 713.04, Substance of Interview Must be Made of Record

A complete written statement as to the substance of any face-to-face, video conference, or telephone interview with regard to an application must be made of record in the application whether or not an agreement with the examiner was reached at the interview.

Title 37 Code of Federal Regulations (CFR) § 1.133 Interviews

Paragraph (b)

In every instance where reconsideration is requested in view of an interview with an examiner, a complete written statement of the reasons presented at the interview as warranting favorable action must be filed by the applicant. An interview does not remove the necessity for reply to Office action as specified in §§ 1.111, 1.135. (35 U.S.C. 132)

37 CFR §1.2 Business to be transacted in writing.

All business with the Patent or Trademark Office should be transacted in writing. The personal attendance of applicants or their attorneys or agents at the Patent and Trademark Office is unnecessary. The action of the Patent and Trademark Office will be based exclusively on the written record in the Office. No attention will be paid to any alleged oral promise, stipulation, or understanding in relation to which there is disagreement or doubt.

The action of the Patent and Trademark Office cannot be based exclusively on the written record in the Office if that record is itself incomplete through the failure to record the substance of interviews.

It is the responsibility of the applicant or the attorney or agent to make the substance of an interview of record in the application file, unless the examiner indicates he or she will do so. It is the examiner's responsibility to see that such a record is made and to correct material inaccuracies which bear directly on the question of patentability.

Examiners must complete an Interview Summary Form for each interview held where a matter of substance has been discussed during the interview by checking the appropriate boxes and filling in the blanks. Discussions regarding only procedural matters, directed solely to restriction requirements for which interview recordation is otherwise provided for in Section 812.01 of the Manual of Patent Examining Procedure, or pointing out typographical errors or unreadable script in Office actions or the like, are excluded from the interview recordation procedures below. Where the substance of an interview is completely recorded in an Examiners Amendment, no separate Interview Summary Record is required.

The Interview Summary Form shall be given an appropriate Paper No., placed in the right hand portion of the file, and listed on the "Contents" section of the file wrapper. In a personal interview, a duplicate of the Form is given to the applicant (or attorney or agent) at the conclusion of the interview. In the case of a telephone or video-conference interview, the copy is mailed to the applicant's correspondence address either with or prior to the next official communication. If additional correspondence from the examiner is not likely before an allowance or if other circumstances dictate, the Form should be mailed promptly after the interview rather than with the next official communication.

The Form provides for recordation of the following information:

- Application Number (Series Code and Serial Number)
- Name of applicant
- Name of examiner
- Date of interview
- Type of interview (telephonic, video-conference, or personal)
- Name of participant(s) (applicant, attorney or agent, examiner, other PTO personnel, etc.)
- An indication whether or not an exhibit was shown or a demonstration conducted
- An identification of the specific prior art discussed
- An indication whether an agreement was reached and if so, a description of the general nature of the agreement (may be by attachment of a copy of amendments or claims agreed as being allowable). Note: Agreement as to allowability is tentative and does not restrict further action by the examiner to the contrary.
- The signature of the examiner who conducted the interview (if Form is not an attachment to a signed Office action)

It is desirable that the examiner orally remind the applicant of his or her obligation to record the substance of the interview of each case. It should be noted, however, that the Interview Summary Form will not normally be considered a complete and proper recordation of the interview unless it includes, or is supplemented by the applicant or the examiner to include, all of the applicable items required below concerning the substance of the interview.

- A complete and proper recordation of the substance of any interview should include at least the following applicable items:
- 1) A brief description of the nature of any exhibit shown or any demonstration conducted,
- 2) an identification of the claims discussed,
- 3) an identification of the specific prior art discussed,
- 4) an identification of the principal proposed amendments of a substantive nature discussed, unless these are already described on the Interview Summary Form completed by the Examiner,
- 5) a brief identification of the general thrust of the principal arguments presented to the examiner,
 - (The identification of arguments need not be lengthy or elaborate. A verbatim or highly detailed description of the arguments is not required. The identification of the arguments is sufficient if the general nature or thrust of the principal arguments made to the examiner can be understood in the context of the application file. Of course, the applicant may desire to emphasize and fully describe those arguments which he or she feels were or might be persuasive to the examiner.)
- 6) a general indication of any other pertinent matters discussed, and
- 7) if appropriate, the general results or outcome of the interview unless already described in the Interview Summary Form completed by the examiner.

Examiners are expected to carefully review the applicant's record of the substance of an interview. If the record is not complete and accurate, the examiner will give the applicant an extendable one month time period to correct the record.

Examiner to Check for Accuracy

If the claims are allowable for other reasons of record, the examiner should send a letter setting forth the examiner's version of the statement attributed to him or her. If the record is complete and accurate, the examiner should place the indication, "Interview Record OK" on the paper recording the substance of the interview along with the date and the examiner's initials.

.

Continuation of Substance of Interview including description of the general nature of what was agreed to if an agreement was reached, or any other comments: Applicant explained the key differences between applicant's invention (with particular reference to Figure 5b of the specification) and showed how the structure was different from that of Currie and Pendharkar. Applicant presented new claims 10 and 11. Applicant explained that a critical feature of the invention is that the graded dopant region of Figure 5b disposed just above the P- substrate forms a distinct drift layer disposed between an active region and a substrate layer. Examiner agreed that above feature was not taught by Currie or Pendharkar but noted that the above feature is not recited in claim 1 or other currently pending claims and as such, new claim 10 which recites that above limitation, raises new issues that would require further consideration and/or search.

UNITED STA	tes Patent and Tradema	UNITED STA United States Address: COMMI P.O. Box	a, Virginia 22313-1450
APPLICATION NUMBER	FILING OR 371(C) DATE	FIRST NAMED APPLICANT	ATTY. DOCKET NO./TITLE
11/622,496	01/12/2007	G.R. Mohan Rao	0299-0001
70653 LAW OFFICES OF EUGEI ONE NORTH WACKER D SUITE 4130 CHICAGO, IL 60606	-		CONFIRMATION NO. 3086 F ATTORNEY NOTICE

NOTICE REGARDING CHANGE OF POWER OF ATTORNEY

This is in response to the Power of Attorney filed 04/08/2010.

• The Power of Attorney to you in this application has been revoked by the applicant. Future correspondence will be mailed to the new address of record(37 CFR 1.33).

/ttkim/

Office of Data Management, Application Assistance Unit (571) 272-4000, or (571) 272-4200, or 1-888-786-0101

UNITED ST	ATES PATENT AND TRADEMA	UNITED STA United States Address: COMMI P. Box	a, Vinginia 22313-1450
APPLICATION NUMBER	FILING OR 371(C) DATE	FIRST NAMED APPLICANT	ATTY. DOCKET NO./TITLE
11/622,496	01/12/2007	G.R. Mohan Rao	0299-0001
			CONFIRMATION NO. 3086
70653		POA ACC	EPTANCE LETTER
LAW OFFICES OF EUGENE M. CUMMINGS, P.C. ONE NORTH WACKER DRIVE SUITE 4130 CHICAGO, IL 60606			OC000000041105747*
			Date Mailed: 04/16/2010

NOTICE OF ACCEPTANCE OF POWER OF ATTORNEY

This is in response to the Power of Attorney filed 04/08/2010.

The Power of Attorney in this application is accepted. Correspondence in this application will be mailed to the above address as provided by 37 CFR 1.33.

/ttkim/

Office of Data Management, Application Assistance Unit (571) 272-4000, or (571) 272-4200, or 1-888-786-0101

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		Application Numb		822498
POWER OF ATTORNEY OR		Filing Date		luary 12, 2007
		First Named Inven		Nohan Reo
	OF POWER OF ATTORNEY	Title		Noond seter Davices with Graded Costant Ha
WITH A NE	W POWER OF ATTORNEY	ArtUnit		
	AND	Examinar Nama	manager and the second	y K. Arois
CHANGE OF C	ORRESPONDENCE ADDRESS	Attorney Docket N		2299-2001
L hereby revoke a	Il previous powers of attorney given i	مستحد می نواند از بر واری می بردین با است. مواله است به بروی است است است از است ا		
	terney is submitted herewith.	Г		1
Number as my Kentified abov and Trademar	nt Procisioner(s) accordated with the following your attorney(s) or agent(s) to prosected the r re, and to transect off business in the United S & Office connected therewish:	spellation		70653
OR I hereby appoint to bansact all	in) Practitioner(s) named bolow as my/our one business in the United States Patent and Trac	mey(s) or agent(s) to lomark Olfoe connec	prosecute the	a app ^{li} cation identified above, and
	Practitioner(s) Name		Registrá	ton Number
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Firm or Individual Name	A			·····
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AppScant/Invent OR	tor.			
Assignee of teo	ord of the entite Intelest. See 37 CFR 3.71. If 37 CFR 3.73(0) (Form PTO/3B096) submitte	rd hereinith or filed on		angel an anne an an ann an an an a' a'
	SIGNATURE of Applik	ant or Assignee of	Record	
Signature	4 R.Mohau Rao		Date	APR11-8,2010
'Nama	G. R. MOHAN RAD		Telephone	214-578-2358-
Title and Company	GREENTHREAD L	S. Fou	NDER	
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If you need assistance in completing the form, call (+200-PTO-9159 and select option 2.

Electronic Acknowledgement Receipt				
EFS ID:	7375420			
Application Number:	11622496			
International Application Number:				
Confirmation Number:	3086			
Title of Invention:	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS			
First Named Inventor/Applicant Name:	G.R. Mohan Rao			
Customer Number:	61400			
Filer:	Konrad Val Sherinian/Amy Bills			
Filer Authorized By:	Konrad Val Sherinian			
Attorney Docket Number:	1388-04			
Receipt Date:	08-APR-2010			
Filing Date:	12-JAN-2007			
Time Stamp:	12:47:10			
Application Type:	Utility under 35 USC 111(a)			

Payment information:

Submitted with Payment no						
File Listing:						
Document Number	Document Description		File Name	File Size(Bytes)/ Message Digest	Multi Part /.zip	Pages (if appl.)
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				7de5c4cd46ffa6f295ce3b2c50c58cc7fe2c4 7b2		
Warnings:						
Information:						

This Acknowledgement Receipt evidences receipt on the noted date by the USPTO of the indicated documents, characterized by the applicant, and including page counts, where applicable. It serves as evidence of receipt similar to a Post Card, as described in MPEP 503.

New Applications Under 35 U.S.C. 111

If a new application is being filed and the application includes the necessary components for a filing date (see 37 CFR 1.53(b)-(d) and MPEP 506), a Filing Receipt (37 CFR 1.54) will be issued in due course and the date shown on this Acknowledgement Receipt will establish the filing date of the application.

National Stage of an International Application under 35 U.S.C. 371

If a timely submission to enter the national stage of an international application is compliant with the conditions of 35 U.S.C. 371 and other applicable requirements a Form PCT/DO/EO/903 indicating acceptance of the application as a national stage submission under 35 U.S.C. 371 will be issued in addition to the Filing Receipt, in due course.

New International Application Filed with the USPTO as a Receiving Office

If a new international application is being filed and the international application includes the necessary components for an international filing date (see PCT Article 11 and MPEP 1810), a Notification of the International Application Number and of the International Filing Date (Form PCT/RO/105) will be issued in due course, subject to prescriptions concerning national security, and the date shown on this Acknowledgement Receipt will establish the international filing date of the application.

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- NAP		Docket Number (O	
THE BOARD OF PATENT APPEALS AND INTER		1388-04	
I hereby certify that this correspondence is being facsimile transmitter to the USPTO or deposited with the United States Postal Service with	ed In re Applica		
sufficient postage as first class mail in an envelope addressed to "Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313- 1450" [37 CER 1.8(a)] 03/10/2010 on	Application 11/622,49		Filed 01/12/2007
I The Course	For		
Signature	Art Unit	Ex	aminer
Typed or printed Baxter W. Banowsky	2892	A	rora, Ajay
Applicant hereby appeals to the Board of Patent Appeals and Interfe	erences from the last	decision of the exami	ner.
The fee feethic Nation of Appendix (07.000, 44.00/5)(4)			510
The fee for this Notice of Appeal is (37 CFR 41.20(b)(1))			<u>ب</u>
Applicant claims small entity status. See 37 CFR 1.27. Therefore by half, and the resulting fee is:	ore, the fee shown a	bove is reduced	\$
A check in the amount of the fee is enclosed.			
Payment by credit card. Form PTO-2038 is attached.			
The Director has already been authorized to charge fees in th	is application to a De	eposit Account.	
The Director is hereby authorized to charge any fees which m to Deposit Account No. <u>50-3886</u>	ay be required, or cr	edit any overpayment	
A petition for an extension of time under 37 CFR 1.136(a) (PT	O/SB/22) is enclose	d.	
WARNING: Information on this form may become public. be included on this form. Provide credit card information			
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applicant/inventor.	- -	Falle	Jan
assignee of record of the entire interest.	Baxt	د er W. Banowsky	gnatore
See 37 CFR 3.71. Statement under 37 CFR 3.73(b) is enclose (Form PTO/SB/96)	su	-	printed name
✓ attorney or agent of record. 58,170 Registration number	214-	871-1300	
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attorney or agent acting under 37 CFR 1.34. Registration number if acting under 37 CFR 1.34.	03/1	0/2010	
			Date

This collection of information is required by 37 CFR 41.31. The information is required to obtain or retain a benefit by the Dubic which is to file (and by the DSTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.11, 1.14 and 41.6. This collection is estimated to take 12 minutes to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

If you need assistance in completing the form, call 1-800-PTO-9199 and select option 2.

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12801 N. Central Expressway Suite 1700 Dallas, Texas 75243 PHONE: 214-871-1300 FACSIMILE: 214-871-0038 www.banowsky.com

BANOWSKY & LEVINE A PROFESSIONAL CORPORATION ATTORNEYS AND COUNSELORS

March 10, 2010

Via First Class Mail

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

RE: Docket No. 1388-04.

Dear Sir/Madam:

Enclosed please find the following documents:

- Notice of Appeal From the Examiner to the Board of Patent Appeals and Interferences;
- 2. Check number 3018 in the amount of \$255.00 representing the fee for the appeal; and,
- 3. A return postcard which I would appreciate you date stamping and returning to me.

If you have any questions regarding the above, please do not hesitate to contact me.

Bes regards anowsky

BWB:jlj Enclosures

	ED STATES PATENT A	AND TRADEMARK OFFICE	UNITED STATES DEPAR United States Patent and Address: COMMISSIONER F P.O. Box 1450 Alexandria, Virginia 22: www.uspto.gov	FOR PATENTS
APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
11/622,496	01/12/2007	G.R. Mohan Rao	1388-04	3086
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12001 N. CEN	TRAL EXPRESSWAY		ARORA	a, AJAY
SUITE 790 DALLAS, TX '	75243		ART UNIT	PAPER NUMBER
			2892	
			MAIL DATE	DELIVERY MODE
			12/30/2009	PAPER

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

		Application No.	Applicant(s)				
		11/622,496	RAO, G.R. MOHAN				
	Office Action Summary	Examiner	Art Unit				
		AJAY K. ARORA	2892				
Period fo	The MAILING DATE of this communication app or Reply	bears on the cover sheet with the	correspondence address				
WHIC - Exte after - If NC - Failu Any	 A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE <u>3</u> MONTH(S) OR THIRTY (30) DAYS, WHICHEVER IS LONGER, FROM THE MAILING DATE OF THIS COMMUNICATION. Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication. If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication. Failure to reply within the set or extended period for reply usitute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b). 						
Status							
1)🖂	Responsive to communication(s) filed on 26 A	ugust 2009.					
		action is non-final.					
3)	Since this application is in condition for allowa	nce except for formal matters, pr	osecution as to the merits is				
	closed in accordance with the practice under E	Ex parte Quayle, 1935 C.D. 11, 4	53 O.G. 213.				
Disposit	ion of Claims						
4)🖂	Claim(s) <u>3-7 and 9</u> is/are pending in the applic	ation.					
	4a) Of the above claim(s) is/are withdra						
	Claim(s) is/are allowed.						
· · _	Claim(s) <u>3-7 and 9</u> is/are rejected.						
· · ·	Claim(s) is/are objected to.						
8)	Claim(s) are subject to restriction and/o	r election requirement.					
Applicat	on Papers						
	The specification is objected to by the Examine	ar .					
· ·	The drawing(s) filed on is/are: a) \Box acc		Fxaminer				
	Applicant may not request that any objection to the						
	Replacement drawing sheet(s) including the correct						
11)	The oath or declaration is objected to by the Ex						
_	ınder 35 U.S.C. § 119						
1 · · .	Acknowledgment is made of a claim for foreign	e priority under 35 U.S.C. § 119(a	a)-(d) or (f).				
a)	All b) Some * c) None of:	a kava kaan na siyaal					
	1. Certified copies of the priority document		tion No.				
	2. Certified copies of the priority document3. Copies of the certified copies of the prio						
		•	ed in this National Stage				
* 9	application from the International Bureau (PCT Rule 17.2(a)). * See the attached detailed Office action for a list of the certified copies not received.						
Attachmen							
	e of References Cited (PTO-892) e of Draftsperson's Patent Drawing Review (PTO-948)	4) 🛄 Interview Summar Paper No(s)/Mail E					
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DETAILED ACTION

Claim Rejections - 35 USC § 112

1. The following is a quotation of the first paragraph of 35 U.S.C. 112:

The specification shall contain a written description of the invention, and of the manner and process of making and using it, in such full, clear, concise, and exact terms as to enable any person skilled in the art to which it pertains, or with which it is most nearly connected, to make and use the same and shall set forth the best mode contemplated by the inventor of carrying out his invention.

2. Claim 5 is rejected under 35 U.S.C. 112, first paragraph, as failing to comply with the written description requirement. The claim(s) contains subject matter which was not described in the specification in such a way as to reasonably convey to one skilled in the relevant art that the inventor(s), at the time the application was filed, had possession of the claimed invention. Amended claim 5 recites "a graded dopant concentration of <u>both</u> donor and acceptor in <u>both</u> the channel region and the well region" (emphasis added, see last 2 lines of claim 5), which does not comply with the written description requirement.

Claim Rejections - 35 USC § 103

3. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

4. Claims 3-7 and 9 are rejected under 35 U.S.C. 103(a) as being unpatentable over Currie (US 6,831,292) of prior record, hereinafter Currie, in view of Pendharkar, US 2006/0113592), hereinafter Pendharkar.

Regarding claim 3, Currie (refer to Figures 1-4 and in particular to Figure 2) teaches a semiconductor device , which may included VLSI (Col. 1, lines 24-27), comprising:

a surface region (all devices have a surface region);

a substrate (202 and 204);

an active channel region with graded dopant concentration (Col. 5, lines 36-41 and Col. 6, lines 32-37);

a graded dopant concentration in the channel region (Col. 5, lines 36-41 and Col. 6, lines 32-37) which can aid carrier movement away from the surface region towards the substrate.

However, creation of a "localized drift electric field" is a known physical effect of variation of dopant concentrations in a device region (for example, see Pendharkar, US 2006/0113592, page 4, para 0034), which also teaches an isolation well may be formed. It would have been obvious to one of ordinary skills in the art at the time of the invention to modify Currie so that the device comprises an isolation well and doping concentrations and gradation are adjusted so that the active channel and the isolation well are capable of providing a localized drift electric field without the application of external electric field. Note that applicant has not claimed a specific magnitude of the drift electric field and hence any magnitude of drift electric field, however small, reads

on the claim. The ordinary artisan would have been motivated to modify Currie for at least the purpose of aiding carrier movement in a specific, desired direction.

Page 4

Claim 4 recites similar limitations to claim 3, except that it requires "graded dopant concentrations in "the substrate, the channel region, and the well region", which is taught by Currie (Col. 5, lines 36-41; Col. 6, lines 32-37 and Col. 7, lines 12-13).

Similarly, claim 5 is substantially similar to claims 3-4 except for the recitation "a graded dopant concentration of both donor and acceptor in both the channel region and the well region to optimize the operating performance of the device, which is taught by Currie (see Col. 6, lines 15-37; Col. 5, lines 36-41 and Col. 7, lines 12-13).

Claim 6 is similar to claims 3-4 except the requirement that the graded dopant concentration be "fabricated with ion implantation". Currie teaches that graded dopant concentration (Col. 5, lines 36-41 and Col. 6, lines 32-37) may be fabricated with ion implantation (Col. 6, lines 53-57), which can provide an aiding or retarding electric field locally in both well and channel regions, in a monolithic integrated circuit.

Even though a rejection is provided above, it is noted that claim 6 is a product claim but recites a method of steps therein, i.e. "fabricated with ion implantation". Therefore, claim 6 amounts to a product by process claim. *"Even though product-by-process claims are limited by and defined by the process, determination of patentability is based on the product itself. The patentability of a product does not depend on its*

method of production. If the product in the product-by-process claim is the same as or obvious from a product of the prior art, the claim is unpatentable even though the prior product was made by a different process." In re Thorpe, 777 F.2d 695, 698, 227 USPQ 964, 966 (Fed. Cir. 1985). See MPEP 2113.

Claim 7 is similar to claims 3-4 except that it requires that "the substrate is an epitaxial layer". The limitation of "epitaxial layer" is taught by Currie and the graded dopant concentration of substrate has already been discussed in claim 4.

All limitations of claim 9 have already been addressed in claims 3-4.

Response to Arguments

5. Applicant's arguments of 8/26/2009 have been considered but are moot in view of the new ground(s) of rejection.

6. However, arguments related to applicant's response to the 35 U.S.C. 112 rejection of claim 5 (see page 6-7 of applicant's response), are still relevant. Applicant states that the disclosure in specification that "in an n-channel IGBT, electrons can be swept from source to drain rapidly, while at the same time holes can be recombined closer to the n+ buffer". Whereas the above shows presence of electrons and holes (due to presence of dopants), it is silent about the associated gradient in dopant concentrations. In particular, it does not show that the dopant concentration is graded for both donor and acceptor in both channel region and the well region, as claimed.

Conclusion

7. Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, THIS ACTION IS MADE FINAL. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to AJAY K. ARORA whose telephone number is (571)272-8347. The examiner can normally be reached on Mon through Fri, 8:30am to 5:00pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Thao X. Le can be reached on (571) 272-1708. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

/Thao X Le/ Supervisory Patent Examiner, Art Unit 2892 /Ajay K. Arora/ Examiner, Art Unit 2892
Notice of References Cited	Application/Control No. 11/622,496	Applicant(s)/Patent Under Reexamination RAO, G.R. MOHAN		
	Examiner	Art Unit	Dego 1 of 1	
	AJAY K. ARORA	2892	Page 1 of 1	

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	А	US-2006/0113592	06-2006	Pendharkar et al.	257/335
	В	US-			
	С	US-			
	D	US-			
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	F	US-			
	G	US-			
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	J	US-			
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FOREIGN PATENT DOCUMENTS

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NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).) Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.

	Application/Control No.	Applicant(s)/Patent Under Reexamination
Search Notes	11622496	RAO, G.R. MOHAN
	Examiner	Art Unit
	AJAY K ARORA	2892

SEARCHED						
Class	Subclass	Date	Examiner			
257	655	12/22/2009	AKA			

SEARCH NOTES					
Date	Examiner				
12/22/2009	AKA				

INTERFERENCE SEARCH					
Class	Subclass	Date	Examiner		

EAST Search History

EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	564	(257/655).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/12/22 10:12
L2	2	("6831292").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/12/22 10:14
L4	10	(US-20040072395-\$ or US-20010046753- \$ or US- 20010050382-\$ or US-20020093281-\$ or US-20030042511- \$).did. or (US- 6743684-\$ or US- 5359221-\$ or US- 5637898-\$ or US- 5627092-\$ or US- 5029277-\$).did. or (US-20020093281-A- \$).did.	US-PGPUB; USPAT; DERWENT	OR	ON	2009/12/22 10:26
L5	0	L4 AND drift WITH aid\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/22 10:27
L6	7	(drift WITH aid\$3) WITH dopant WITH concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/22 10:27

EAST Search History (Interference)

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Index of Claims			Ap	Application/Control No.			Applicant(s)/Patent Under Reexamination				
			11	11622496				RAO, G.R. MOHAN			
			Ex	aminer			Art Unit	Art Unit			
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	ED STATES PATENT A	UNITED STATES DEPARTMENT OF COMMER United States Patent and Trademark Office Address: COMMISSIONER FOR PATENTS P.O. Box 1450 Alexandria, Virginia 22313-1450 www.uspto.gov			
APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
11/622,496	01/12/2007	G.R. Mohan Rao	1388-04	3086	
	7590 09/29/2009 &LEVINE, P.C		EXAM	INER	
12001 N. CEN	TRAL EXPRESSWAY		ARORA	DRA, AJAY	
SUITE 790 DALLAS, TX '	75243		ART UNIT	PAPER NUMBER	
,			2892		
			MAIL DATE	DELIVERY MODE	
			09/29/2009	PAPER	

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

	Application No.	Applicant(s)				
	11/622,496	RAO, G.R. MOH	IAN			
Interview Summary	Examiner	Art Unit				
	AJAY K. ARORA	2892				
All participants (applicant, applicant's representative, PTO	personnel):					
(1) <u>Baxter Banowsky</u> .	(3) <u>Ajay K. Arora</u> .					
(2) <u>G.R. Mohan Rao</u> .	(4)					
Date of Interview: <u>13 August 2009</u> .						
Type: a)⊠ Telephonic b)⊡ Video Conference c)⊡ Personal [copy given to: 1)⊡ applicant 2	2) applicant's representative	e]				
Exhibit shown or demonstration conducted: d) Yes If Yes, brief description:	e)⊠ No.					
Claim(s) discussed: <u>3 and 5</u> .						
Identification of prior art discussed: <u><i>Currie</i></u> .						
Agreement with respect to the claims f) was reached. g)⊠ was not reached. h)∏ N	√A.				
Substance of Interview including description of the general nature of what was agreed to if an agreement was reached, or any other comments: Applicant described how applicant's invention is different from the Currie reference. Examiner explained how some of the same aspects were also in the disclosure of Currie reference. Examiner pointed out that the features discussed by applicant were not recited in the claims and stressed that although claims are interpretted in light of the specification, limitations from the specification are not read into the claims. (A fuller description, if necessary, and a copy of the amendments which the examiner agreed would render the claims allowable, if available, must be attached. Also, where no copy of the amendments that would render the claims allowable is available, a summary thereof must be attached.) THE FORMAL WRITTEN REPLY TO THE LAST OFFICE ACTION MUST INCLUDE THE SUBSTANCE OF THE INTERVIEW. (See MPEP Section 713.04). If a reply to the last Office action has already been filed, APPLICANT IS GIVEN A NON-EXTENDABLE PERIOD OF THE LONGER OF ONE MONTH OR THIRTY DAYS FROM THIS INTERVIEW DATE, OR THE MAILING DATE OF THE INTERVIEW SUMMARY FORM, WHICHEVER IS LATER, TO FILE A STATEMENT OF THE SUBSTANCE OF THE INTERVIEW. See Summary of Record of Interview requirements on reverse side or on attached sheet.						
/Ajay K. Arora/ Examiner, Art Unit 2892 U.S. Patent and Trademark Office						

PTOL-413 (Rev. 04-03)

Interview Summary

Attorney Docket No. **1388-04** Customer No. **000061400**

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of	§	
RAO, G.R. MOHAN	\$ §	Confirmation No. 3086
	ş	
Serial No. 11/622,496	§	Group Art Unit: 2892
Filed: 12 JANUARY 2007	8 §	Examiner: ARORA, AJAY
	§	
For: SEMICONDUCTOR DEVICES	§	
WITH GRADED DOPANT REGIONS	§	

AMENDMENT AND RESPONSE TO OFFICE ACTION MAILED MAY 27, 2009

I. INTRODUCTORY COMMENTS:

The present paper is submitted as a complete response to the non-final Office Action mailed May 27, 2009, having a shortened statutory period of response of three months. Applicant does not believe that any extension of time or any additional fees are necessary for the consideration of the present paper. However, in the event that an extension of time or any additional fees are necessary for consideration of the present paper, I authorize the Commissioner to charge such fees, including fees for extension of time, to Deposit Account No. 50-3886.

Amendments to the Claims begin on page 2 of this paper.

Remarks/Arguments begin on page 6 of this paper.

II. AMENDMENTS TO THE CLAIMS:

The text of all claims under examination is submitted, and the status of each is identified. This listing of claims replaces all prior versions and listings in the application.

Listing of Claims

Claims 1-2 (Cancelled)

3. (currently amended) A VLSI digital semiconductor device with graded dopant concentration in the well regions and the active channel regions, to aid carrier movement away from the active surface regions, towards the substrate.

A VLSI Digital Semiconductor device comprising:

a surface region;

<u>a substrate;</u>

an active channel region capable of providing a localized drift electric field without the application of an external potential;

an isolation well region capable of providing a localized drift electric field without the application of an external potential; and

a graded dopant concentration in either the channel region or the well region to aid carrier movement away from the surface region towards the substrate.

4. (currently amended) A VLSI digital semiconductor device with graded dopant concentration in the active channel regions, the well regions and the substrate region to aid carrier movement away from the active surface regions, deeper towards the substrate.

A VLSI Digital Semiconductor device comprising:

a surface region;

<u>a substrate;</u>

an active channel region capable of providing a localized drift electric field without the application of an external potential;

an isolation well region capable of providing a localized drift electric field without the application of an external potential; and

graded dopant concentrations in the substrate, the channel region and the well region to aid carrier movement away from the active surface region, towards the substrate.

5. (currently amended) A VLSI digital semiconductor device with at least one each of dopant concentration of both donor and acceptor in both the well and channel regions, to optimize the operating performance of the device.

A VLSI Digital Semiconductor device comprising:

a surface region;

<u>a substrate;</u>

an active channel region capable of providing a localized drift electric field without the application of an external potential;

an isolation well region capable of providing a localized drift electric field without the application of an external potential; and

a graded dopant concentration of both donor and acceptor in both the channel region and the well region to optimize the operating performance of the device.

6. (currently amended) A VLSI digital semiconductor device with at least one graded dopant concentration fabricated with ion implantation, to provide an aiding or retarding electric field locally, in both well and channel regions, in a monolithic integrated circuit.

A VLSI Digital Semiconductor device comprising:

a surface region;

a substrate;

an active channel region capable of providing a localized drift electric field without the application of an external potential;

an isolation well region capable of providing a localized drift electric field without the application of an external potential; and

a graded dopant concentration fabricated with ion implantation in both the channel region and the well region to provide an aiding or retarding electric field locally, in both the well region and the channel region, in a monolithic integrated circuit.

7. (currently amended) A VLSI digital semiconductor device with at least one graded dopant concentration in an epitaxial layer where the epitaxial layer forms the substratum for well and channel regions.

A VLSI Digital Semiconductor device comprising:

a surface region;

a substrate;

an active channel region capable of providing a localized drift electric field without the application of an external potential;

an isolation well region capable of providing a localized drift electric field without the application of an external potential; and

wherein said substrate is an epitaxial layer comprising at least one graded dopant concentration.

8. (Cancelled)

9. (New) <u>A VLSI Digital Semiconductor device comprising:</u>

a surface region;

<u>a substrate;</u>

an active channel region capable of providing a localized drift electric field without the application of an external potential;

an isolation well region capable of providing a localized drift electric field without the

application of an external potential; and

a graded dopant concentration in either the channel region or the well region to aid carrier movement toward the surface.

III. REMARKS:

Claims 3 through 7 are pending herein.

Claims 1, 2 and 8 have been cancelled without prejudice or disclaimer. Claims 3-7 have been amended, more particularly, to point out the claimed subject matter. Claim 9 is new. It is respectfully submitted that Claims 3-7 and 9 are in full compliance with the broad dictates of 35 U.S.C. § 112. Favorable consideration of Claims 3-7 and 9 is respectfully requested.

Claim 5 stands rejected under 35 U.S.C. § 112 as failing to comply with the written description requirement. Insofar as this reference may be applied against the claim 5 as currently amended, this rejection is respectfully traversed.

The limitation of claim 5, reciting "with at least one each of dopant concentration of <u>both</u> donor and receptor in <u>both</u> the well and channel regions" fully complies with the written description requirement. Paragraph 12 of the specification provides "in an n-channel IGBT, electrons can be swept from source to drain rapidly, while at the same time holes can be recombined closer to the n+ buffer layer."

Likewise, paragraph 4 and figures 3(a), (b), (c) and (d) of the specification describe the prior art, upon which the current invention improves. "FIG. 3(a) shows a typical CMOS VLSI device employing a twin well substrate, on which active devices are subsequently fabricated. FIGS. 3(b), 3(c), and 3(d) illustrate device cross sections, as practiced today." Further, paragraph 8 of the specification provides that "FIGURES 3(a), 3(b), 3(c), 3(d) illustrate cross sections commonly used CMOS silicon substrate with two wells (one n-well in which p-channel transistors are subsequently fabricated, and, one p-well in which n-channel transistors are

subsequently fabricated) - typical IC, EEPROM using tunnel insulator, DRAM and NAND flash." It is well known in the art that p-ch xstors are in n-well and vice versa in CMOS circuits. These references in the specification clearly show the concept of transistors in wells in connection with the prior art. The embodiments in the specification use the prior art described in paragraphs 4 and 8 and figures 3(a), (b), (c) and (d) and applies graded dopants to produce localized electric fields to improve performance. Accordingly, paragraph 10 of the specification describes Figures 5(a), (b) and (c) which depict how the invention would be applied to the prior art depicted in Figure 3, including the concept of transistors within wells.

It would have been clear to one skilled in the art that the invention described in the specification would be applicable to doped concentrations in <u>both</u> donor and receptor in <u>both</u> the well and channel regions.

Additionally, claims 3-7 stand rejected under 35 U.S.C. § 102(a) as being anticipated by Currie (US 6,831,292). Insofar as this reference may be applied against the present claims, this rejection is respectfully traversed.

Each of claims 3-7 have been amended to clarify that the claimed invention relates to the field of VLSI digital semiconductor devices which include graded dopant concentrations in regions capable of providing a localized drift electric field without the application of an external potential. The Currie reference discloses a strained layer of Si, Ge or SiGe (Column 3, lines 46-58). The Currie reference does not teach a graded dopant concentration in a material capable of providing a localized drift electric field. Silicon and Germanium each have four valence

electrons. Accordingly, a strained SiGe layer, by its physical nature, is not capable of providing a localized electric field without the application of an external potential.

The amendment to claims 3-7 is supported by the description of the invention contained in the specification. Specifically, paragraph 11 of the specification contains a description of the invention including the range of doping concentrations. Additionally, this paragraph discloses that "[t]he relative slope of the donor concentration throughout the base, creates a suitable aiding drift electric field, to help the holes (p-n-p transistor) transverse from emitter to collector. Since the aiding drift field helps hole conduction, the current gain at a given frequency is enhanced, relative to a uniformly-doped-(base) BJT."

Additionally, Figures 5(a), (b) and (c) clearly illustrate how the current invention differs from the prior art, such as Currie.

Accordingly, for the foregoing reasons, it is respectfully submitted that the cited reference does not disclose or suggest the claimed VLSI digital semiconductor device with graded dopant concentrations in regions capable of providing a localized drift electric field without the application of an external potential. The rejection of claims 3-7 under 35 U.S.C. §102(a) as anticipated by the cited reference should therefore be withdrawn. When read in light of the specification, Applicant submits that none of the foregoing amendments narrow the claims with regard to the claimed semiconductor device.

For all the foregoing reasons, it is respectfully submitted that claims 3-7 and 9 are in condition for allowance. Favorable reconsideration and allowance of claims 3-7 and 9 is respectfully requested.

Respectfully submitted,

Date: August 26, 2009

/Baxter W. Banowsky/ Baxter W. Banowsky Registration No: 58,170

BANOWSKY & LEVINE, P.C.

12001 N. Central Expressway Suite 790 Dallas, Texas 75243 (214) 871-1300 (214) 871-0038 (facsimile) Customer No. **000061400**

Electronic Ac	cknowledgement Receipt
EFS ID:	5958155
Application Number:	11622496
International Application Number:	
Confirmation Number:	3086
Title of Invention:	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS
First Named Inventor/Applicant Name:	G.R. Mohan Rao
Customer Number:	61400
Filer:	Baxter Ward Banowsky.
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Attorney Docket Number:	1388-04
Receipt Date:	26-AUG-2009
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Time Stamp:	15:54:11
Application Type:	Utility under 35 USC 111(a)

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File Listing:										
Document Number	Document Description	File Name	File Name File Size(Bytes)/ Multi Message Digest Part /.zip							
1		OA_05-27-09_rsp.pdf	82950	yes	9					
			de6fa1bbf7a0f8c18785e6a55fd09d19cf1b2 ec5	-						

	Multipart Description/PDF files in .zip description									
	Document Description	Start	End							
	Amendment/Req. Reconsideration-After Non-Final Reject	1	1							
	Claims	2	5							
	Applicant Arguments/Remarks Made in an Amendment	6	9							
Warnings:										
Information:										
	Total Files Size (in bytes):	82	950							

This Acknowledgement Receipt evidences receipt on the noted date by the USPTO of the indicated documents, characterized by the applicant, and including page counts, where applicable. It serves as evidence of receipt similar to a Post Card, as described in MPEP 503.

New Applications Under 35 U.S.C. 111

If a new application is being filed and the application includes the necessary components for a filing date (see 37 CFR 1.53(b)-(d) and MPEP 506), a Filing Receipt (37 CFR 1.54) will be issued in due course and the date shown on this Acknowledgement Receipt will establish the filing date of the application.

National Stage of an International Application under 35 U.S.C. 371

If a timely submission to enter the national stage of an international application is compliant with the conditions of 35 U.S.C. 371 and other applicable requirements a Form PCT/DO/EO/903 indicating acceptance of the application as a national stage submission under 35 U.S.C. 371 will be issued in addition to the Filing Receipt, in due course.

New International Application Filed with the USPTO as a Receiving Office

If a new international application is being filed and the international application includes the necessary components for an international filing date (see PCT Article 11 and MPEP 1810), a Notification of the International Application Number and of the International Filing Date (Form PCT/RO/105) will be issued in due course, subject to prescriptions concerning national security, and the date shown on this Acknowledgement Receipt will establish the international filing date of the application.

PTO/SB/06 (07-06)

Approved for use through 1/31/2007. OMB 0651-0032 ademark Office; U.S. DEPARTMENT OF COMMERCE LLS Datent and Trad

P	ATENT APPLI	CATION FE Substitute for			N RECORD		Docket Number 22,496		ing Date 12/2007	To be Maile
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			(Column '	·/ ·		ENTITY	OR		LL ENTITY	
_	FOR	N	ED NU	MBER EXTRA	RATE (\$)	FEE (\$)	4	RATE (\$)	FEE (\$)	
	BASIC FEE (37 CFR 1.16(a), (b), c	or (c))	N/A		N/A	N/A			N/A	
	SEARCH FEE (37 CFR 1.16(k), (i), c	or (m))	N/A		N/A	N/A			N/A	
	EXAMINATION FE (37 CFR 1.16(o), (p), c		N/A		N/A	N/A			N/A	
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	(Column 1) CLAIMS			(Column 2) HIGHEST	(Column 3)		SMALL ENTITY			
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	Total (37 CFR 1.16(i))	* 6	Minus	** 20	= 0	X \$26 =	0	OR	X \$ =	
	Independent (37 CFR 1.16(h))	* 6	Minus	***8	= 0	X \$110 =	0	OR	X \$ =	
	Application Si	ze Fee (37 CFR 1	.16(s))							
FIRST PRESENTATION OF MULTIPLE DEPENDENT CLAIM (37 CFR 1.16(j))								OR		
						TOTAL ADD'L FEE	0	OR	TOTAL ADD'L FEE	
		(Column 1)		(Column 2)	(Column 3)					
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Application Size Fee (37 CFR 1.16(s))										
FIRST PRESENTATION OF MULTIPLE DEPENDENT CLAIM (37 CFR 1.18(j))							OR			
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lf I	the entry in column 1 the "Highest Numbe f the "Highest Numb "Highest Number P	er Previously Paid er Previously Paid	For" IN TH	HS SPACE is less HIS SPACE is less	than 20, enter "20" s than 3, enter "3".	Legal II /VICTO	nstrument Ex R c. BARLOW	V/	•	

process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.16. The information is required to obtain or retain a benefit by the public which is to ime (and by including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450, DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

If you need assistance in completing the form, call 1-800-PTO-9199 and select option 2.

	<u>ed States Patent a</u>	AND TRADEMARK OFFICE	UNITED STATES DEPAR United States Patent and Address: COMMISSIONER F P. O. Box 1450 Alexandria, Virginia 22: www.uspto.gov	FOR PATENTS
APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
11/622,496	01/12/2007	G.R. Mohan Rao	1388-04	3086
	7590 05/27/2009 &LEVINE, P.C		EXAM	IINER
12001 N. CEN	TRAL EXPRESSWAY		ARORA	, AJAY
SUITE 790 DALLAS, TX '	75243		ART UNIT	PAPER NUMBER
			2892	
			MAIL DATE	DELIVERY MODE
			05/27/2009	PAPER

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

		Application No.	Applicant(s)
		11/622,496	RAO, G.R. MOHAN
	Office Action Summary	Examiner	Art Unit
		AJAY K. ARORA	2892
Period fo	The MAILING DATE of this communication app or Reply	pears on the cover sheet with the	correspondence address
WHIC - Exte after - If NC - Failu Any	ORTENED STATUTORY PERIOD FOR REPL CHEVER IS LONGER, FROM THE MAILING D nsions of time may be available under the provisions of 37 CFR 1.1 SIX (6) MONTHS from the mailing date of this communication. D period for reply is specified above, the maximum statutory period re to reply within the set or extended period for reply will, by statute reply received by the Office later than three months after the mailin ed patent term adjustment. See 37 CFR 1.704(b).	ATE OF THIS COMMUNICATIC 136(a). In no event, however, may a reply be t will apply and will expire SIX (6) MONTHS fror e, cause the application to become ABANDON	N. imely filed n the mailing date of this communication. ED (35 U.S.C. § 133).
Status			
1)🖂	Responsive to communication(s) filed on <u>10 A</u>	pril 2009.	
· · _ ·		s action is non-final.	
3)	Since this application is in condition for allowa	nce except for formal matters, pr	rosecution as to the merits is
	closed in accordance with the practice under A	Ex parte Quayle, 1935 C.D. 11, 4	53 O.G. 213.
Disposit	ion of Claims		
-	Claim(s) <u>3-8</u> is/are pending in the application.		
· ·	4a) Of the above claim(s) is/are withdra	wn from consideration	
	Claim(s) is/are allowed.		
· ·	Claim(s) <u>3-8</u> is/are rejected.		
	Claim(s) is/are objected to.		
	Claim(s) are subject to restriction and/c	or election requirement	
	claim(s) are subject to restriction and/c	si election requirement.	
Applicat	ion Papers		
9)	The specification is objected to by the Examine	er.	
10)	The drawing(s) filed on is/are: a) acc	epted or b) objected to by the	Examiner.
	Applicant may not request that any objection to the	drawing(s) be held in abeyance. Se	ee 37 CFR 1.85(a).
	Replacement drawing sheet(s) including the correc	tion is required if the drawing(s) is o	bjected to. See 37 CFR 1.121(d).
11)	The oath or declaration is objected to by the Ex	xaminer. Note the attached Offic	e Action or form PTO-152.
Priority (ınder 35 U.S.C. § 119		
	Acknowledgment is made of a claim for foreigr	n priority under 35 U.S.C. & 119(a	$a_{-}(d)$ or (f)
· ·	\square All b) \square Some * c) \square None of:		
	1. Certified copies of the priority document	ts have been received	
	2. Certified copies of the priority document		tion No
	3. Copies of the certified copies of the prior		
	application from the International Burea	•	in the National Olage
* 9	See the attached detailed Office action for a list		red
Attachmen	t(s)		
I	e of References Cited (PTO-892)	4) 🔲 Interview Summar	y (PTO-413)
2) 🗌 Notic	e of Draftsperson's Patent Drawing Review (PTO-948)	Paper No(s)/Mail [Date
	nation Disclosure Statement(s) (PTO/SB/08) r No(s)/Mail Date	5) Notice of Informal 6) Other:	Patent Application
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Page 2

DETAILED ACTION

Continued Examination Under 37 CFR 1.114

1. A request for continued examination under 37 CFR 1.114, including the fee set forth in 37 CFR 1.17(e), was filed in this application after final rejection. Since this application is eligible for continued examination under 37 CFR 1.114, and the fee set forth in 37 CFR 1.17(e) has been timely paid, the finality of the previous Office action has been withdrawn pursuant to 37 CFR 1.114. Applicant's submission filed on 04/10/2009 has been entered.

Claim Rejections - 35 USC § 112

2. The following is a quotation of the first paragraph of 35 U.S.C. 112:

The specification shall contain a written description of the invention, and of the manner and process of making and using it, in such full, clear, concise, and exact terms as to enable any person skilled in the art to which it pertains, or with which it is most nearly connected, to make and use the same and shall set forth the best mode contemplated by the inventor of carrying out his invention.

3. Claim 5 is rejected under 35 U.S.C. 112, first paragraph, as failing to comply with the written description requirement. The claim(s) contains subject matter which was not described in the specification in such a way as to reasonably convey to one skilled in the relevant art that the inventor(s), at the time the application was filed, had possession of the claimed invention. Amended claim 5 recites "with at least one each of dopant

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concentration of both donor and acceptor in both the well and channel regions"

(emphasis added), which does not comply with the written description requirement.

Claim Rejections - 35 USC § 102

4. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(a) the invention was known or used by others in this country, or patented or described in a printed publication in this or a foreign country, before the invention thereof by the applicant for a patent.

5. Claims 3-8 are rejected under 35 U.S.C. 102(a) as being anticipated by Currie (US 6,831,292), hereinafter Currie.

Regarding claim 3, Currie (US 6,831,292) (refer to Figures 1-4 and in particular to Figure 2) teaches a semiconductor device, which may included VLSI (Col. 1, lines 24-27), with graded dopant concentration (Col. 5, lines 36-41 and Col. 6, lines 32-37) in the well regions and the active channel regions (Col. 7, lines 12-13) which can aid carrier movement away from the active surface regions, towards the substrate.

Regarding claim 4, Currie (refer to Figures 1-4 and in particular to Figure 2) teaches a semiconductor device , which may included VLSI (Col. 1, lines 24-27), with graded dopant concentration (Col. 5, lines 36-41 and Col. 6, lines 32-37) in the active channel

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regions, the well regions and the substrate region (Col. 7, lines 12-13), which can aid carrier movement away from the active surface regions, deeper towards the substrate.

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Regarding claim 5, Currie (refer to Figures 1-4 and in particular to Figure 2) teaches a semiconductor device , which may included VLSI (Col. 1, lines 24-27), with at least one each of dopant concentration (Col. 5, lines 36-41 and Col. 6, lines 32-37) of both donor and acceptor (Col. 6, lines 15-25) in both the well and channel regions (Col. 7, lines 12-13), to optimize the operating performance of the device.

Regarding claim 6, Currie (refer to Figures 1-4 and in particular to Figure 2) teaches a semiconductor device , which may included VLSI (Col. 1, lines 24-27), with at least one graded dopant concentration (Col. 5, lines 36-41 and Col. 6, lines 32-37) fabricated with ion implantation (Col. 6, lines 53-57), which can provide an aiding or retarding electric field locally in both well and channel regions, in a monolithic integrated circuit.

Even though a rejection is provided above, it is noted that claim 6 is a product claim but recites a method of steps therein, i.e. "fabricated with ion implantation". Therefore, claim 8 amounts to a product by process claim. *"Even though product-by-process claims are limited by and defined by the process, determination of patentability is based on the product itself. The patentability of a product does not depend on its method of production. If the product in the product-by-process claim is the same as or obvious from a product of the prior art, the claim is unpatentable even though the prior product*

Application/Control Number: 11/622,496 Page 5 Art Unit: 2892 was made by a different process." In re Thorpe, 777 F.2d 695, 698, 227 USPQ 964, 966 (Fed. Cir. 1985). See MPEP 2113.

Regarding claim 7, Currie (refer to Figures 1-4 and in particular to Figure 2) teaches a semiconductor device , which may included VLSI (Col. 1, lines 24-27), with at least one graded dopant concentration (Col. 5, lines 36-41 and Col. 6, lines 32-37) in an epitaxial layer (Col. 5, lines 6-12) where the epitaxial layer (124 of Figures 1 and 2) forms the substratum for well and channel regions.

Regarding claim 8, Currie (refer to Figures 1-4 and in particular to Figure 2) teaches a semiconductor device , which may included VLSI (Col. 1, lines 24-27), where one layer consists of dopant gradients in both well and channel regions (Col. 5, lines 36-41 and Col. 6, lines 32-37).

Note that claim 8 is a product claim but recites a method of steps therein, i.e. "one layer of dopant from one wafer, is transferred to another wafer" and "wafer bonding or similar processes". Therefore, claim 8 amounts to a product by process claim. "Even though product-by-process claims are limited by and defined by the process, determination of patentability is based on the product itself. The patentability of a product does not depend on its method of production. If the product in the product-by-process claim is the same as or obvious from a product of the prior art, the claim is unpatentable even

Application/Control Number: 11/622,496Page 6Art Unit: 2892though the prior product was made by a different process." In re Thorpe, 777 F.2d 695,698, 227 USPQ 964, 966 (Fed. Cir. 1985). See MPEP 2113.

Response to Arguments

6. Applicant's arguments with respect to claims 3-8 have been considered but are moot in view of the new ground(s) of rejection.

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to AJAY K. ARORA whose telephone number is (571)272-8347. The examiner can normally be reached on Mon through Fri, 8:30am to 5:00pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Thao X. Le can be reached on (571) 272-1708. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a

USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

/A. K. A./ Examiner, Art Unit 2892 /Chuong A Luu/ Primary Examiner, Art Unit 2892

Examiner Art Unit Page 1 of 1	Notice of References Cited	Application/Control No. 11/622,496	Applicant(s)/Pater Reexamination RAO, G.R. MOH/	
	Notice of Actentices offen	Examiner AJAY K. ARORA	Art Unit 2892	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	А	US-6,831,292	12-2004	Currie et al.	257/19
	В	US-			
	С	US-			
	D	US-			
	Е	US-			
	F	US-			
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	н	US-			
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	L	US-			
	М	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	0					
	Р					
	Q					
	R					
	s					
	Т					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).) Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.

Index of Claims				1162249 Examine	11622496 Examiner				Applicant(s)/Patent Under Reexamination RAO, G.R. MOHAN Art Unit 2892					
✓ Rejected -			Cancelle	Cancelled N Non-Ele			ected	cted A		Appeal				
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	Application/Control No.	Applicant(s)/Patent Under Reexamination
Search Notes	11622496	RAO, G.R. MOHAN
	Examiner	Art Unit
	AJAY K ARORA	2892

	SEARCHED		
Class	Subclass	Date	Examiner
257	655	5/24/2009	AKA

Date	Examiner
5/24/2009	AKA
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	INTERFERENCE SEARCH		
Class	Subclass	Date	Examiner

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L9	551	(257/655).OCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/24 12:52
L8	2	("5029277").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/24 12:17
L7	2	("6831292").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/24 11:36
L4	4	("4001864").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/24 11:10
L3	4	L1 AND (well WITH carrier WITH (movement OR mobility) WITH ((away WITH active WITH surface) OR (towards WITH substrate)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/24 11:06
12	62	L1 AND (((carrier OR electron OR hole) WITH (movement OR mobility)) SAME ((emitter WITH collector) OR (source WITH drain)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/24 11:05

L1	695	VLSI AND	US-PGPUB;	OR	ON	2009/05/24
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		gradation OR	USOCR; EPO;			
		gradient) WITH	JPO;			
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PTO/SB/30EFS (05/07) Approved for use through 11/30/2007. OMB 0651-0031 U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

	REG	UEST FC				NL	
Application		Filing	-	Docket Number	-	Art	1
Number	11/622,496	Date	2007-01-12	(if applicable)	1388-04	Unit	2892
First Named Inventor	RAO, G.R. MOI	HAN		Examiner Name	ARORA, AJAY		
Request for C	ontinued Examir	nation (RCE)		R 1.114 does not a	above-identified application oply to any utility or plant appli WWW.USPTO.GOV		l prior to June 8,
		S	UBMISSION REQ	UIRED UNDER 37	' CFR 1.114		
in which they	were filed unless	applicant in		applicant does not wi	nents enclosed with the RCE v sh to have any previously filed		
	y submitted. If a on even if this bo			any amendments file	d after the final Office action r	nay be cor	nsidered as a
□ Co	nsider the argun	nents in the A	oppeal Brief or Reply	Brief previously filed	on		
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Aff	idavit(s)/ Declara	ation(s)					
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Suspension of action on the above-identified application is requested under 37 CFR 1.103(c) for a period of months (Period of suspension shall not exceed 3 months; Fee under 37 CFR 1.17(i) required)							
Other							
FEES							
The RCE fee under 37 CFR 1.17(e) is required by 37 CFR 1.114 when the RCE is filed. Image: State of the constraint of the const							
SIGNATURE OF APPLICANT, ATTORNEY, OR AGENT REQUIRED							
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PTO/SB/30EFS (05/07) Approved for use through 11/30/2007. OMB 0651-0031

U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Signature of Registered U.S. Patent Practitioner				
Signature	/Baxter W. Banowsky/	Date (YYYY-MM-DD)	2009-04-10	
Name	Baxter W. Banowsky	Registration Number	58170	

This collection of information is required by 37 CFR 1.114. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.11 and 1.14. This collection is estimated to take 12 minutes to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450.

If you need assistance in completing the form, call 1-800-PTO-9199 and select option 2.

The Privacy Act of 1974 (P.L. 93-579) requires that you be given certain information in connection with your submission of the attached form related to a patent application or patent. Accordingly, pursuant to the requirements of the Act, please be advised that: (1) the general authority for the collection of this information is 35 U.S.C. 2(b)(2); (2) furnishing of the information solicited is voluntary; and (3) the principal purpose for which the information is used by the U.S. Patent and Trademark Office is to process and/or examine your submission related to a patent application or patent. If you do not furnish the requested information, the U.S. Patent and Trademark Office may not be able to process and/or examine your submission, which may result in termination of proceedings or abandonment of the application or expiration of the patent.

The information provided by you in this form will be subject to the following routine uses:

- 1. The information on this form will be treated confidentially to the extent allowed under the Freedom of Information Act (5 U.S.C. 552) and the Privacy Act (5 U.S.C. 552a). Records from this system of records may be disclosed to the Department of Justice to determine whether the Freedom of Information Act requires disclosure of these record s.
- 2. A record from this system of records may be disclosed, as a routine use, in the course of presenting evidence to a court, magistrate, or administrative tribunal, including disclosures to opposing counsel in the course of settlement negotiations.
- 3. A record in this system of records may be disclosed, as a routine use, to a Member of Congress submitting a request involving an individual, to whom the record pertains, when the individual has requested assistance from the Member with respect to the subject matter of the record.
- 4. A record in this system of records may be disclosed, as a routine use, to a contractor of the Agency having need for the information in order to perform a contract. Recipients of information shall be required to comply with the requirements of the Privacy Act of 1974, as amended, pursuant to 5 U.S.C. 552a(m).
- 5. A record related to an International Application filed under the Patent Cooperation Treaty in this system of records may be disclosed, as a routine use, to the International Bureau of the World Intellectual Property Organization, pursuant to the Patent Cooperation Treaty.
- 6. A record in this system of records may be disclosed, as a routine use, to another federal agency for purposes of National Security review (35 U.S.C. 181) and for review pursuant to the Atomic Energy Act (42 U.S.C. 218(c)).
- 7. A record from this system of records may be disclosed, as a routine use, to the Administrator, General Services, or his/her designee, during an inspection of records conducted by GSA as part of that agency's responsibility to recommend improvements in records management practices and programs, under authority of 44 U.S.C. 2904 and 2906. Such disclosure shall be made in accordance with the GSA regulations governing inspection of records for this purpose, and any other relevant (i.e., GSA or Commerce) directive. Such disclosure shall not be used to make determinations about individuals.
- 8. A record from this system of records may be disclosed, as a routine use, to the public after either publication of the application pursuant to 35 U.S.C. 122(b) or issuance of a patent pursuant to 35 U.S.C. 151. Further, a record may be disclosed, subject to the limitations of 37 CFR 1.14, as a routine use, to the public if the record was filed in an application which became abandoned or in which the proceedings were terminated and which application is referenced by either a published application, an application open to public inspections or an issued patent.
- 9. A record from this system of records may be disclosed, as a routine use, to a Federal, State, or local law enforcement agency, if the USPTO becomes aware of a violation or potential violation of law or regulation.

Attorney Docket No. **1388-04** Customer No. **000061400**

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of	§	
DAO C.D. MOHAN	§	()- ()- ()- ()- ()- ()()- ()()()
RAO, G.R. MOHAN	§ 8	Confirmation No. 3086
Serial No. 11/622,496	§ §	Group Art Unit: 2892
Filed: 12 JANUARY 2007	ş	Examinan ADODA ALAV
rneu: 12 JANUARY 2007	8 §	Examiner: ARORA, AJAY
For: SEMICONDUCTOR DEVICES	§	
WITH GRADED DOPANT REGIONS	Ş	

AMENDMENT AND RESPONSE TO OFFICE ACTION MAILED JANUARY 6, 2009

I. INTRODUCTORY COMMENTS:

The present paper is submitted as a complete response to the final Office Action mailed January 6, 2009, having a shortened statutory period of response of three months. Applicant believes that a one month extension of time and the corresponding fees are necessary for the consideration of the present paper, such fees being paid contemporaneously with the filing of this paper. However, in the event that a further extension of time or any additional fees are necessary for consideration of the present paper, I authorize the Commissioner to charge such fees, including fees for extension of time, to Deposit Account No. 50-3886.

Amendments to the Claims begin on page 2 of this paper.

Remarks/Arguments begin on page 4 of this paper.
II. AMENDMENTS TO THE CLAIMS:

The text of all claims under examination is submitted, and the status of each is identified. This listing of claims replaces all prior versions and listings in the application.

Listing of Claims

Claims 1-2 (Cancelled)

3. (currently amended) A VLSI digital semiconductor device with graded dopant concentration in the well regions <u>and the active channel regions</u>, to aid carrier movement away from the active surface regions, towards the substrate.

4. (currently amended) A VLSI digital semiconductor device with graded dopant concentration in the <u>active channel regions, the well regions and the substrate region to aid carrier movement</u> away from the active surface regions, deeper towards the substrate.

5. (currently amended) A VLSI digital semiconductor device with at least one each of dopant concentration of both donor and acceptor in both the well and channel regions, to optimize the operating performance of the device.

6. (currently amended) A VLSI digital semiconductor device with at least one graded dopant concentration fabricated with ion implantation, to provide an aiding or retarding electric field locally. in both well and channel regions, in a monolithic integrated circuit.

7. (currently amended) A VLSI digital semiconductor device with at least one graded dopant concentration in an epitaxial layer where the epitaxial layer forms the substratum for well and channel regions.

8. (currently amended) A VLSI digital semiconductor device where one layer consisting of dopant <u>gradients in both well and channel regions</u> from one wafer, is transferred to another wafer having either same polarity or different polarity dopant through wafer bonding or similar processes.

III. REMARKS:

Claims 3 through 8 are pending herein.

Claims 1-2 have been cancelled without prejudice or disclaimer. Claims 3-8 have been amended, more particularly, to point out the claimed subject matter. It is respectfully submitted that Claims 3-8 are in full compliance with the broad dictates of 35 U.S.C. § 112. Favorable consideration of Claims 3-8 are respectfully requested.

Claims 3-8 stand rejected under 35 U.S.C. § 102(b) as being anticipated by various references more particularly described below. Insofar as these references may be applied against the present claims, this rejection is respectfully traversed.

Each of claims 3-8 have been amended to clarify that the claimed invention relates to the field of VLSI digital semiconductor devices which include graded dopant concentrations in both the active and well regions. By definition, a VLSI semiconductor device means a device consisting of at least one million active elements (an active element is a semiconductor transistor or gate consisting of at least two trnasistors) that can be active when a voltage (or current) is applied. By contrast, SSI (small scale integration) is 1 to 1,000 active elements, MSI (medium scale integration) is up to 100,000 active elements and LSI (large scale integration) is 100,000 to 1,000,000 active elements. As is more fully set forth below, each of the cited references pertains to non-VSLI non-digital technology.

Claims 3 and 6 stand rejected under 35 U.S.C. § 102(b) as being anticipated by Rhodes (US 2003/0042511), hereinafter Rhodes. Rhodes discloses a semiconductor based CMOS imaging device. Rhodes does not disclose or anticipate a VLSI digital semiconductor device.

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Rhodes describes a CMOS image sensor- but, his sensor elements only uses electrons (a CMOS gate, by strict text book definition has a n-channel transistor that conducts electrons and a p-channel transistor that conducts holes). The "graded dopant" as described by Rhodes, is only in the "sensing element." Rhodes may have one million sensors (he may have a few CMOS trnasistors in periphery on non image sensing function). However, that does not make the device in Rhodes VLSI and certainly not CMOS VLSI.

Further, Rhodes does not teach a graded dopant layer in both active and well regions.

In the present VLSI digital invention, every one of this 1 million (+) gates, albeit CMOS, has graded dopant for electrons as well as holes. Additionally, the present invention also allows more than one gradient for electrons and more than one gradient for holes. Neither Rhodes nor, for that matter, any of the other cited prior art show this novelty.

Claim 4 stands rejected under 35 U.S.C. § 102(b) as being anticipated by Cathey (US 2002/0093281), hereinafter Cathey. Cathey discloses an electron field emitter for use in computer or other display devices. Cathey does not disclose or anticipate a VLSI digital semiconductor device with graded dopant concentrations in both the active and well regions.

Claim 5 stands rejected under 35 U.S.C. § 102(b) as being anticipated by Kane (US 5,029,277), hereinafter Kane. Kane discloses a method for temperature compensation of a bipolar transistor junction through optically-induced carrier density enhancement. Kane does not disclose or anticipate a VLSI digital semiconductor device with graded dopant concentrations in both the active and well regions.

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Claim 7 stands rejected under 35 U.S.C. § 102(b) as being anticipated by Baliga (US 5,637,898), hereinafter Baliga. Baliga discloses a to semiconductor switching device for high power applications. Baliga does not disclose or anticipate a VLSI digital semiconductor device with graded dopant concentrations in both the active and well regions.

Claim 8 stands rejected under 35 U.S.C. § 102(b) as being anticipated by Macris (US 2002/0134419), hereinafter Macris. Macris discloses a heat sink. Macris does not disclose or anticipate a VLSI digital semiconductor device with graded dopant concentrations in both the active and well regions.

Accordingly, for the foregoing reasons, it is respectfully submitted that the cited references do not disclose or suggest the claimed VLSI digital semiconductor device with graded dopant concentrations in both the active and well regions. The rejection of claim 3-8 under 35 U.S.C. §102(b) as anticipated by the cited references should therefore be withdrawn. When read in light of the specification, Applicant submits that none of the foregoing amendments narrow the claims with regard to the claimed semiconductor device.

For all the foregoing reasons, it is respectfully submitted that claims 3-8 are in condition for allowance. Favorable reconsideration and allowance of claims 3-8 is respectfully requested.

Respectfully submitted,

Date: April 10, 2009

/Baxter W. Banowsky/ Baxter W. Banowsky Registration No: 58,170

BANOWSKY & LEVINE, P.C.

12001 N. Central Expressway Suite 790 Dallas, Texas 75243 (214) 871-1300 (214) 871-0038 (facsimile) Customer No. **000061400**

Electronic Patent Application Fee Transmittal								
Application Number:	116	522496						
Filing Date:	12-	Jan-2007						
Title of Invention: SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS								
First Named Inventor/Applicant Name: G.R. Mohan Rao								
Filer:	Filer: Baxter Ward Banowsky.							
Attorney Docket Number:	138	38-04						
Filed as Small Entity								
Utility under 35 USC 111(a) Filing Fees								
Description		Fee Code	Quantity	Amount	Sub-Total in USD(\$)			
Basic Filing:								
Pages:								
Claims:								
Miscellaneous-Filing:								
Petition:								
Patent-Appeals-and-Interference:								
Post-Allowance-and-Post-Issuance:								
Extension-of-Time:								
Extension - 1 month with \$0 paid		2251	1	65	65			

Description	Fee Code Quantity Amoun		Amount	Sub-Total in USD(\$)
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Request for continued examination	2801	1	405	405
	Tot) (\$)	470	

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EFS ID:	5133457						
Application Number:	11622496						
International Application Number:							
Confirmation Number:	3086						
Title of Invention:	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS						
First Named Inventor/Applicant Name:	G.R. Mohan Rao						
Customer Number:	61400						
Filer:	Baxter Ward Banowsky.						
Filer Authorized By:							
Attorney Docket Number:	1388-04						
Receipt Date:	10-APR-2009						
Filing Date:	12-JAN-2007						
Time Stamp:	11:52:58						
Application Type:	Utility under 35 USC 111(a)						

Payment information:

Submitted with Payment yes							
Payment Type	Payment Type Credit Card						
Payment was successfully received in RAM \$470							
RAM confirmation Number 6840							
Deposit Account 503886							
Authorized User BANOWSKY,BAXTER W.							
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Charge any Additional Fees required under 37 C.F.I	R. Section 1.17 (Patent application and reexamination processing fees)						

Charge any Additional Fees required under 37 C.F.R. Section 1.19 (Document supply fees)

Charge any Additional Fees required under 37 C.F.R. Section 1.20 (Post Issuance fees)

Charge any Additional Fees required under 37 C.F.R. Section 1.21 (Miscellaneous fees and charges)

Document Number	Document Description	File Name	File Size(Bytes)/ Message Digest	Multi Part /.zip	Pages (if appl.)		
1	Request for Continued Examination	rce.pdf	625825	20	3		
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Warnings:							
Information:							
2		0A_01-06-09_rsp.pdf	78798	yes	7		
2		0A_01-00-09_15p.pdf	9558007e9641fe4bcc3b3d9484fd7117181 b7053	yes	7		
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	Document Description Start End						
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	Claims		2	:	3		
	Applicant Arguments/Remarks	Made in an Amendment	4		7		
Warnings:							
Information:							
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If a new application is being filed and the application includes the necessary components for a filing date (see 37 CFR 1.53(b)-(d) and MPEP 506), a Filing Receipt (37 CFR 1.54) will be issued in due course and the date shown on this Acknowledgement Receipt will establish the filing date of the application.

National Stage of an International Application under 35 U.S.C. 371

If a timely submission to enter the national stage of an international application is compliant with the conditions of 35 U.S.C. 371 and other applicable requirements a Form PCT/DO/EO/903 indicating acceptance of the application as a national stage submission under 35 U.S.C. 371 will be issued in addition to the Filing Receipt, in due course.

New International Application Filed with the USPTO as a Receiving Office

If a new international application is being filed and the international application includes the necessary components for an international filing date (see PCT Article 11 and MPEP 1810), a Notification of the International Application Number and of the International Filing Date (Form PCT/RO/105) will be issued in due course, subject to prescriptions concerning national security, and the date shown on this Acknowledgement Receipt will establish the international filing date of the application.

Electronic Ac	Electronic Acknowledgement Receipt						
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Application Number:	11622496						
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Payment information:

Submitted with Payment yes							
Payment Type	Payment Type Credit Card						
Payment was successfully received in RAM \$470							
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Authorized User BANOWSKY, BAXTER W.							
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Charge any Additional Fees required under 37 C.F.R. S	ection 1.17 (Patent application and reexamination processing fees)						

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Charge any Additional Fees required under 37 C.F.R. Section 1.20 (Post Issuance fees)

Charge any Additional Fees required under 37 C.F.R. Section 1.21 (Miscellaneous fees and charges)

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Information: 78798 78798 95807/641164bcch3d94940(7117181 5807/641164bcch3d94940(7117181 Document Description/PDF files in .zip description Start 1 Amendment Submitted/Entered with Filing of CPA/RCE Applicant Arguments/Remarks Made in an Amendment 4 Start Start 2 Amendment Submitted/Entered with Filing of CPA/RCE Amendments/Remarks Made in an Amendment 4 342429 Start 344299 Start	5
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3 Fee Worksheet (PTO-06) fee-info.pdf no	
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PTO/SB/06 (07-06)

Approved for use through 1/31/2007. OMB 0651-0032 ademark Office; U.S. DEPARTMENT OF COMMERCE LLS Datent and Trad

P	ATENT APPLI	CATION FE Substitute for			N RECORD			Docket Number 2,496		ing Date 12/2007	To be Maile
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	505		(Column 1	· · ·	Column 2)		_		OR		
	FOR BASIC FEE	N	UMBER FIL	.ED NUM	MBER EXTRA	RATE (FEE (\$)		RATE (\$) N/A	FEE (\$)
-	(37 CFR 1.16(a), (b), o SEARCH FEE	or (c))					_				
-	(37 CFR 1.16(k), (i), o		N/A		N/A	N/A	_			N/A	
	(37 CFR 1.16(o), (p), o AL CLAIMS		N/A		N/A	N/A	_			N/A	
7 (CFR 1.16(i)) EPENDENT CLAIM	<u></u>	min	us 20 = *		X \$	=		OR	X\$ =	
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	04/10/2009	REMAINING AFTER AMENDMENT		NUMBER PREVIOUSLY PAID FOR	PRESENT EXTRA	RATE	(\$)	ADDITIONAL FEE (\$)		RATE (\$)	ADDITIONAL FEE (\$)
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process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.16. The information is required to obtain or retain a benefit by the public which is to ime (and by including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450, DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

If you need assistance in completing the form, call 1-800-PTO-9199 and select option 2.

	<u>ed States Patent a</u>	AND TRADEMARK OFFICE	UNITED STATES DEPAR United States Patent and Address: COMMISSIONER F P.O. Box 1450 Alexandria, Virginia 223 www.uspto.gov	Trademark Office FOR PATENTS
APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
11/622,496	01/12/2007	G.R. Mohan Rao	1388-04	3086
	7590 01/06/2009 &LEVINE, P.C		EXAM	INER
12001 N. CENT	TRAL EXPRESSWAY		ARORA	, AJAY
SUITE 790 DALLAS, TX 7	75243		ART UNIT	PAPER NUMBER
			2892	
			MAIL DATE	DELIVERY MODE
			01/06/2009	PAPER

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

		Application No.	Applicant(s)					
		11/622,496	RAO, G.R. MOHAN					
	Office Action Summary	Examiner	Art Unit					
		AJAY K. ARORA	2892					
Period fo	The MAILING DATE of this communication app or Reply	bears on the cover sheet v	vith the correspondence address					
WHIC - Exter after - If NC - Failu Any	ORTENED STATUTORY PERIOD FOR REPLY CHEVER IS LONGER, FROM THE MAILING D nsions of time may be available under the provisions of 37 CFR 1.1 SIX (6) MONTHS from the mailing date of this communication. Period for reply is specified above, the maximum statutory period v re to reply within the set or extended period for reply will, by statute reply received by the Office later than three months after the mailing ad patent term adjustment. See 37 CFR 1.704(b).	ATE OF THIS COMMUN 36(a). In no event, however, may a will apply and will expire SIX (6) MC , cause the application to become A	ICATION. reply be timely filed NTHS from the mailing date of this communication. BANDONED (35 U.S.C. § 133).					
Status								
1)	Responsive to communication(s) filed on 28 O	ctober 2008.						
/ /—		action is non-final.						
3)	3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is							
	closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.							
Dispositi	Disposition of Claims							
4)	• 4)⊠ Claim(s) <u>3-8</u> is/are pending in the application.							
· ·	4a) Of the above claim(s) is/are withdrawn from consideration.							
	5) Claim(s) is/are allowed.							
· · _ ·	6) Claim(s) $3-8$ is/are rejected.							
	Claim(s) is/are objected to.							
	Claim(s) are subject to restriction and/o	r election requirement.						
	on Papers							
-	The specification is objected to by the Examine							
10)	The drawing(s) filed on is/are∶a)∏ acc	· · · - ·	•					
	Applicant may not request that any objection to the							
_	Replacement drawing sheet(s) including the correct							
11)∐	The oath or declaration is objected to by the Ex	caminer. Note the attache	d Office Action or form PTO-152.					
Priority ι	ınder 35 U.S.C. § 119							
· · .	Acknowledgment is made of a claim for foreign ☐ All b)	priority under 35 U.S.C.	§ 119(a)-(d) or (f).					
,,.	1. Certified copies of the priority document	s have been received.						
	2. Certified copies of the priority document		Application No					
	3. Copies of the certified copies of the prio	rity documents have bee	n received in this National Stage					
	application from the International Burea	u (PCT Rule 17.2(a)).						
* 5	See the attached detailed Office action for a list	of the certified copies no	t received.					
Attachmen	t(s)							
1) 🗌 Notic	e of References Cited (PTO-892)		Summary (PTO-413)					
	e of Draftsperson's Patent Drawing Review (PTO-948)		(s)/Mail Date					
	nation Disclosure Statement(s) (PTO/SB/08) r No(s)/Mail Date	5) 🔛 Notice of 6) 🛄 Other:	Informal Patent Application					
U.S. Patent and T PTOL-326 (R	rademark Office	ction Summary	Part of Paper No./Mail Date 20090102					

DETAILED ACTION

Claim Rejections - 35 USC § 102

1. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless –

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

2. Claims 3 and 6 are rejected under 35 U.S.C. 102(b) as being anticipated by Rhodes (US 2003/0042511) of prior record, hereinafter Rhodes.

Regarding claim 3, Rhodes (refer to Figures 5-14) teaches a semiconductor device with graded dopant concentration (page 4, para 0046, 1st sentence) in the well regions (160, 170, 180) to aid carrier movement away from the active surface regions, towards the substrate (page 6, para 0061; page 4, para 0045 & 0049).

Regarding claim 6, Rhodes (US 2003/0042511) (refer to Figures 5-14) teaches a semiconductor device with at least one graded dopant concentration (page 4, para 0046, 1st sentence) fabricated with ion implantation (page 4, para 0047, last sentence), to provide an aiding or retarding electric field locally in a monolithic integrated circuit.

Note that claim 6 is a product claim but recites a method of steps therein, i.e. "fabricated with ion implantation". Therefore, claim 8 amounts to a product by process claim. "Even though product-by-process claims are limited by and defined by the process, determination of patentability is based on the product itself. The patentability of a product does not depend on its method of production. If the product in the product-by-process claim is the same as or obvious from a product of the prior art, the claim is unpatentable even though the prior product was made by a different process." In re Thorpe, 777 F.2d 695, 698, 227 USPQ 964, 966 (Fed. Cir. 1985). See MPEP 2113.

3. Claim 4 is rejected under 35 U.S.C. 102(b) as being anticipated by Cathey (US 2002/0093281) of prior record, hereinafter Cathey.

Regarding claim 4, Cathey teaches a semiconductor device with graded dopant concentration in the substrate (page 2, para 0027) region to aid carrier movement away from the active surface regions, deeper towards the substrate (page 3, claims 1, 5 and 6).

Claim 5 is rejected under 35 U.S.C. 102(b) as being anticipated by Kane (US 5,029,277) of prior record, hereinafter Kane.

Regarding claim 5, Kane teaches a semiconductor device with at least one each of dopant concentration of both donor and acceptor, to optimize the operating performance of the device (Col. 5, lines 5-40).

Page 4

5. Claim 7 is rejected under 35 U.S.C. 102(b) as being anticipated by Baliga (US 5,637,898) of prior record, hereinafter Baliga.

Regarding claim 7, Baliga (US 5,637,898) teaches a semiconductor device with at least one graded dopant concentration in an epitaxial layer (Col. 4, lines 15-21 and Col. 3, lines 45-50).

Claim 8 is rejected under 35 U.S.C. 102(b) as being anticipated by Macris (US 2002/0134419) of prior record, hereinafter Macris.

Regarding claim 8, Macris teaches a semiconductor device where one layer of dopant from one wafer, is transferred to another wafer having either same polarity or different polarity dopant through wafer bonding or similar processes (page 4, para 0076).

Note that claim 8 is a product claim but recites a method of steps therein, i.e. "one layer of dopant from one wafer, is transferred to another wafer" and "wafer bonding or similar processes". Therefore, claim 8 amounts to a product by process claim. *"Even though product-by-process claims are limited by and defined by the process, determination of*

patentability is based on the product itself. The patentability of a product does not depend on its method of production. If the product in the product-by-process claim is the same as or obvious from a product of the prior art, the claim is unpatentable even though the prior product was made by a different process." In re Thorpe, 777 F.2d 695, 698, 227 USPQ 964, 966 (Fed. Cir. 1985). See MPEP 2113.

Response to Arguments

7. Applicant's arguments filed 10/28/2008 have been fully considered but they are not persuasive.

8. In response to applicant's arguments, the recitation "A VLSI digital semiconductor device" (see claims 3-8) has not been given patentable weight because the recitation occurs in the preamble. A preamble is generally not accorded any patentable weight where it merely recites the purpose of a process or the intended use of a structure, and where the body of the claim does not depend on the preamble for completeness but, instead, the process steps or structural limitations are able to stand alone. See *In re Hirao*, 535 F.2d 67, 190 USPQ 15 (CCPA 1976) and *Kropa v. Robie*, 187 F.2d 150, 152, 88 USPQ 478, 481 (CCPA 1951).

9. In response to applicant's argument that the references fail to show certain features of applicant's invention, it is noted that the features upon which applicant relies

(i.e., "every one of this 1 million (+) gates, albeit CMOS, has graded dopant for electrons as well as holes" - see page 4, 2nd paragraph, of applicant's response) are not recited in the rejected claim(s). Although the claims are interpreted in light of the specification, limitations from the specification are not read into the claims. See *In re Van Geuns*, 988 F.2d 1181, 26 USPQ2d 1057 (Fed. Cir. 1993).

10. Other arguments presented by the applicant on page 4-5 are similar to the above addressed arguments.

Conclusion

11. **THIS ACTION IS MADE FINAL.** Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the mailing date of this final action.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to AJAY K. ARORA whose telephone number is (571)272-8347. The examiner can normally be reached on Mon through Fri, 8am to 4:30pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Thao X. Le can be reached on (571) 272-1708. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

/A. K. A./ Examiner, Art Unit 2892 /Thao X Le/ Supervisory Patent Examiner, Art Unit 2892

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	539	(257/655). CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/01/02 21:01

1/2/2009 9:08:30 PM

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Index of Claims					Application/C 11622496 Examiner AJAY K AROF		trol N	0.	Applica Reexar RAO, G Art Uni 2892	nina 6.R.	ation	tent Unde	9r	
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	Application/Control No.	Applicant(s)/Patent Under Reexamination
Search Notes	11622496	RAO, G.R. MOHAN
	Examiner	Art Unit
	AJAY K ARORA	2892

SEARCHED								
Class	Subclass	Date	Examiner					
257	655	1/2/2009	AKA					

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INTERFERENCE SEARCH							
Class	Subclass	Date	Examiner				

/A. K. A./	
Examiner.Art Unit 2892	

Attorney Docket No. **1388-04** Customer No. **000061400**

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Confirmation No. 3086
Group Art Unit: 2892
Examiner: ARORA, AJAY

AMENDMENT AND RESPONSE TO OFFICE ACTION MAILED JULY 28, 2008

I. INTRODUCTORY COMMENTS:

The present paper is submitted as a complete response to the non-final Office Action mailed July 28, 2008 having a shortened statutory period of response of three months. Applicant does not believe that any extension of time or any additional fees are necessary for the consideration of the present paper. However, in the event that an extension of time or any additional fees are necessary for consideration of the present paper, I authorize the Commissioner to charge such fees, including fees for extension of time, to Deposit Account No. 50-3886.

Amendments to the Claims begin on page 2 of this paper.

Remarks/Arguments begin on page 3 of this paper.

II. AMENDMENTS TO THE CLAIMS:

The text of all claims under examination is submitted, and the status of each is identified. This listing of claims replaces all prior versions and listings in the application.

Listing of Claims

Claims 1-2 (Cancelled)

3. (currently amended) A <u>VLSI digital</u> semiconductor device with graded dopant concentration in the well regions, to aid carrier movement away from the active surface regions, towards the substrate.

4. (currently amended) A <u>VLSI digital</u> semiconductor device with graded dopant concentration in the substrate region to aid carrier movement away from the active surface regions, deeper towards the substrate.

(currently amended) A <u>VLSI digital</u> semiconductor device with at least one each of dopant concentration of both donor and acceptor, to optimize the operating performance of the device.
 (currently amended) A <u>VLSI digital</u> semiconductor device with at least one graded dopant concentration fabricated with ion implantation, to provide an aiding or retarding electric field locally in a monolithic integrated circuit.

7. (currently amended) A <u>VLSI digital</u> semiconductor device with at least one graded dopant concentration in an epitaxial layer.

8. (currently amended) A <u>VLSI digital</u> semiconductor device where one layer of dopant from one wafer, is transferred to another wafer having either same polarity or different polarity dopant through wafer bonding or similar processes.

III. REMARKS:

Claims 3 through 8 are pending herein.

Claims 1-2 have been cancelled without prejudice or disclaimer. Claims 3-8 have been amended, more particularly, to point out the claimed subject matter. It is respectfully submitted that Claims 3-8 are in full compliance with the broad dictates of 35 U.S.C. § 112. Favorable consideration of Claims 3-8 are respectfully requested.

Claims 3-8 stand rejected under 35 U.S.C. § 102(b) as being anticipated by various references more particularly described below. Insofar as these references may be applied against the present claims, this rejection is respectfully traversed.

Each of claims 3-8 have been amended to clarify that the claimed invention relates to the field of VLSI digital semiconductor devices. By definition, a VLSI semiconductor device means a device consisting of at least one million active elements (an active element is a semiconductor transistor or gate consisting of at least two trnasistors) that can be active when a voltage (or current) is applied. By contrast, SSI (small scale integration) is 1 to 1,000 active elements, MSI (medium scale integration) is up to 100,000 active elements and LSI (large scale integration) is 100,000 to 1,000,000 active elements. As is more fully set forth below, each of the cited references pertains to non-VSLI non-digital technology.

Claims 3 and 6 stand rejected under 35 U.S.C. § 102(b) as being anticipated by Rhodes (US 2003/0042511), hereinafter Rhodes. Rhodes discloses a semiconductor based CMOS imaging device. Rhodes does not disclose or anticipate a VLSI digital semiconductor device.

Rhodes describes a CMOS image sensor- but, his sensor elements only uses electrons (a CMOS gate, by strict text book definition has a n-channel transistor that conducts electrons and a p-channel transistor that conducts holes). The "graded dopant" as described by Rhodes, is only in the "sensing element." Rhodes may have one million sensors (he may have a few CMOS transistors in periphery on non image sensing function). However, that does not make the device in Rhodes VLSI and certainly not CMOS VLSI.

In the present VLSI digital invention, every one of this 1 million (+) gates, albeit CMOS, has graded dopant for electrons as well as holes. Additionally, the present invention also allows more than one gradient for electrons and more than one gradient for holes. Neither Rhodes nor, for that matter, any of the other cited prior art show this novelty.

Claim 4 stands rejected under 35 U.S.C. § 102(b) as being anticipated by Cathey (US 2002/0093281), hereinafter Cathey. Cathey discloses an electron field emitter for use in computer or other display devices. Cathey does not disclose or anticipate a VLSI digital semiconductor device.

Claim 5 stands rejected under 35 U.S.C. § 102(b) as being anticipated by Kane (US 5,029,277), hereinafter Kane. Kane discloses a method for temperature compensation of a bipolar transistor junction through optically-induced carrier density enhancement. Kane does not disclose or anticipate a VLSI digital semiconductor device.

Claim 7 stands rejected under 35 U.S.C. § 102(b) as being anticipated by Baliga (US 5,637,898), hereinafter Baliga. Baliga discloses a to semiconductor switching device for high power applications. Baliga does not disclose or anticipate a VLSI digital semiconductor device.

Claim 8 stands rejected under 35 U.S.C. § 102(b) as being anticipated by Macris (US 2002/0134419), hereinafter Macris. Macris discloses a heat sink. Macris does not disclose or anticipate a VLSI digital semiconductor device.

Accordingly, for the foregoing reasons, it is respectfully submitted that the cited references do not disclose or suggest the claimed VLSI digital semiconductor device. The rejection of claim 3-8 under 35 U.S.C. §102(b) as anticipated by the cited references should therefore be withdrawn. When read in light of the specification, Applicant submits that none of the foregoing amendments narrow the claims with regard to the claimed semiconductor device.

For all the foregoing reasons, it is respectfully submitted that claims 3-8 are in condition for allowance. Favorable reconsideration and allowance of claims 3-8 is respectfully requested. Respectfully submitted,

Date: October 28, 2008

/Baxter W. Banowsky/ Baxter W. Banowsky Registration No: 58,170

BANOWSKY & LEVINE, P.C.

12001 N. Central Expressway Suite 790 Dallas, Texas 75243 (214) 871-1300 (214) 871-0038 (facsimile) Customer No. **000061400**

Electronic Ac	knowledgement Receipt
EFS ID:	4187673
Application Number:	11622496
International Application Number:	
Confirmation Number:	3086
Title of Invention:	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS
First Named Inventor/Applicant Name:	G.R. Mohan Rao
Customer Number:	61400
Filer:	Baxter Ward Banowsky.
Filer Authorized By:	
Attorney Docket Number:	1388-04
Receipt Date:	28-OCT-2008
Filing Date:	12-JAN-2007
Time Stamp:	12:38:01
Application Type:	Utility under 35 USC 111(a)

Payment information:

Submitted wi	th Payment	no	no							
File Listing:										
Document Number	Document Description	File Name	File Size(Bytes)/ Message Digest	Multi Part /.zip	Pages (if appl.)					
1		OA07_28_08_rsp.pdf	95157	yes	5					
'		0/10/_20_00_130.041	946d28a7cd361b68ab61b5db9f538127f39 5c268	yes	5					

	Multipart Description/PDF files in .zip description							
	Document Description	Start	End					
	Extension of Time	1	1					
	Claims	2	2					
	Applicant Arguments/Remarks Made in an Amendment	3	5					
Warnings:								
Information:								
	Total Files Size (in bytes):	95	157					

This Acknowledgement Receipt evidences receipt on the noted date by the USPTO of the indicated documents, characterized by the applicant, and including page counts, where applicable. It serves as evidence of receipt similar to a Post Card, as described in MPEP 503.

New Applications Under 35 U.S.C. 111

If a new application is being filed and the application includes the necessary components for a filing date (see 37 CFR 1.53(b)-(d) and MPEP 506), a Filing Receipt (37 CFR 1.54) will be issued in due course and the date shown on this Acknowledgement Receipt will establish the filing date of the application.

National Stage of an International Application under 35 U.S.C. 371

If a timely submission to enter the national stage of an international application is compliant with the conditions of 35 U.S.C. 371 and other applicable requirements a Form PCT/DO/EO/903 indicating acceptance of the application as a national stage submission under 35 U.S.C. 371 will be issued in addition to the Filing Receipt, in due course.

New International Application Filed with the USPTO as a Receiving Office

If a new international application is being filed and the international application includes the necessary components for an international filing date (see PCT Article 11 and MPEP 1810), a Notification of the International Application Number and of the International Filing Date (Form PCT/RO/105) will be issued in due course, subject to prescriptions concerning national security, and the date shown on this Acknowledgement Receipt will establish the international filing date of the application.

PTO/SB/06 (07-06)

Approved for use through 1/31/2007. OMB 0651-0032 U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

P/	Under the Pap			pplication or l	Docket Number	Application of information unless it displays a valid ON Application or Docket Number 11/622,496 01/12/2007		OMB control number.			
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	FOR	N	JMBER FIL	ED NUN	IBER EXTRA		RATE (\$)	FEE (\$)		RATE (\$)	FEE (\$)
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	SEARCH FEE (37 CFR 1.16(k), (i), c	or (m))	N/A		N/A		N/A			N/A	
	EXAMINATION FE (37 CFR 1.16(o), (p), o	-	N/A		N/A		N/A			N/A	
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L Z	Independent (37 CFR 1.16(h))	* 6	Minus	***8	= 0		X \$110 =	0	OR	X \$ =	
AMENDMENT	Application Si	ze Fee (37 CFR 1	.16(s))								
		ITATION OF MULTIF	LE DEPEN	DENT CLAIM (37 CFF	R 1.16(j))				OR		
						• •	total Add'l Fee	0	OR	total Add'l Fee	
		(Column 1)		(Column 2)	(Column 3)						
		CLAIMS REMAINING AFTER AMENDMENT		HIGHEST NUMBER PREVIOUSLY PAID FOR	PRESENT EXTRA		RATE (\$)	ADDITIONAL FEE (\$)		RATE (\$)	ADDITIONAL FEE (\$)
AMENDMENT	Total (37 CFR 1.16(i))	*	Minus	**	=		X \$ =		OR	X \$ =	
DM	Independent (37 CFR 1.16(h))	*	Minus	***	=		X\$ =		OR	X \$ =	
μ Π	Application Si	ze Fee (37 CFR 1	.16(s))								
AN	FIRST PRESEN	ITATION OF MULTIF	LE DEPEN	DENT CLAIM (37 CFF	R 1.16(j))				OR		
** lf *** l	* If the entry in column 1 is less than the entry in column 2, write *0" in column 3. ** If the "Highest Number Previously Paid For" IN THIS SPACE is less than 20, enter "20". *** If the "Highest Number Previously Paid For" IN THIS SPACE is less than 3, enter "3". The "Highest Number Previously Paid For" (Total or Independent) is the highest number found in the appropriate box in column 1.										
Thie c	his collection of information is required by 37 CFR 1.16. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to										

process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.16. The information is required to obtain or retain a benefit by the public which is to ime (and by including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450, DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

If you need assistance in completing the form, call 1-800-PTO-9199 and select option 2.

	ed States Patent	AND TRADEMARK OFFICE	UNITED STATES DEPAR United States Patent and Address: COMMISSIONER F P.O. Box 1450 Alexandria, Virginia 22: www.uspto.gov	FOR PATENTS
APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
11/622,496	01/12/2007	G.R. Mohan Rao	1388-04	3086
	7590 07/28/2008 &LEVINE, P.C		EXAM	IINER
12001 N. CEN	TRAL EXPRESSWAY		ARORA	, AJAY
SUITE 790 DALLAS, TX ⁷	75243		ART UNIT	PAPER NUMBER
			2892	
			MAIL DATE	DELIVERY MODE
			07/28/2008	PAPER

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

		Application No.	Applicant(s)		
		11/622,496	RAO, G.R. M	IOHAN	
	Office Action Summary	Examiner	Art Unit		
		AJAY K. ARORA	2892		
The MAILING DATE of this communication appears on the cover sheet with the correspondence address Period for Reply					
 A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE <u>3</u> MONTH(S) OR THIRTY (30) DAYS, WHICHEVER IS LONGER, FROM THE MAILING DATE OF THIS COMMUNICATION. Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication. If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication. Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earmed patent term adjustment. See 37 CFR 1.704(b). 					
Status					
1)🛛	Responsive to communication(s) filed on 13	3 May 2008.			
·		his action is non-fina			
3)	Since this application is in condition for allowance except for formal matters, prosecution as to the merits is				
	closed in accordance with the practice under Ex parte Quayle, 1935 C.D. 11, 453 O.G. 213.				
Disposit	on of Claims				
4)⊠ Claim(s) <u>1-8</u> is/are pending in the application.					
4a) Of the above claim(s) <u>1 and 2</u> is/are withdrawn from consideration.					
5) Claim(s) is/are allowed.					
6) Claim(s) $3-8$ is/are rejected.					
7) Claim(s) is/are objected to.					
8) Claim(s) are subject to restriction and/or election requirement.					
	on Papers				
9) The specification is objected to by the Examiner.					
10) The drawing(s) filed on is/are: a) accepted or b) discted to by the Examiner.					
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).					
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).					
11) The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.					
Priority u	ınder 35 U.S.C. § 119				
12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).					
a) All b) Some * c) None of: 1. Certified copies of the priority documents have been received.					
2. Certified copies of the priority documents have been received in Application No					
	3. Copies of the certified copies of the priority documents have been received in this National Stage				
* (application from the International Bureau (PCT Rule 17.2(a)).				
* See the attached detailed Office action for a list of the certified copies not received.					
l					
Attachmen	t(s)				
	e of References Cited (PTO-892)		nterview Summary (PTO-413)		
	e of Draftsperson's Patent Drawing Review (PTO-948)		Paper No(s)/Mail Date lotice of Informal Patent Applicatior		
	nation Disclosure Statement(s) (PTO/SB/08) r No(s)/Mail Date	· =	Other:		
J.S. Patent and T PTOL-326 (F		e Action Summary	Part of Paper No./N	Apil Dato 20080718	
Election/Restrictions

1. Applicant's election of embodiment 3, claims 3-8 in the reply filed on 05/13/2008 is acknowledged. Because examiner agrees that claims 3-8 are generic to all embodiments as stated by applicant on page 2, lines 12-13 of applicant's response, as a condition for election without traverse, and applicant did not distinctly and specifically point out any additional supposed errors in the restriction requirement, the election has been treated as an election without traverse (MPEP § 818.03(a)).

Claim Rejections - 35 USC § 102

2. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless –

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

3. Claims 3 and 6 are rejected under 35 U.S.C. 102(b) as being anticipated by Rhodes (US 2003/0042511), hereinafter Rhodes.

Regarding claim 3, Rhodes (refer to Figures 5-14) teaches a semiconductor device with graded dopant concentration (page 4, para 0046, 1st sentence) in the well regions (160, 170, 180) to aid carrier movement away from the active surface regions, towards the substrate (page 6, para 0061; page 4, para 0045 & 0049).

Regarding claim 6, Rhodes (US 2003/0042511) (refer to Figures 5-14) teaches a semiconductor device with at least one graded dopant concentration (page 4, para 0046, 1st sentence) fabricated with ion implantation (page 4, para 0047, last sentence), to provide an aiding or retarding electric field locally in a monolithic integrated circuit.

Note that claim 6 is a product claim but recites a method of steps therein, i.e. "fabricated with ion implantation". Therefore, claim 8 amounts to a product by process claim. "Even though product-by-process claims are limited by and defined by the process, determination of patentability is based on the product itself. The patentability of a product does not depend on its method of production. If the product in the product-by-process claim is the same as or obvious from a product of the prior art, the claim is unpatentable even though the prior product was made by a different process." In re Thorpe, 777 F.2d 695, 698, 227 USPQ 964, 966 (Fed. Cir. 1985). See MPEP 2113.

4. Claim 4 is rejected under 35 U.S.C. 102(b) as being anticipated by Cathey (US 2002/0093281), hereinafter Cathey.

Regarding claim 4, Cathey teaches a semiconductor device with graded dopant concentration in the substrate (page 2, para 0027) region to aid carrier movement away from the active surface regions, deeper towards the substrate (page 3, claims 1, 5 and 6).

5. Claim 5 is rejected under 35 U.S.C. 102(b) as being anticipated by Kane (US 5,029,277), hereinafter Kane.

Regarding claim 5, Kane teaches a semiconductor device with at least one each of dopant concentration of both donor and acceptor, to optimize the operating performance of the device (Col. 5, lines 5-40).

Claim 7 is rejected under 35 U.S.C. 102(b) as being anticipated by Baliga (US 5,637,898), hereinafter Baliga.

Regarding claim 7, Baliga (US 5,637,898) teaches a semiconductor device with at least one graded dopant concentration in an epitaxial layer (Col. 4, lines 15-21 and Col. 3, lines 45-50).

Claim 8 is rejected under 35 U.S.C. 102(b) as being anticipated by Macris (US 2002/0134419), hereinafter Macris.

Regarding claim 8, Macris teaches a semiconductor device where one layer of dopant from one wafer, is transferred to another wafer having either same polarity or different polarity dopant through wafer bonding or similar processes (page 4, para 0076).

Note that claim 8 is a product claim but recites a method of steps therein, i.e. "one layer of dopant from one wafer, is transferred to another wafer" and "wafer bonding or similar processes". Therefore, claim 8 amounts to a product by process claim. *"Even though product-by-process claims are limited by and defined by the process, determination of patentability is based on the product itself. The patentability of a product does not depend on its method of production. If the product in the product-by-process claim is the same as or obvious from a product of the prior art, the claim is unpatentable even though the prior product was made by a different process." In re Thorpe, 777 F.2d 695, 698, 227 USPQ 964, 966 (Fed. Cir. 1985). See MPEP 2113.*

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to AJAY K. ARORA whose telephone number is (571)272-8347. The examiner can normally be reached on Mon through Fri, 8am to 4:30pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Thao X. Le can be reached on (571) 272-1708. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

/A. K. A./ Examiner, Art Unit 2892 /Thao X Le/ Supervisory Patent Examiner, Art Unit 2892

Notice of References Cited	Application/Control No. 11/622,496	Applicant(s)/Patent Under Reexamination RAO, G.R. MOHAN				
Notice of References Cited	Examiner	Art Unit				
	AJAY K. ARORA	2892	Page 1 of 1			

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	А	US-2003/0042511	03-2003	Rhodes, Howard E.	257/232
*	В	US-2002/0093281	07-2002	Cathey, David A.	313/336
*	С	US-5,029,277	07-1991	Kane, Robert C.	250/214C
*	D	US-5,637,898	06-1997	Baliga, Bantval J.	257/330
*	Е	US-2002/0134419	09-2002	Macris, Chris	136/204
	F	US-			
	G	US-			
	Т	US-			
	Ι	US-			
	J	US-			
	К	US-			
	L	US-			
	М	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
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NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).) Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.

	Index of Claims				Application/Control No. 11622496 Examiner AJAY K ARORA			Applicant(s)/Patent Under Reexamination RAO, G.R. MOHAN Art Unit 2892						
✓ Rejected -		С	Cancelled N		N	Non-Ele	ected	ected A		Appeal				
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	Claims r	enumbered	in the s	ame o	order as	s presented by ap	plica	ant		СРА] Т.D). 🗆	R.1.47
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	Application/Control No.	Applicant(s)/Patent Under Reexamination
Search Notes	11622496	RAO, G.R. MOHAN
	Examiner	Art Unit
	AJAY K ARORA	2892

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Class	Subclass	Date	Examiner
257	655, 269	7/24/2008	AKA

Date	Examiner
7/24/2008	AKA

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Class	Subclass	Date	Examiner



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UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Address: COMMISSIONER FOR PATENTS P.O. Box 1450 Alexandria, Virginia 22313-1450 www.uspto.gov

BIB DATA SHEET

CONFIRMATION NO. 3086

SERIAL NUMBER	FILING or 371(c) DATE	CLASS	GROUP ART	UNIT	ATTORNEY DOCKE NO.				
11/622,496	01/12/2007	257	2892		1388-04				
	RULE								
APPLICANTS G.R. Mohan Ra	o, McKinney, TX;								
	A ************************************								
** FOREIGN APPLIC	ATIONS *********************	*****							
** IF REQUIRED, FOI 02/08/2007	REIGN FILING LICENS	E GRANTED ** ** SMA	LL ENTITY **						
Foreign Priority claimed 35 USC 119(a-d) conditions me	□ Yes ☑ No et □ Yes ☑ No □ Met af Allowa	ter Ince STATE OR COUNTRY	SHEETS DRAWINGS	TOTA CLAIN					
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UNITED STATE	S								
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	FILING FEE FEES: Authority has been given in Paper BECEIVED No								
	for following		🖵 1.18 F	ees (lss	ue)				
			C Other						
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EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp	
L1	579	(257/655,269).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/24 09:14	
S1	2	("20070158790").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/04/08 11:10	
82	58	("20020074585" "20040063288" "4001864" "4347654" "4866000" "5130262" "5213988" "5329144" "5480816" "5496746" "5569612" "5575862" "5797999" "6211028" "6452086" "6472715" "6670544" "6683343" "6696314" "6706550" "6713813" "6737722" "6744117" "6747883" "6753202" "6754093" "6756616" "RE37441"). PN.	2" JPO; 4" DERWENT; 6" IBM_TDB 2" 8" 5" 3" 2" 3" 3"	OR	ON	2008/04/08 11:19	
S3	1096	(graded OR gradation) WITH (dopant OR doping) WITH concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/08 11:47	
S4	805	S3 AND ("257" OR "438").clas.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/08 11:47	
S5	253	(graded OR gradation) WITH (dopant OR doping) WITH concentration WITH (semiconductor OR silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/08 11:49	

S6	7	S5 SAME (carrier WITH (movement OR mobility))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/08 11:51
S7	48	S5 AND (((carrier OR electron OR hole) WITH (movement OR mobility)) SAME ((emitter WITH collector) OR (source WITH drain)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/08 11:55
S 8	58	("20020074585" "20040063288" "4001864" "4347654" "4866000" "5130262" "5213988" "5329144" "5480816" "5496746" "5569612" "5575862" "5797999" "6211028" "6452086" "6472715" "6670544" "6683343" "6696314" "6706550" "6713813" "6737722" "6744117" "6747883" "6753202" "6754093" "6756616" "RE37441"). PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/18 12:16
S9	13	S8 AND ("dopant concentration" OR "concentratino of dopant")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/18 12:16
S10	13	S8 AND ("dopant concentration" OR "concentration of dopant")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/18 12:17
S11			US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/18 12:22

S12	1136 (graded OR gradation) WITH (dopant OR doping) WITH concentration		US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/18 12:22
S13	86	S12 AND (dop\$3 WITH (concentrat\$3 OR amount OR quantity) WITH (variable OR varying OR grad\$3)) AND ((doping OR dopant) WITH well) AND ((carrier OR charge) WITH (moving OR movement OR mobile OR mobility))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/18 12:22
S14	29	("20020068409" "6303450" "6437406" "6458665" "6483158" "6489223" "6509241"). PN. OR ("6743684"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/07/18 13:13
S15	34	uniform\$2 WITH dop\$3 WITH drift WITH epitaxial	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/23 15:19
S16	2	("5637898").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/23 15:26
S17	0	(non-uniform\$2 OR nonuniform\$2 OR grad43 OR grading OR gradient) WITH (dopant OR doping) WITH well WITH carrier WITH (movement OR mobility) WITH ((away WITH active WITH surface) OR (towards WITH substrate))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/23 15:40

S18	4	(non-uniform\$2 OR nonuniform\$2 OR grad\$3 OR grading OR gradient) WITH (dopant OR doping) WITH well WITH carrier WITH (movement OR mobility) WITH ((away WITH active WITH surface) OR (towards WITH substrate))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/23 15:40
S19	4	("4001864").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/23 15:43
S20	58	("20020074585" "20040063288" "4001864" "4347654" "4866000" "5130262" "5213988" "5329144" "5480816" "5496746" "5569612" "5575862" "5797999" "6211028" "6452086" "6472715" "6670544" "6683343" "6696314" "6706550" "6713813" "6737722" "6744117" "6747883" "6753202" "6754093" "6756616" "RE37441"). PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/23 15:57
S21	92	S15 S19 S20	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/23 15:58
S22	39	S21 AND ((non-uniform \$2 OR nonuniform\$2 OR grad\$3 OR grading OR gradient) WITH (dopant OR doping))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/23 15:58
S23	60	S21 AND well	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM TDB	OR	ON	2008/07/23 15:59

S24	39	S22 AND well	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/23 15:59
S25	2	S22 AND (well WITH carrier WITH (movement OR mobility) WITH ((away WITH active WITH surface) OR (towards WITH substrate)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/23 16:00
S26	3 S22 AND (well WITH (carrier OR movement OR mobility) WITH ((away WITH active WITH surface) OR (towards WITH substrate)))		US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/23 16:00
S27	2 ("20030042511").PN.		US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/23 16:05
S28	2	S21 AND (substrate WITH carrier WITH away WITH ((active WITH surface) OR (towards NEAR2 substrate) OR (direction NEAR4 substrate)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/23 17:17
S29	3	S21 AND (substrate WITH (carrier OR holes OR electron OR majority OR charge) WITH away WITH ((active WITH surface) OR (towards NEAR2 substrate) OR (direction NEAR4 substrate)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/23 17:18
S30	30	S21 AND ((non-uniform \$2 OR nonuniform\$2 OR grad\$3 OR grading OR gradient) WITH (dopant OR doping) WITH substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/23 17:26

S31	253	(grad\$3 OR grading OR gradient) NEAR2 (dopant OR doping) NEAR4 substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/23 17:33
S32	5	dopant WITH concentration WITH donor WITH acceptor WITH optimiz\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/23 18:02
	2	10/182,784	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/23 18:06
S34	0	S20 AND (dopant WITH concentration WITH donor WITH acceptor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/23 18:22
S35	0	S20 AND (dopant WITH donor WITH acceptor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/23 18:22
\$36	5	(dopant WITH donor WITH acceptor WITH optimiz\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/23 18:26
\$37	5	(dopant WITH donor WITH acceptor WITH (optimiz\$ OR optimization OR optimal))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/23 18:27
S38	487	(donor WITH acceptor WITH (optimiz\$ OR optimization OR optimal))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/23 18:27

S 39	14	S38 AND semiconductor. ab.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/23 18:28
S40	0	(layer WITH dopant WITH wafer WITH transfer\$4 WITH ((another OR second OR alternate) NEAR1 wafer)) AND (wafer NEAR1 bond \$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/23 18:49
S41	0	(dopant WITH wafer WITH transfer\$4 WITH ((another OR second OR alternate) NEAR1 wafer)) AND (wafer NEAR1 bond \$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/23 18:49
S42	0	(dopant WITH transfer\$4 WITH ((another OR second OR alternate) NEAR1 wafer)) AND (wafer NEAR1 bond\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/23 18:50
S43	0	(dopant WITH transfer\$4 WITH ((another OR second OR alternate) NEAR1 wafer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/23 18:50
S44	14807	wafer NEAR1 bond\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/23 18:51
S45	33	S44 AND (dopant WITH transfer\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/23 18:51

7/24/2008 9:26:20 AM

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of	§	
	§	
RAO, G.R. MOHAN	§	Confirmation No. 3086
	§	
Serial No. 11/622,496	§	Group Art Unit: 2892
	§	
Filed: 12 JANUARY 2007	§	Examiner: AJAY K. ARORA
	§	
For: SEMICONDUCTOR DEVICES	§	
WITH GRADED DOPANT REGIONS	§	

ELECTION UNDER 35 U.S.C. § 121

This paper is in response to the restriction requirement set forth in the Office Action mailed April 15, 2008, having a one month shortened statutory period for response, wherein the Examiner required restriction between the following embodiments:

Embodiment 1	-	Figure 4
Embodiment 2	-	Figure 5(a)
Embodiment 3	-	Figures 5(b) and 5(c)

Applicant elects Embodiment 3 for initial prosecution on the merits. Applicant identifies Claims 3 through 8 as encompassing the elected species.

Applicant notes that the examiner has determined that no claims are generic. Applicant respectfully traverses this finding and asserts that claims 3-8 are generic as to all embodiments. Initially, Applicant notes that this is a division application of Application Serial No. 10/934,915. In Application Serial No. 10/934,915 the Office issued an election/restriction requirement similar to the present office action. In that office action, dated March 28, 2006, the office asserted that claim 8 in the present application (claim 9 in Application Serial No. 10/934,915)

was generic as to all species. Additionally, the office asserted that claim 7 in the present application (claim 8 in Application Serial No. 10/934,915) was generic as to embodiments 1 and 3.

With the exception of Fig. 4 and the references to it in the specification, the balance of the specification and illustrations are of CMOS technology. A CMOS device has both p-ch and n-ch transistors (and both p and n wells). Accordingly, graded dopant concentrations have to be "optimized" for both donors and acceptors. Further, sweeping away minority carriers with donor gradient is generic to all of the embodiments as set forth in paragraph 12 of the specification with respect to IGBT and paragraph 13 with respect to CMOS. Additionally, although the epitaxial layer is only illustrated in Fig. 4, it is referred to in paragraph 13 as being applicable to the CMOS devices of Figs. 5(a), (b) and (c).

To the extent that the examiner agrees with Applicant that claims 3 through 8 are generic, then this election may be considered without traverse.

Applicant reserves the right to file one or more Divisional Applications for the nonelected inventions which the Examiner has indicated are patentably distinct.

Applicant does not believe that any extension of time or any additional fees are necessary for the consideration of the present paper. However, in the event that an extension of time or any additional fees are necessary for consideration of the present paper, I authorize the Commissioner to charge such fees, including fees for extension of time, to Deposit Account No. 50-3886.

2

342

Attorney Docket No. **1388-04** Customer No. **61400**

Respectfully submitted,

Date: May 13, 2008

<u>/s/ Baxter W. Banowsky</u> Baxter W. Banowsky Registration No: 58,170

BANOWSKY & LEVINE, P.C.

12001 N. Central Expressway Suite 790 Dallas, Texas 75243 (214) 871-1300 (214) 871-0038 (facsimile) Customer No. **61400**

Electronic Acl	knowledgement Receipt
EFS ID:	3293940
Application Number:	11622496
International Application Number:	
Confirmation Number:	3086
Title of Invention:	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS
First Named Inventor/Applicant Name:	G.R. Mohan Rao
Customer Number:	61400
Filer:	Baxter Ward Banowsky.
Filer Authorized By:	
Attorney Docket Number:	1388-04
Receipt Date:	13-MAY-2008
Filing Date:	12-JAN-2007
Time Stamp:	10:54:17
Application Type:	Utility under 35 USC 111(a)

Payment information:

Submitted wit	th Payment	no							
File Listin	ıg:								
Document Number	Document Description	File Name	File Size(Bytes) /Message Digest	Multi Part /.zip	Pages (if appl.)				
1	Response to Election / Restriction	election.pdf	82764		3				
1	Filed	election.pdf	712fac00bdb00669b974700556a19ee7 05446d44	no	3				
Warnings:									
Information:									

This Acknowledgement Receipt evidences receipt on the noted date by the USPTO of the indicated documents, characterized by the applicant, and including page counts, where applicable. It serves as evidence of receipt similar to a Post Card, as described in MPEP 503.

New Applications Under 35 U.S.C. 111

If a new application is being filed and the application includes the necessary components for a filing date (see 37 CFR 1.53(b)-(d) and MPEP 506), a Filing Receipt (37 CFR 1.54) will be issued in due course and the date shown on this Acknowledgement Receipt will establish the filing date of the application.

National Stage of an International Application under 35 U.S.C. 371

If a timely submission to enter the national stage of an international application is compliant with the conditions of 35 U.S.C. 371 and other applicable requirements a Form PCT/DO/EO/903 indicating acceptance of the application as a national stage submission under 35 U.S.C. 371 will be issued in addition to the Filing Receipt, in due course.

New International Application Filed with the USPTO as a Receiving Office

If a new international application is being filed and the international application includes the necessary components for an international filing date (see PCT Article 11 and MPEP 1810), a Notification of the International Application Number and of the International Filing Date (Form PCT/RO/105) will be issued in due course, subject to prescriptions concerning national security, and the date shown on this Acknowledgement Receipt will establish the international filing date of the application.

	<u>ed States Patent a</u>	AND TRADEMARK OFFICE	UNITED STATES DEPAR United States Patent and Address: COMMISSIONER F P.O. Box 1450 Alexandria, Virginia 22: www.uspto.gov	FOR PATENTS
APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
11/622,496	01/12/2007	G.R. Mohan Rao	1388-04	3086
	7590 04/15/2008 &LEVINE, P.C		EXAM	IINER
12001 N. CEN	TRAL EXPRESSWAY		ARORA	, AJAY
SUITE 790 DALLAS, TX '	75243		ART UNIT	PAPER NUMBER
			2892	
			MAIL DATE	DELIVERY MODE
			04/15/2008	PAPER

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

		Application No.	Applicant(s)
		11/622,496	RAO, G.R. MOHAN
	Office Action Summary	Examiner	Art Unit
		AJAY K. ARORA	2892
Period fo	The MAILING DATE of this communication app or Reply	pears on the cover sheet with the	correspondence address
WHIC - Exte after - If NC - Failu Any	ORTENED STATUTORY PERIOD FOR REPL CHEVER IS LONGER, FROM THE MAILING D nsions of time may be available under the provisions of 37 CFR 1.1 SIX (6) MONTHS from the mailing date of this communication. Deperiod for reply is specified above, the maximum statutory period re to reply within the set or extended period for reply will, by statute reply received by the Office later than three months after the mailing ed patent term adjustment. See 37 CFR 1.704(b).	ATE OF THIS COMMUNICATIO (36(a). In no event, however, may a reply be ti will apply and will expire SIX (6) MONTHS from e, cause the application to become ABANDON	N. mely filed n the mailing date of this communication. ED (35 U.S.C. § 133).
Status			
1)🖂	Responsive to communication(s) filed on <u>12 Ja</u>	anuarv 2007.	
· · _	· · ·	s action is non-final.	
3)	Since this application is in condition for allowa	nce except for formal matters, pr	osecution as to the merits is
	closed in accordance with the practice under E	Ex parte Quayle, 1935 C.D. 11, 4	53 O.G. 213.
Disposit	ion of Claims		
-	Claim(s) <u>1-8</u> is/are pending in the application.		
	4a) Of the above claim(s) is/are withdra	wn from consideration	
5)	Claim(s) is/are allowed.		
· · _	Claim(s) is/are rejected.		
7)	Claim(s) is/are objected to.		
8)		lection requirement.	
Appliest			
	ion Papers		
	The specification is objected to by the Examine		
	The drawing(s) filed on is/are: a) acc		
	Applicant may not request that any objection to the		
	Replacement drawing sheet(s) including the correct		•
11)	The oath or declaration is objected to by the Ex	xaminer. Note the attached Office	e Action or form PTO-152.
Priority	under 35 U.S.C. § 119		
,	Acknowledgment is made of a claim for foreign	n priority under 35 U.S.C. § 119(a	ı)-(d) or (f).
a)	☐ All b) Some * c) None of: 1. Certified copies of the priority document	to have been reasilyed	
	2. Certified copies of the priority document		tion No
	3. Copies of the certified copies of the prior		
	application from the International Burea	•	ed in this National Stage
* 9	See the attached detailed Office action for a list		ed
Attachmen			
	e of References Cited (PTO-892) e of Draftsperson's Patent Drawing Review (PTO-948)	4) 🛄 Interview Summary Paper No(s)/Mail D	
=	mation Disclosure Statement(s) (PTO/SB/08)	5) 🔲 Notice of Informal I	
	r No(s)/Mail Date	6) 🗌 Other:	
U.S. Patent and T PTOL-326 (F		ction Summary P	art of Paper No./Mail Date 20080408

DETAILED ACTION

Election/Restrictions

1. This application contains claims directed to the following patentably distinct species :

- Embodiment 1 of Figure 4
- Embodiment 2 of Figure 5a
- Embodiment 3 of Figures 5b and 5c

The species are independent or distinct because claims to the different species recite the mutually exclusive characteristics of such species. In addition, these species are not obvious variants of each other based on the current record.

Applicant is required under 35 U.S.C. 121 to elect a single disclosed species for prosecution on the merits to which the claims shall be restricted if no generic claim is finally held to be allowable. Currently, no claims are generic.

There is an examination and search burden for these patentably distinct species due to their mutually exclusive characteristics. The species require a different field of search (e.g., searching different classes/subclasses or electronic resources, or employing different search queries); and/or the prior art applicable to one species would not likely be applicable to another species; and/or the species are likely to raise different non-prior art issues under 35 U.S.C. 101 and/or 35 U.S.C. 112, first paragraph.

Page 2

Applicant is advised that the reply to this requirement to be complete must include (i) an election of a species to be examined even though the requirement may be traversed (37 CFR 1.143) and (ii) identification of the claims encompassing the elected species, including any claims subsequently added. An argument that a claim is allowable or that all claims are generic is considered nonresponsive unless accompanied by an election.

The election of the species may be made with or without traverse. To preserve a right to petition, the election must be made with traverse. If the reply does not distinctly and specifically point out supposed errors in the election of species requirement, the election shall be treated as an election without traverse. Traversal must be presented at the time of election in order to be considered timely. Failure to timely traverse the requirement will result in the loss of right to petition under 37 CFR 1.144. If claims are added after the election, applicant must indicate which of these claims are readable on the elected species.

Should applicant traverse on the ground that the species are not patentably distinct, applicant should submit evidence or identify such evidence now of record showing the species to be obvious variants or clearly admit on the record that this is the case. In either instance, if the examiner finds one of the species unpatentable over the prior art, the evidence or admission may be used in a rejection under 35 U.S.C. 103(a) of the other species.

Page 3

Upon the allowance of a generic claim, applicant will be entitled to consideration of claims to additional species which depend from or otherwise require all the limitations of an allowable generic claim as provided by 37 CFR 1.141.

Conclusion

2. Any inquiry concerning this communication or earlier communications from the examiner should be directed to AJAY K. ARORA whose telephone number is (571)272-8347. The examiner can normally be reached on Mon through Fri, 8am to 4:30pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Thao X. Le can be reached on (571) 272-1708. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

/A. K. A./

/Thao X Le/

Examiner, Art Unit 2892

Supervisory Patent Examiner, Art Unit 2892

Index of Claims					Application/C 11622496 Examiner AJAY K AROF		trol N	0.	Applica Reexar RAO, G Art Uni 2892	nina 6.R.	ation	ient Und	er	
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	United State	<u>s Patent</u>	and Tradema	UNITED STAT United States Address: COMMIS P.C. Box I	Virginia 22313-1450
APPLICATION NUMBER	FILING or 371(c) DATE	GRP ART UNIT	FIL FEE REC'D	ATTY.DOCKET.NO	TOT CLAIMS IND CLAIMS
11/622,496	01/12/2007	2811	925	1388-04	8 8
					CONFIRMATION NO. 3086
61400				UPDATE	D FILING RECEIPT
BANOWSKY 8	LEVINE, P.C				
	TRAL EXPRES	SSWAY			
SUITE 790					000000026392551*
DALLAS, TX 7	'5243				

Date Mailed: 10/25/2007

Receipt is acknowledged of this non-provisional patent application. The application will be taken up for examination in due course. Applicant will be notified as to the results of the examination. Any correspondence concerning the application must include the following identification information: the U.S. APPLICATION NUMBER, FILING DATE, NAME OF APPLICANT, and TITLE OF INVENTION. Fees transmitted by check or draft are subject to collection. Please verify the accuracy of the data presented on this receipt. If an error is noted on this Filing Receipt, please write to the Office of Initial Patent Examination's Filing Receipt Corrections. Please provide a copy of this Filing Receipt with the changes noted thereon. If you received a "Notice to File Missing Parts" for this application, please submit any corrections to this Filing Receipt with your reply to the Notice. When the USPTO processes the reply to the Notice, the USPTO will generate another Filing Receipt incorporating the requested corrections

Applicant(s)

G.R. Mohan Rao, McKinney, TX; Power of Attorney: The patent practitioners associated with Customer Number <u>61400</u>

Domestic Priority data as claimed by applicant

This application is a DIV of 10/934,915 09/03/2004 ABN

Foreign Applications

If Required, Foreign Filing License Granted: 02/08/2007

The country code and number of your priority application, to be used for filing abroad under the Paris Convention, is **US 11/622,496**

Projected Publication Date: Not Applicable

Non-Publication Request: No

Early Publication Request: No ** SMALL ENTITY **

Title

SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS

Preliminary Class

257

PROTECTING YOUR INVENTION OUTSIDE THE UNITED STATES

Since the rights granted by a U.S. patent extend only throughout the territory of the United States and have no effect in a foreign country, an inventor who wishes patent protection in another country must apply for a patent in a specific country or in regional patent offices. Applicants may wish to consider the filing of an international application under the Patent Cooperation Treaty (PCT). An international (PCT) application generally has the same effect as a regular national patent application in each PCT-member country. The PCT process **simplifies** the filing of patent applications on the same invention in member countries, but **does not result** in a grant of "an international patent" and does not eliminate the need of applicants to file additional documents and fees in countries where patent protection is desired.

Almost every country has its own patent law, and a person desiring a patent in a particular country must make an application for patent in that country in accordance with its particular laws. Since the laws of many countries differ in various respects from the patent law of the United States, applicants are advised to seek guidance from specific foreign countries to ensure that patent rights are not lost prematurely.

Applicants also are advised that in the case of inventions made in the United States, the Director of the USPTO must issue a license before applicants can apply for a patent in a foreign country. The filing of a U.S. patent application serves as a request for a foreign filing license. The application's filing receipt contains further information and guidance as to the status of applicant's license for foreign filing.

Applicants may wish to consult the USPTO booklet, "General Information Concerning Patents" (specifically, the section entitled "Treaties and Foreign Patents") for more information on timeframes and deadlines for filing foreign patent applications. The guide is available either by contacting the USPTO Contact Center at 800-786-9199, or it can be viewed on the USPTO website at http://www.uspto.gov/web/offices/pac/doc/general/index.html.

For information on preventing theft of your intellectual property (patents, trademarks and copyrights), you may wish to consult the U.S. Government website, http://www.stopfakes.gov. Part of a Department of Commerce initiative, this website includes self-help "toolkits" giving innovators guidance on how to protect intellectual property in specific countries such as China, Korea and Mexico. For questions regarding patent enforcement issues, applicants may call the U.S. Government hotline at 1-866-999-HALT (1-866-999-4158).

LICENSE FOR FOREIGN FILING UNDER

Title 35, United States Code, Section 184

Title 37, Code of Federal Regulations, 5.11 & 5.15

GRANTED

The applicant has been granted a license under 35 U.S.C. 184, if the phrase "IF REQUIRED, FOREIGN FILING LICENSE GRANTED" followed by a date appears on this form. Such licenses are issued in all applications where the conditions for issuance of a license have been met, regardless of whether or not a license may be required as

page 2 of 3

set forth in 37 CFR 5.15. The scope and limitations of this license are set forth in 37 CFR 5.15(a) unless an earlier license has been issued under 37 CFR 5.15(b). The license is subject to revocation upon written notification. The date indicated is the effective date of the license, unless an earlier license of similar scope has been granted under 37 CFR 5.13 or 5.14.

This license is to be retained by the licensee and may be used at any time on or after the effective date thereof unless it is revoked. This license is automatically transferred to any related applications(s) filed under 37 CFR 1.53(d). This license is not retroactive.

The grant of a license does not in any way lessen the responsibility of a licensee for the security of the subject matter as imposed by any Government contract or the provisions of existing laws relating to espionage and the national security or the export of technical data. Licensees should apprise themselves of current regulations especially with respect to certain countries, of other agencies, particularly the Office of Defense Trade Controls, Department of State (with respect to Arms, Munitions and Implements of War (22 CFR 121-128)); the Bureau of Industry and Security, Department of Commerce (15 CFR parts 730-774); the Office of Foreign AssetsControl, Department of Treasury (31 CFR Parts 500+) and the Department of Energy.

NOT GRANTED

No license under 35 U.S.C. 184 has been granted at this time, if the phrase "IF REQUIRED, FOREIGN FILING LICENSE GRANTED" DOES NOT appear on this form. Applicant may still petition for a license under 37 CFR 5.12, if a license is desired before the expiration of 6 months from the filing date of the application. If 6 months has lapsed from the filing date of this application and the licensee has not received any indication of a secrecy order under 35 U.S.C. 181, the licensee may foreign file the application pursuant to 37 CFR 5.15(b).

UNITED STATES PATENT AND TRADEMARK OFFICE



APPLICATION NUMBER FILING OR 371(c) DATE FIRST NAMED APP	PLICANT ATTY. DOCKET NO./TITLE
--	--------------------------------

11/622,496

01/12/2007

G.R. Mohan Rao

1388-04

CONFIRMATION NO. 3086

61400 BANOWSKY &LEVINE, P.C 12001 N. CENTRAL EXPRESSWAY SUITE 790 DALLAS, TX75243

Title: SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS

Publication No. US-2007-0158790-A1 Publication Date: 07/12/2007

NOTICE OF PUBLICATION OF APPLICATION

The above-identified application will be electronically published as a patent application publication pursuant to 37 CFR 1.211, et seq. The patent application publication number and publication date are set forth above.

The publication may be accessed through the USPTO's publically available Searchable Databases via the Internet at www.uspto.gov. The direct link to access the publication is currently http://www.uspto.gov/patft/.

The publication process established by the Office does not provide for mailing a copy of the publication to applicant. A copy of the publication may be obtained from the Office upon payment of the appropriate fee set forth in 37 CFR 1.19(a)(1). Orders for copies of patent application publications are handled by the USPTO's Office of Public Records. The Office of Public Records can be reached by telephone at (703) 308-9726 or (800) 972-6382, by facsimile at (703) 305-8759, by mail addressed to the United States Patent and Trademark Office, Office of Public Records, Alexandria, VA 22313-1450 or via the Internet.

In addition, information on the status of the application, including the mailing date of Office actions and the dates of receipt of correspondence filed in the Office, may also be accessed via the Internet through the Patent Electronic Business Center at www.uspto.gov using the public side of the Patent Application Information and Retrieval (PAIR) system. The direct link to access this status information is currently http://pair.uspto.gov/. Prior to publication, such status information is confidential and may only be obtained by applicant using the private side of PAIR.

Further assistance in electronically accessing the publication, or about PAIR, is available by calling the Patent Electronic Business Center at 1-866-217-9197.

Pre-Grant Publication Division, 703-605-4283

UNITED STATES PATENT AND TRADEMARK OFFICE



APPLICATION NUMBER FILING OR 371(c) DATE FIRST NAMED APP	PLICANT ATTY. DOCKET NO./TITLE
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11/622,496

01/12/2007

G.R. Mohan Rao

1388-04

CONFIRMATION NO. 3086

61400 BANOWSKY &LEVINE, P.C 12001 N. CENTRAL EXPRESSWAY SUITE 790 DALLAS, TX75243

Title: SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS

Publication No. US-2007-0158790-A1 Publication Date: 07/12/2007

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In addition, information on the status of the application, including the mailing date of Office actions and the dates of receipt of correspondence filed in the Office, may also be accessed via the Internet through the Patent Electronic Business Center at www.uspto.gov using the public side of the Patent Application Information and Retrieval (PAIR) system. The direct link to access this status information is currently http://pair.uspto.gov/. Prior to publication, such status information is confidential and may only be obtained by applicant using the private side of PAIR.

Further assistance in electronically accessing the publication, or about PAIR, is available by calling the Patent Electronic Business Center at 1-866-217-9197.

Pre-Grant Publication Division, 703-605-4283

UNITED STATES	s Patent and Tradema	UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Address COMMISSIONER FOR PATENTS PO. Box 1450 Adexmacha, Vinnia 22313-1450 www.uspto.gov		
APPLICATION NUMBER	FILING OR 371 (c) DATE	FIRST NAMED APPLICANT	ATTY. DOCKET NO./TITLE	
11/622,496	01/12/2007	G.R. Mohan Rao	1388-04	
			CONFIRMATION NO. 3086	

BANOWSKY &LEVINE, P.C 12001 N. CENTRAL EXPRESSWAY SUITE 790 DALLAS, TX 75243

Date Mailed: 04/20/2007

OC00000023487076

NOTICE OF ACCEPTANCE OF POWER OF ATTORNEY

This is in response to the Power of Attorney filed 03/26/2007.

The Power of Attorney in this application is accepted. Correspondence in this application will be mailed to the above address as provided by 37 CFR 1.33.

Initial Patent Examination (571) 272-4000, or 1-800-PTO-9199 OFFICE COPY



Drw

Attorney Docket No. 1388-03 Customer No. 61400

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of	ş
RAO, G.R. MOHAN	ş Ş
Serial No. 11/622,496	
Filed: 12 JANUARY 2007	
For: SEMICONDUCTOR DEVICES	§ 8
WITH GRADED DOPANT REGIONS	8

Confirmation No. **3086** Group Art Unit: **2811**

TRANSMITTAL

Mail Stop Amendment Hon. Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

Please file the following documents in the subject application:

- 1. This transmittal with Certificate of Mailing;
- 2. Power of Attorney and Correspondence Address Indication Form;
- 3. Check No. 94, in the amount of \$500.00, to cover the fees associated with the above referenced application for including 5 independent claims over 3; and
- 4. A return postcard which I would appreciate you date stamping and returning to me.

You are hereby authorized and requested to charge any additional fees or underpayment of fees related to this application to deposit account no. 50-3886. Please credit any over payment of fees to such deposit account as well.

03/27/2007 FMETEKI1 00000016 11622496

01 FC:2201

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Hon. Commissioner for Patents March 20, 2007 Page 2

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Date: 3/20/07

BANOWSKY & LEVINE, P.C.

12001 N. Central Expressway Suite 790 Dallas, Texas 75243 (214) 871-1300 (214) 871-0038 (facsimile) Customer No. **61400** Attorney Docket No. 1388-03 Customer No. 61400

Respectfully submitted,

Baxter W. Banowsky

Registration No: 58,170

Certificate of Mailing

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on 3 - 20 - 07

Jackie L. Jenkins Printed Name Jackie L. Jenkins Signature
OIPE was						
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FILING RECEIPT

Winstead Sechrest & Minick P.C. P.O. Box 50784 Dallas, TX75201

Date Mailed: 02/08/2007

Receipt is acknowledged of this regular Patent Application. It will be considered in its order and you will be notified as to the results of the examination. Be sure to provide the U.S. APPLICATION NUMBER, FILING DATE, NAME OF APPLICANT, and TITLE OF INVENTION when inquiring about this application. Fees transmitted by check or draft are subject to collection. Please verify the accuracy of the data presented on this receipt. If an error is noted on this Filing Receipt, please mail to the Commissioner for Patents P.O. Box 1450 Alexandria Va 22313-1450. Please provide a copy of this Filing Receipt with the changes noted thereon. If you received a "Notice to File Missing Parts" for this application, please submit any corrections to this Filing Receipt with your reply to the Notice. When the USPTO processes the reply to the Notice, the USPTO will generate another Filing Receipt incorporating the requested corrections (if appropriate).

Applicant(s)

G.R. Mohan Rao, McKinney, TX;

Power of Attorney: None

Domestic Priority data as claimed by applicant

This application is a DIV of 10/934,915 09/03/2004

Foreign Applications

If Required, Foreign Filing License Granted: 02/08/2007

The country code and number of your priority application, to be used for filing abroad under the Paris Convention, is US11/622,496

Projected Publication Date: 05/17/2007

Non-Publication Request: No

Early Publication Request: No

** SMALL ENTITY **

Title

SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS

Preliminary Class

257

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APPLICATION NUMBER	FILING OR 371 (c) DATE	FIRST NAMED APPLICANT	ATTORNEY DOCKET NUMBER				
11/622,496	01/12/2007	G.R. Mohan Rao	43218-P001US				

Winstead Sechrest & Minick P.C. P.O. Box 50784 Dallas, TX 75201

Date Mailed: 02/08/2007

LETTER

FORMALITIES

CONFIRMATION NO. 3086

NOTICE TO FILE MISSING PARTS OF NONPROVISIONAL APPLICATION

FILED UNDER 37 CFR 1.53(b)

Filing Date Granted

Items Required To Avoid Abandonment:

An application number and filing date have been accorded to this application. The item(s) indicated below, however, are missing. Applicant is given TWO MONTHS from the date of this Notice within which to file all required items and pay any fees required below to avoid abandonment. Extensions of time may be obtained by filing a petition accompanied by the extension fee under the provisions of 37 CFR 1.136(a).

• Additional claim fees of \$500 as a small entity, including any required multiple dependent claim fee, are required. Applicant must submit the additional claim fees or cancel the additional claims for which fees are due.

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Total additional fee(s) required for this application is \$500 for a small entity

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Office of Initial Patent Examination (571) 272-4000, or 1-800-PTO-9199, or 1-800-972-6382 PART 3 - OFFICE COPY

SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS

CROSS-REFERENCE TO RELATED APPLICATION

[0001] This application is a Divisional of U.S. application Ser. No. 10/934,915, filed on September 3, 2004, which application is incorporated herein by reference.

FIELD OF INVENTION

[0002] This present invention relates to all semiconductor devices and systems. Particularly it applies to diffused diodes, avalanche diodes, Schottky devices, power MOS transistors, JFET's, RF bipolar transistors, IGBTs (Insulated Gate Bipolar Transistors), varactors, digital VLSI, mixed signal circuits and sensor devices including camera ICs employing CCD (Charge Coupled Device) as well as CMOS technologies.

BACKGROUND OF INVENTION

[0003] Bipolar Junction transistors (BJT) are minority carrier devices as the principle device conduction mechanism. However, majority carriers also a small yet finite role in modulating the conductivity in BJTs. Consequently, both carriers (electrons and holes) play a role in the switching performance of BJTs. The maximum frequency of operation in BJTs is limited by the base transit time as well as the quick recombination of the majority carriers when the device is switched off (prior to beginning the next cycle). The dominant carrier mechanism in BJTs is carrier diffusion. Carrier drift current component is fairly small, especially in uniformly doped base BJTs. Efforts have been made in graded base transistors to create an `aiding drift field', to enhance the diffusing minority carrier's speed from emitter to collector. However, most semiconductor devices, including various power MOSFETs (traditional, DMOS, lateral, vertical and a host of other configurations), IGBT's (Insulated Gated Base Transistors), still use a uniformly doped drift epitaxial region in the base. FIG. 1 shows the relative doping concentration versus distance in a BJT. FIG. 2 shows the `uniformly doped epi region' in a IGBT. In contrast to BJTs, MOS devices are majority carrier devices for conduction. The conduction is channel dominated. The channel can be a surface in one plane in planar devices. The surface can also be on the sidewalls in a vertical device. Other device architectures to combine planar and vertical conductions are also possible. The maximum frequency of operation is dictated primarily by source-drain separation distance. Most MOS devices use a uniformly doped substrate (or a well region). When a MOSFET is optimally integrated with a BJT in a monolithic fashion, an IGBT results. The IGBT inherits the advantages of both MOSFET and BJT. It also brings new challenges because the required characteristics (electron transit and hole recombination as fast as possible in the case of an n-channel IGBT) require different dopant gradients either in the same layer at different positions, or at the interfaces of similar or dissimilar layers.

[0004] 'Retrograde' wells have been attempted, with little success, to help improve soft error immunity in SRAM's and visual quality in imaging circuits. FIG. 3(a) shows a typical CMOS VLSI device employing a twin well substrate, on which active devices are subsequently fabricated. FIGS. 3(b), 3(c), and 3(d) illustrate device cross sections, as practiced today. 'Retrograde' and 'halo' wells have also been attempted to improve refresh time in DRAM's (dynamic random access memories), as well as, reducing dark current (background noise) and enhance RGB (Red, Green, Blue) color resolution in digital camera Ics. Most of these techniques

either divert the minority carriers away form the active regions of critical charge storage nodes at the surface, or, increase minority carrier density locally as the particular application requires.

BRIEF DESCRIPTION OF DRAWINGS

[0005] For a more complete understanding of the present invention, and the advantages thereof, reference is now made to the following descriptions taken in conjunction with the accompanying drawings, in which:

[0006] FIGURE 1 illustrates the relative doping profiles of emitter, base, and collector, for the two most popular bipolar junction transistors: namely, A - uniform base, and B - graded base;

[0007] FIGURE 2 illustrates the cross section of a commercial IGBT with a uniform epitaxial drift region (base);

[0008] FIGURES 3(a), 3(b), 3(c), 3(d) illustrate cross sections commonly used CMOS silicon substrate with two wells (one n-well in which p-channel transistors are subsequently fabricated, and, one p-well in which n-channel transistors are subsequently fabricated) - typical IC, EEPROM using tunnel insulator, DRAM and NAND flash;

[0009] FIGURE 4 illustrates the cross section of a IGBT, using one embodiment of the invention described here, where the dopant is optimally graded in the eptaxial drift region; and

[0010] FIGURES 5(a), 5(b), 5(c) illustrate the cross sections of a MOS silicon substrate with two wells, and, an underlying layer using embodiments of the invention to improve performance in each application - VLSI logic, DRAM/image IC, nonvolatile memory IC.

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DETAILED DESCRIPTION OF THE INVENTION

[0011] The relative doping concentrations of emitter and collector regions varies from 10^{18} to 10^{20} /cm³, where as the base region is 10^{14} to 10^{16} /cm³ depending on the desired characteristics of the BJT. In graded base p-n-p transistors, the donor dopant concentration may be 10 to 100X at the emitter-base junction, relative to the base-collector junction (1 X). The gradient can be linear, quasi linear, exponential or complimentary error function. The relative slope of the donor concentration throughout the base, creates a suitable aiding drift electric field, to help the holes (p-n-p transistor) transverse from emitter to collector. Since the aiding drift field helps hole conduction, the current gain at a given frequency is enhanced, relative to a uniformly-doped-(base) BJT. The improvement in cut-off frequency (or, frequency at unity gain, f_T) can be as large as 2x-5x.Similar performance improvements are also applicable to n-p-n transistors.

[0012] As illustrated in FIG. 4, in one embodiment according to the invention, a donor gradient is established from the emitter-drift epitaxial base region junction of the punch-through IGBT, to the drift epitaxial base region - n^t buffer layer boundary (electrons in this case are accelerated in their transit from emitter to collector). The `average' base resistance is optimized, so that conductivity modulation and lifetime (for minority carriers) in base region are not compromised. By sweeping the carriers towards the n` buffer region two advantages are obtained - the frequency of operation (combination of t_{on} and t_{off} as is known in the IGBT commercial nomenclature) can be enhanced. More importantly, during t_{off} , holes can be recombined much quicker at the n^t buffer layer, compared to a uniformly doped n⁻epitaxial drift region by

establishing a different dopant gradient near the n+ buffer layer. It should be noted that the drift region can also be a non-epitaxial silicon substrate. Epitaxy enhances lifetime, but, epitaxy is not mandatory. Different layers of dopan regions can be transferred through wafer to wafer bonding (or other similar transfer mechanisms) for eventual device fabrication. The "reverse recovery time" for an IGBT is significantly improved due to the optimized graded dopant in the so called "drift region" as well as at the interfaces of the drift region. Graded dopants can also be implemented in the n+ buffer layer as well as other regions adjacent to the respective layers. Two important performance enhancements are the result of dopant gradients. For example, in an n-channel IGBT, electrons can be swept from source to drain rapidly, while at the same time holes can be recombined closer to the n+ buffer layer. This can improve t(on) and t(off) in the same device.

The following paragraph, beginning on page 5, line 6, and ending on page 11, line 28, is amended as indicated in the marked up version below:

[0013] As illustrated in FIGS. 5(a), 5(b), 5(c), donor gradient is also of benefit to very large scale integrated circuits (VLSI) - VLSI logic, DRAM, nonvolatile memory like NAND flash. Spurious minority carriers can be generated by clock switching in digital VLSI logic and memory IC'S. These unwanted carriers can discharge dynamically-held 'actively held high' nodes. Statically held nodes (with V_{ee}) can not be affected, in most cases. Degradation of refresh time in DRAM's is one of the results, because the capacitor holds charge dynamically. Similarly, degradation of CMOS digital images, in digital imaging IC's is another result of the havoc caused by minority carriers. Pixel and color resolution can be significantly enhanced in imaging IC's with the embodiments described here. Creating 'Sub Terrain' recombination centers

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underneath the wells (gold doping, platinum doping) as is done in some high-voltage diodes is not practical for VLSI circuits. Hence, a novel technique has been described here by creating a drift field to sweep these unwanted minority carriers into the substrate as quickly as possible, from the active circuitry at the surface. In a preferred embodiment, the subterrain n-layer has a graded donor concentration to sweep the minority carriers deep into the substrate. One or more of such layers can also be implemented through wafer to wafer bonding or similar "transfer" mechanisms. This n-layer can be a deeply-implanted layer. It can also be an epitaxial layer. The n-well and p-well also can be graded or retrograded in dopants, as desired, to sweep those carriers away from the surface as well. The graded dopant can also be implemented in surface channel MOS devices to accelerate majority carriers towards the drain. In nonvolatile memory devices, to decrease programming time, carriers should be accelerated towards the surface when programming of memory cells is executed. The graded dopant can also be used to fabricate superior Junction field-effect transistors where the "channel pinchoff" is controlled by a graded channel instead of a uniformly doped channel (as practiced in prior art).

[0014] One of ordinary skill and familiarity in the art will recognize that the concepts taught herein can be customized and tailored to a particular application in many advantageous ways. For instance, minority carriers can be channeled to the surface, to aid programming in nonvolatile memory devices (NOR, NAND, multivalued-cell). Moreover, single well, as well triple-well CMOS fabrication techniques can also be optimized to incorporate these embodiments, individually and collectively. Any modifications of such embodiments (described here) fall within the spirit and scope of the invention. Hence, they fall within the scope of the claims described below

[0015] Although the invention has been described with reference to specific embodiments, these descriptions are not meant to be construed in a limiting sense. Various modifications of the disclosed embodiments, as well as alternative embodiments of the invention will become apparent to persons skilled in the art upon reference to the description of the invention. It should be appreciated by those skilled in the art that the conception and the specific embodiment disclosed may be readily utilized as a basis for modifying or designing other structures for carrying out the same purposes of the present invention. It should also be realized by those skilled in the art that such equivalent constructions do not depart from the spirit and scope of the invention as set forth in the appended claims.

[0016] It is therefore, contemplated that the claims will cover any such modifications or embodiments that fall within the true scope of the invention.

WHAT IS CLAIMED IS:

1. A semiconductor device with graded dopant concentration in the active region, to aid carrier movement from emitter to collector.

2. A semiconductor device with graded dopant concentration in the active region, to aid carrier movement from source to drain.

3. A semiconductor device with graded dopant concentration in the well regions, to aid carrier movement away from the active surface regions, towards the substrate.

4. A semiconductor device with graded dopant concentration in the substrate region to aid carrier movement away from the active surface regions, deeper towards the substrate.

5. A semiconductor device with at least one each of dopant concentration of both donor and acceptor, to optimize the operating performance of the device.

6. A semiconductor device with at least one graded dopant concentration fabricated with ion implantation, to provide an aiding or retarding electric field locally in a monolithic integrated circuit.

7. A semiconductor device with at least one graded dopant concentration in an epitaxial layer.

8. A semiconductor device where one layer of dopant from one wafer, is transferred to another wafer having either same polarity or different polarity dopant through wafer bonding or similar processes.

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ABSTRACT

[0017] Most semiconductor devices manufactured today, have uniform dopant concentration, either in the lateral or vertical device active (and isolation) regions. By grading the dopant concentration, the performance in various semiconductor devices can be significantly improved. Performance improvements can be obtained in application specific areas like increase in frequency of operation for digital logic, various power MOSFET and IGBT ICS, improvement in refresh time for DRAM's, decrease in programming time for nonvolatile memory, better visual quality including pixel resolution and color sensitivity for imaging ICs, better sensitivity for varactors in tunable filters, higher drive capabilities for JFET's, and a host of other applications.



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Dopant Concentration (per Cm3+

Figure 1 Prior Art



FIGURE 2 Prior art



FIGURE 3(a) Prior art (Twin well CMOS) for a CMOS integrated circuit



FIGURE 3(b) Prior art for a two-device EEPROM memory cell



FIGURE 3(c) Prior art for a 1T-1C DRAM memory cell



FIGURE 3(d) Prior art for a NAND flash memory cell

Note: Control/ Sect transistors have a single insulator - traditional MOS transistor. Storage nodes have a stacked gate structure, typically with

a floating gate and control gate comprising the stack.



FIGURE 4 A dopant - concentration grinded drift region in a IGBT



FIGURE 5(a) A CMOS Substrate for digital, mixed, signal, and senors IC's



FIGURE 5(b) CMOS Substrate for a DRAM or image sensor, with one embodiment of the invention



FIGURE 5(c) CMOS Substrate for a NAND flash device to improve programming times

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Additional foreign application numbers are listed on a supplemental priority data sheet PTO/SB/02B attached hereto. [Page 1 of 2]							

[Page 1 of 2] This collection of information is required by 35 U.S.C. 115 and 37 CFR 1.63. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 21 minutes to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer. U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450, DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450. If you need assistance in completing the form, call 1-800-PTO-9199 and select option 2.



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DECLARATION — Utility or Design Patent Application

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Filing Date:						
Title of Invention:	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIO				PANT REGIONS	
First Named Inventor/Applicant Name:	G.F	R. Mohan Rao				
Filer:	Baxter Ward Banowsky.					
Attorney Docket Number:	138	38-03				
Filed as Small Entity						
Utility Filing Fees						
Description		Fee Code	Quantity	Amount	Sub-Total in USD(\$)	
Basic Filing:						
Utility filing Fee (Electronic filing)		4011	1	75	75	
Utility Search Fee		2111	1	250	250	
Utility Examination Fee		2311	1	100	100	
Pages:						
Claims:						
Miscellaneous-Filing:						
Petition:						
Patent-Appeals-and-Interference:						

Description	Fee Code	Quantity	Amount	Sub-Total in USD(\$)
Post-Allowance-and-Post-Issuance:				
Extension-of-Time:				
Miscellaneous:				
	Tota) (\$)	425	

Electronic Acknowledgement Receipt						
EFS ID:	1434580					
Application Number:	11622496					
International Application Number:						
Confirmation Number:	3086					
Title of Invention:	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS					
First Named Inventor/Applicant Name:	G.R. Mohan Rao					
Customer Number:	61400					
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Filer Authorized By:						
Attorney Docket Number:	1388-03					
Receipt Date:	12-JAN-2007					
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Document Number	Document Description	File Name	File Size(Bytes)	Multi Part /.zip	Pages (if appl.)		
1	Specification	specification.pdf	83116	no	7		
Warnings:		· · · · · · · · · · · · · · · · · · ·					
Information							
2	Claims	claims.pdf	72618	no	1		
Warnings:							
Information							
3	Abstract	abstract.pdf	72564	no	1		
Warnings:							
Information		r					
4	Drawings	drawings.pdf	115914	no	10		
Warnings:							
Information							
5	Oath or Declaration filed	Oath.pdf	105074	no	2		
Warnings:							
Information		1					
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